

Service Manual



Service Manual

LG-P520



Model : LG-P520

Table Of Contents

1. INTRODUCTION	5	4.13 Microphone Trouble	106
1.1 Purpose	5	4.14 SIM Card Interface Trouble	108
1.2 Regulatory Information	5	4.15 Micro SD Trouble	110
1.3 Abbreviation	7	4.16 Bluetooth Trouble	112
2. PERFORMANC	9	4.18 FM Radio Trouble	114
2.1 H/W Features	9	5. DOWNLOAD.....	116
2.2 Technical Specification.....	11	6. BLOCK DIAGRAM	129
3. TECHNICAL BRIEF	16	7. CIRCUIT DIAGRAM	131
3.1 Functional Block Diagram.....	16	8. BGA Pin Map.....	137
3.2 Digital Main Processor (PMB8810, U101/U401)	17	9. PCB LAYOUT	143
3.3 Power Management.....	22	10. STAND ALONE TEST	147
3.4 FEM with integrated Power Amplifier Module (SKY77547, U301, U302)	34	10.1 Introduction	147
3.5 Crystal(26 MHz, X100, X400)	36	10.2 Setting Method	147
3.6 RF Subsystem of PMB8810 (U101, U401)	37	10.3 Tx Test.....	149
3.7 MEMORY	42	10.4 Rx Test	150
3.8 Bluetooth module.....	48	11. AUTO CALIBRATION.....	151
3.9 Dual SIM Card Interface	50	11.1 Overview.....	151
3.10 LCD Interface.....	51	11.2 Configuration of HotKimchi.....	151
3.11 Battery Charger Interface	54	11.3 Description of Basic File	152
3.12 Keypad Interface.....	55	11.4 Auto Calibration setup.....	153
3.13 Audio Front-End.....	56	11.5 Procedure	154
3.14 Camera Interface(1.3M Fixed Focus Camera)	62	11.6 AGC.....	156
3.15 Vibrator Interface	64	11.7 APC	156
4. TROUBLE SHOOTING	65	11.8 ADC.....	156
4.1 Trouble shooting test setup	65	11.9 Target Power.....	156
4.2 RF Component	66	12. EXPLODED VIEW & REPLACEMENT	
4.3 RX Trouble.....	68	PART LIST.....	157
4.4 TX Trouble	74	12.1 EXPLODED VIEW.....	157
4.5 Power On Trouble	80	12.2 Replacement Parts	159
4.6 Charging Trouble.....	83	12.3 Accessory.....	173
4.7 Vibrator Trouble	85		
4.8 LCD Trouble.....	87		
4.9 Camera Trouble.....	91		
4.10 Speaker Trouble	98		
4.11 Earphone Trouble	100		
4.12 Receiver Trouble.....	103		



1. INTRODUCTION

1.1 Purpose

This manual provides the information necessary to repair, calibration, description and download the features of this model.

1.2 Regulatory Information

A. Security

Toll fraud, the unauthorized use of telecommunications system by an unauthorized part (for example, persons other than your company's employees, agents, subcontractors, or person working on your company's behalf) can result in substantial additional charges for your telecommunications services. System users are responsible for the security of own system. There are may be risks of toll fraud associated with your telecommunications system. System users are responsible for programming and configuring the equipment to prevent unauthorized use. The manufacturer does not warrant that this product is immune from the above case but will prevent unauthorized use of common-carrier telecommunication service of facilities accessed through or connected to it.

The manufacturer will not be responsible for any charges that result from such unauthorized use.

B. Incidence of Harm

If a telephone company determines that the equipment provided to customer is faulty and possibly causing harm or interruption in service to the telephone network, it should disconnect telephone service until repair can be done. A telephone company may temporarily disconnect service as long as repair is not done.

C. Changes in Service

A local telephone company may make changes in its communications facilities or procedure. If these changes could reasonably be expected to affect the use of the this phone or compatibility with the network, the telephone company is required to give advanced written notice to the user, allowing the user to take appropriate steps to maintain telephone service.

D. Maintenance Limitations

Maintenance limitations on this model must be performed only by the manufacturer or its authorized agent. The user may not make any changes and/or repairs expect as specifically noted in this manual. Therefore, note that unauthorized alternations or repair may affect the regulatory status of the system and may void any remaining warranty.

1. INTRODUCTION

E. Notice of Radiated Emissions

This model complies with rules regarding radiation and radio frequency emission as defined by local regulatory agencies. In accordance with these agencies, you may be required to provide information such as the following to the end user.

F. Pictures

The pictures in this manual are for illustrative purposes only; your actual hardware may look slightly different.

G. Interference and Attenuation

Phone may interfere with sensitive laboratory equipment, medical equipment, etc. Interference from unsuppressed engines or electric motors may cause problems.

H. Electrostatic Sensitive Devices

ATTENTION

Boards, which contain Electrostatic Sensitive Device (ESD), are indicated by the sign. Following information is ESD handling:



- Service personnel should ground themselves by using a wrist strap when exchange system boards.
- When repairs are made to a system board, they should spread the floor with anti-static mat which is also grounded.
- Use a suitable, grounded soldering iron.
- Keep sensitive parts in these protective packages until these are used.
- When returning system boards or parts like EEPROM to the factory, use the protective package as described.

1.3 Abbreviations

For the purposes of this manual, following abbreviations apply:

APC	Automatic Power Control
BB	Baseband
BER	Bit Error Ratio
CC-CV	Constant Current – Constant Voltage
DAC	Digital to Analog Converter
DCS	Digital Communication System
dBm	dB relative to 1 milli watt
DSP	Digital Signal Processing
EEPROM	Electrical Erasable Programmable Read-Only Memory
ESD	Electrostatic Discharge
FPCB	Flexible Printed Circuit Board
GMSK	Gaussian Minimum Shift Keying
GPIO	General Purpose Interface Bus
GSM	Global System for Mobile Communications
IQUI	International Portable User Identity
IF	Intermediate Frequency
LCD	Liquid Crystal Display
LDO	Low Drop Output
LED	Light Emitting Diode
OPLL	Offset Phase Locked Loop

1. INTRODUCTION

PAM	Power Amplifier Module
PCB	Printed Circuit Board
PGA	Programmable Gain Amplifier
PLL	Phase Locked Loop
PSTN	Public Switched Telephone Network
RF	Radio Frequency
RLR	Receiving Loudness Rating
RMS	Root Mean Square
RTC	Real Time Clock
SAW	Surface Acoustic Wave
SIM	Subscriber Identity Module
SLR	Sending Loudness Rating
SRAM	Static Random Access Memory
PSRAM	Pseudo SRAM
STMR	Side Tone Masking Rating
TA	Travel Adapter
TDD	Time Division Duplex
TDMA	Time Division Multiple Access
UART	Universal Asynchronous Receiver/Transmitter
VCO	Voltage Controlled Oscillator
VCTCXO	Voltage Control Temperature Compensated Crystal Oscillator
WAP	Wireless Application Protocol

2. PERFORMANCE

2.1 H/W Features

Item	Feature	Comment
Standard Battery	Lithium-ion r, 3.7V, 1,500mAh	
Stand by TIME	Up to 370 hrs (Paging Period 5, RSSI -85dBm)	
Talk time	Up to 200min : GSM Tx Level 7	
Charging time	Approx. 4 hours	
RX Sensitivity	GSM, EGSM: -109dBm, DCS: -109dBm	
TX output power	GSM, EGSM: 33dBm(Level 5), DCS , PCS: 30dBm(Level 0)	
GPRS compatibility	Class 12	
SIM card type	3V Small	
Display	MAIN : 2.2" TFT 176 × 220 pixel 262K Color	
Status Indicator	Hard icons. Key Pad 0 ~ 9, #, *, Up/Down Left/Right Navigation Key Send Key, PWR Key ,Soft Key(Left/Right) Volume up/down, Camera hot key, SIM switch key	
ANT	Internal	
EAR Phone Jack	Yes	
PC Synchronization	Yes	
Speech coding	EFR/FR/HR/AMR	
Data and Fax	Yes	
Vibrator	Yes	
Loud Speaker	Yes	
Voice Recoding	Yes	
Microphone	Yes	

2. PERFORMANCE

Item	Feature	Comment
Speaker/Receiver	18x12Φ Speaker/ Receiver	
Travel Adapter	Yes	
MIDI	SW MIDI (Mono SPK)	
Camera	2M	
Bluetooth / FM Radio	Bluetooth version 2.1 / 76~108MHz supported	

2.2 Technical Specification

Item	Description	Specification					
1	Frequency Band	EGSM TX: 880 ~ 915MHz RX: 925 ~ 960 MHz DCS TX: 1710 ~ 1785 MHz RX: 1805 ~ 1880 MHz PCS TX: 1850 ~ 1910 MHz RX: 1930 ~ 1990 MHz					
2	Phase Error	RMS < 5 degrees Peak < 20 degrees					
3	Frequency Error	< 0.1 ppm					
4	Power Level	EGSM					
		Level	Power	Toler.	Level	Power	Toler.
		5	33dBm	±2dB	13	17dBm	± 3dB
		6	31dBm	±3dB	14	15dBm	± 3dB
		7	29dBm	±3dB	15	13dBm	± 3dB
		8	27dBm	±3dB	16	11dBm	± 5dB
		9	25dBm	±3dB	17	9dBm	± 5dB
		10	23dBm	±3dB	18	7dBm	± 5dB
		11	21dBm	±3dB	19	5dBm	± 5dB
		12	19dBm	±3dB			
		DCS/PCS					
		Level	Power	Toler.	Level	Power	Toler.
		0	30dBm	±2dB	8	14dBm	± 3dB
		1	28dBm	±3dB	9	12dBm	± 4dB
		2	26dBm	±3dB	10	10dBm	± 4dB
		3	24dBm	±3dB	11	8dBm	± 4dB
		4	22dBm	±3dB	12	6dBm	± 4dB
		5	20dBm	±3dB	13	4dBm	± 4dB
		6	18dBm	±3dB	14	2dBm	± 5dB
		7	16dBm	±3dB	15	0dBm	± 5dB

2. PERFORMANCE

Item	Description	Specification	
5	Output RF Spectrum (due to modulation)	EGSM	
		Offset from Carrier (kHz).	Max. dBc
		100	+0.5
		200	-30
		250	-33
		400	-60
		600~ <1,200	-60
		1,200~ <1,800	-60
		1,800~ <3,000	-63
		3,000~ <6,000	-65
		6,000	-71
		DCS/PCS	
		Offset from Carrier (kHz).	Max. dBc
		100	+0.5
		200	-30
		250	-33
		400	-60
		600~ <1,200	-60
		1,200~ <1,800	-60
		1,800~ <3,000	-65
		3,000~ <6,000	-65
		6,000	-73
6	Output RF Spectrum (due to switching transient)	EGSM	
		Offset from Carrier (kHz).	Max. dBm
		400	-19
		600	-21
		1,200	-21
		1,800	-24

2. PERFORMANCE

Item	Description	Specification		
6	Output RF Spectrum (due to switching transient)	DCS/PCS		
		Offset from Carrier (kHz).		Max. dBm
		400		-22
		600		-24
		1,200		-24
		1,800		-27
7	Spurious Emissions	Conduction, Emission Status		
8	Bit Error Ratio	EGSM BER (Class II) < 2.439% @-102 dBm DCS,PCS BER (Class II) < 2.439% @-102 dBm		
9	RX Level Report Accuracy	±3 dB		
10	SLR	8±3 dB		
11	Sending Response	Frequency (Hz)	Max.(dB)	Min.(dB)
		100	-12	-
		200	0	-
		300	0	-12
		1,000	0	-6
		2,000	4	-6
		3,000	4	-6
		3,400	4	-9
		4,000	0	-
12	RLR	2±3 dB		

2. PERFORMANCE

Item	Description	Specification		
13	Receiving Response	Frequency (Hz)	Max.(dB)	Min.(dB)
		100	-12	-
		200	0	-
		300	2	-7
		500	*	-5
		1,000	0	-5
		3,000	2	-5
		3,400	2	-10
		4,000	2	
		* Mean that Adopt a straight line in between 300 Hz and 1,000 Hz to be Max. level in the range.		
14	STMR	18±5 dB		
15	Stability Margin	> 6 dB		
16	Distortion	dB to ARL (dB)		Level Ratio (dB)
		-35		17.5
		-30		22.5
		-20		30.7
		-10		33.3
		0		33.7
		7		31.7
		10		25.5
17	Side Tone Distortion	Three stage distortion < 10%		
18	System frequency (26 MHz) tolerance	≤ 2.5 ppm		
19	32.768KHz tolerance	≤ 30 ppm		
20	Ringer Volume	At least 65 dBspl under below conditions: 1. Ringer set as ringer. 2. Test distance set as 50 cm		

2. PERFORMANCE

Item	Description	Specification	
21	Charge Current	Fast Charge : Typ. 650 mA Slow Charge : Typ. 80mA Total Charging Time : < 4 hours	
22	Antenna Display	Bar Number	Power
		7	-92 Over
		7 -> 5	-93 \pm 2
		5 -> 4	-98 \pm 2
		4 -> 2	-101 \pm 2
		2 -> 1	-104 \pm 2
		1 -> 0	-106 \pm 2
		0 -> OFF	-106 Under
23	Battery Indicator	Battery Bar Number	Voltage
		3	≥ 3.77
		3 -> 2	3.77 \pm 0.05 V
		2 -> 1	3.67 \pm 0.05 V
		1 -> 0	3.60 \pm 0.05 V
24	Low Voltage Warning (Blinking Bar)	$\leq 3.60 \pm 0.05V$ (Call), one time per one minute	
		$\leq 3.60 \pm 0.05V$ (Standby), one time per three minute	
25	Forced shut down Voltage	3.33 \pm 0.05V	
26	Sustain RTC without battery	Over 50 hours	
27	Battery Type	Lithium-Ion Battery Standard Voltage = 3.7 V Battery full charge voltage = 4.2 V Capacity: 1,500mAh	
28	Travel Charger	Switching-mode charger Input: 100 ~ 240V, 50/60 Hz Output: 5.1V, 700 mA	

3. TECHNICAL BRIEF

3. TECHNICAL BRIEF

3.1 Functional Block Diagram

The functional component arrangement is mentioned below diagram.

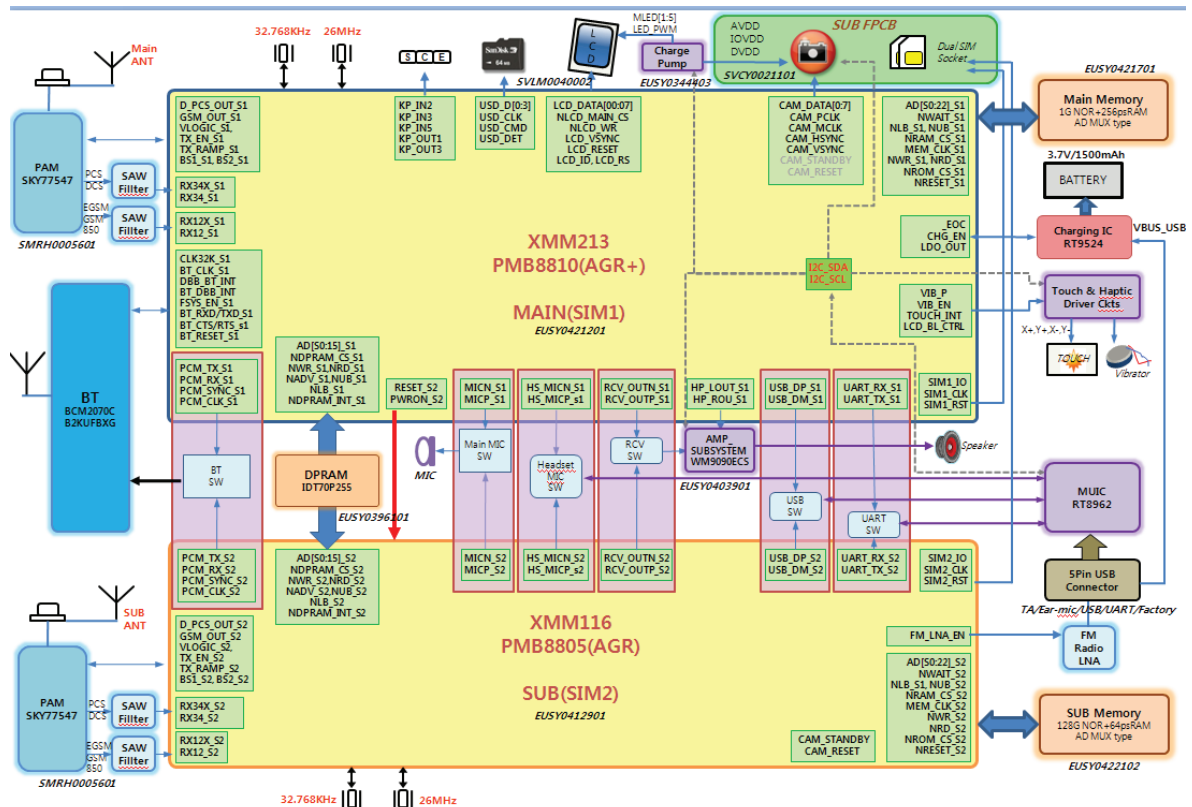


Figure. 3.1.1 Functional Block Diagram

3.2 Digital Main Processor (PMB8810, U101/U401)

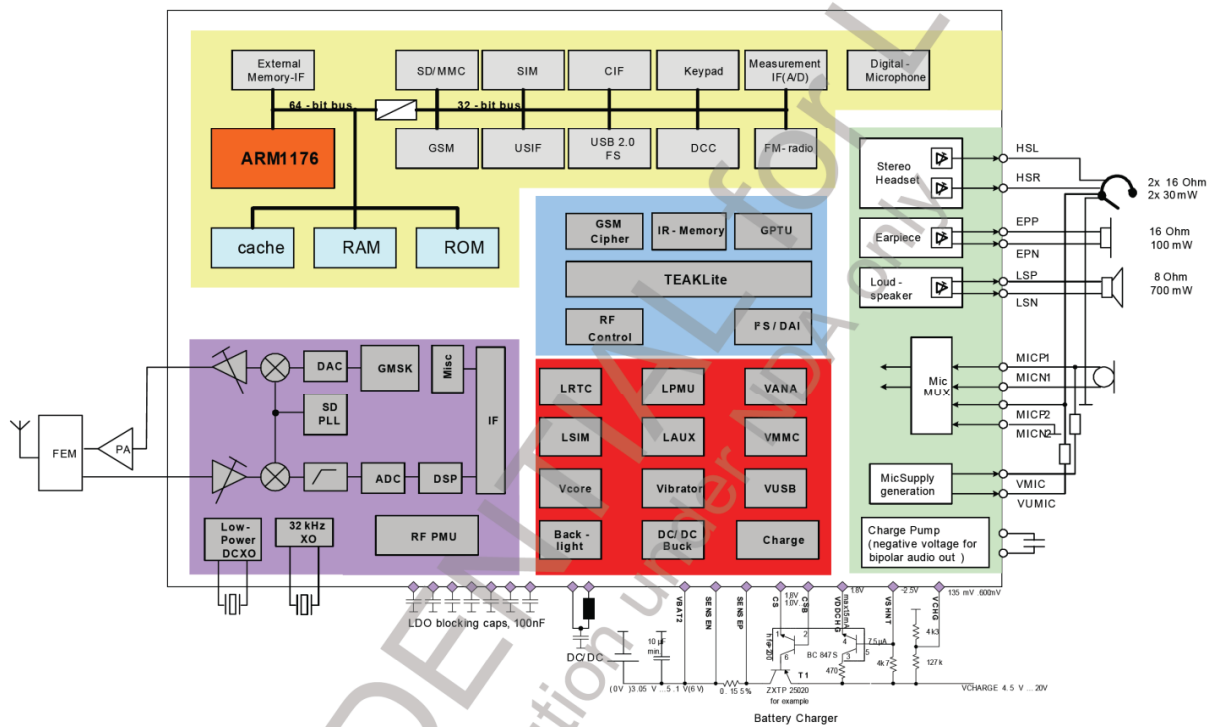


Figure. 3.2.1 X-Gold tm 213 Hardware Block Diagram

3. TECHNICAL BRIEF

3.2.1 General

Technology:

- SoC, Monolithic, 65 nm CMOS
- Package:
 - eWLB, 8x8x0.8 mm
 - 0.5 mm pitch
 - 217 balls / 6-layer PCB

3.2.2 RF Transceiver

- Dual-band direct conversion receiver
- Tri/Quad-band possible with external circuitry
- Fully integrated digital controlled XO
- Additional buffer for 2 external system clocks
- Fully digital RF-Synthesizer incl. $\Sigma\Delta$ -Transmitter

3.2.3 Baseband

- DSP:
 - 156 MHz TeakLite™
- MCU:
 - ARM1176® @ 208 MHz
- MCU RAM:
 - 3.00Mbit
- Memory I/F:
 - 512 Mbit (can be extended to 2 Gbit in AD-Mux/Demux, and up to 4 Gbit in AAD-Mux mode)
- Modem:
 - GPRS class 12, (RX/TX CS1-CS4)
 - EGPRS class 12, (RX MCS1-MCS9, TX MCS1-MCS4)
- Cipher Units:
 - A51/2/3
 - GEA-1/2/3
- Security:
 - OMTP TR0
 - Secure Boot
 - RSA(ROM)/SHA-1(HW accel.)
 - OCDS disabling
 - Certificate Management

- Speech Codec:
 - FR / HR / EFR / NB-AMR
- Audio Codec (running on ARM1176):
 - SP-MIDI
 - SB-ADPCM
 - MP3
 - WB-AMR
 - AAC/AAC+/eAAC+
- Others:
 - DARP (SAIC)
 - TTY
- Customization:
 - E-Fuses

3.2.4 External Memory

- External Bus Unit
 - 25-bit address bus (512 Mbit) - can be extended to 27 address bits (2 Gbit)
 - 16-bit data bus
 - 1.8V & 2.8V support
- Flash / RAM
 - NOR Type
 - Serial Flash SPI and SPI-4
 - Parallel Flash (Page & Burst Mode)
 - 16-bit Demultiplexed
 - 16-bit AD-multiplexed
 - 16-bit AAD-multiplexed
 - iNAND Type e.g. oneNAND
- Memory card
 - SD/MMC card interface with 1 or 4 data lines

3.2.5 Connectivity

- 3xUSIF (configurable either as SPI or UART), I2C, I2S; Interfaces @ 1.8V
- Direct (U)SIM 1.8/3V
- USB2.0 up to 480 Mbit/s (High Speed) w/ external USB Phy over ULPI interface
- Stereo Headset (Amplifier integrated)
- 3 external analog measurement PIN's
- Bluetooth, A-GPS, WLAN support (I2C, I2S, SPI)

3. TECHNICAL BRIEF

3.2.6 Mixed Signal

- Improved audio performance
- Loudspeaker Audio Class D Amplifier, 700 mW@8 Ω mono for hands-free and ringing
- Stereo Headset 2x30 mW@16 Ω w/o coupling C
- Mono Earpiece 100 mW@16 Ω
- Digital microphone supported
- Differential microphone inputs

3.2.7 FM Radio

- Integrated FM radio
 - FM Stereo RDS Receiver
 - Sensitivity 2 μ V EMF
 - Support for US & EU bands
 - Stereo recording

3.2.8 Power Management

- Direct-to-Battery Connection
 - LDOs (incl. capless)
 - DC/DC step-down converter
- Battery Type
 - Li-Ion
- Charging control
 - Battery temperature
 - Watchdog protection
 - Start-up on flat battery
- External Charger
 - Switch mode
- USB battery charging
 - USB charging spec 1.0 compliant

3.2.9 Display

- Type
 - 320*240, QVGA, 262k color (parallel)
- Interface
 - Parallel 8/9bit MIPI-DBI Type B
 - Serial MIPI-DBI Type C
 - Interf. voltage at 1.8V or 2.8V
- gRacr - Display Controller (Hardware)
 - 30 fps Display update without DMA (up to 60 fps) (full or partial)
 - Video post processing Scaling, Rotation (90° steps), Mirroring
 - Overlay with alpha blending
 - Color conversion YUV -> RGB
 - 2D vector graphics (Lines, filled rectangles, Bit block transfer (e.g. sprites, scrolling, antialiased bitmap fonts)

3.2.10 Camera

- 2.0 Mpx CMOS
- HW JPEG encoder (39 Mpx/sec)
- 39 MHz Pixel Rate
- 15 fps@2.0 Mpx full resolution

3.2.11 Video Capabilities

- Video Decoding MPEG-4/H.263
 - QCIF@30 fps
 - QVGA@15fps
- Video Encoding MPEG-4/H.263
 - QCIF@15 fps

3.2.12 Audio Capabilities

- Polyphonic ring tones
 - 64 voices MIDI, SP-MIDI
 - FM synthesizer
- AMR-WB
- True ring tones (MP3)
- MP3, eAAC+
- G.722 SB-ADPCM encoding/decoding

3. TECHNICAL BRIEF

3.3 Power Management

A mobile platform requires power supplies for different functions. These power supplies are generated in the integrated power management Unit (PMU). The PMU is designed to deliver the power for a typical standard phone.

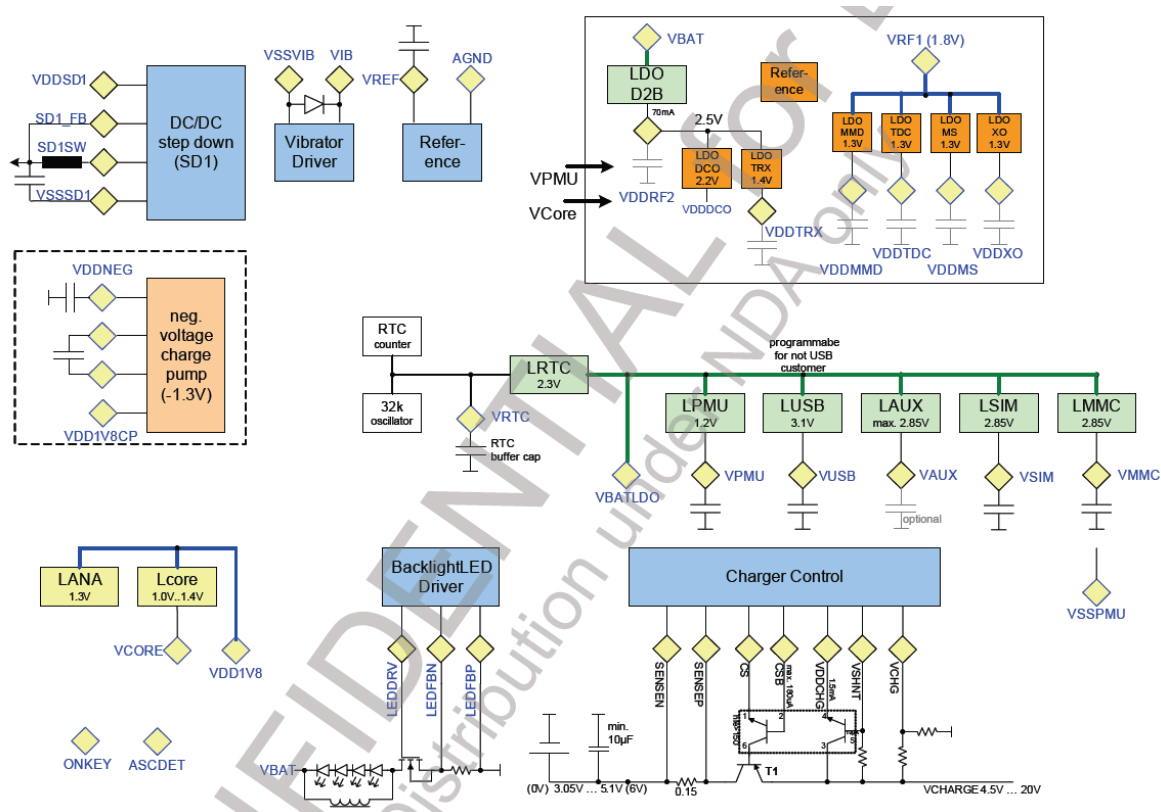


Figure. 3-2-1 Block Figure of the PMU Modules X-Gold tm 213

- **DC/DC Step Down Converter for 1.8V (SD1)**

The DC/DC converter generates a 1.8V supply rail. This voltage rail is used to supply main parts of the system, like the digital core of the chip (via LDO LCORE), some parts of the mixed signal macro, parts of the RF macro and the external memory if a 1.8V memory is used. The efficiency of the DC/DC converter is optimized for an average load current of 100mA. That is the load current estimated for the GSM talk mode.

- **Linear voltage Regulators (low dropout) LDOs**

The LDOs are used to generate the supply for the different supply domains not directly supplied out of the DC/DC converter.

The VSIM output current is high enough to drive USB SIM cards.

- **LCORE**

The LCORE LDO provides the VCORE supply used for most of the digital parts of the chip

- **LPMU**

The LPMU provides VPMU supply for the PMU supply, e.g. for the startup state machine and analog parts like ADC, sense amplifier etc.

- **LUSB**

The LUSB LDO generates the supply for the USB transceiver (output driver and input). If no USB interface is required, LUSB can be used as general purpose LDO.

- **LAUX**

The LAUX generates VAUX. It is a general purpose LDO and can be used for different functions depending on the phone application, e.g. for the display or Camera.

- **LMMC**

The LMMC generates VMMC. It is a general purpose LDO and can be used e.g. for memory cards

- **LSIM**

The LSIM LDO generates the VSIM supply for the SIM card and interface. It is designed to supply Standard SIM cards.

- **Other LDOs**

The RF module has implemented several LDO's for different RF Power domain.

The mixed signal module has some LDO's for the audio driver and microphone supply.

3. TECHNICAL BRIEF

Supply Domain LDO Name	Voltage	Max. Current	Output Cap	Input Domain	Comment
VBAT	0 ... 6.0 V				Operating range is 3.05 V ... 5.5 V, system emergency switch off voltage is about 2.8 V
VDD1V8	1.8 V	450 mA	22 μ F	VBAT	This voltage is generated by the DC/DC converter with 3.3 μ H inductor, The voltage is used for: Memory supply, and via LDO's for digital core supply, mixed signal supply and RF supply.
LCORE	1.2 V	300 mA	2x100 nF	VDD1V8	
LANA	1.3 V	10 mA	No	VDD1V8	No ball
LRTC	2.3 V	2 mA	≥ 100 nF	VBAT	This supply is only used for the HPBG, the 32.768 kHz oscillator and the real-time clock counter required during the sleep- and low-power mode.
LPMU	1.2 V	15 mA	100 nF	VBAT	Supply for the digital part of the PMU including digital control of DC/DC converter. This voltage is also used for the N-DEMOS driver of DC/DC converter and the class-D amplifier and the core PLL.
LUSB	3.1 V	40 mA	100 nF	VBAT	Used for the USB driver supply or as general purpose LDO with programmable output voltages (2.5 V, 2.85 V, 3.1 V)
LAUX	1.5 V ... 2.85 V	150 mA	470 nF	VBAT	General purpose LDO for e.g. Display, Bluetooth, Camera etc. Programmable output voltages are (1.5 V, 1.8 V, 2.5 V, 2.85 V)
LSIM	1.8 V / 2.85 V	30 mA	≥ 100 nF	VBAT	LDO dedicated to the SIM-Card supply. It is chip internal connected to the SIM interface driver.
LMMC	1.5 V ... 2.85 V	150 mA	≥ 470 nF	VBAT	General purpose LDO, targeted for MMC/SD card supply.
VDDNEG	-1.3 V	100 mA	100 nF	VDD1V8	Negative voltage for the bipolar headset audio driver. Generated by a charge pump.

Table. 3.3.1 Power supply Domains (without RF)

3.3.1 Power on and startup

▪ Analog startup Circuit

Because the POR circuit and the LPBG are directly connected to the battery, it is not possible to switch them off. If the battery voltage exceed the power on reset threshold (2.5V), the power on reset is released, the LPMU regulator and the LRTC voltage regulator are switched on. The LPMU regulator starts in its ultra-low power mode

The LPMU regulator generates a control signal (lpmu_OK) that enables the 50KHZ PMU oscillator. The output clock of the oscillator is checked with a fully coded counter. A counter overflow releases the reset (vpmu_rst_n) signal for the small PMU state-machine.

▪ Small first digital State-Machine

The small PMU state-machine is always connected to VPMU After starting from reset the small startup state machine enters the SYSTEM OFF state and only continuous the startup procedure if a switch on event like first connect, on-key, wake up or charge detect occurs.

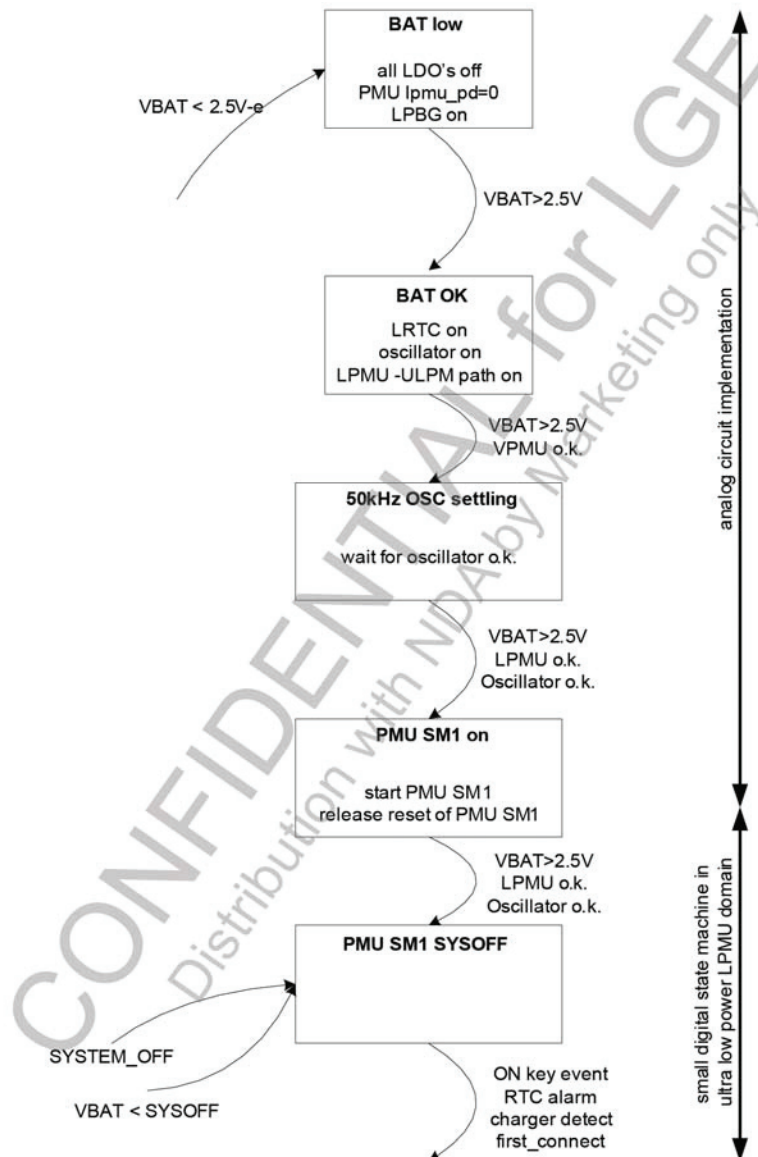
▪ PMU-main State-Machine

The main PMU state-machine is always connected to VPMU also. The power up sequence driven by the PMU state-machine can be seen in Figure18. After enabling the reference (HPGB) and waiting for the settling time, the battery voltage is measured and compared with the power on threshold. If the battery voltage is high enough, the SD1 DC/DC converter and the LCORE LDO are started. A timer ensures that the supply voltage will be stable before the DCXO is enabled. The DCXO settling time is ensured using a fixed timer. After an overflow of this timer, the reset is released for the rest of the system. The PMU state machine remains in this System-ON state until the system is switched into the OFF state. For example the system sleep mode is completely configured by software(for example switching off the LDO's, switching of the DCXO etc.) and controlled by the VCXO_enable signal. The reason for the startup is stored in the ResetSourceRead register.

3. TECHNICAL BRIEF

▪ Battery Measurement

The ADC and the oscillator for the ADC needs the VDD_ADC supply voltage from the LADC LDO. LADC uses either the charger voltage VDD_CHARGE or VDDRTC as input voltage. The input voltage is selected automatically by a bulk switch circuit. LADC, the ADC and the oscillator are enabled on request for every battery measurement if the charger unit is not running. This is handled by an ADC control block in one of the state-machines. If the charger unit is running the ADC is controlled by the charger state-machine



**Figure.3.3.2 First Part of the State Machine,
Running in Different Power Domains than the Second Part**

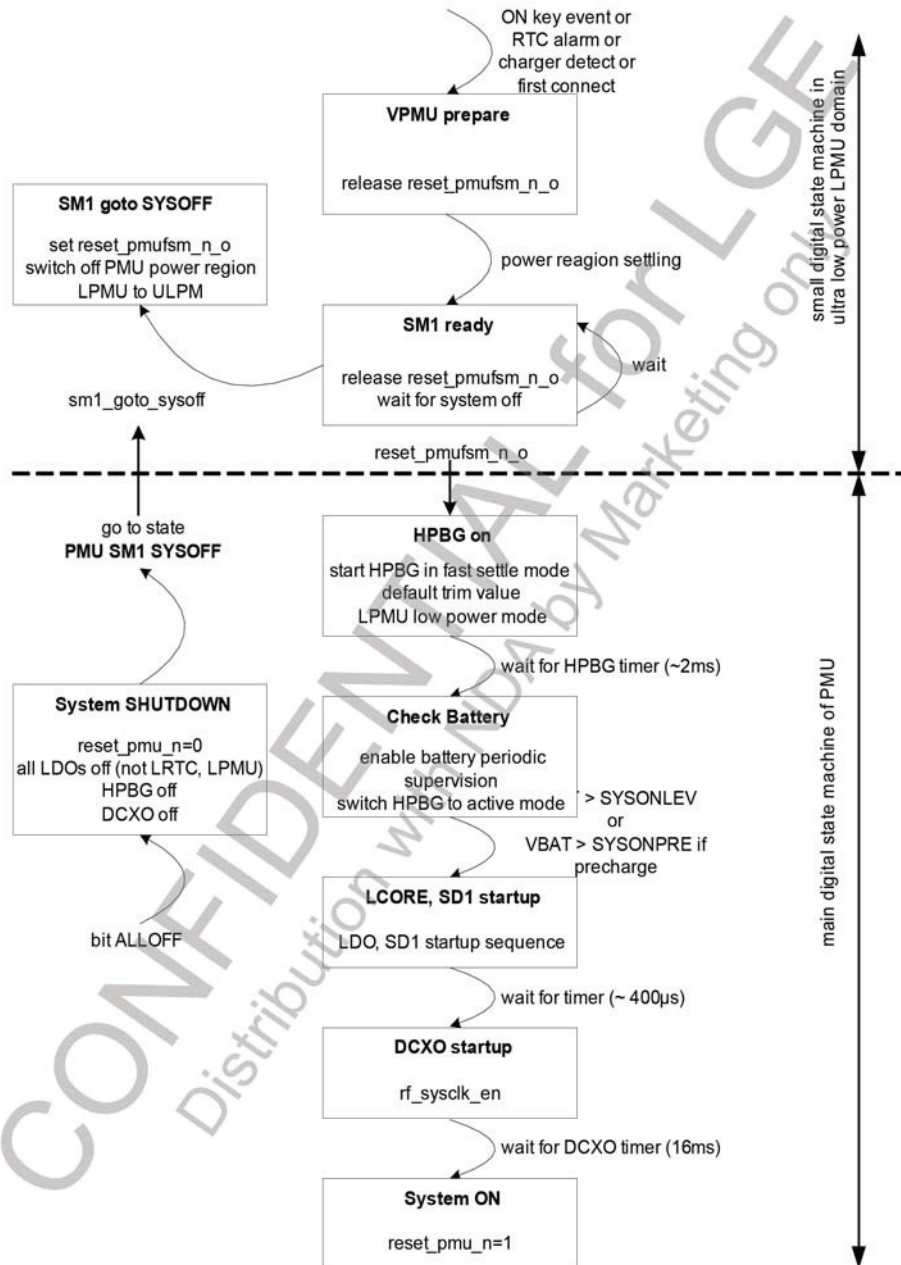


Figure 3.3.3 Second (Main) Part of the Startup State Machine in the VPMU Domain

3. TECHNICAL BRIEF

3.3.2 Switching on due to first connect

If the battery voltage is connected the first time, that means the system enters the first time the SYSOFF state, this is stored in a first connect flag. If the first connect flag is set, the system will start immediately and not wait for any other system on event in the SYSOFF state.

3.3.3 Switching on due to on-Key event

The on key is connected to the ONKEY pad. The ESD protection and the input structure of this pad are connected to VRTC. If the ONKEY pad is forced to VRTC by an external key or similar circuit, the system starts. The ONKEY is sampled with the PMU clock. It has to be sampled four times high before a valid on event is generated. The status of the ON key can be read in the PMU registers, so it can be used as a functional key during phone operation also.

3.3.4 Switching on due to RTC alarm

The real time clock can generate a wakeup signal called RTC alarm. This signal is sampled from the state-machine and after successfully detecting a high, the system is switched on.

3.3.5 Switching on due to charging

When a battery with a voltage below the SSONLEV level is inserted, the state machine will not start the system. As long as the battery voltage stays lower than SYSONLEV the system will stay off. The only possibility to start up the system is due to an external charger.

If an external charger is connected and detected and the battery is charged above the SYSONPRE voltage level the system will start up.

The PMU main state machine waits in the Check battery state until the battery voltage condition is fulfilled. The charger state machine provides the necessary pre-charge indication signal. This pre-charge signal is denounced in a small counter to have a stable signal. This is important, especially in half/full-wave charging where the charger detection is switching between charger detected/not detected according the AC supply frequency. Reasons for details on pre-charging see the charger chapter. The charger is controlled by an independent state machine. The pre-charge signal is used to trigger the pre-charge signal is used to trigger the pre-charge functionality. The charger state machine fully control the pre-charge, the PMU-state machine now changes to state HPBG on state and the system starts. This state change is indicated to the charger state-machine to enable the charger watchdog for safety.

3.3.6 Power Supply Start-up sequence

In order to avoid an excessive drop on the battery voltage caused by in-rush current during system power-on, possibly leading to system instability and “hick-ups” a staggered turn-on approach for the regulators is implemented. The regulators are turned on in a well defined sequence, thus spreading the in-rush current transients over time.

The IO's of X-GOLD TM 213 are isolated in OFF mode (core supply is off). The isolation signal is controlled by the PMU state machine. This ensures that the PADs are in a well defined state during core supply settling. This allows to power up the LCORE core regulator and wait for the core to reach reset state before powering up the I/O supply regulators.

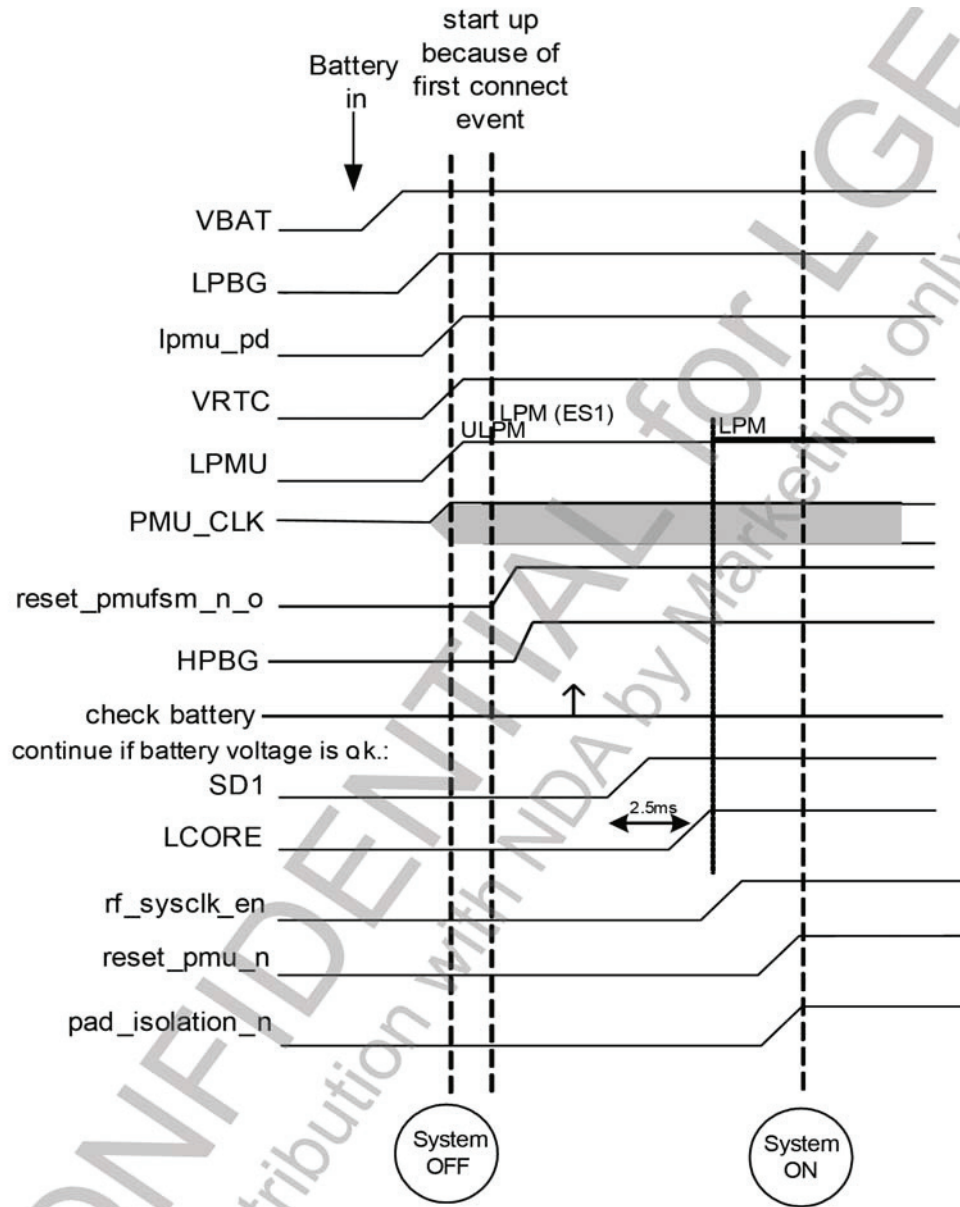


Figure 3.3.4 Start Up Sequence (triggered by First Connect Event)

3. TECHNICAL BRIEF

3.3.7 External Reset Handling

The chip reset can be controlled by an external RESET_N ball. If this ball is pulled low, the chip will be reset. All PMU registers are reset during the external reset including LSIM control bits. The PMU statemachines are also not reset from the external reset. An SW or watchdog reset will not reset the PMU registers. A SW and Watchdog reset is seen on the reset_n pad to allow the reset of external devices. Basically there are three reset sources, first the reset signal controlled by the PMU (reset_pmu_n_o), second the reset signal controlled by the SCU (resetout_o) and third the external reset (RESET_N). The SCU reset is triggered by SW (for example due to a SW reset or watchdog reset). The PMU reset is controlled by the PMU state machine. The output of the reset handling block is the reset_postscu_n_o signal. This signal controls for example the μ C subsystem and releases reset for the controller. During normal start up, the PMU releases the reset_pmu_n_o signal after entering the SYSTEM ON state. At this time the resetout_o signal is high, the RESET_N pad is not pulled low and therefore the reset_postscu_n_o signal follows the reset_pmu_n_o signal. That means the μ C reset will be released and the μ C starts operation. If the SW triggers an external reset via the SCU, signal resetout_o will be forced to low for a certain time and RESET_N will be forced to low by the open drain driver. At the same time the feedback to the SCU will be masked to not reset the baseband. The RESET_N pad is in the VDDRTC domain but the internal pull up is connected to the VDD_VDIG1 (1.8V) domain. That allows the pad to be used as reset for external devices running in the VDD1V8 domain. The RESET_N pad can also be used to monitor the chip internal reset condition during startup.

The open drain driver is a weak driver, that means it can be forced to high during debug from external pushing some current into the pad. In testmode signal reset_pmu_n_o is high, that means the chip reset is fully controlled from external.

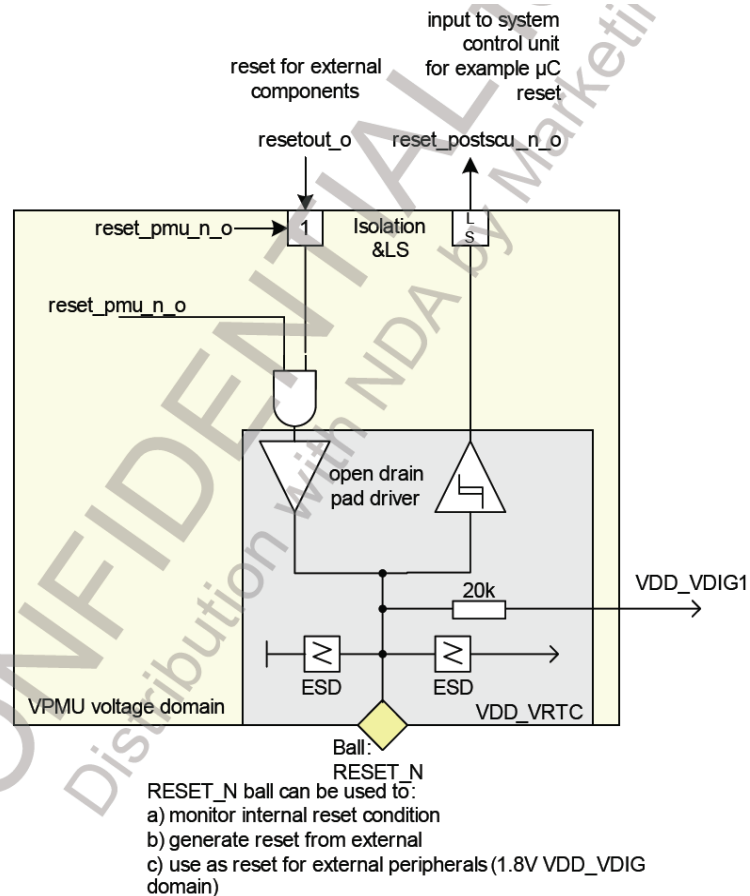


Figure 3.3.5 PMU, CGU and External Reset

3.3.8 Sysclock Switching

The PMU controls the `rf_sysclk_en` signal of the DCXO in the RF macro. During startup the PMU enables the DCXO. After the system is running the DCXO is controlled by the SCU of the baseband by using the `vcxo_enable` signal. This is handled by a dedicated logic in the PMU, see **Figure 3.3.6**. As long as `rf_sysclk_en_pmu`, the output of the PMU state-machine is high, `vcxo_enable` controls the `rf_sysclk_en` signal to the RF. If `rf_sysclk_en_pmu` is low, the DXCO is switched off, independent from `vcxo_enable`.

3. TECHNICAL BRIEF

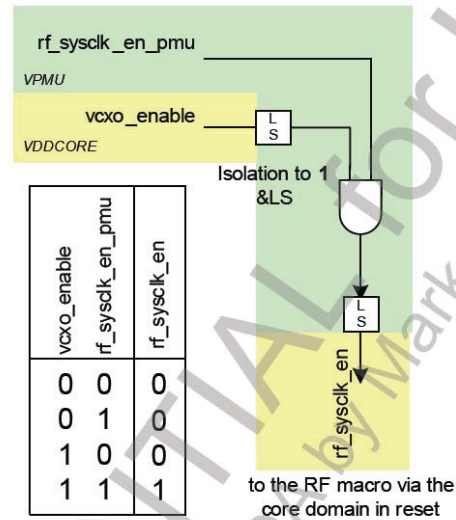


Figure 3.3.6 How sysclock Enable is Routed in the PMU

3.3.9 Undervoltage Shutdown

In active mode the PMU periodically measures the battery voltage using the ADC from the charger unit. If the battery is measured to be below the programmable shut-down level (called SYSOFF), the system changes to OFF mode. This is done via the SHUTDOWN state of the PMU state machine. (see chapter switch OFF)

3.3.10 Software Reset

A software reset does not affect any PMU register. The PMU register are reset with the `reset_pmufsm_no` signal. That means all PMU register are reset in OFF state. For details about the SW reset see chapter **External Reset Handling**

3.3.11 PMU Clock

During the first startup (for example plugging in a battery) a PMU internal oscillator is used for generation of the PMU clock (pmu_clock). The frequency is slightly above 32 kHz (typ. 50 kHz) to be out of the audio band also for worst case devices. After first startup the software shall enable the 32 kHz crystal oscillator. It is not possible to use the 32 kHz oscillator during first startup, because the settling time of the oscillator can be quite long. After the 32 kHz oscillator is running and settled the software shall switch the PMU clock to the 32 kHz clock and disable the internal PMU oscillator for power saving reasons. The 32 kHz oscillator shall never be disabled after the PMU clock has been switched. The ADC in the charger unit has its own oscillator generating a frequency of about 10 MHz. This oscillator is running during charging and during battery measurements triggered by the PMU. It is off otherwise.

3.3.12 System Sleep Mode

The sleep mode is controlled by using the VCXO_enable signal. This signal is used to switch the LDO's and the DC/DC converter SD1 in a programmable way into its low power mode (PFM). In addition DC/DC converter SD1 can be configured to change the output voltage to a lower value for additional power saving. VCXO_enable is also used to deactivate the HPBG and setting LDO LPMU in the ultra-low-power mode. In addition the DCXO is switched off by the VCXO_enable signal. The VCXO_enable signal is also used to switch some LDO's (software configured) to sleep and/or off mode or to change the output voltages of said LDO's. The state of the main PMU state machine is not changed due to VCXO_enable.

3.3.13 DC/DC Pre-Load Register Handling

The DC/DC converter works in different modes. If the mode is switched from PFM to PWM the pulse-width of the DC/DC converter depends on the current battery voltage (and on the output voltage). The PMU state-machine knows the battery voltage because of the battery supervision function. Depending on this value it selects a startup pulse-width for the DC/DC converter out of a register table. (4-values)

3.3.14 Power Down Sequence

Setting bit OFF in the GeneralControl register switches the system into OFF mode. After the turn off event, the state-machine switches to the SHUTDOWN state. The reset_pmu_n_o signal changes to low, the I/O pads are isolated using the padisolation_n signal, the LCORE LDO and the SD1 DC/DC converter are switched off, the LPMU LDO is switched to ultra-low power mode, the DCXO is turned off and the bandgap buffer is disabled. Before switching OFF the software shall have enabled the 32 kHz oscillator and has switched the PMU clock to the 32 kHz clock to archive the target OFF current .

3. TECHNICAL BRIEF

3.4 FEM with integrated Power Amplifier Module (SKY77547, U301, U302)

3.4.1 Internal Block Diagram

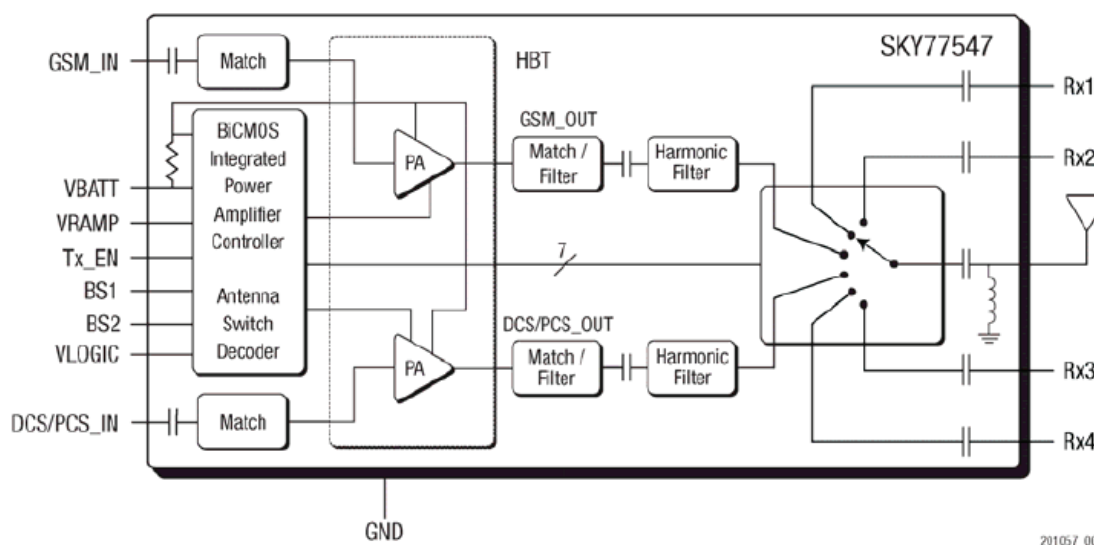


Figure. 3.4.1 SKY77547 FUNCTIONAL BLOCK DIAGRAM

3.4.2 General Description

The **SKY77547** is a transmit and receive front-end module (FEM) with Integrated Power Amplifier Control for quad-band cellular handsets comprising GSM850/900 and DCS1800/PCS1900 operation. Designed in a low profile, compact form factor.

The FEM also supports Class 12 General Packet Radio Service (GPRS) multi-slot operation.

The module consists of a GSM850/900 PA block and a DCS1800/PCS1900 PA block, impedance matching circuitry for 50 Ω input and output impedances, TX harmonics filtering, high linearity and a low insertion loss PHEMT RF switch, and a Power Amplifier Control (PAC) block with internal current sense resistor. A custom BiCMOS integrated circuit provides the internal PAC function and decoder circuitry to control the RF switches. The two Heterojunction Bipolar Transistor (HBT) PA blocks are fabricated onto a single Gallium Arsenide (GaAs) die. One PA block supports the GSM850/900 bands and the other PA block supports the DCS1800/PCS1900 bands. Both PA blocks share common power supply pads to distribute current. The output of each PA block and the outputs to the four receive pads are connected to the antenna pad through a PHEMT RF switch. The GaAs die, PHEMT die, Silicon (Si) die and passive components are mounted on a multi-layer laminate substrate. The assembly is encapsulated with plastic overmold.

3. TECHNICAL BRIEF

Mode	VLOGIC	Input Control Bits		
		TX_EN	BS1	BS2
STANDBY	0	X	X	X
RX1	1	0	0	0
RX2	1	0	0	1
RX3	1	0	1	1
RX4	1	0	1	0
LB_TX	1	1	0	X
HB_TX	1	1	1	X

1. X = DON'T CARE

2. RX1, RX2, RX3, and RX4 are broadband receive ports and each supports the GSM850, GSM900, DCS, and PCS bands.

Table 3.4.1 Band SW Logic Table

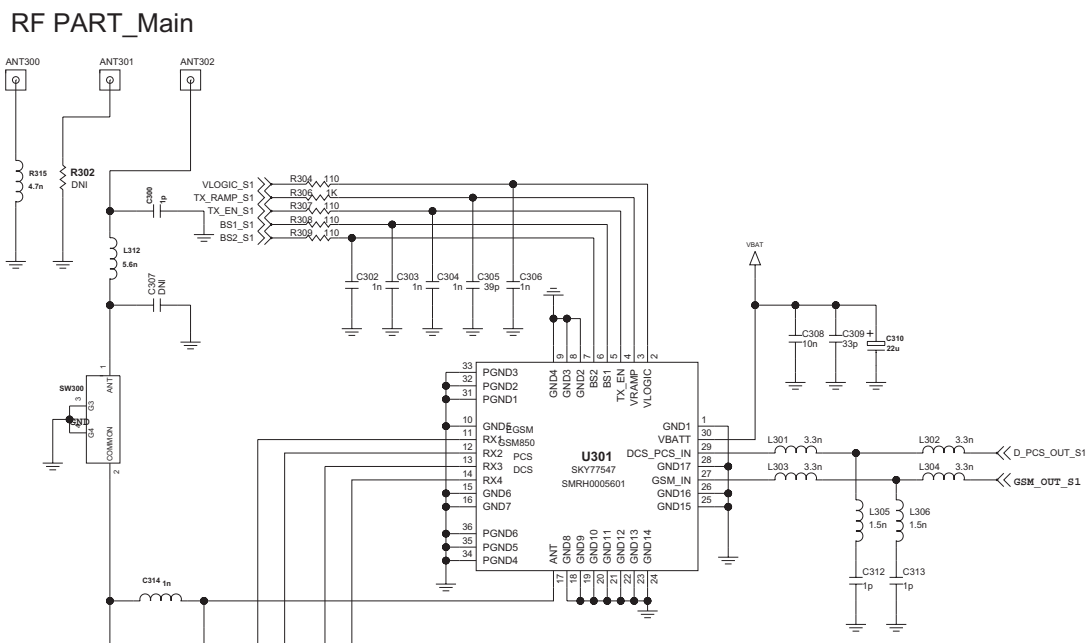
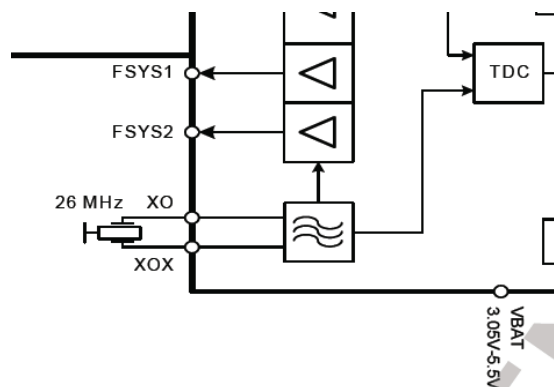


Figure 3.4.2 FEM CIRCUIT DIAGRAM

3. TECHNICAL BRIEF

3.5 Crystal(26 MHz, X100, X400)



The X-GOLDTM213 RF-Subsystem contains a fully integrated 26 MHz digitally controlled crystal oscillator, designed for 8 pF crystals. The only external part of the oscillator is the crystal itself. Overall pulling range of the DCXO is approximately ± 55 ppm, controllable by a 13-bit tuning word.

This frequency serves as comparison frequency within the RF-PLL and as clock frequency for the digital circuitry. The 26 MHz reference clock can also be applied to external components like Bluetooth or GPS, via the two buffered output signals FSY1 and FSY2.

Figure. 3.5.1 Crystal Oscillator External Connection

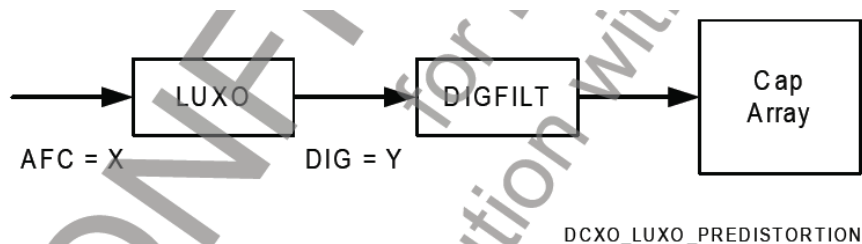


Figure. 3.5.2 Digital PREDISTORTION with LUXO

The DCXO tuning characteristic should be a first order linear function of the programming word AFC. The variable capacitance array is a first order linear function of the digital word DIG, which leads to a nonlinear curve ppm vs. DIG (and also a nonlinear ppm vs. AFC for DIG=AFC). In order to linearize the ppm vs. AFC curve the implementation of a predistortion is necessary.

To get the wanted linear ppm vs. AFC tuning curve some digital predistortion of the AFC word is required. This predistortion is performed by the linearization unit for crystal oscillator (LUXO). The LUXO calculates the corresponding DIG value according to the given AFC value.

3.6 RF Subsystem of PMB8810 (U101, U401)

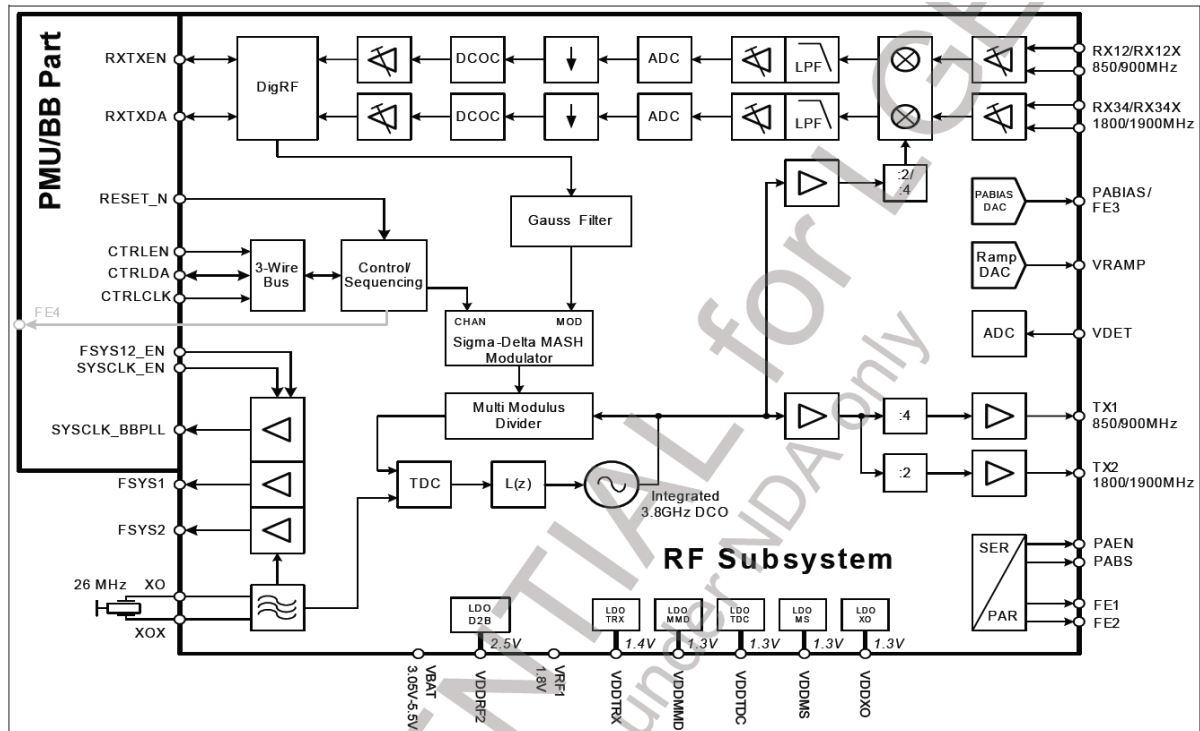


Figure. 3-6-1 Block DIAGRAM of RF Subsystem

3.6.1 GENERAL DESCRIPTION

The PMB8810 RF subsystem is designed for dual-band GSM voice and data applications (GPRS class 12). The system can be configured to support one low band, GSM850 or EGSM900, and one high band, DCS1800 or PCS1900. A block diagram of the RF subsystem is given in Figure 3-6-1.

3. TECHNICAL BRIEF

3.6.2 FUNCTIONAL DESCRIPTION

3.6.2.1 Receiver

The X-GOLD™213 dual-band receiver is based on a Direct Conversion Receiver (DCR) architecture. Input impedance of the LNAs is optimized to achieve a matching without (external) high quality inductors. By use of frequency dividers (by 2/4) the LO frequency is derived from the RF frequency synthesizer. The receive path is fully differential to suppress the on-chip interferences and reduce DC-offsets. The analog chain of the receiver contains two LNAs (low/high band), a quadrature mixer followed by an analog baseband filter and 14-bit continuous-time delta-sigma analog-to-digital converter. The filtered and digitized signal is fed into the digital signal processing chain, which provides decimation, DC offset removal and programmable gain control.

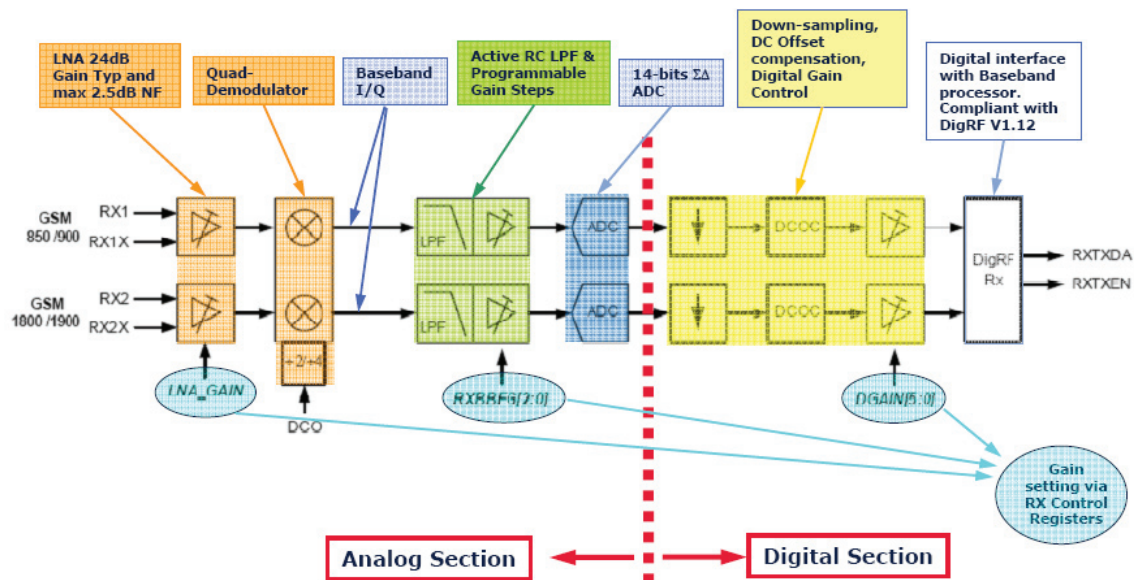


Figure. 3.6.2 RECEIVER CHAIN BLOCK DIAGRAM

3.6.2.2 Transmitter

The GMSK transmitter supports power class 4 for GSM850 or GSM900 as well as power class 1 for DCS1800 or PCS1900. The digital transmitter architecture is based on a fractional-N sigma-delta synthesizer for constant envelope GMSK modulation. This configuration allows a very low power design without any external components.

Up- and down-ramping is performed via the ramping DAC connected to VRAMP.

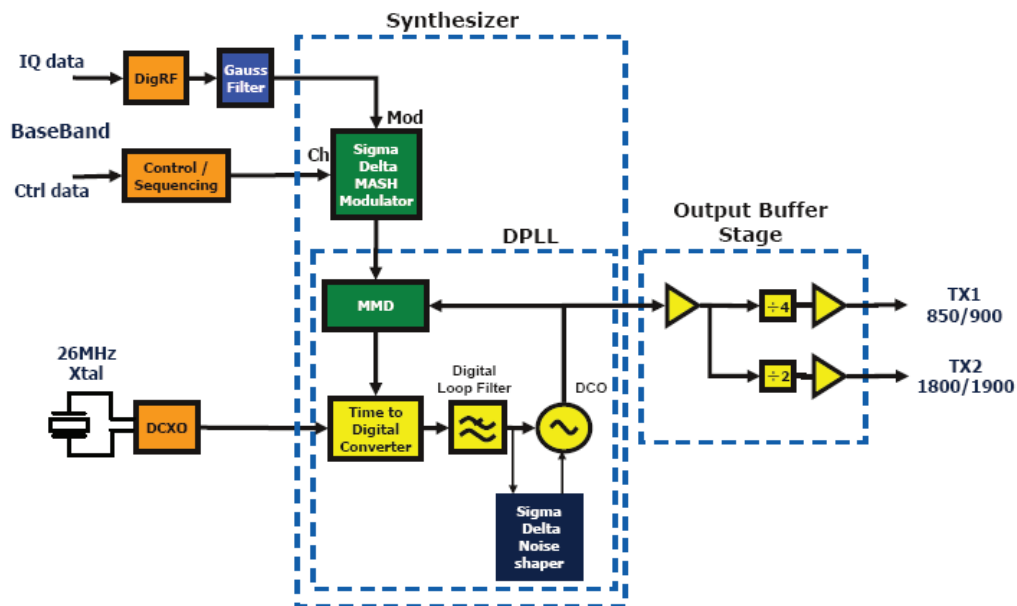


Figure. 3.6.3 TRANSMITTER CHAIN BLOCK DIAGRAM

RF synthesizer

The RF subsystem contains a fractional-N sigma-delta synthesizer for the frequency synthesis. Respective to the chosen band of operation the phase locked loop (PLL) operates at twice or forth of the target signal frequency. In receive operation mode the divided output signal of the digital controlled oscillator output (DCO) serves as local oscillator signal for the balanced mixer. For transmit operation the fractional-N sigma-delta synthesizer is used as modulation loop to process the phase/frequency signal. The 26 MHz reference signal of the phase detector incorporated in the PLL is provided by the reference oscillator.

3. TECHNICAL BRIEF

3.6.2.3 Front-end/PA Control Interface

Two outputs (FE1, FE2) for direct control of antenna switch modules enable to select RX- and TX-mode as well as low- and high-band operation.

An extra band select signal PABS for the power amplifier is used, to support discrete PA and switching modules. Time accurate power dissipation of the PA is achieved by the control signal PAEN.

A minor set of power amplifiers require a bias voltage to enhance power efficiency. Support of this power amplifiers is achieved by the implemented bias DAC.

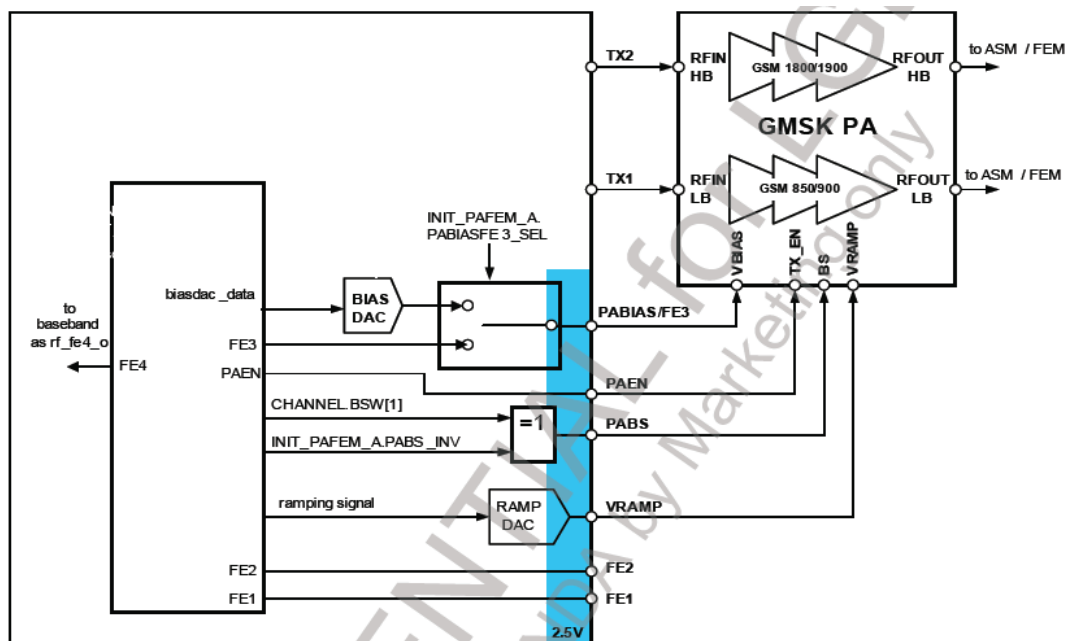


Figure. 3.6.4 PA AND FEM CONTROL BLOCK DIAGRAM

3.6.2.4 Power Supply

To increase power efficiency most parts of the RF subsystem are supplied by the DCDC converter situated in the PMU subsystem. Conversion of the 1.8 V output voltage of the DCDC to the 1.3 V/1.4 V circuit supply voltages is achieved by several Low-DropOut regulators (LDO).

One embedded direct-to-battery LDO provides the 2.5 V supply voltage for the remaining circuits.

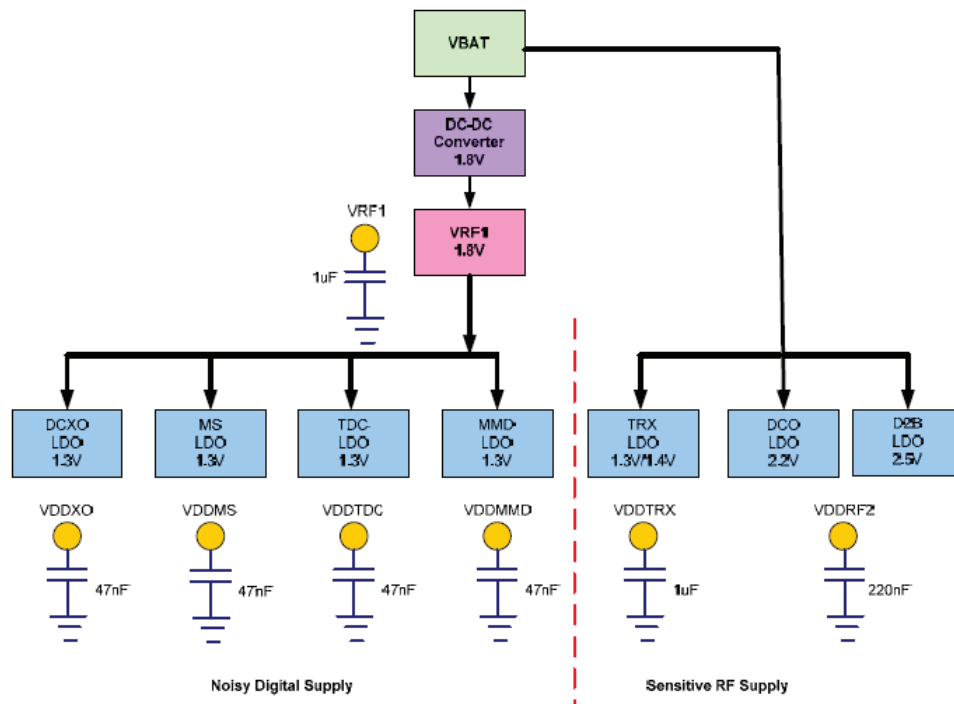


Figure. 3.6.5 POWER SUPPLY BLOCK DIAGRAM

3. TECHNICAL BRIEF

3.7 MEMORY

LGP520 is composed of 3 memories.

2 Main Memory(NOR+pSRAM) are connected each Main Chip(SIM1 AGR+ / SIM2 AGR+).
and 1 DPRAM is used to communicate between 2 Main Memory(NOR+pSRAM).

3.7.1 Main memory (KA8520N00A-BWWW, U100 / S71VS128RC0AHK4L0,U402)

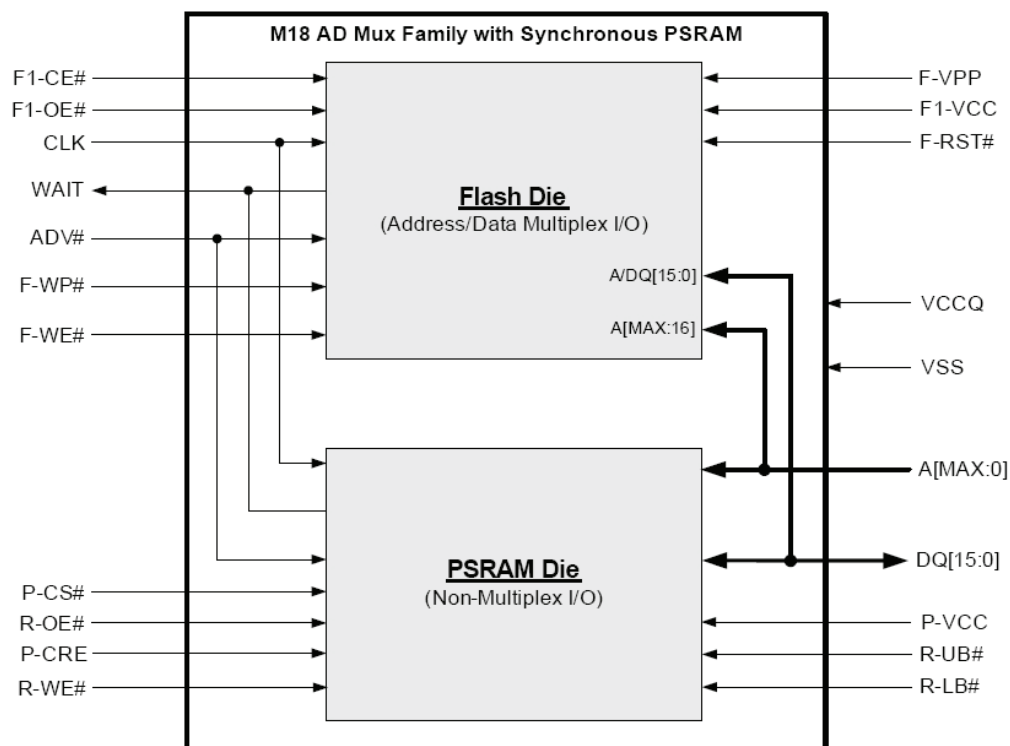


Figure. 3.7.1 MAIN MEMORY BLOCK DIAGRAM

The Numonyx™ StrataFlash® Cellular Memory (M18) device provides high read and write performance at low voltage on a 16-bit data bus.

The flash memory device has a multi-partition architecture with read-while-program and read-while-erase capability.

The device supports synchronous burst reads up to 108 MHz using ADV# and CLK address-latching on some litho/density combinations and up to 133 MHz using CLK address-latching only on some litho/density combinations.

It is listed below in the following table.

Litho (nm)	Density (Mbit)	Supports frequency up to (MHz)	Sync read address-latching
90	256	133	CLK-latching
	512	108	Legacy-latching
65	128	133	CLK-latching
	256	133	CLK-latching
	512	108	Legacy-latching
	512	133	CLK-latching
	1024	108	Legacy-latching
	1024	133	CLK-latching

Table 3_7_1 M18 Frequency combinations

In continuous-burst mode, a data Read can traverse partition boundaries.

Upon initial power-up or return from reset, the device defaults to asynchronous arrayread mode.

Synchronous burst-mode reads are enabled by programming the Read Configuration Register. In synchronous burst mode, output data is synchronized with a user-supplied clock signal. A WAIT signal provides easy CPU-to-flash memory synchronization.

Designed for low-voltage applications, the device supports read operations with VCC at 1.8 V, and erase and program operations with VPP at 1.8 V or 9.0 V. VCC and VPP can be tied together for a simple, ultra-low power design. In addition to voltage flexibility, a dedicated VPP connection provides complete data protection when VPP is less than VPPLK.

A Status Register provides status and error conditions of erase and program operations.

One-Time-Programmable (OTP) registers allow unique flash device identification that can be used to increase flash content security. Also, the individual block-lock feature provides zero-latency block locking and unlocking to protect against unwanted program or erase of the array.

The flash memory device offers three power savings features:

- Automatic Power Savings (APS) mode: The device automatically enters APS following a read-cycle completion.
- Standby mode: Standby is initiated when the system deselects the device by deasserting CE#.
- Deep Power-Down (DPD) mode: DPD provides the lowest power consumption and is enabled by programming in the Enhanced Configuration Register. DPD is initiated by asserting the DPD pin.

3. TECHNICAL BRIEF

3.7.2 LGP520 SIM1 Part Main Memory (KA8520N00M-BWWW, U100)

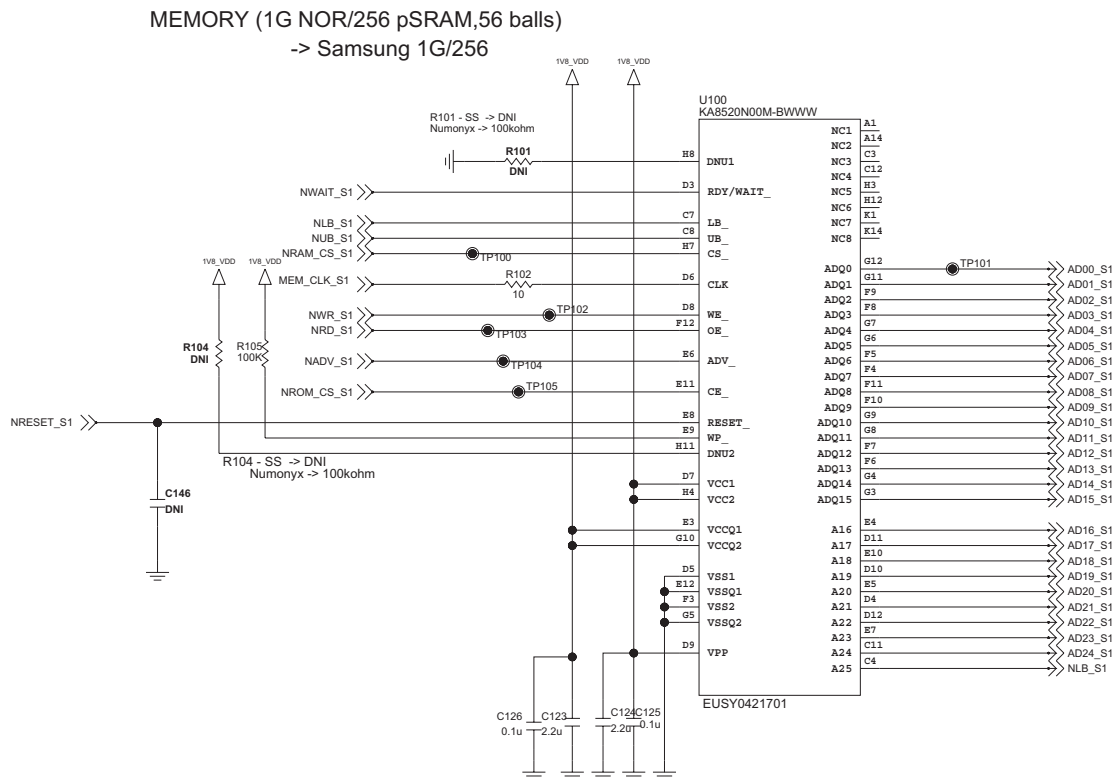


Figure. 3.7.2 SIM1 Part Memory(NOR+pSRAM) Circuit Diagram

3.7.3 LGP520 SIM2 Part Main Memory (S71VS128RC0ZHK200, U402)

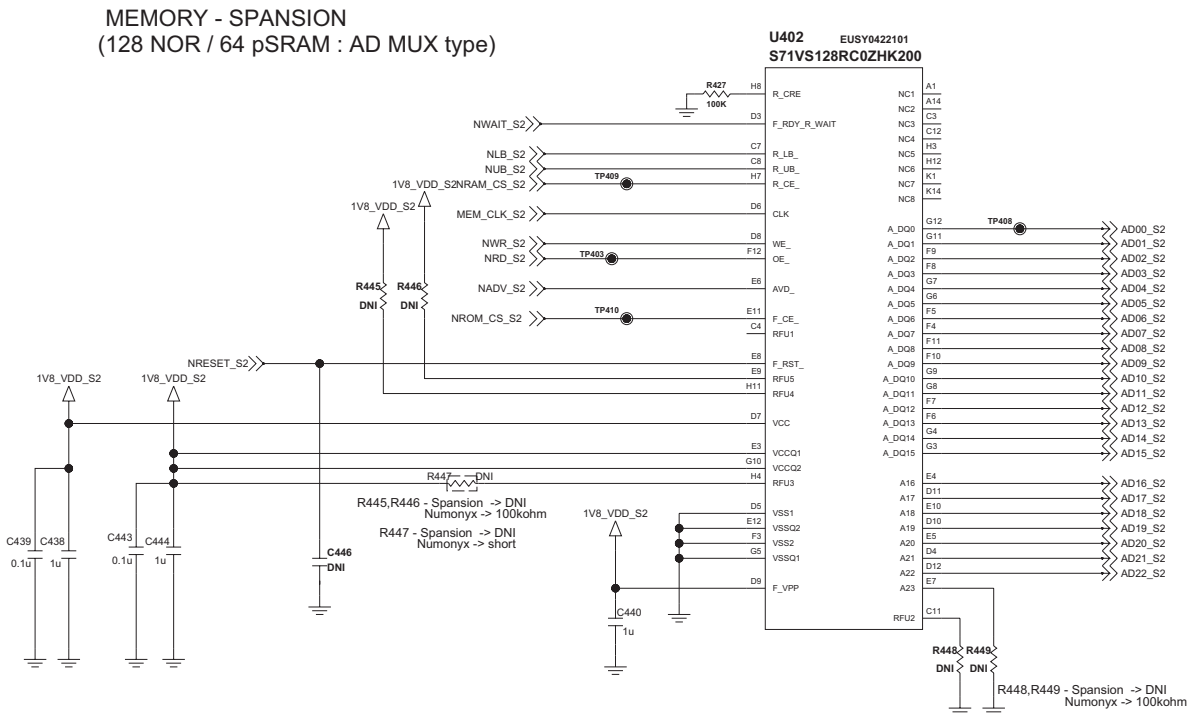


Figure. 3.7.3 SIM2 Part Main Memory(NOR+pSRAM) Circuit Diagram

3. TECHNICAL BRIEF

3.7.4 Dual Port Memory (IDT70P255 , U400)

The IDT70P255 consist of an array of 16k, 8k, and 4k words of 16 dual-ported SRAM cells, IO, address lines, and control signals (CS#, ADV#, OE#, and WE#). Between the two access ports, one is a dedicated time multiplexed address and data interface; the other is a pin selectable port to either standard SRAM or time multiplexed address and data interface. Independent control signals for each port permit simultaneous access to any location in memory. To handle the situation of writing and reading to the same location, a BUSY# pin is provided on each port. For port to port communication, an Interrupt (INT#) pin is also available on each port.

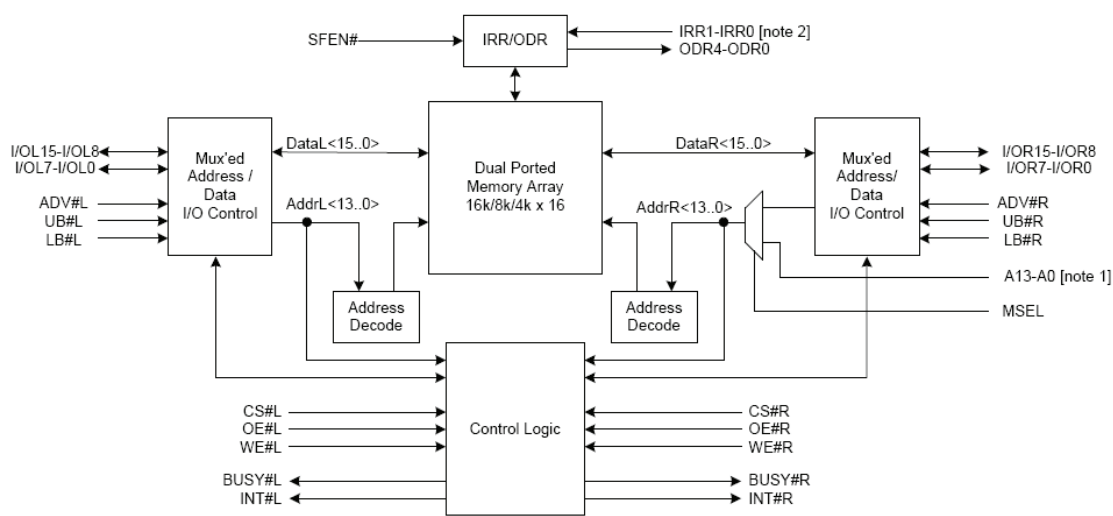


Figure. 3.7.4 Dual Port MEMORY BLOCK DIAGRAM

3.7.5 LGP520 Dual Port Memory (IDT70P255, U400)

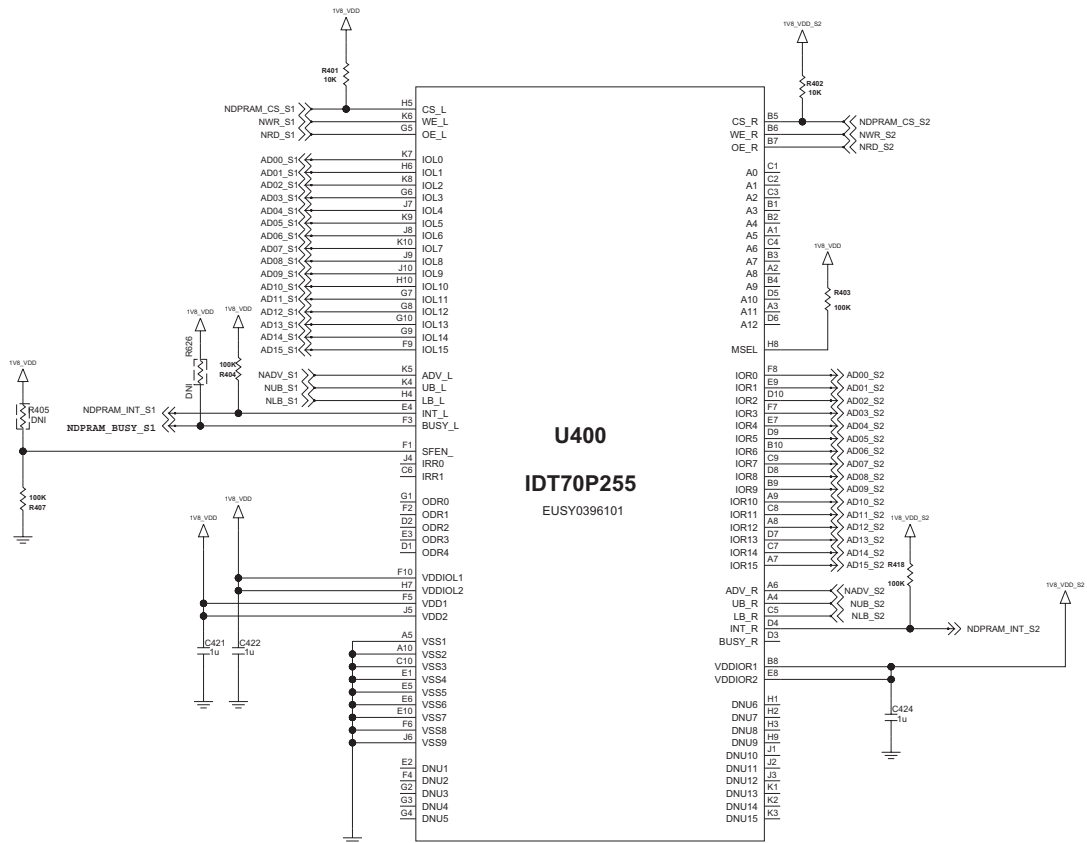


Figure. 3.7.3 Dual Port Memory Circuit Diagram

3. TECHNICAL BRIEF

3.8 Bluetooth module

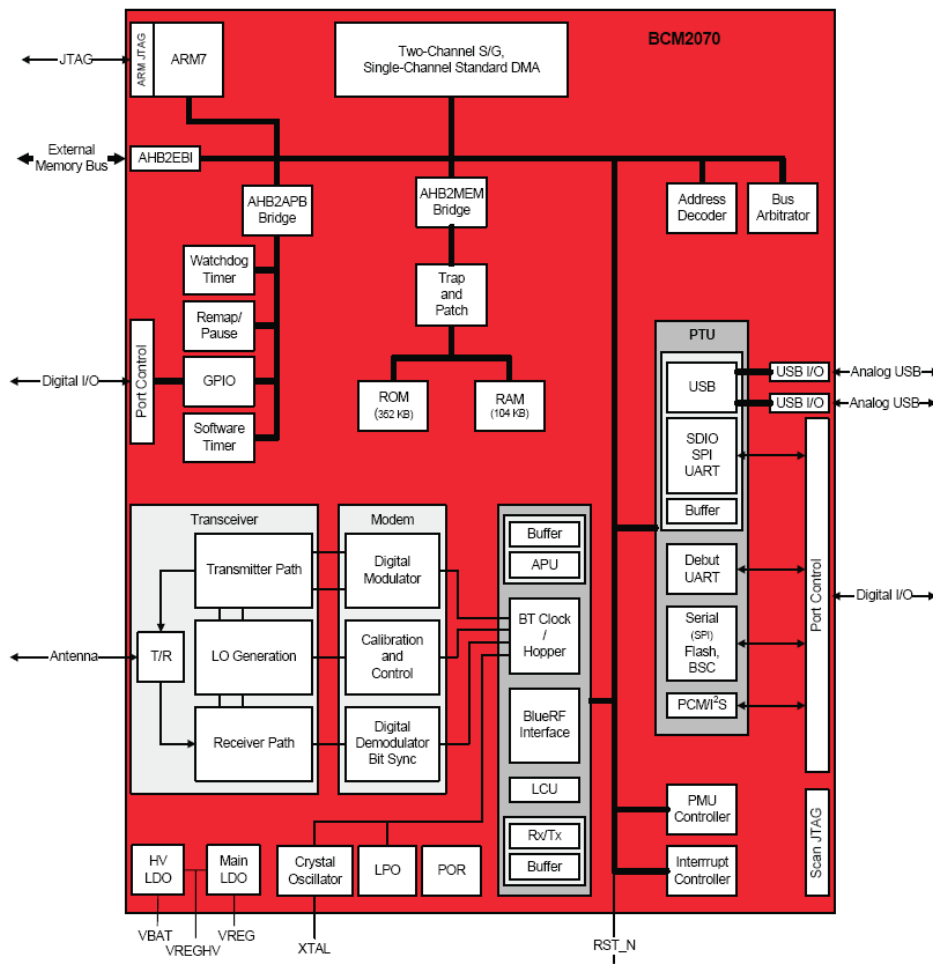


Figure 3.8.1. Bluetooth BLOCK DIAGRAM

This module has an integrated radio transceiver that has been optimized for use in 2.4GHz Bluetooth Wireless systems. It has been designed to provide low-power, robust communications for applications Operating in the globally available 2.4GHz unlicensed ISM band. It is fully compliant with the Bluetooth Radio Specification and enhanced data rate specification and meets or exceed the requirement to provide the highest communication link quality of service.

3.8.1 Transmitter path

This module features a fully integrated zero IF transmitter. The baseband transmitted data is digitally modulated in the modem block and up-converted to the 2.4GHz ISM band in the Transmitter path. The transmitter path consists of signal filtering, I/Q up-conversion, high-output power amplifier (PA), and RF filtering. It also incorporates modulation schemes P/4-DQPSK for 2 Mbps and 8-DPSK for 3 Mbps to support enhanced data rate.

• Digital modulator

The digital modulator performs the data modulation and filtering required for the GFSK, B/4DQPSK, and 8-DPSK signal. The fully digital modulator minimizes any frequency drift or anomalies in the modulation characteristics of the transmitted signal and is much more stable than direct VCO modulation schemes.

• Power Amplifier

The integrated PA for the BCM2070 is configurable for Class 2 operation, transmitting up to +4 dBm as well as Class 1 operation and transmit power up to +12 dBm at the chip, GFSK, >2.5V supply. Due to the linear nature of the PA, combined with some integrated filtering, no external filters are required for meeting Bluetooth and regulatory harmonic and spurious requirements. For integrated mobile handset applications, where Bluetooth is integrated next to the cellular radio, minimal external filtering can be applied to achieve near thermal noise levels for spurious and radiated noise emissions.

Using a highly linearized, temperature compensated design the PA can transmit +12 dBm for Basic rate and +10 dBm for enhanced data rates (2 to 3 Mbps). A flexible supply voltage range allows the PA to operate from 1.2V to 3.0V. The minimum supply voltage at VDDTF is 1.8V to achieve +10dBm of transmit power.

3.8.2 Receiver path

The receiver path uses a low IF scheme to down-convert the received signal for demodulation in the digital demodulator and bit synchronizer. The receiver path provides a high degree of linearity, an extended dynamic range, and high order on-chip channel filtering to ensure reliable operation in the noisy 2.4GHz ISM band. The front-end topology, with built-in out-of-band attenuation, enables the device to be used in most applications with no off-chip filtering. For integrated handset operation where the Bluetooth function is integrated close to the cellular transmitter, minimal external filtering is required to eliminate the desensitization of the receiver by the cellular transmit signal.

3.9 Dual SIM Card Interface

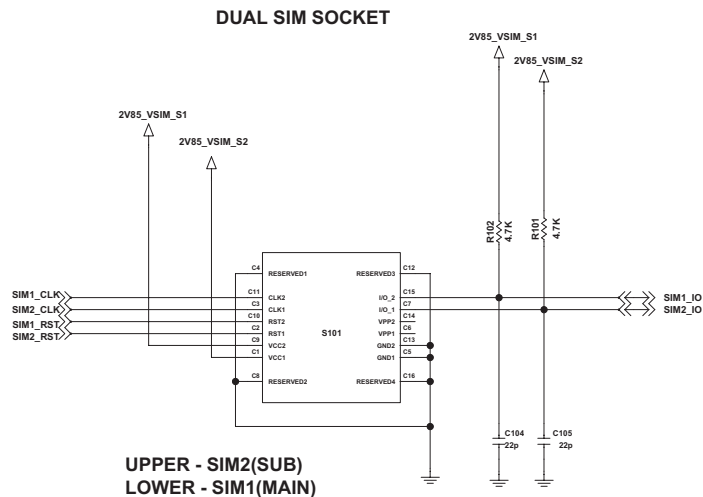


Figure 3.9.1. Dual SIM CARD Interface

The Main Base Band Processor(XMM2130) provides SIM Interface Module. The XMM2130 checks status Periodically During established call mode whether SIM card is inserted or not, but it doesn't check during deep sleep mode. In order to communicate with SIM card, 3 signals SIM_IO, SIM_CLK, SIM_RST.

LGP520 supports dual SIM mode and each SIM supports 3.0V SIM Card.

SIM interface scheme is shown in (Figure 3.9.1).

SIM_IO, SIM_CLK, SIM_RST ports are used to communicate with Main Chip(AGR+)

Signal	Description
SIM_RST	This signal makes SIM card to HW default status.
SIM_CLK	SIM card reference clock.
SIM1_IO / SIM2_IO	This signal is interface datum.

3.10 LCD Interface

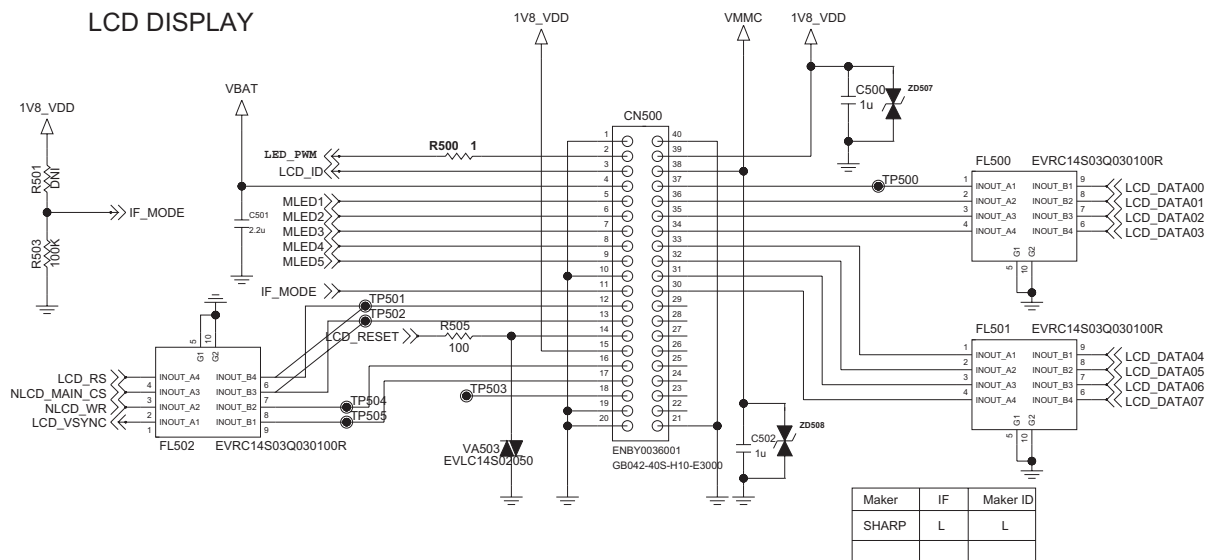


Figure 3.10.1. LCD Interface

LGDP4525B is a 262,144-color one-chip SoC driver for a-TFT liquid crystal display with resolution of 320RGBx240dots, comprising a 528-channel source driver, a 220-channel gate driver, 87120 bytes RAM for graphic data of 320RGBx240 dots, and power supply circuit. LGDP4525B can operate with low I/O interface power supply up to 1.65V, with an incorporated voltage follower circuit to generate voltage levels for driving an LCD. The LGDP4525B also supports a function to display in 8 colors and a standby mode, allowing for precise power control by software.

3. TECHNICAL BRIEF

BACKLIGHT CHARGE PUMP

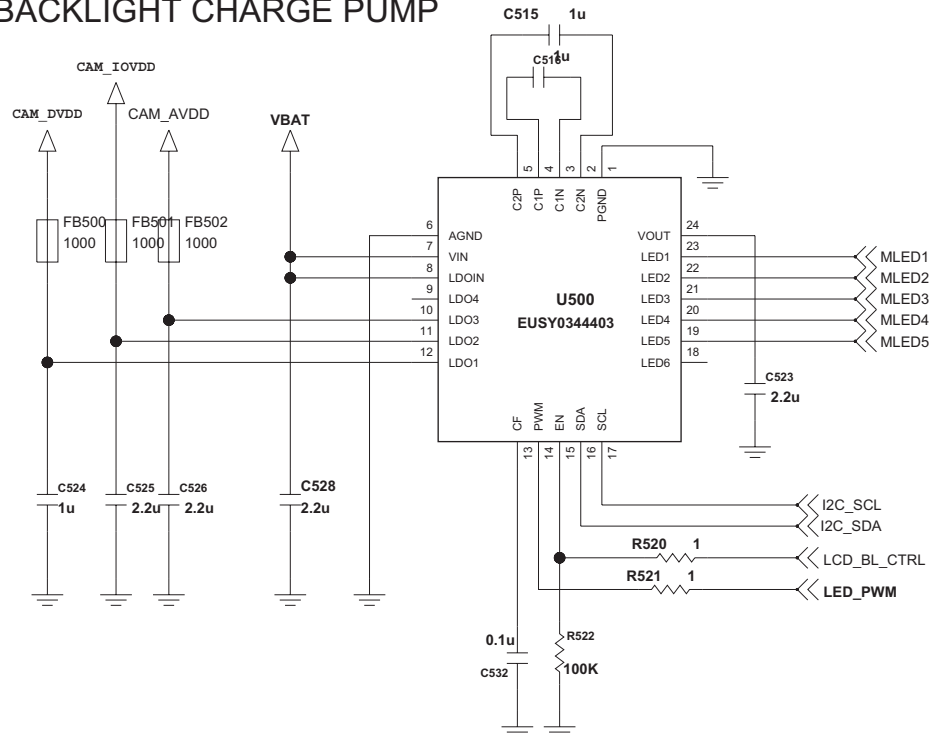


Figure 3.10.2. RT9396 CIRCUIT DIAGRAM

The RT9396 is a high efficiency charge pump LED driver using Semtech's proprietary mAhXLife™ technology. Performance is optimized for use in single-cell Li-ion battery applications.

The charge pump provides backlight current in conjunction with four matched current sinks. The load and supply conditions determine whether the charge pump operates in 1x, 1.5x, or 2x mode. An optional fading feature that gradually adjusts the backlight current is provided to simplify control software. The RT9396 also provides two low-dropout, low-noise linear regulators for powering a camera module or other peripheral circuits.

The RT9396 uses the proprietary SemWire™ single wire interface. The interface controls all functions of the device, including backlight current and two LDO voltage outputs. The single wire implementation minimizes microcontroller and interface pin counts.

In sleep mode, the device reduces quiescent current to 100μA while continuing to monitor the serial interface. The two LDOs can be enabled when the device is in sleep mode. Total current reduces to 0.1μA in shutdown.

LED Backlight Current Sinks

The backlight current is set via the SemWire interface. The current is regulated to one of 32 values between 0.5mA and 25mA. The step size varies depending upon the current setting. Between 0.5mA and 12mA, the step size is 0.5mA. The step size increases to 1mA for settings between 12mA and 15mA and 2mA for settings greater than 15mA. This feature allows finer adjustment for dimming functions in the low current setting range and coarse adjustment at higher current settings where small current changes are not visibly noticeable in LED brightness.

All backlight current sinks have matched currents, even when there is variation in the forward voltages (ΔV_F) of the LEDs. A ΔV_F of 1.2V is supported when the input voltage is at 3.0V. Higher ΔV_F LED mismatch is supported when V_{IN} is higher than 3.0V. All current sink outputs are compared and the lowest output is used for setting the voltage regulation at the V_{OUT} pin. This is done to ensure that sufficient bias exists for all LEDs.

The backlight LEDs default to the off state upon powerup. For backlight applications using less than four LEDs, any unused output must be left open and the unused LED driver must remain disabled. When writing to the Backlight Enable Control register, a zero (0) must be written to the corresponding bit of any unused output.

Backlight Quiescent Current

The quiescent current required to operate all four backlights is reduced by 1.5mA when backlight current is set to 4.0mA or less. This feature results in higher efficiency under light-load conditions. Further reduction in quiescent current will result from using fewer than four LEDs.

3. TECHNICAL BRIEF

3.11 Battery Charger Interface

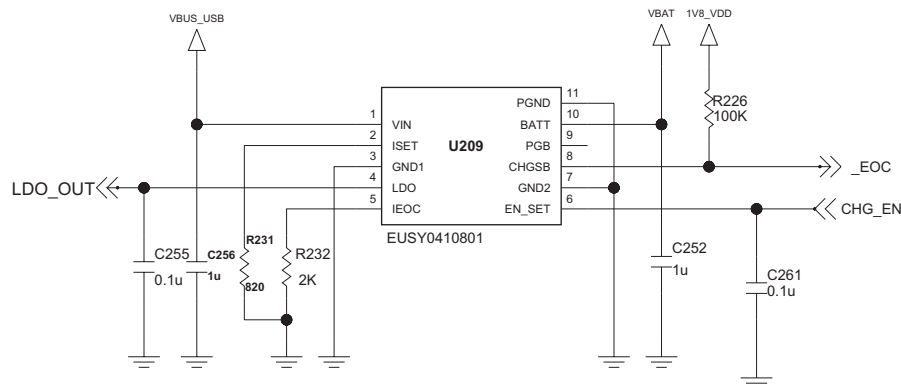


Figure 3.11.1 BATTERY CHARGER BLOCK

The RT9524 is an intelligent, stand-alone constant current, constant-voltage (CCCV), thermally regulated dual input linear charger designed for charging a single-cell lithium-ion (Li+) battery.

The IC controls the charging sequence from the prequalification state through constant current fast charge, top-off charge, and full-charge indication.

Proprietary thermal-regulation circuitry limits the die temperature during fast charging or when the IC is exposed to high ambient temperatures, allowing maximum charging current without damaging the IC.

The RT9524 accepts input supply range from -0.3V to 28V, but disables charging if the input voltages exceed +6.9V to protect against unqualified or faulty AC adapters cables. The IC operates over the extended temperature range (-40°C to +85°C)

3.12 Keypad Interface

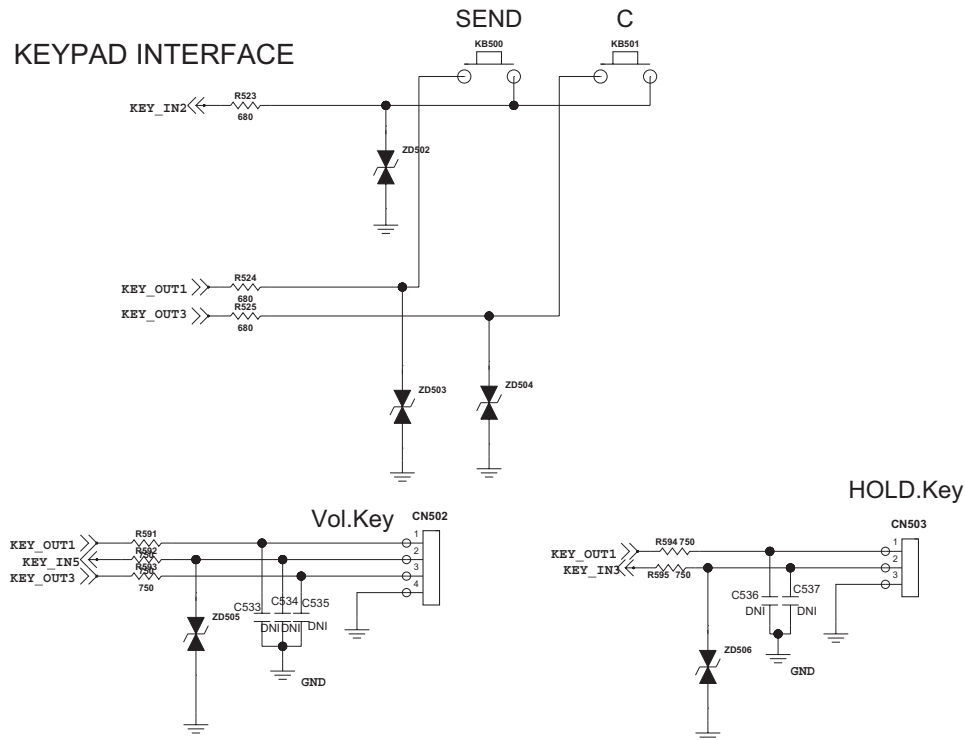


Figure 3.12.1 MAIN KEY STRUCTURE

The Keypad Interface is a peripheral controller, which can be used for scanning external keypad matrices with up to 8 rows and 8 columns (that is 64 standard keys). By adding an additional row of keys connected to ground the number of keys can be extended by up to 8 keys. This results in a maximum number of 72 keys to be identified by the Keypad Interface Controller.

The Keypad Scan Module reduces the number of interrupts and polling through the processor and therefore reduces the power consumption. The module is able to debounce and scan the external keypad matrix automatically without any software intervention. After debouncing it generates an interrupt. The interface controller contains information about the key (or key combination) that was pressed and how long it was pressed.

3. TECHNICAL BRIEF

3.13 Audio Front-End

3.13.1 Functional Overview

The audio front-end of X-GOLD™213 offers the digital and analog circuit blocks for both receive and transmit audio operation, from a mobile phone perspective (called audio-in and audio-out subsequently). It features a high-quality, stereo digital-to-analog path with amplifier stages for connecting acoustic transducers to X-GOLD™213. In audio-in path the supply voltage generation for electret microphones, a low-noise amplifier and analog to digital conversion are integrated in X-GOLD™213. A more detailed functional description will be given in the following sections.

The audio front-end itself can be considered to be organized in three sub-blocks:

- Interface to processor cores (TEAKLite® and - indirectly - ARM)
- Digital filters
- Analog part

The following figure shows an architecture overview of the Audio section.

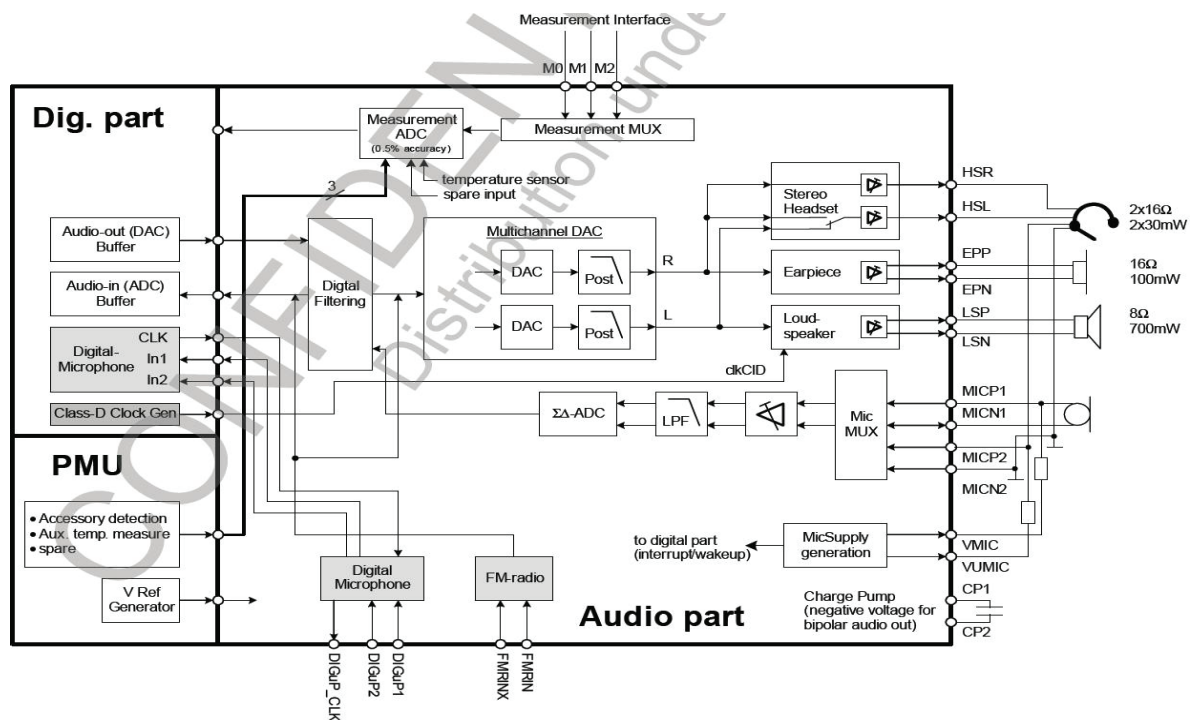


Figure 3.13.1 Audio Section Overview

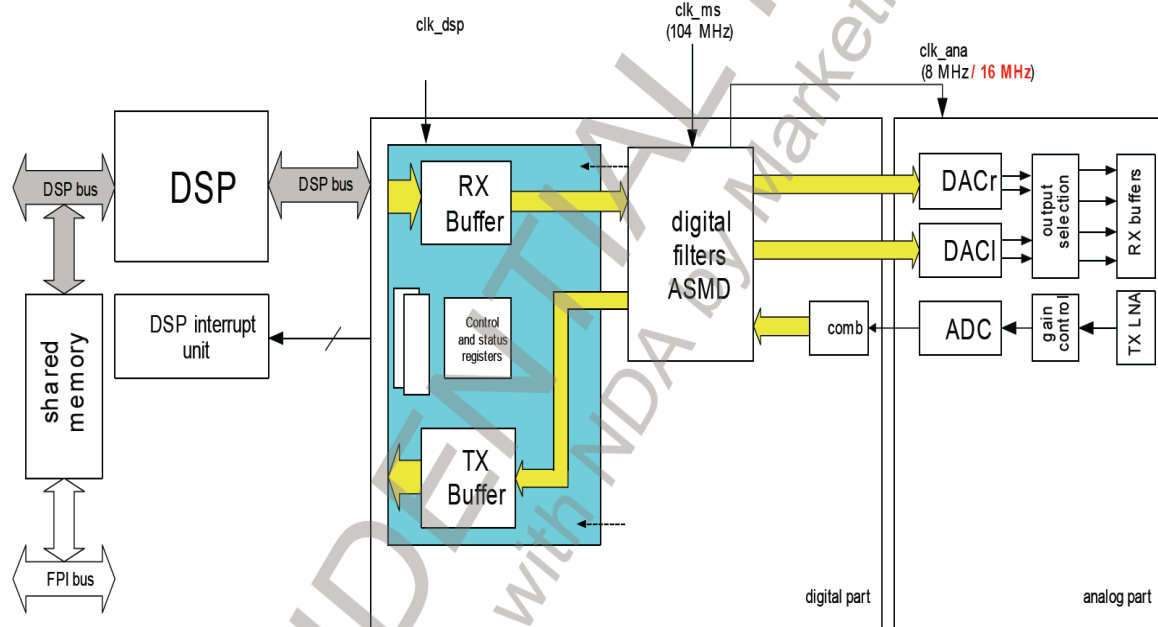


Figure 3.13.2 Overview of Clocking and Interfaces of Audio Front End

The audio front-end of X-GOLD™213 has the following major operation modes:

- Power-down: All analog parts are in power down and all clocks of the digital part are switched off.
- Audio mode: Digital decimation/interpolation filters are connected to the interface buffers and the analog part is enabled.

These major modes can be modified by certain control register settings.

- Due to the new gain settings in the TX path, the maximum input voltage is limited to 0.8 Vpp.
- In both voiceband paths, the value range for voice samples is confined to 97.5%, i.e. to [-31948, 31947] or [8334H, 7CCBH] in X-GOLD™213.
- On the TX path, 83% "1"s on the VTPDM line correspond to a 16-bit value of 7CCBH and 17% "1"s correspond to a 16-bit value of 8334H at the digital filter output. Thus the usable range is 66%. This range can be scaled to 100% by Firmware.
- The high-pass functions of the voiceband filters have to be implemented in firmware on TEAKLite®.

3. TECHNICAL BRIEF

3.13.2 Digital Part

The digital part of the X-GOLD™213 audio front-end comprises an interface to the TEAKLite® bus, interfaces to the interrupt units of TEAKLite®, digital interpolation filters for oversampling digital-to-analog conversion, digital decimation filters for analog-to-digital conversion and an interface to the analog part of the audio front-end. For the digital microphone all the filtering is done in a dedicated hardware. The output sample stream is then fed in a duplicated ring buffer structure like the data from the analog microphone path (after A/D conversion and subsequent digital filtering).

▪ Interpolation Filter

The interpolation path of the X-GOLD™213 audio front-end increases the sampling rate of the audio samples to the rate of the digital-to-analog converter. Because the input sampling rates can vary between 8 kHz and 47.619 kHz the filter characteristic and oversampling ratio can be adjusted to the respective sampling rate. The requirements for the interpolation filters depend on the sampling rate, because a sufficient out-of-band discrimination in the audio frequency band (20 Hz,...,20 kHz) has to be ensured.

▪ Decimation Filter

The digital decimation filter on X-GOLD™213 has two operating modes: 8 kHz output sampling rate and 16 kHz output sampling rate (or 16 kHz output sample rate and 16kHz bandwidth in case of doubled ASMD clock).

3.13.3 Analog Part

The analog part of the X-GOLD™213 audio front-end in audio-out direction consists of a stereo digital to analog converter (multi-bit oversampling converter) which transforms the output of the digital interpolation filter into analog signals. It is followed by the gain control/amplifier section. The DAC outputs can be switched to several output buffers. In audio-in section there is an input multiplexer which selects either one of two differential microphone inputs to be connected to the low-noise amplifier and analog pre-filter. The signals from the analog pre-filter are input to a second-order sigma-delta analog-to-digital converter. In addition there is a connection for FM-radio playing.

▪ Audio-out Part

The analog audio-out part consists of two multi-bit digital-to-analogue converters (DAC) and an output stage. The signal sources are switched to the output drivers in the output stage. The output drivers consist of: a) one mono, differential class-D Loudspeaker driver, b) one mono, differential Earpiece driver and c) one stereo, single-ended (with uni- or bipolar signals), Headset driver.

▪ Digital-to-analog converters

The multi-bit oversampling DACs of the X-GOLD™213 audio front-end convert the 16-bit data words coming from the digital interpolation filters to analogue signals.

▪ Output Amplifier

The different output buffers in X-GOLD™213 are driven by the outputs of the selection block. The differential earpiece driver can be used to drive a 16 Ω earpiece and works in differential. The two single ended headset drivers can be used to drive a 16 Ω headset. They can work unipolar mode, where an AC coupling of the headset might be needed, or can work also in bipolar mode. The differential loudspeaker driver can be used to drive a 8 Ω loudspeaker. As it is a class-D amplifier the needed suppression of the higher harmonics of the switching signals has to be achieved by the external circuitry. The buffers are designed to be short circuit protected.

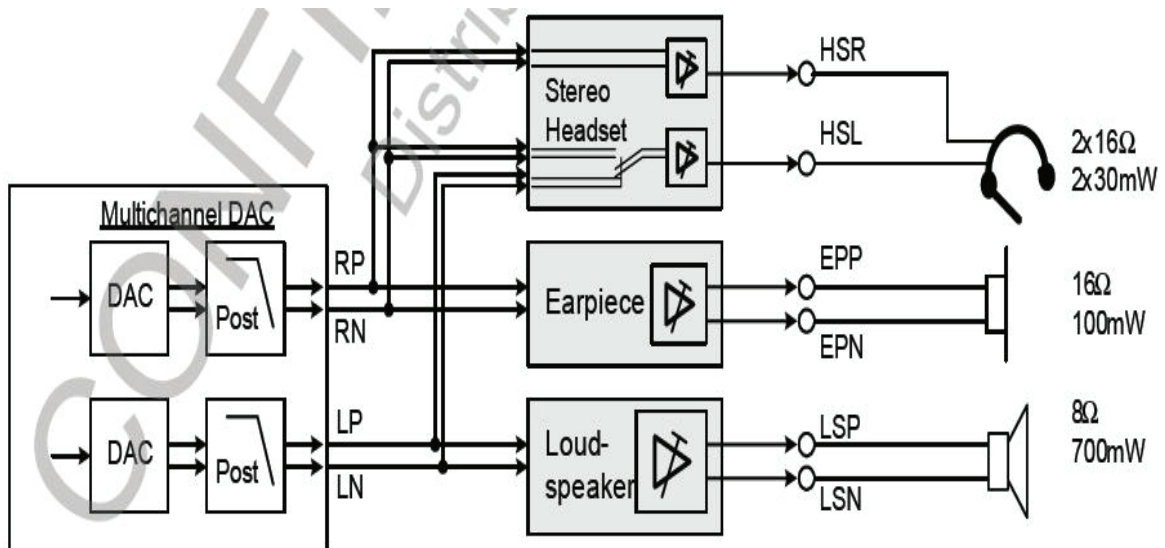


Figure 3.13.3 Switching for R/L DACs onto Buffers

3. TECHNICAL BRIEF

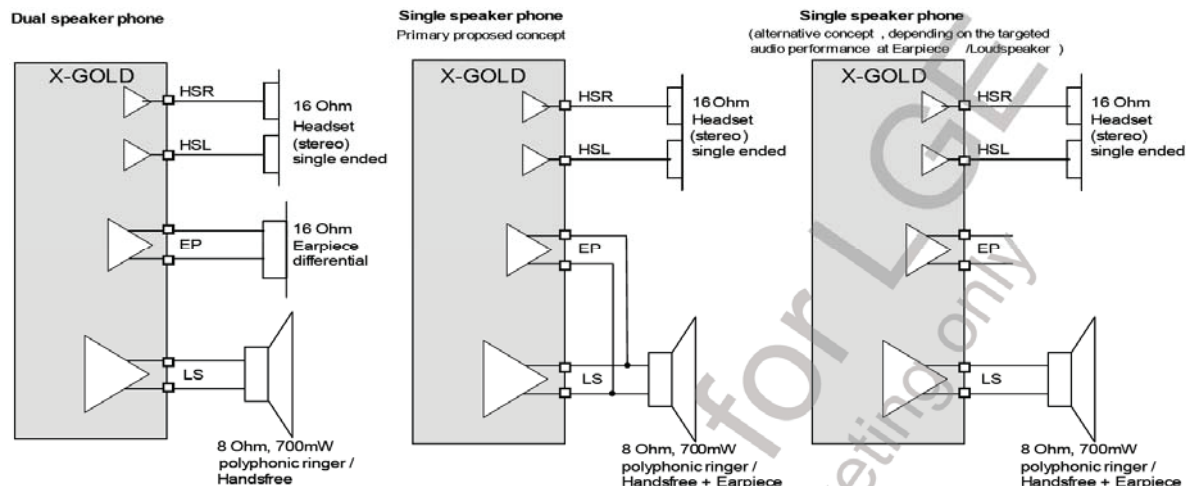


Figure 3.13.4 Different Application Scenarios

In order to achieve the single-speaker concept by parallel connection of Earpiece and Headset amplifier the Earpiece amplifier have to sustain the up to 5 V voltage of the class-D amplifier.

▪ Audio-in Path

The audio-in path of X-GOLD™213 provides two differential microphone input sources, MIC1 and MIC2.

- The inputs for microphone MIC1 are MICP1 and MICN1.
- The inputs for microphone MIC2 are MICP2 and MICN2.

The audio-in path consists of an input selector, a low noise amplifier and following pre-filter with gain control, a second order $\Sigma\Delta$ -converter and a digital decimation filter. It supports both standard GSM (bandwidth 3.5 kHz) and wideband (bandwidth 7 kHz) speech bands.

The differential input signal from the microphone first passes a low noise amplifier and following pre-filter and an anti-aliasing pre-filtering stage achieving an overall variable gain ranging from 0 dB to +39 dB. The signal is then modulated by a second order $\Sigma\Delta$ -converter which is clocked with the same clock rate as the digital to analog converters. The $\Sigma\Delta$ -converter delivers a 1-bit pulse density modulated data stream at a rate of 2 MHz to the digital decimation filter which reduces the rate to 8 kHz or 16 kHz, depending on the current mode.

To improve SNR the sample frequency can be doubled in dedicated modes and the modulated data stream is 4MHz instead of 2 MHz.

▪ Microphone Supply

X-GOLD™213 has a single ended power-supply concept for electret microphones:

For both modes a minimal load capacitance of t.b.d. nF is necessary to guarantee stable operation of the buffer.

The maximal load capacitance must not exceed t.b.d. nF.

2 microphone supplies VMIC and VUMIC are available. The supply VUMIC has a ultra-low-power mode, where the current consumption is minimum, whilst at the same time the noise performance is reduced.

For this purpose the VUMIC is directly supplied out of the VMIC regulator, the Mic-Buffer can be switched off and only the quiescent current of the VMIC regulator is present. This mode can be used to supply a headset and allow accessory detection with highly reduced current consumption For normal operation the supply can be switched to normal operation mode with improved noise performance. In case of an digital microphone VMIC can be used for supplying this microphone.

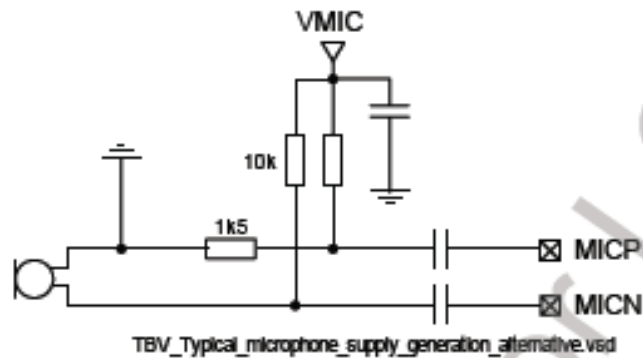


Figure 3.13.5 Typical Microphone Supply Generation (alternative)

3. TECHNICAL BRIEF

3.14 Camera Interface(1.3M Fixed Focus Camera)

3.14.1 PMB8810 Camera Interface

The Camera Interface (CIF) represents a complete video and still picture input interface (see Figure 26).

The CIF contains image processing, scaling, and compression functions. The integrated image processing unit supports image sensors with integrated $YCbCr$ processing.

Scaling is used for downsizing the sensor data for either displaying them on the LCD, or for generating data streams for MPEG-4 compression. In general, $YCbCr$ 4:2:2 JPEG compressed images should use the full sensor resolution, but they can also be downscaled to a lower resolution for smaller JPEG files. Scaling also can be used for digital zoom effects, because the scalers are capable of up-scaling as well.

CIF All data is transmitted via the memory interface to an AHB bus system using a bus master interface.

Programming is done by register read/write transactions using an AHB slave interface.

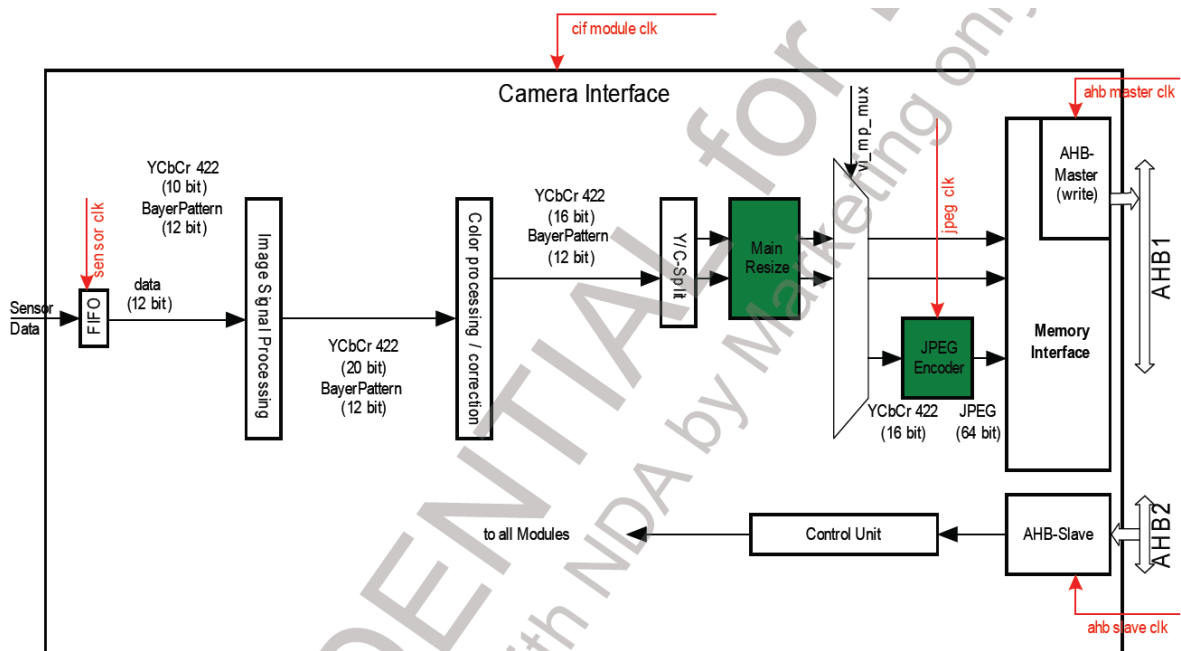


Figure 3.14.1 Block Diagram of Camera Interface

Functional Overview of CIF

The following list gives an overview over the CIF's functionality:

- 78 MHz system clock
- 78 MHz sensor clock
- 78 MHz JPEG encoder clock
- 32-bit AHB slave programming interface
- ITU-R BT 601 compliant video interface supporting YC_bC_r
- ITU-R BT 656 compliant video interface supporting YC_bC_r data
- 8-bit camera interface
- 12-bit resolution per color component internally
- YC_bC_r 4:2:2 processing
- Hardware JPEG encoder incl. JFIF1.02 stream generator and programmable quantization and Huffman tables
- Windowing and frame synchronization
- Continuous resize support
- Frame skip support for video (e.g. MPEG-4) encoding
- Macro block line, frame end, capture error, data loss interrupts and sync. (h_start, v_start) interrupts
- Programmable polarity for synchronization signals
- Luminance/chrominance and chrominance blue/red swapping for YUV input signals
- Maximum input resolution of 3 Mpixels (2048x1536 pixels)
- Main scaler with pixel-accurate up- and down-scaling to any resolution between 3 MP (2048x1536) and 32x16
- pixel in processing mode
- Buffer in system memory organized as ring-buffer
- Buffer overflow protection for raw data and JPEG files
- Asynchronous reset input, software reset for the entire IP and separate software resets for all sub-modules
- Interconnect test support
- Semi planar storage format
- Color processing (contrast, saturation, brightness, hue)
- Power management by software controlled clock disabling of currently not needed sub-modules

3. TECHNICAL BRIEF

3.15 Vibrator Interface

Support PWM signal which generated by hardware itself via register control

Direct connect to the VIB and VSSVIB pin from XMM2130 without any external component required

It is capable to driver the vibrator motor up to 150mA

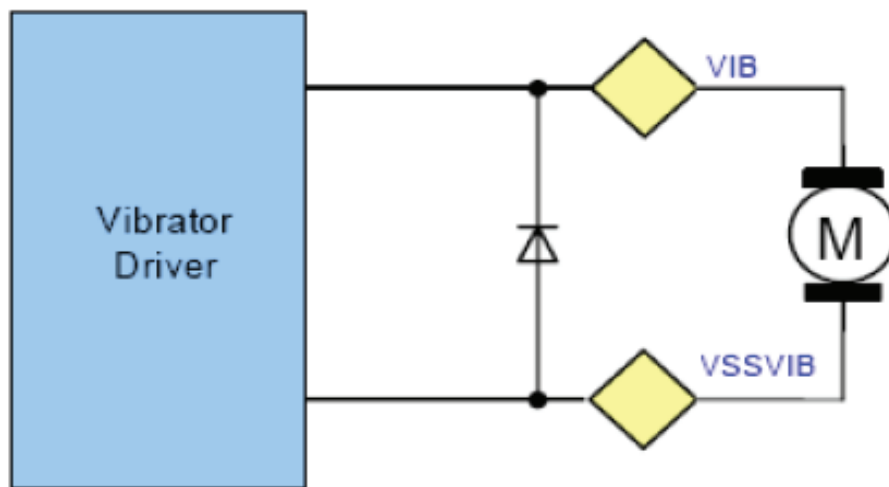


Figure 3.15.1 Vibrator Driver Block Diagram

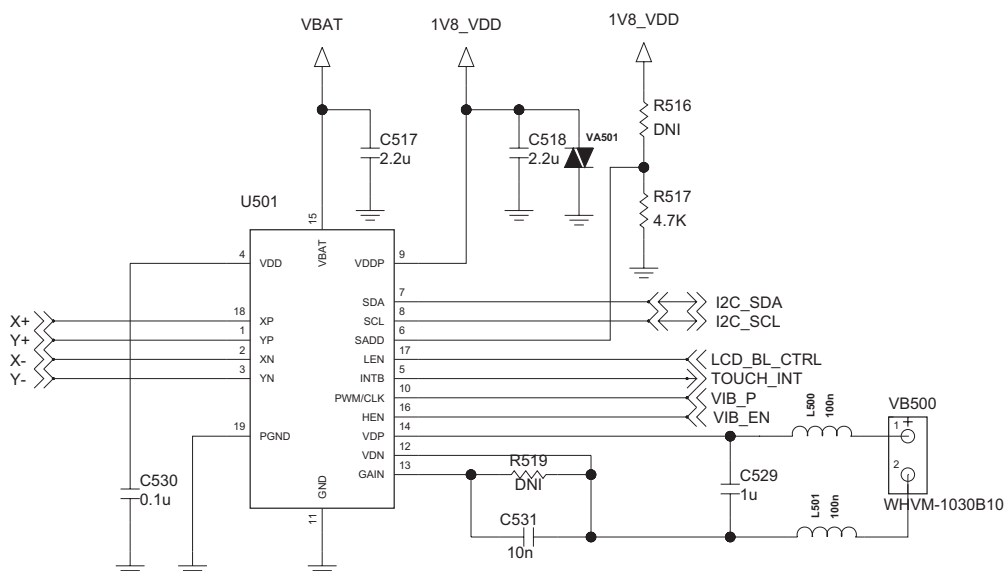


Figure 3.15.2 Vibrator Driver Block

4. TROUBLE SHOOTING

4.1 Trouble shooting test setup

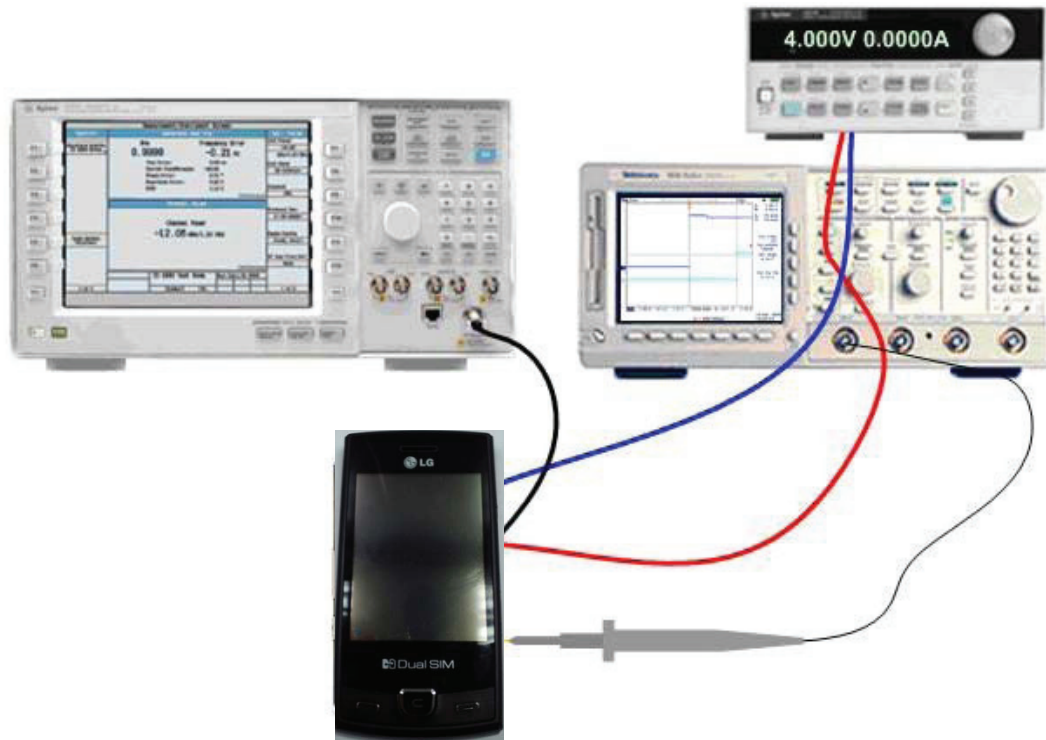


Figure 4.1.1 Equipment setup

Power on all of test equipment

- Connect PIF-UNION JIG or dummy battery to the DUT for power up.
- Connect mobile switch cable between Communication test set and DUT when you need to make a phone call.
- Follow trouble shooting procedure

4. TROUBLE SHOOTING

4.2 RF Component

4.2.1 SIM 1 (main)

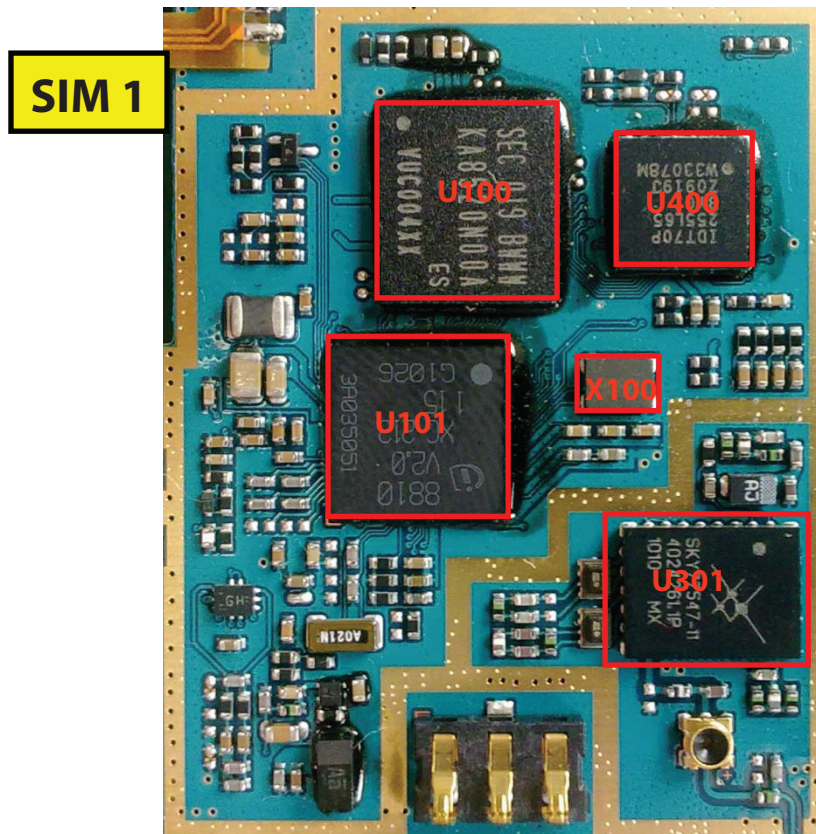


Figure 4.2.1 SIM 1 (main) block

U100	MEMORY (1G NOR/256 pSRAM,56 balls) KA8520N00M
U101 (PMB8810)	Main Chip (A-GOLDRADIO+)
U301	FEM(Tx Module)
X400	Crystal, 26MHz Clock
U400	DPRAM

4.2.2 SIM 2 (sub)

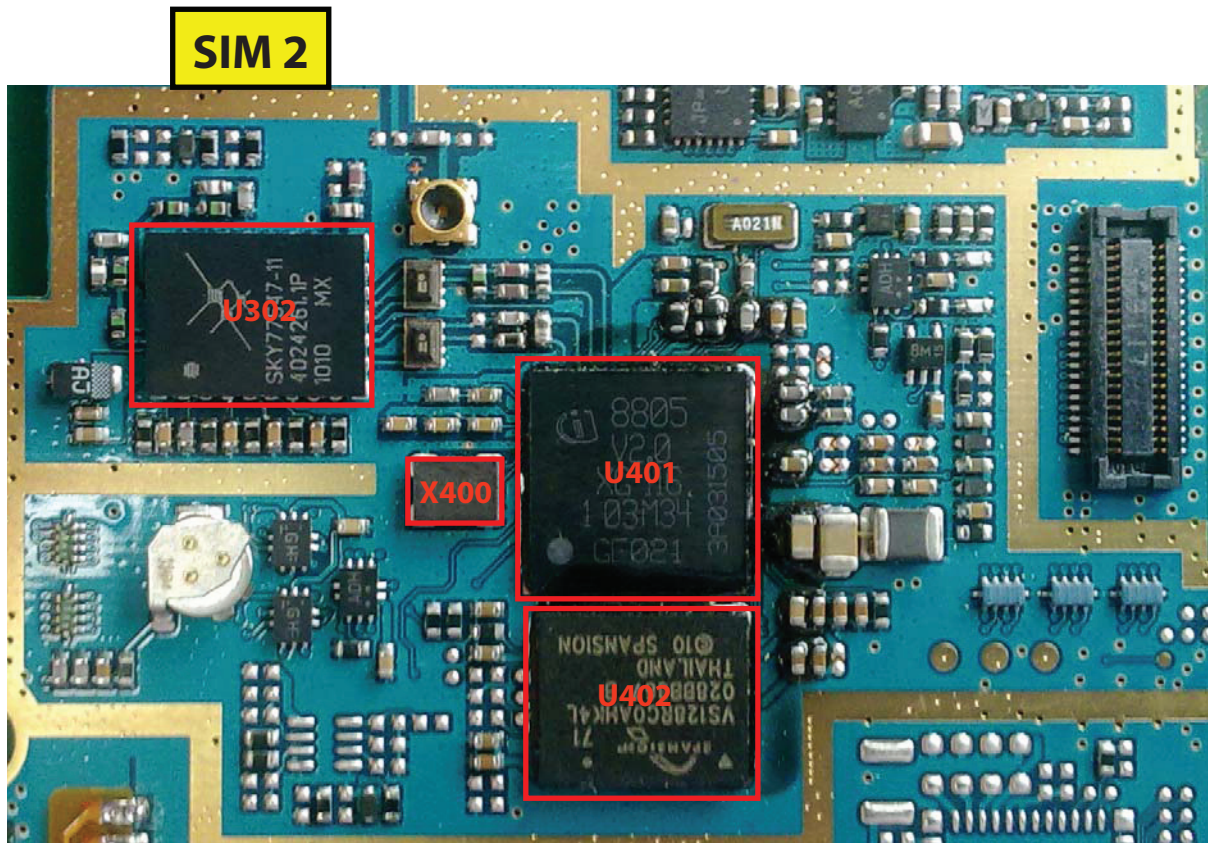


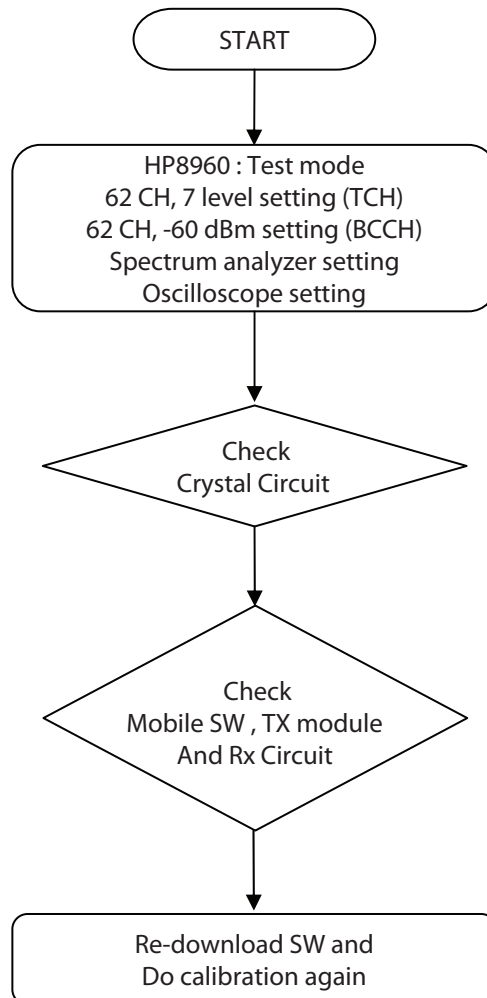
Figure 4.2.2 SIM 2 (sub) block

U402	Memory(128 NOR / 64 pSRAM) S71VS128RC0ZHK200
U401 (PMB8805)	Sub Chip (A-GOLDRADIO)
U302	FEM(Tx Module)
X400	Crystal, 26MHz Clock

4. TROUBLE SHOOTING

4.3 RX Trouble

CHECKING FLOW



4.3.1 Checking Crystal Circuit

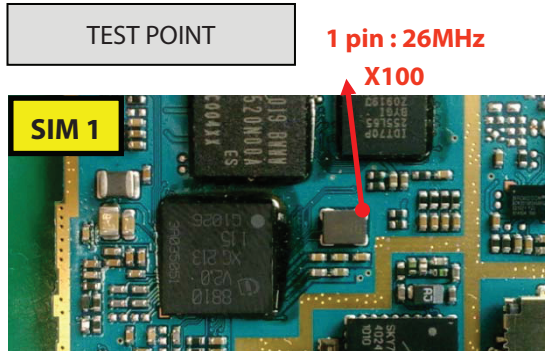


Figure 4.3.1 SIM 1 (main) crystal

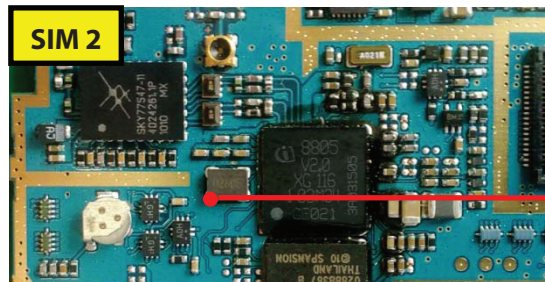


Figure 4.3.2 SIM 2 (sub) crystal

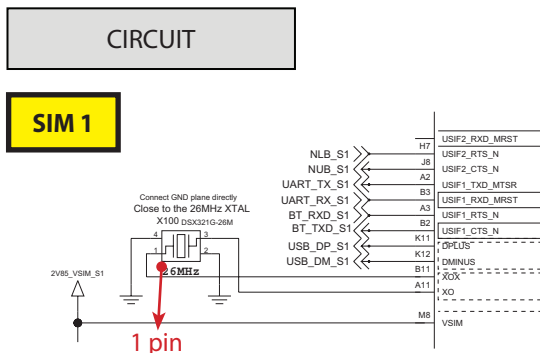
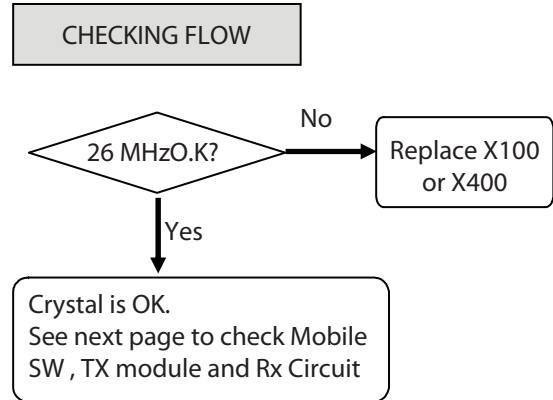


Figure 4.3.3 SIM 1 crystal circuit

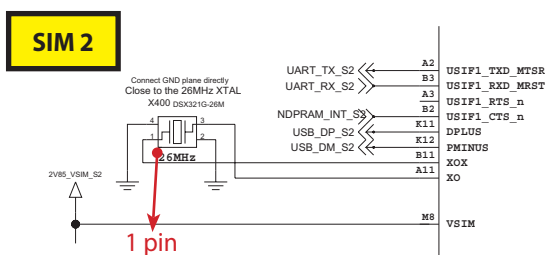


Figure 4.3.4 SIM 2 crystal circuit

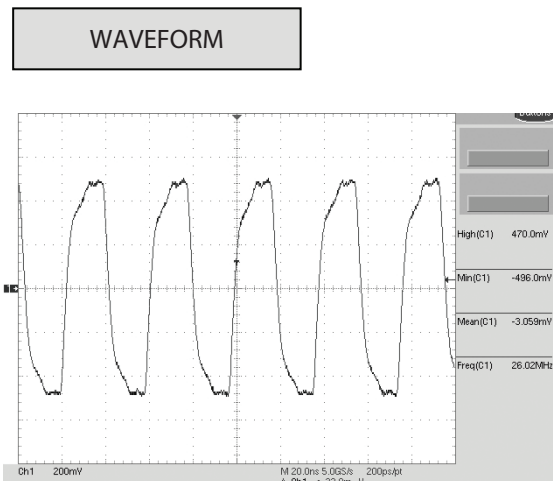


Figure 4.3.5 26MHz output waveform

4. TROUBLE SHOOTING

4.3.2 Checking Mobile SW & FEM

TEST POINT

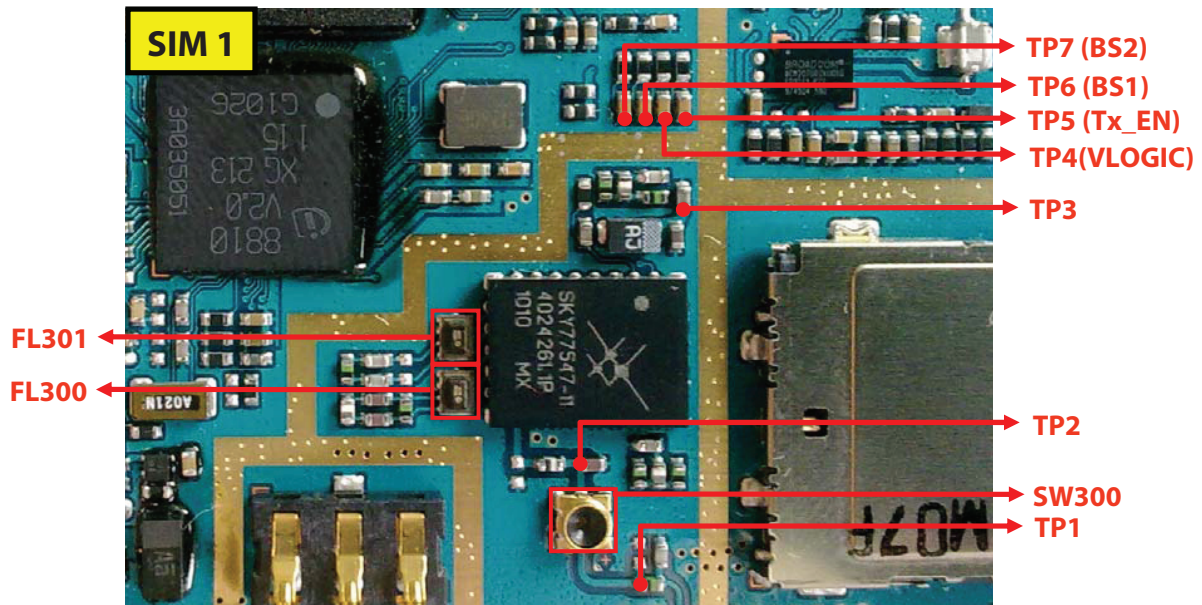


Figure 4.3.6 SIM 1 Mobile SW & FEM

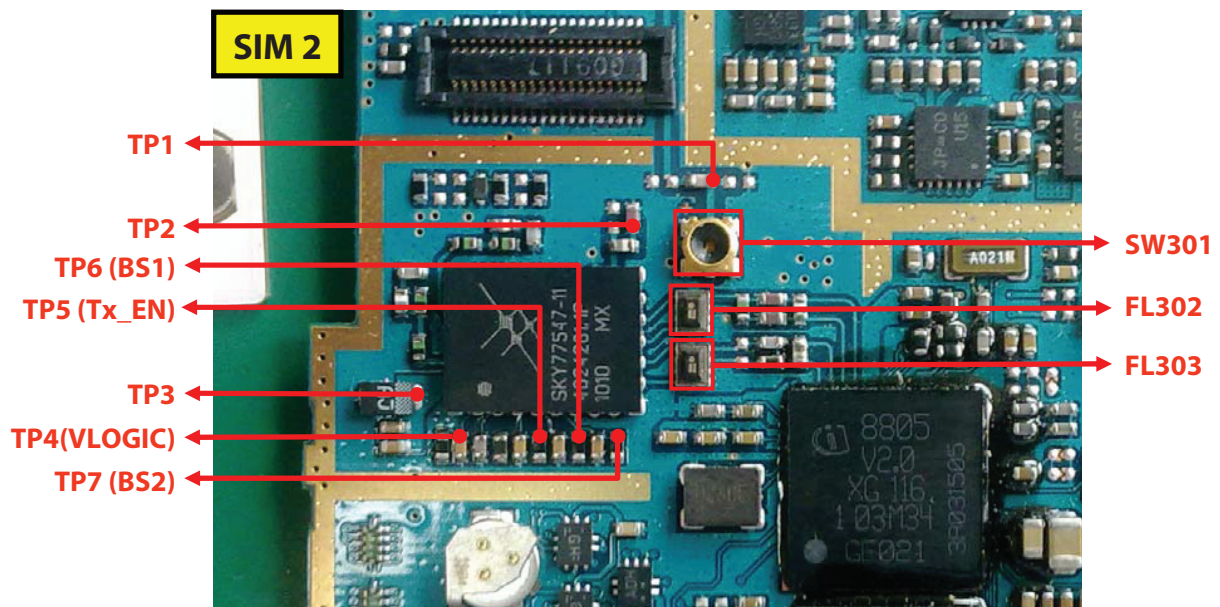


Figure 4.3.7 SIM 2 Mobile SW & FEM

CIRCUIT

SIM 1



CONTROL LOGIC

EGSM Rx



CIRCUIT

SIM 2



Figure 4.3.10 SIM2 Mobile SW & FEM circuit

CONTROL LOGIC

EGSM Rx

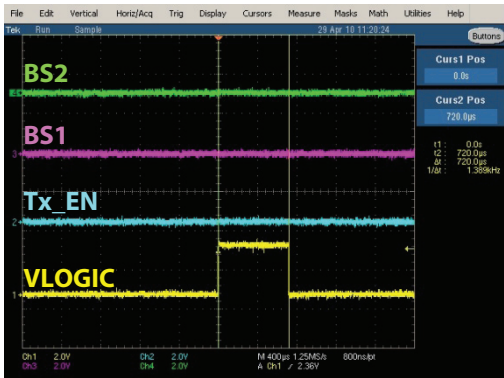
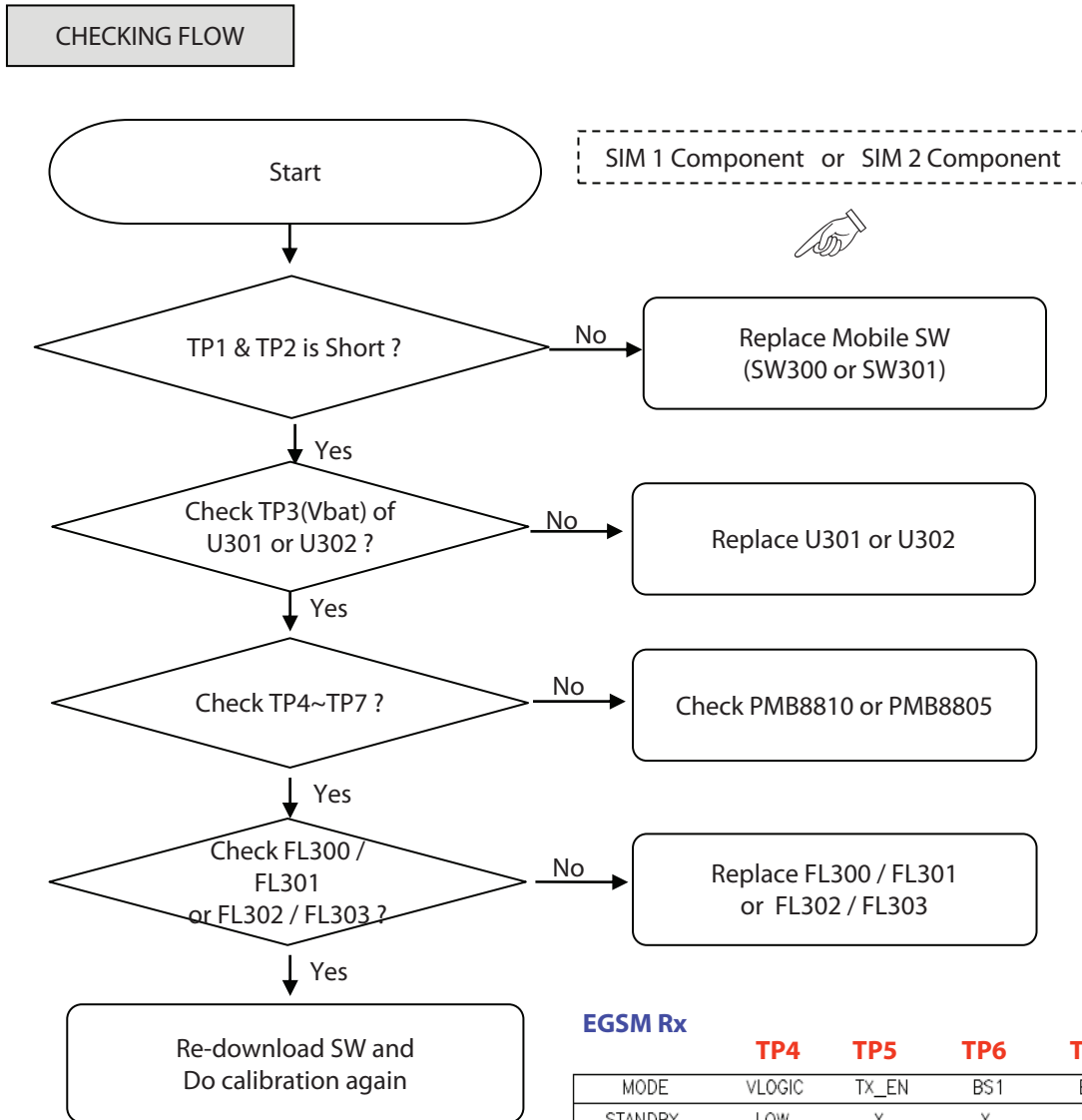


Figure 4.3.11 SIM 2 TP4 ~ TP7 scope waveform

4. TROUBLE SHOOTING



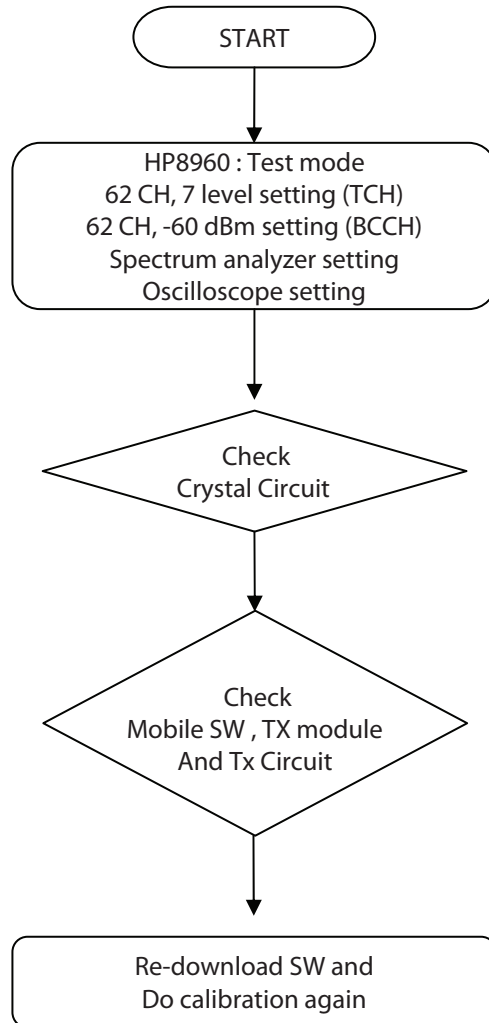
EGSM Rx

	TP4	TP5	TP6	TP7
MODE	VLOGIC	TX_EN	BS1	BS2
STANDBY	LOW	X	X	X
EGSM_RX	HIGH	LOW	LOW	LOW
GSM850_RX	HIGH	LOW	LOW	HIGH
PCS_RX	HIGH	LOW	HIGH	HIGH
DCS_RX	HIGH	LOW	HIGH	LOW
LB_TX	HIGH	HIGH	LOW	X
HB_TX	HIGH	HIGH	HIGH	X

4. TROUBLE SHOOTING

4.4 TX Trouble

CHECKING FLOW



4.4.1 Checking Crystal Circuit

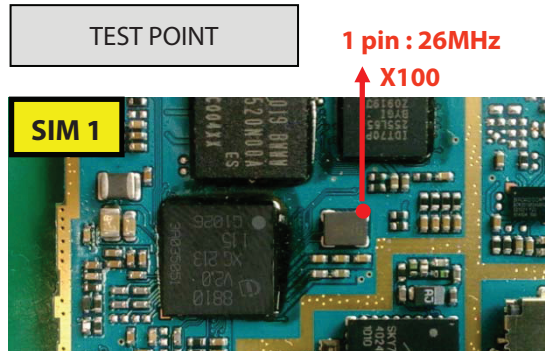


Figure 4.4.1 SIM 1 (main) crystal

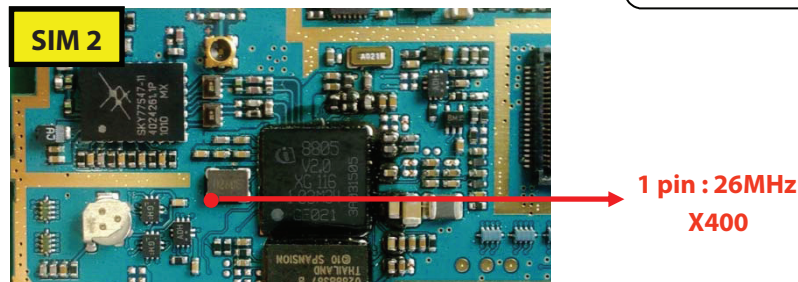


Figure 4.4.2 SIM 2 (sub) crystal

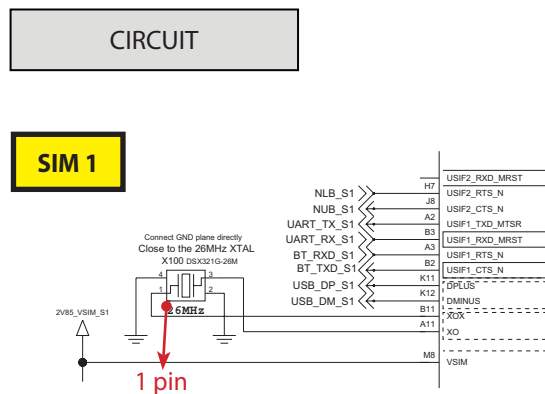
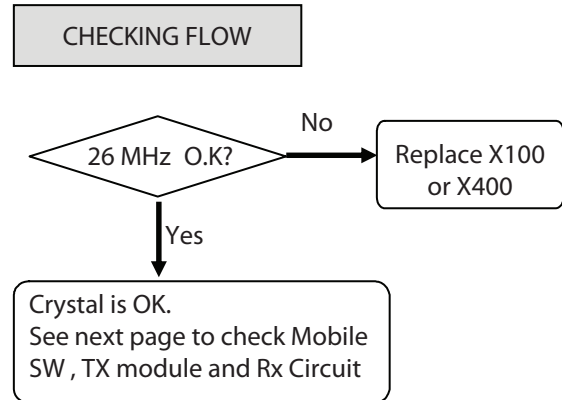


Figure 4.4.3 SIM 1 crystal circuit

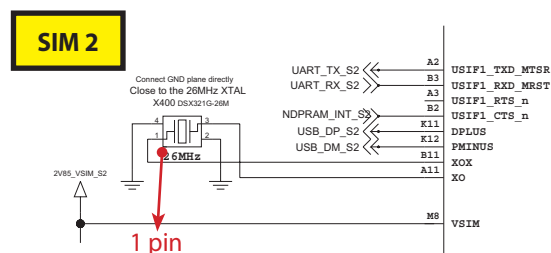


Figure 4.4.4 SIM 2 crystal circuit

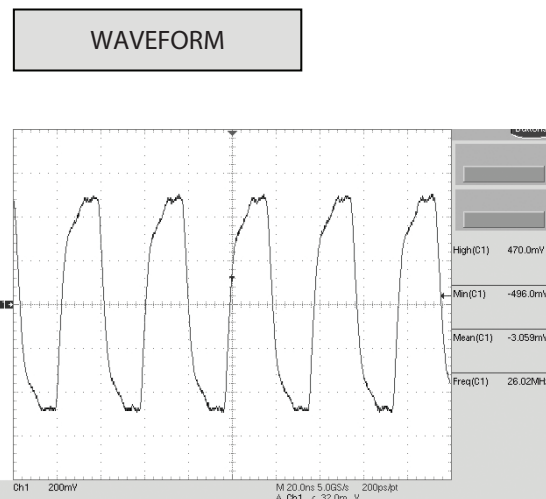


Figure 4.4.5 26MHz output waveform

4. TROUBLE SHOOTING

4.4.2 Checking Mobile SW & TX Module

TEST POINT

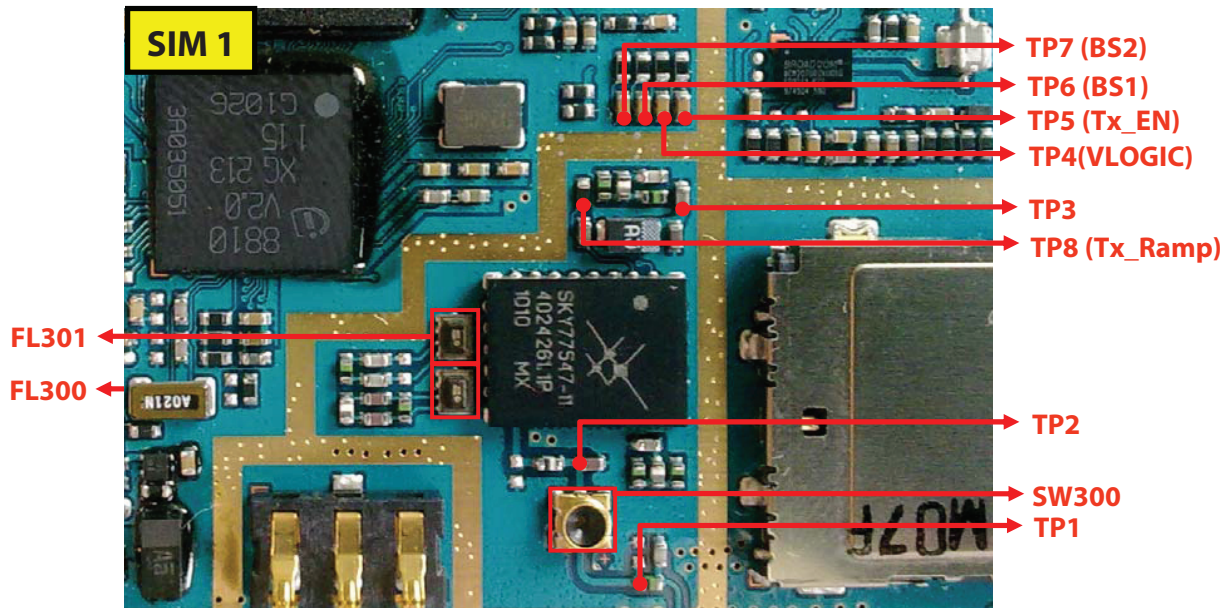


Figure 4.4.6 SIM 1 Mobile SW & TX Module

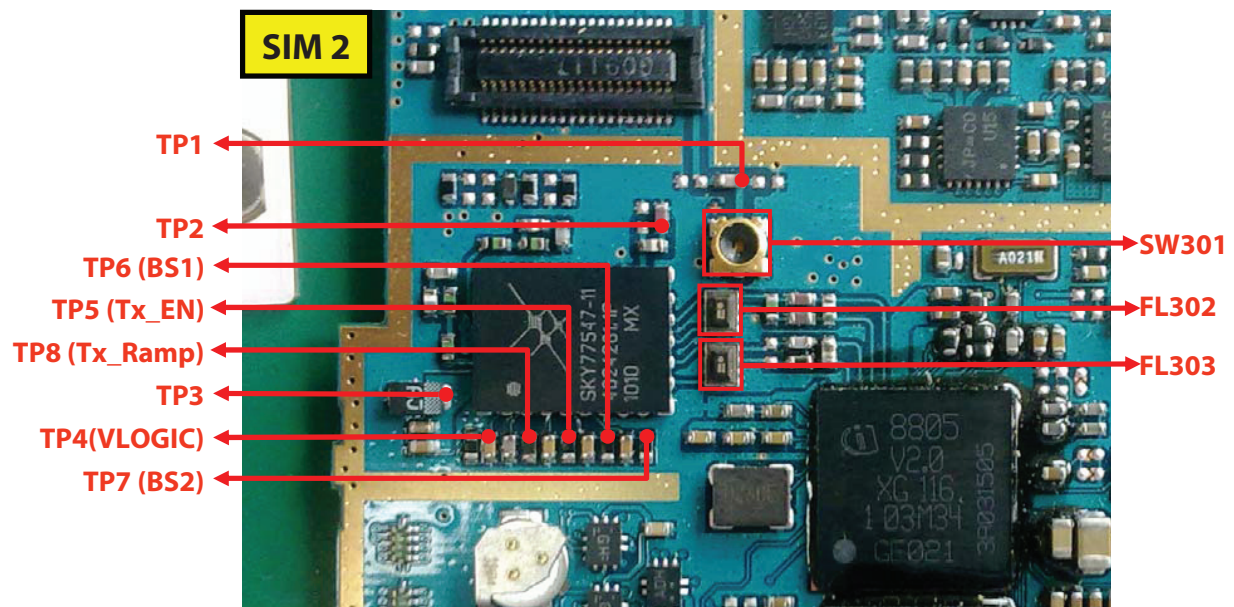


Figure 4.4.7 SIM 2 Mobile SW & TX Module

CIRCUIT

SIM 1



CONTROL LOGIC

The screenshot shows an oscilloscope interface with two waveforms. The top trace, labeled **Tx_EN** in yellow, is a square wave. The bottom trace, labeled **Tx_Ramp** in green, is a ramp signal that starts at a low level and then ramps up. The scope is set to 1.0V/div, 20.0ns/div, and 12.5MS/s. The date and time are 29 Apr 18 11:28:32. The right side of the screen shows a control panel with buttons for **Curs1 Pos** (0.0s), **Curs2 Pos** (55.0µs), and a table of measurements: t1: 0.0s, t2: 35.0µs, Δt: 35.0µs, 1/dt: 27.7kHz.

CIRCUIT

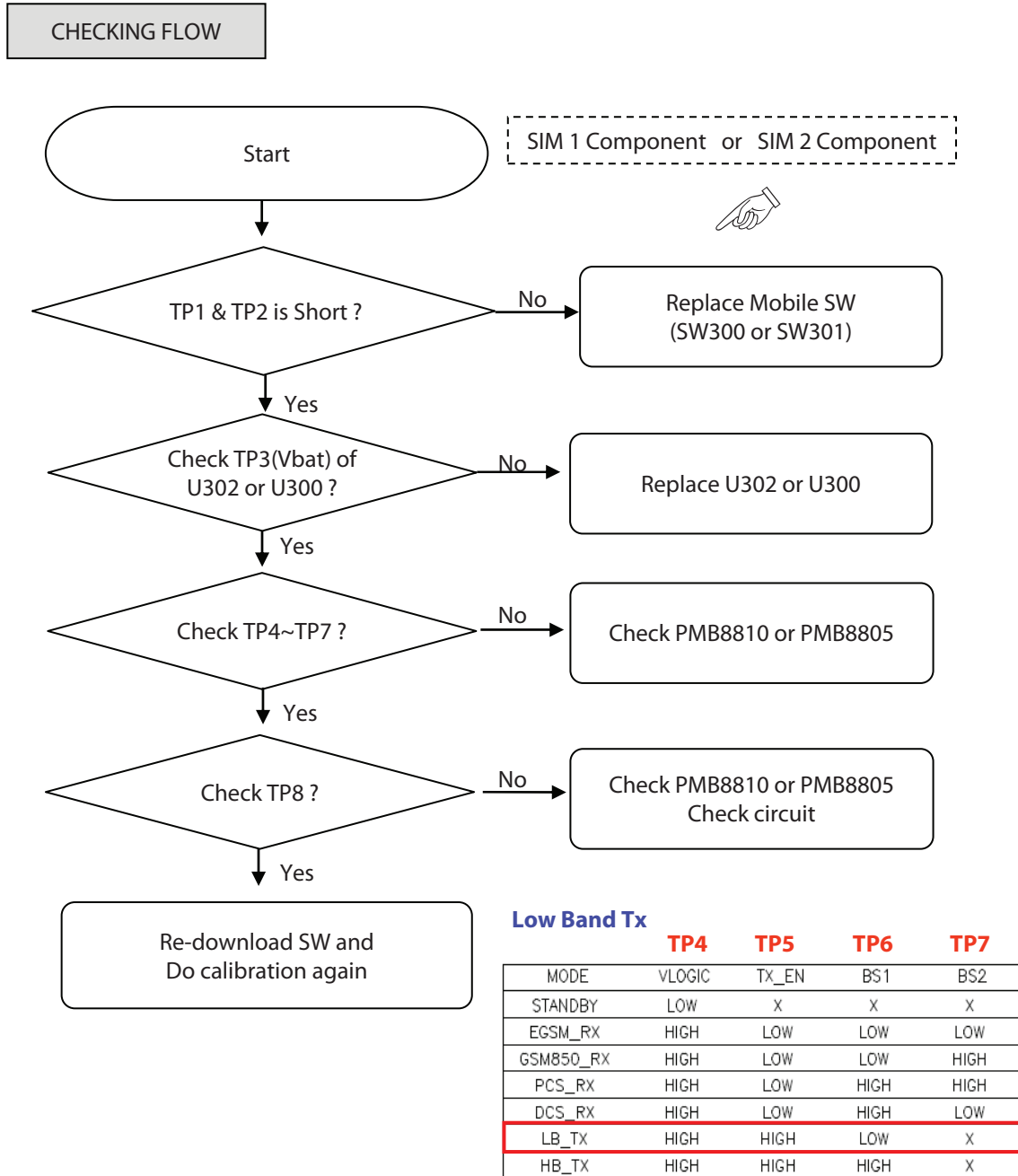
SIM 2



CONTROL LOGIC

Low Band Tx





4. TROUBLE SHOOTING

4.5 Power On Trouble

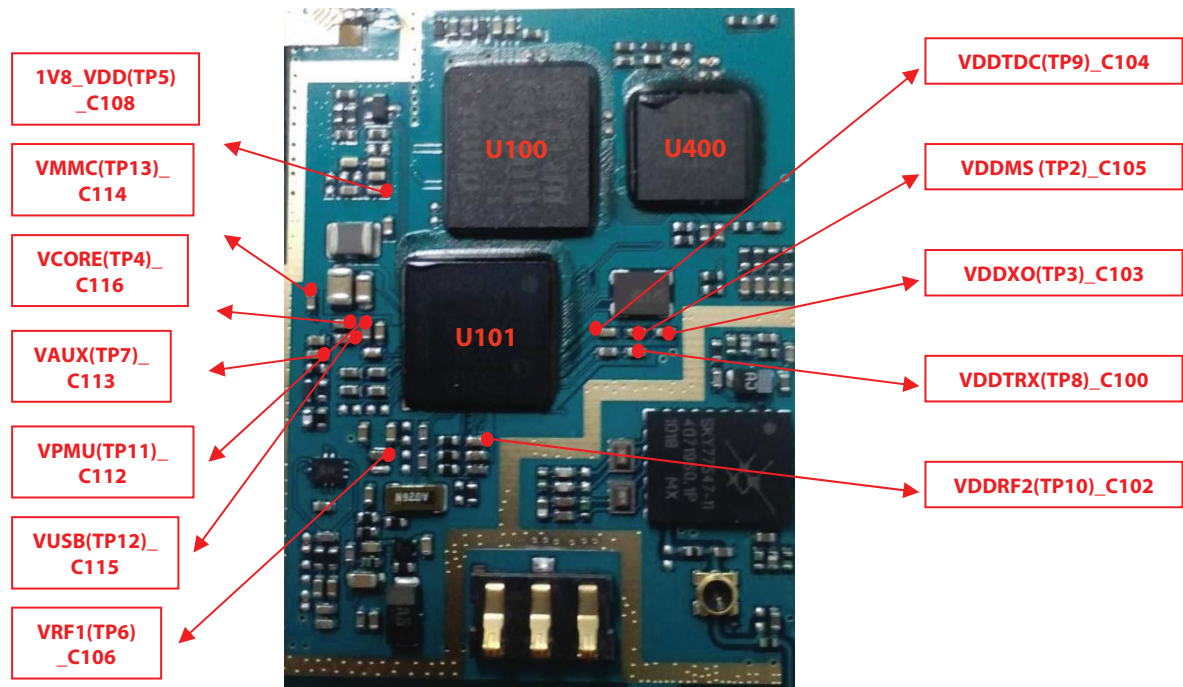


Figure 4.5.1

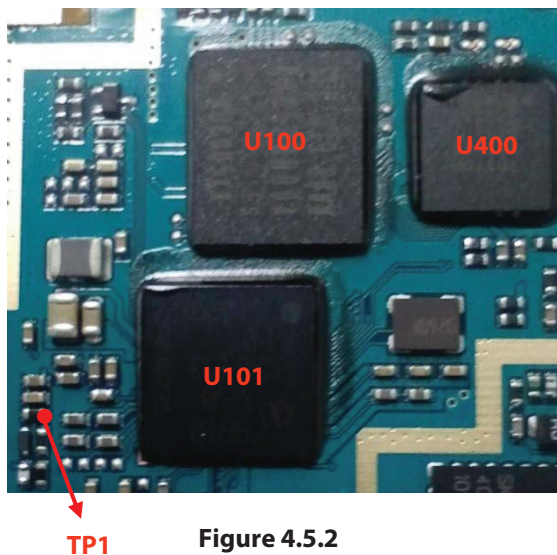


Figure 4.5.2

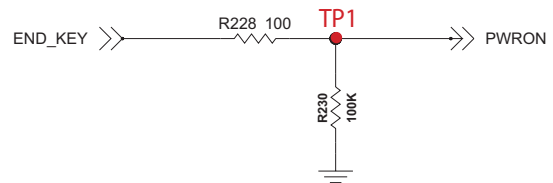
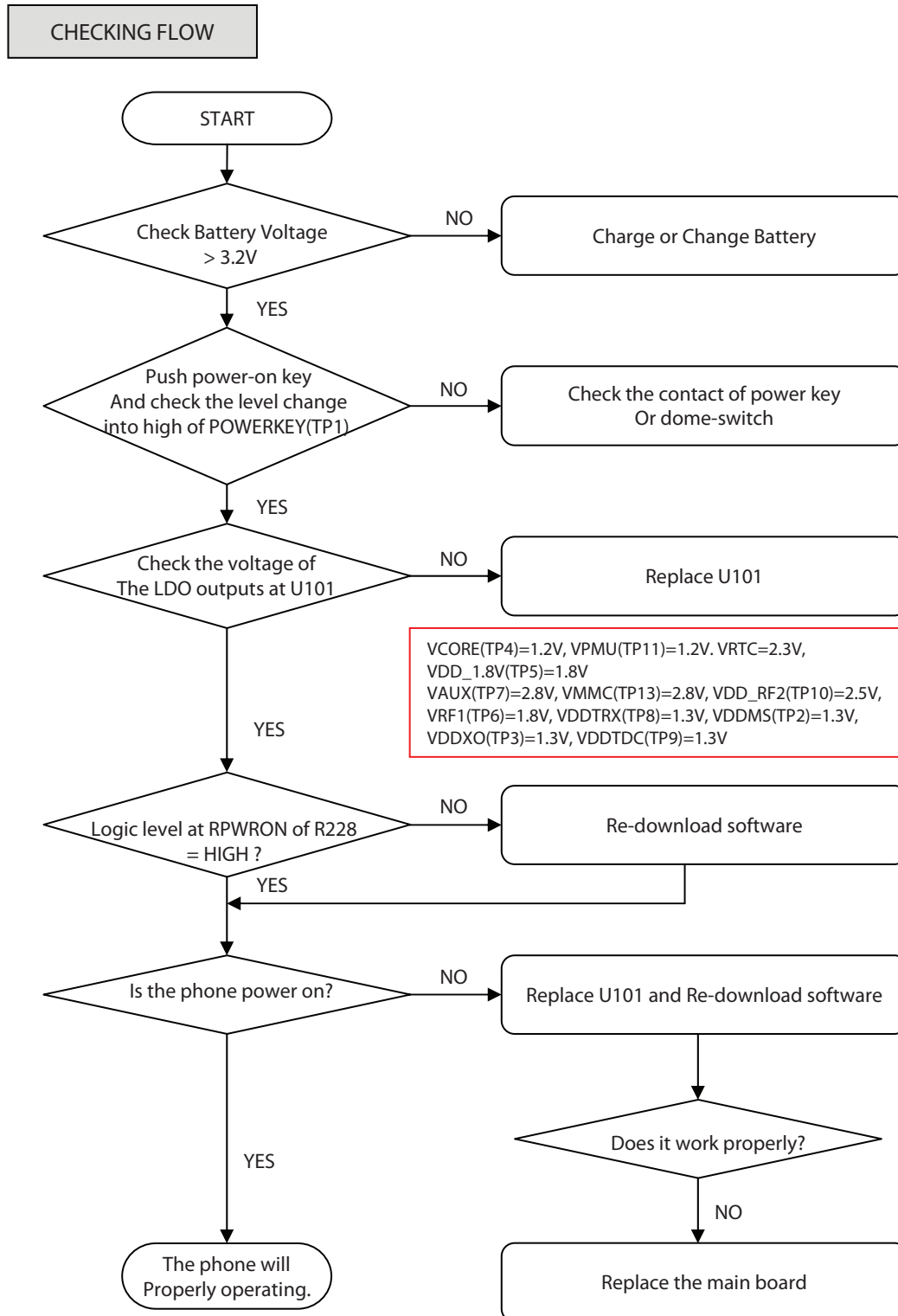


Figure 4.5.3 Remote power on



4. TROUBLE SHOOTING



4.6 Charging Trouble

TEST POINT

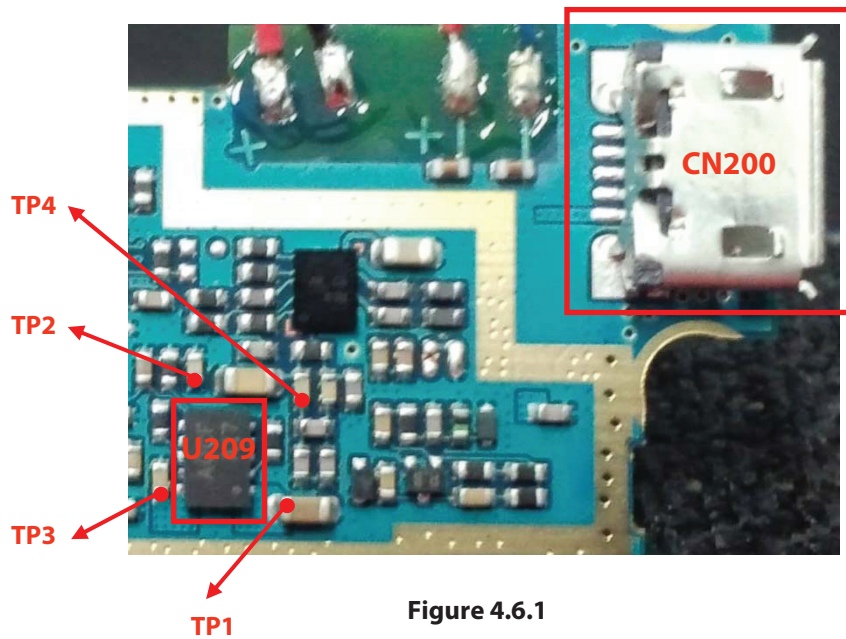


Figure 4.6.1

CIRCUIT

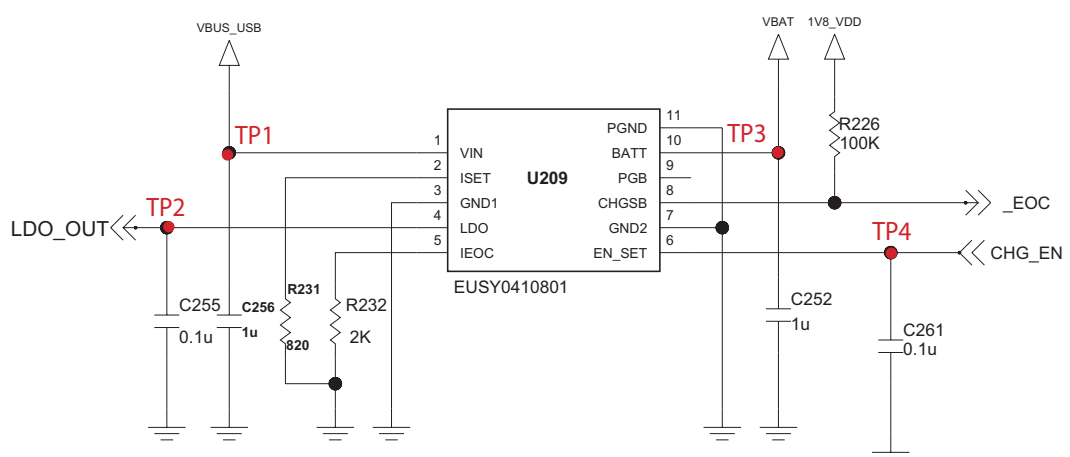
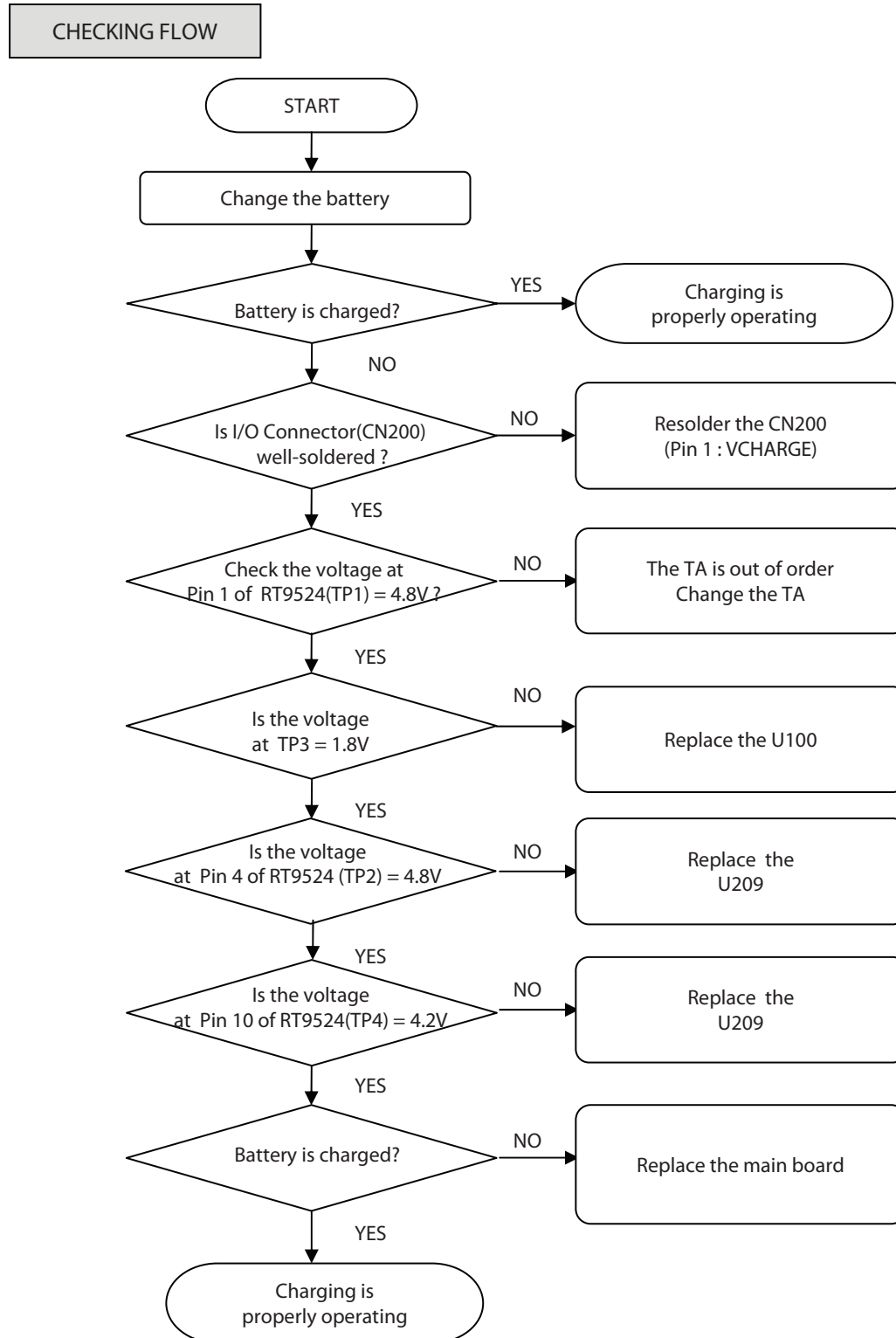


Figure 4.6.2

4. TROUBLE SHOOTING



4.7 Vibrator Trouble

TEST POINT

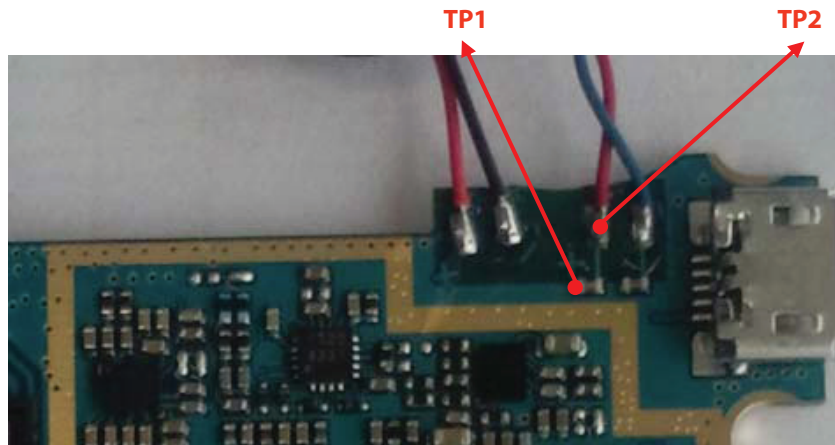


Figure 4.7.1

CIRCUIT

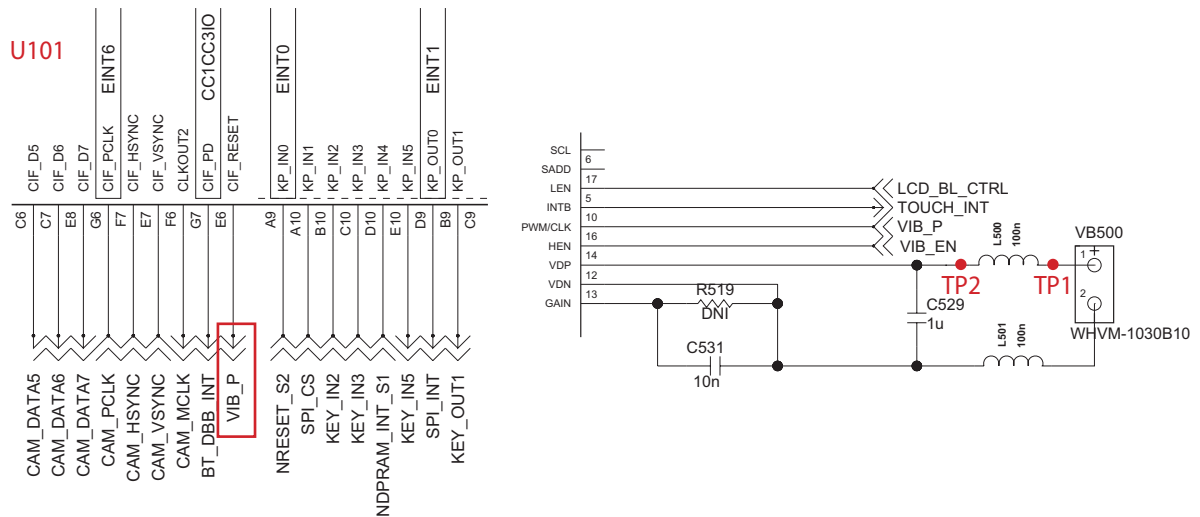
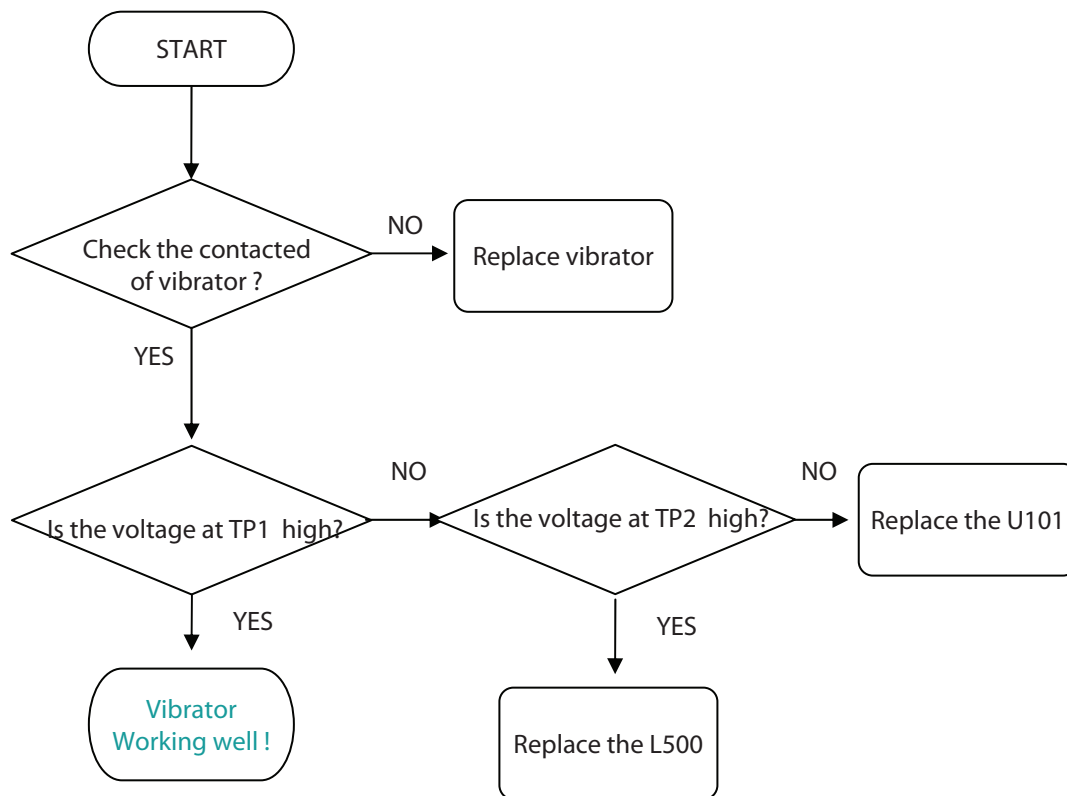


Figure 4.7.2

4. TROUBLE SHOOTING

CHECKING FLOW

SETTING : Enter the engineering mode, and set vibrator on at vibration of BB test menu



4.8 LCD Trouble

TEST POINT

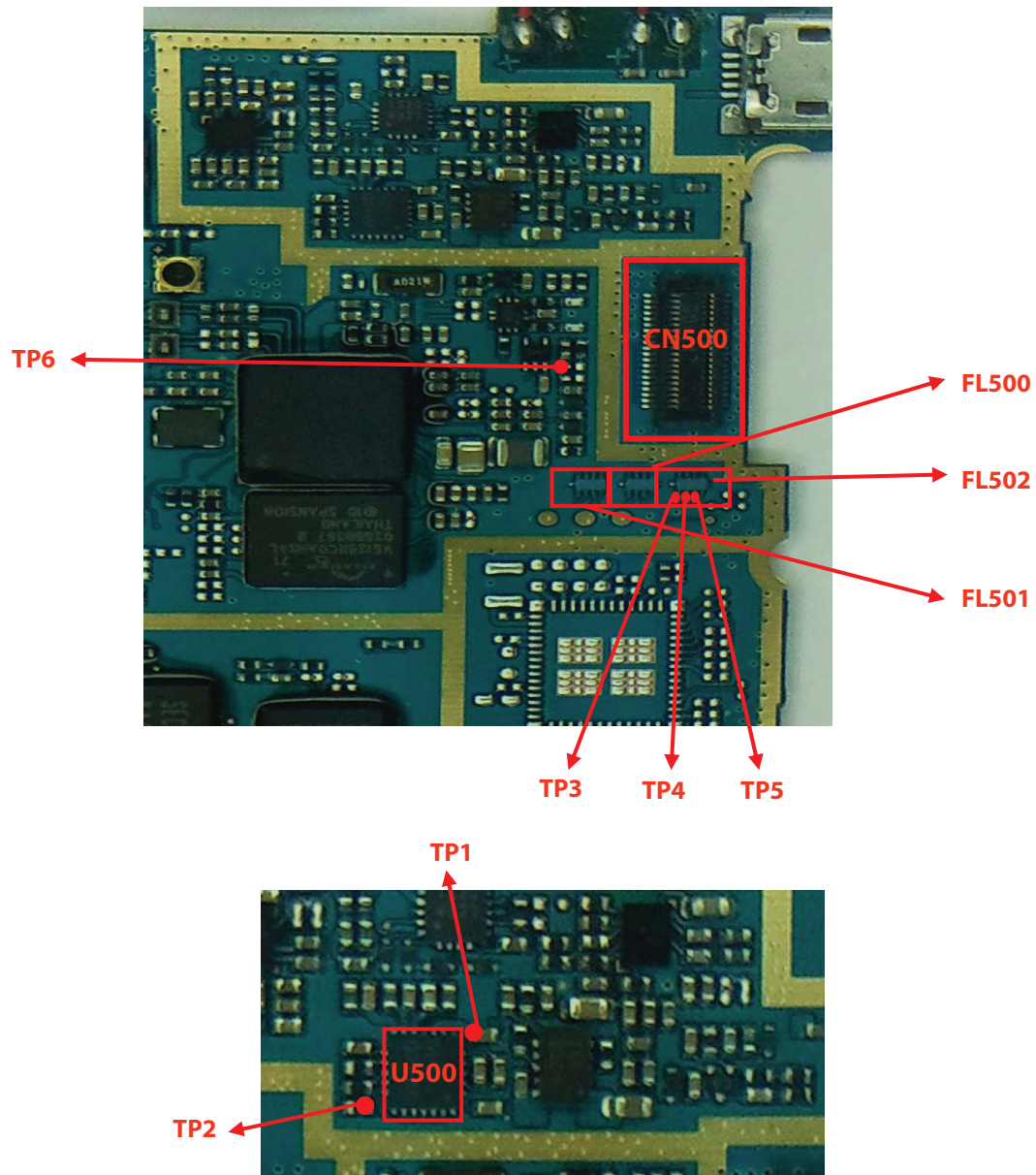
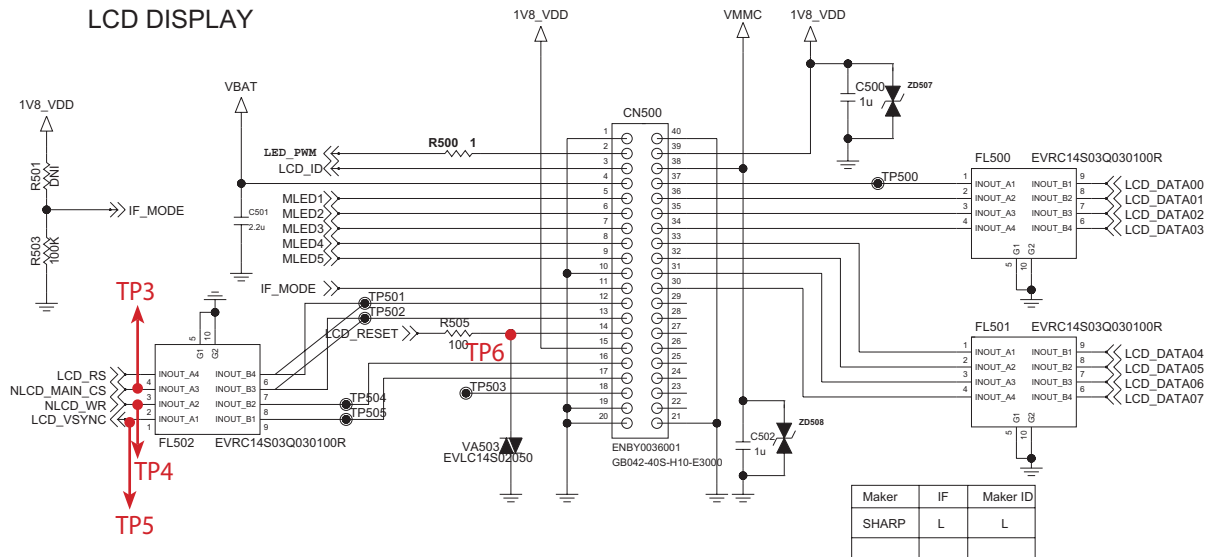


Figure 4.8.1

4. TROUBLE SHOOTING

CIRCUIT



BACKLIGHT CHARGE PUMP

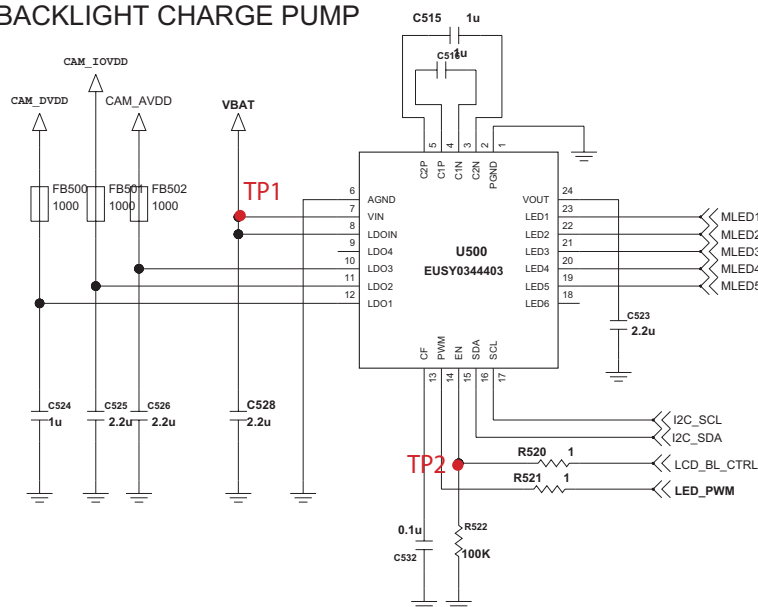
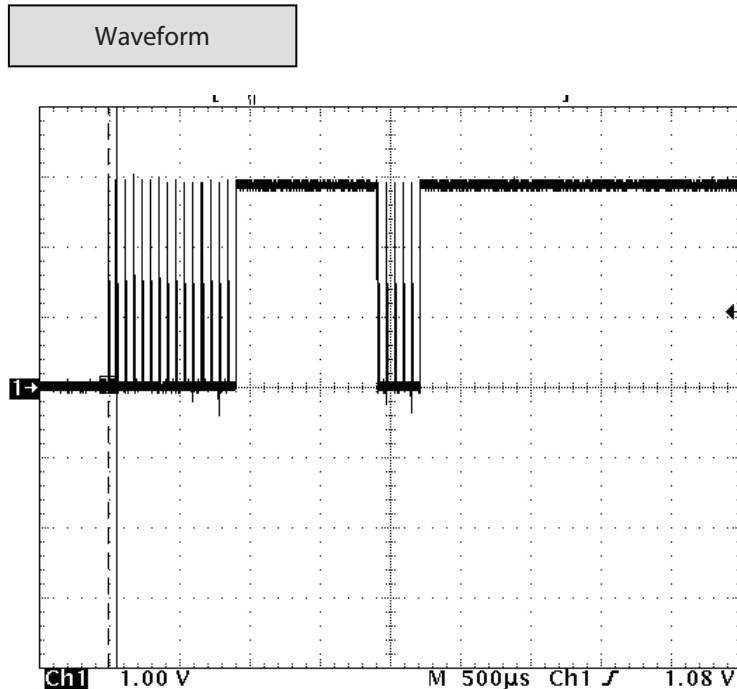


Figure 4.8.2



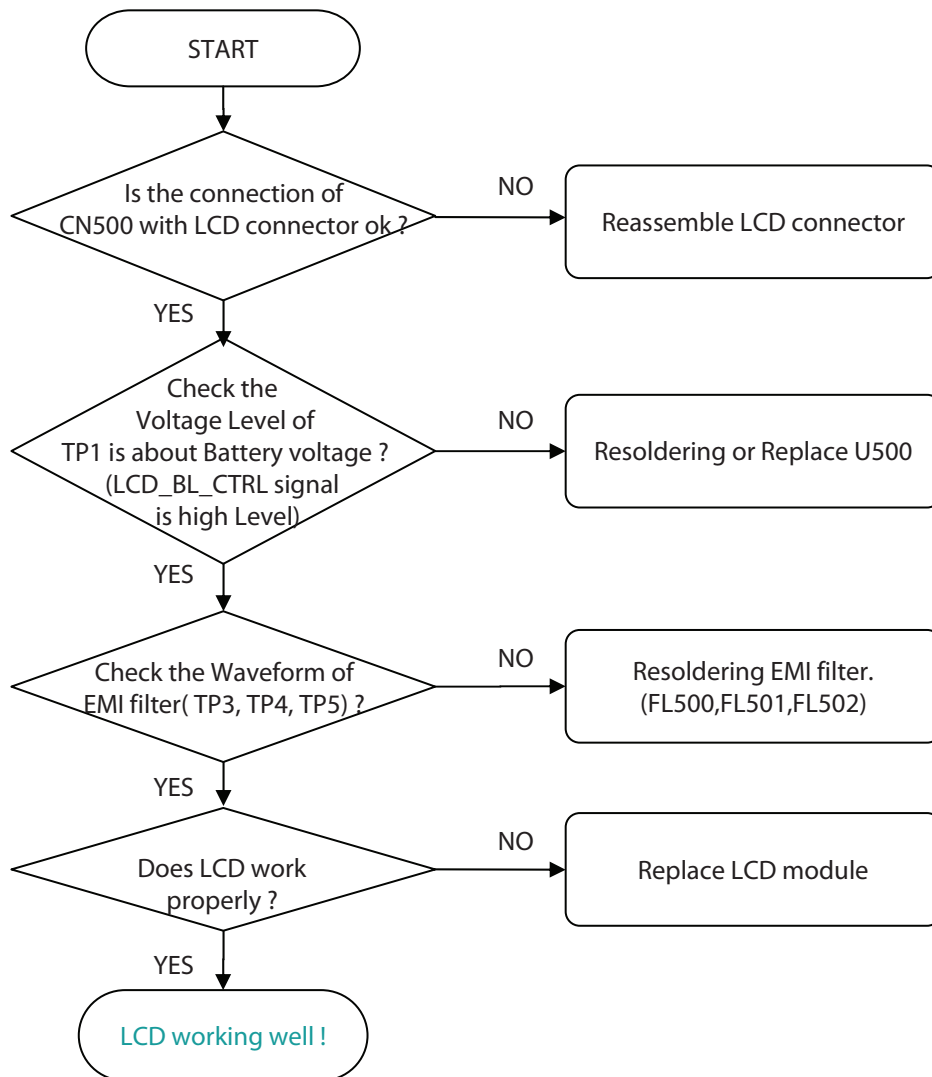
Graph 4.8.1. LCD Backlight Control Signal Waveform



Graph 4.8.2. LCD Data Waveform

4. TROUBLE SHOOTING

CHECKING FLOW



4.9 Camera Trouble

TEST POINT

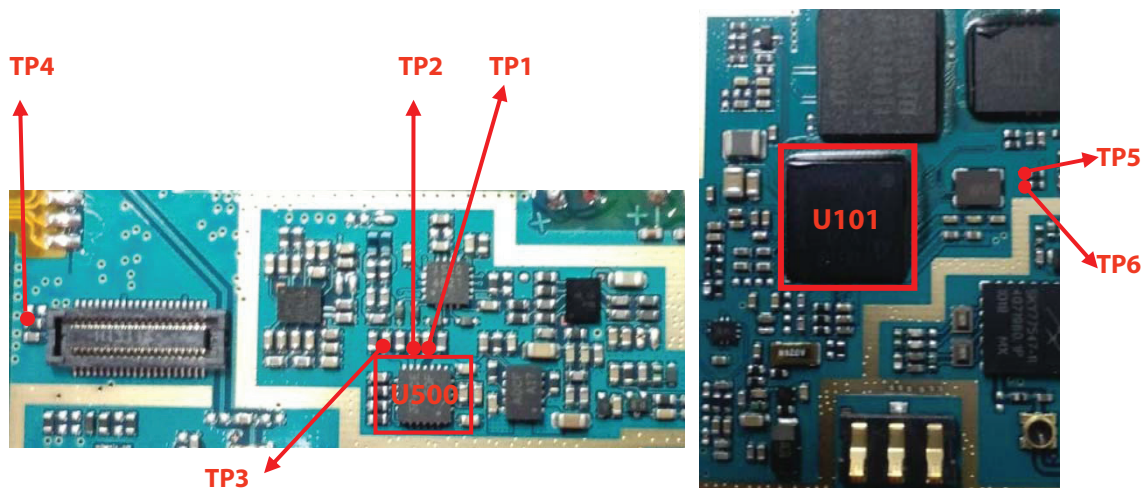
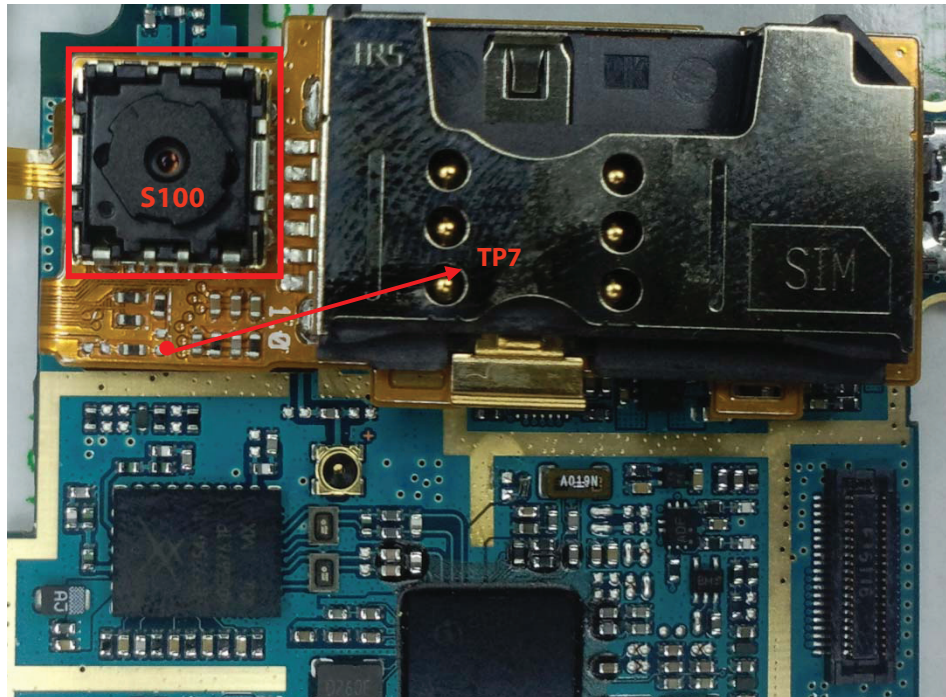


Figure 4.9.1

4. TROUBLE SHOOTING

CIRCUIT

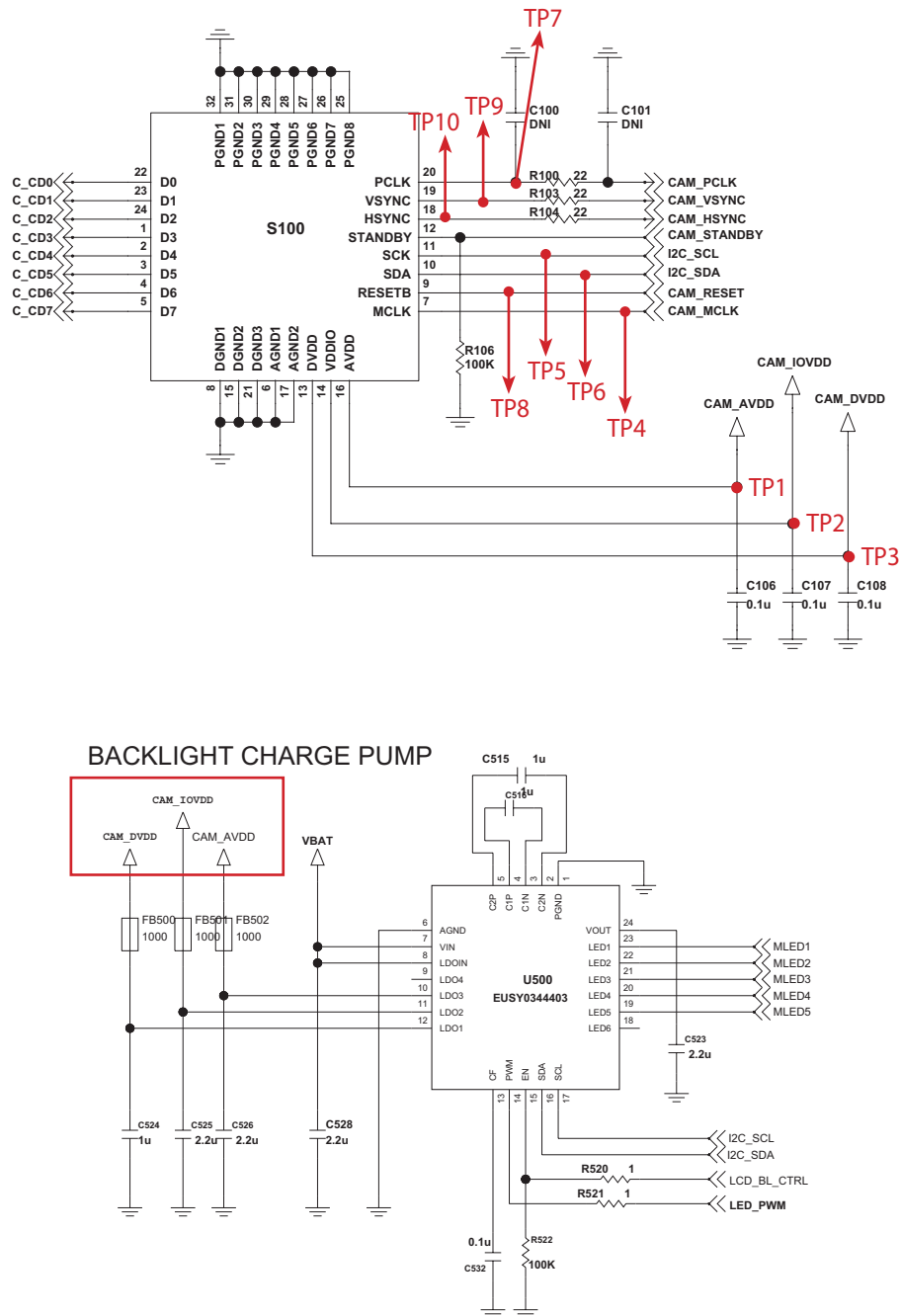
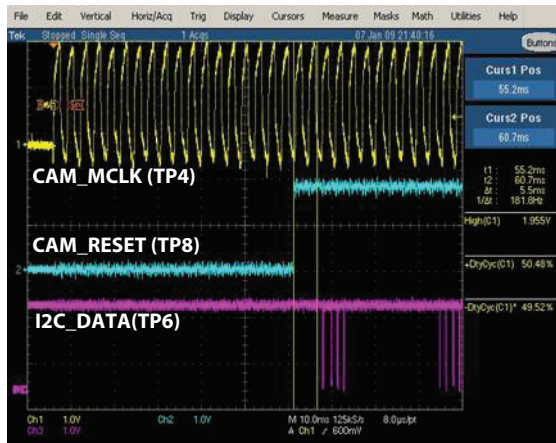


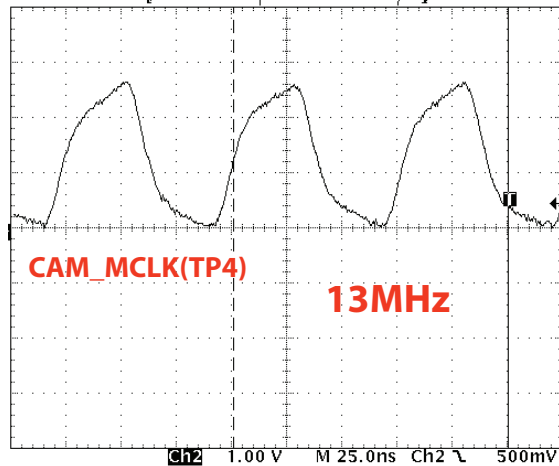
Figure 4.9.2

4. TROUBLE SHOOTING

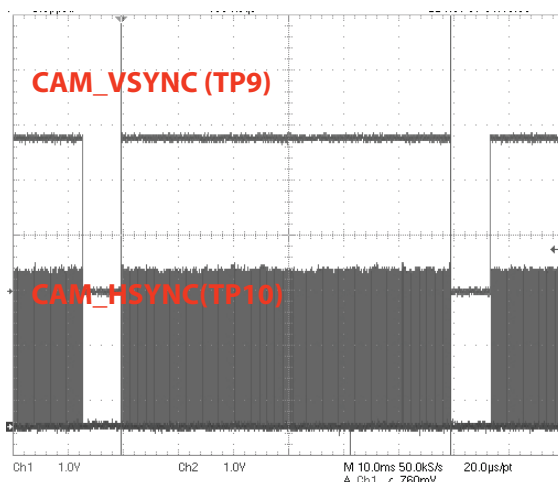
Waveform



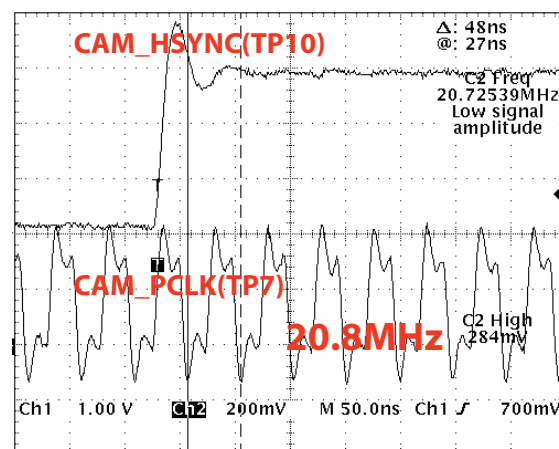
Graph 4.9.1. I2C Data Waveform



Graph 4.9.2. MCLK Waveform

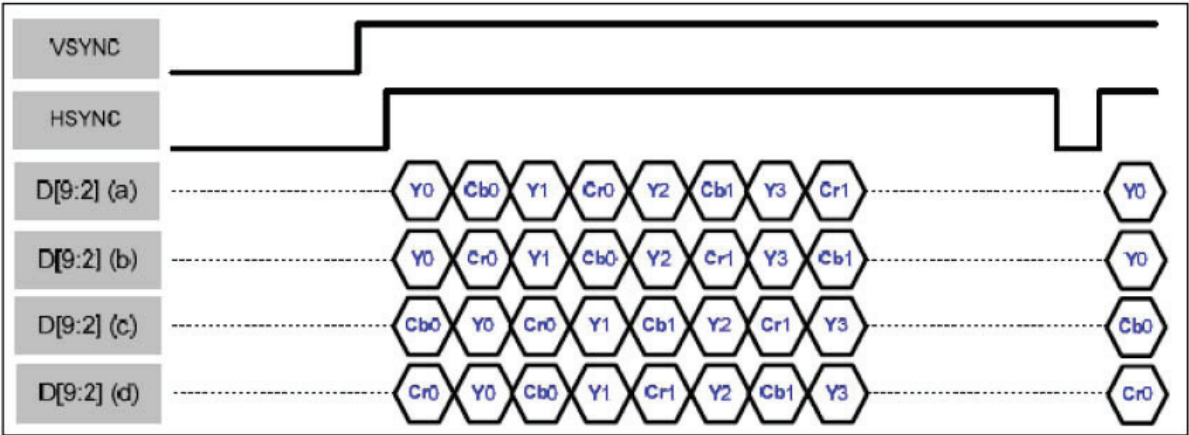


Graph 4.9.3. CAM_VSYNC vs. CAM_HSYNC Waveform



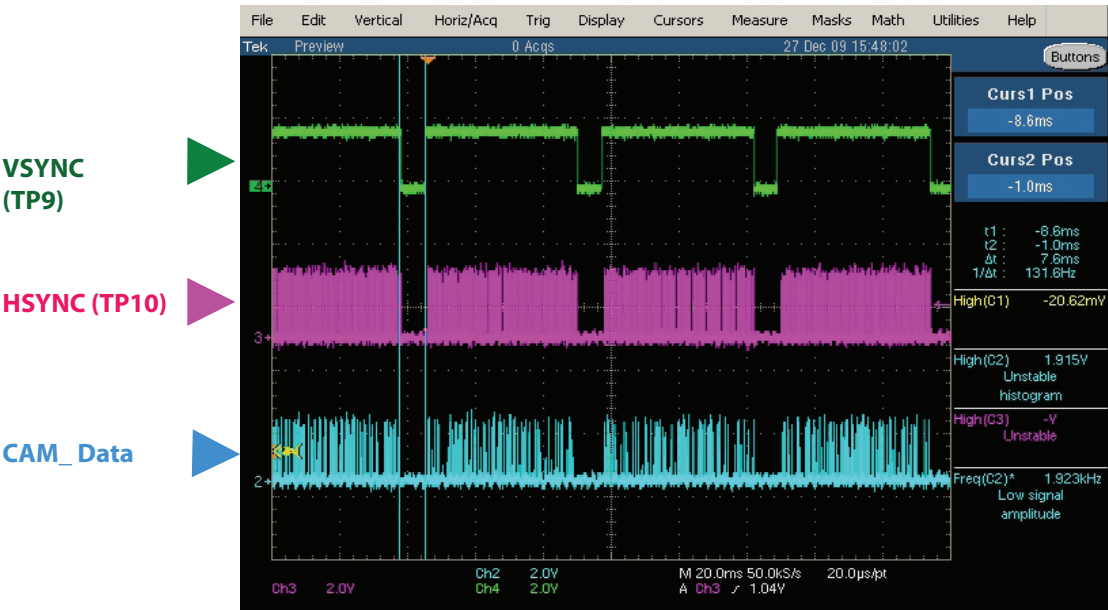
Graph 4.9.4. CAM_HSYNC vs. CAM_PCLK Waveform

4. TROUBLE SHOOTING



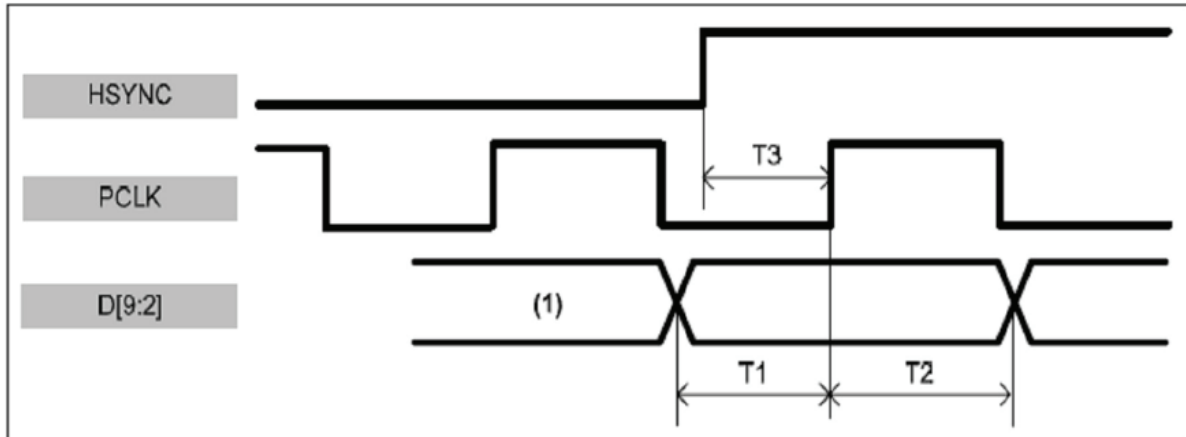
[NOTE] The data output sequence, (a) to (d) can be selected by register setting.

Graph 4.9.5.CAM Output Timing Waveform



Graph 4.9.6.CAM Output Timing Waveform

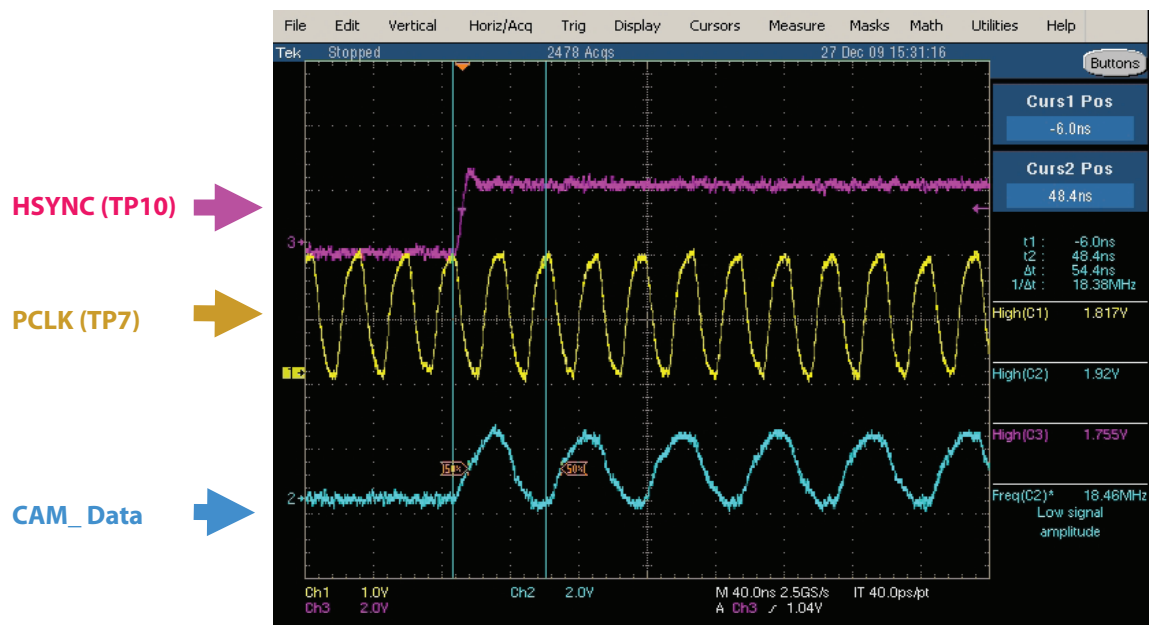
4. TROUBLE SHOOTING



[NOTE] (1): blank & start code, otherwise '0' for ITU-R.656 output format:

SYMBOL	PARAMETER	MIN	MAX	UNIT
T1	Data Setup Time to PCLK	4	-	ns
T2	Data Hold Time to PCLK	4	-	ns
T3	HSYNC↑ to PCLK↑ delay	4	-	ns

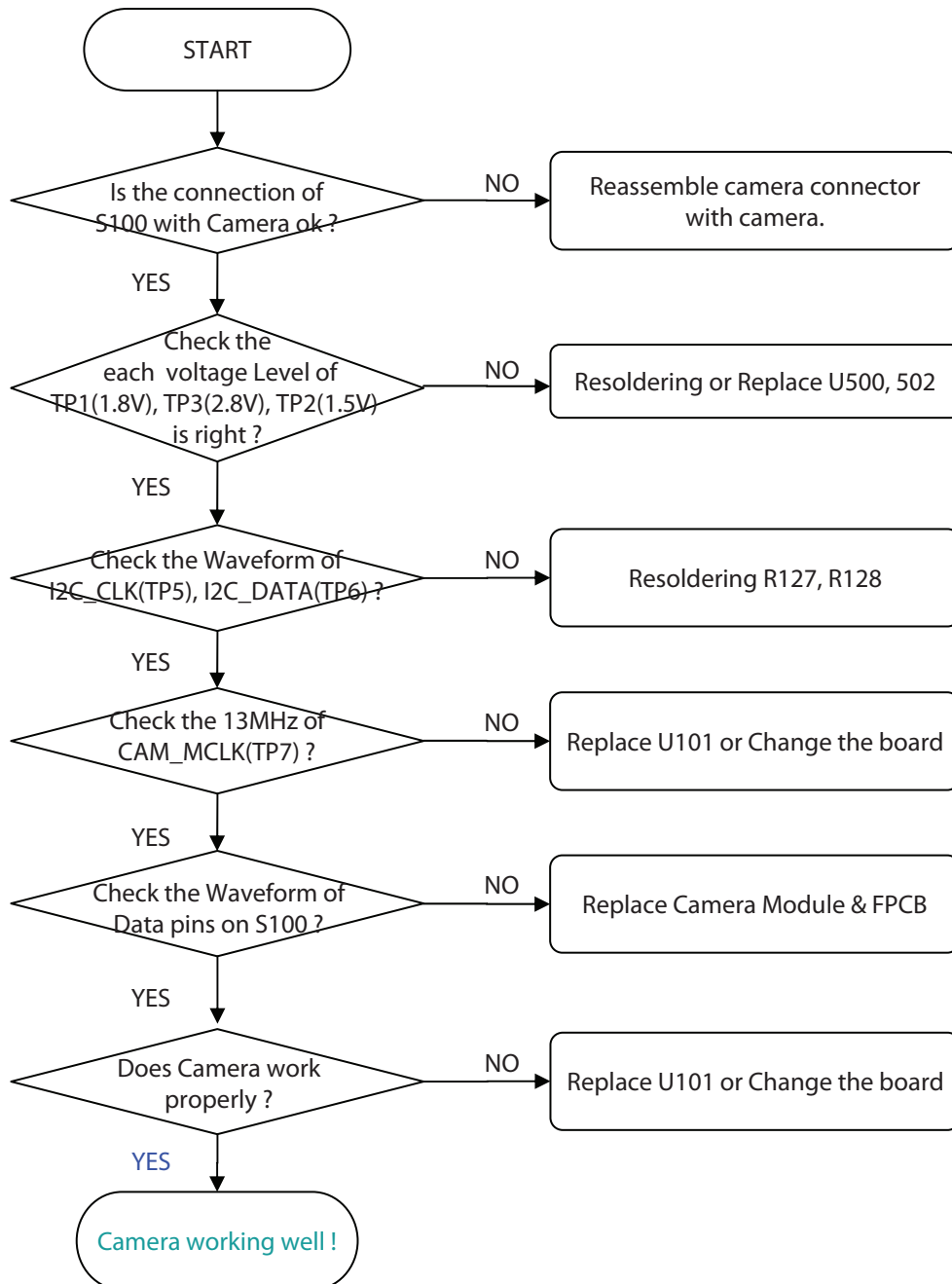
Graph 4.9.7. Output Data and Pixel Clock Timing



Graph 4.9.8. Output Data and Pixel Clock Timing

4. TROUBLE SHOOTING

CHECKING FLOW



4.10 Speaker Trouble

TEST POINT

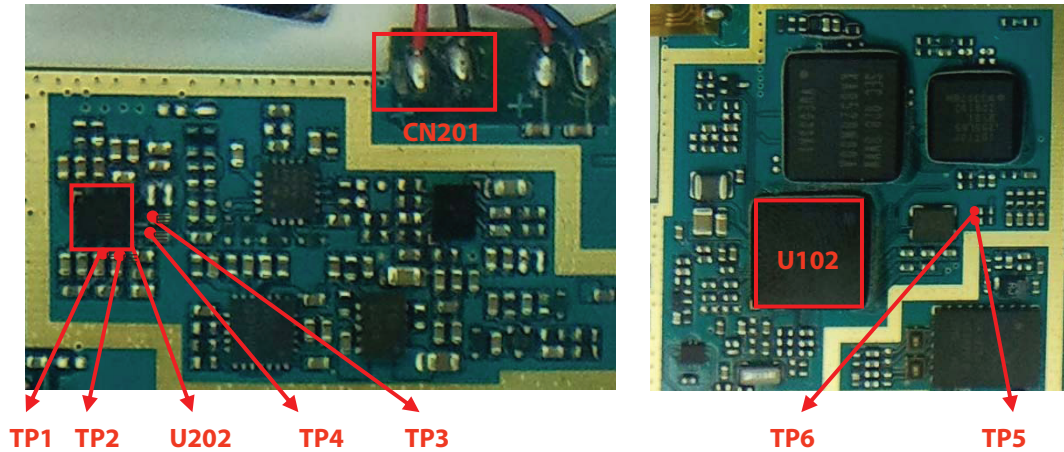


Figure 4.10.1

CIRCUIT

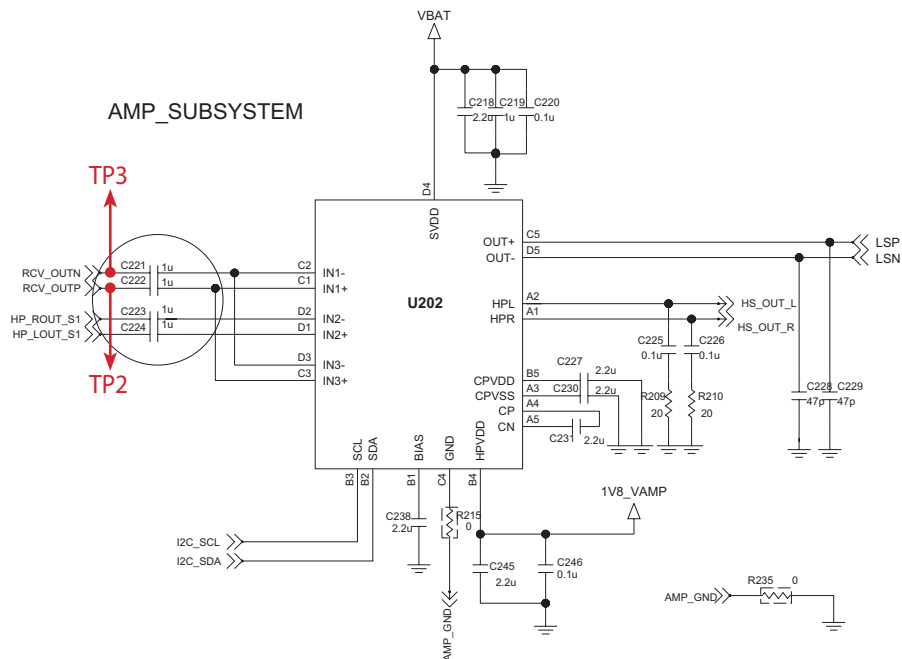


Figure 4.10.2

4. TROUBLE SHOOTING

4.10 Speaker Trouble

CIRCUIT

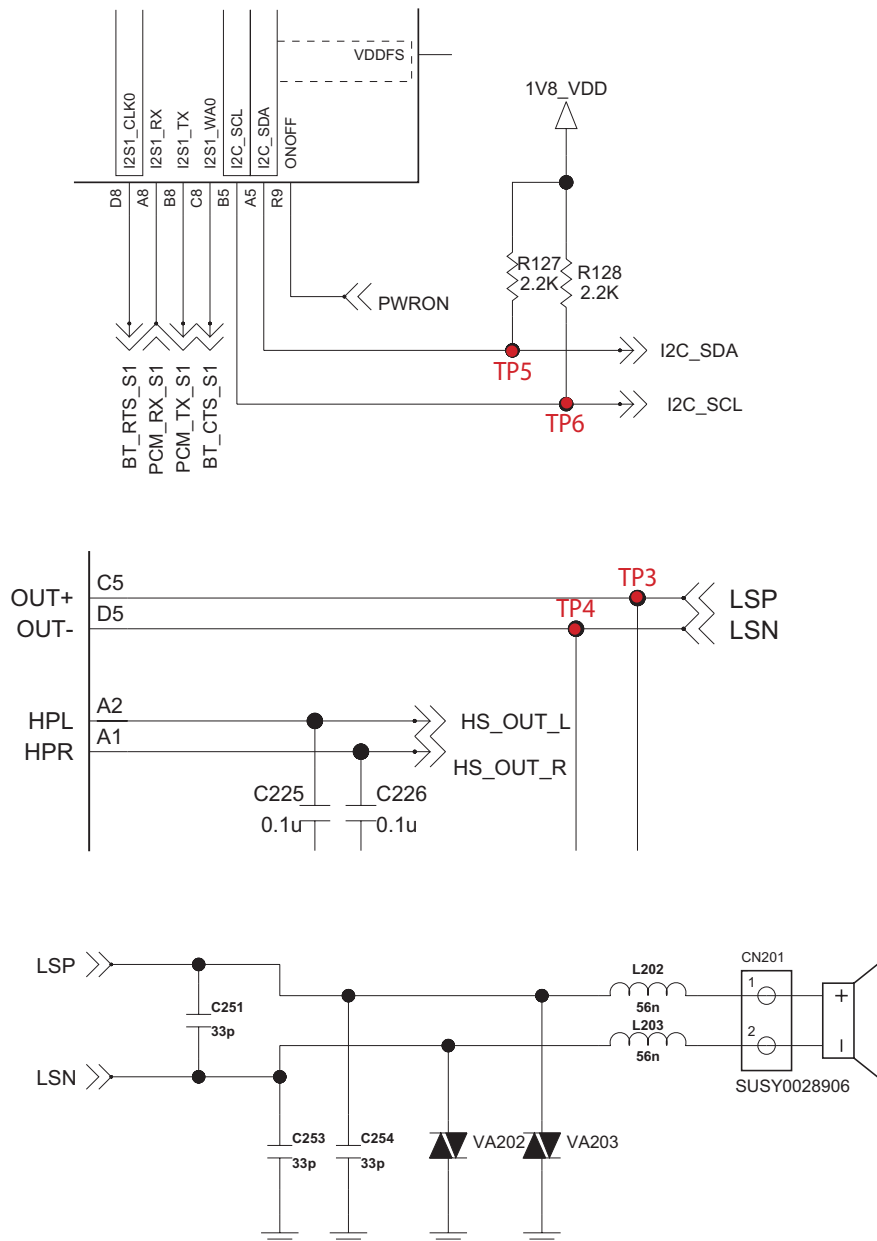
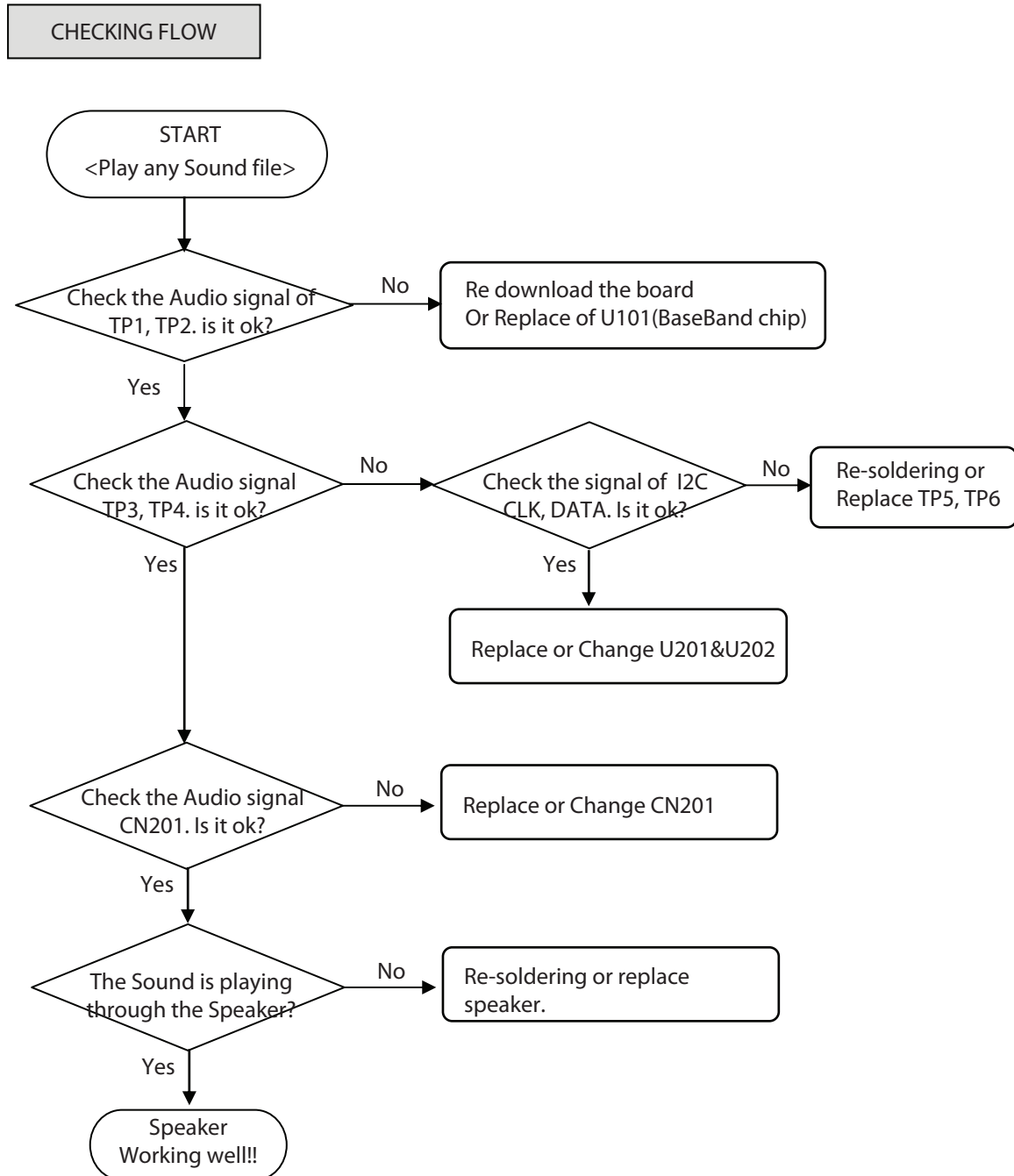


Figure 4.10.3



4. TROUBLE SHOOTING

4.11 Earphone Trouble

TEST POINT

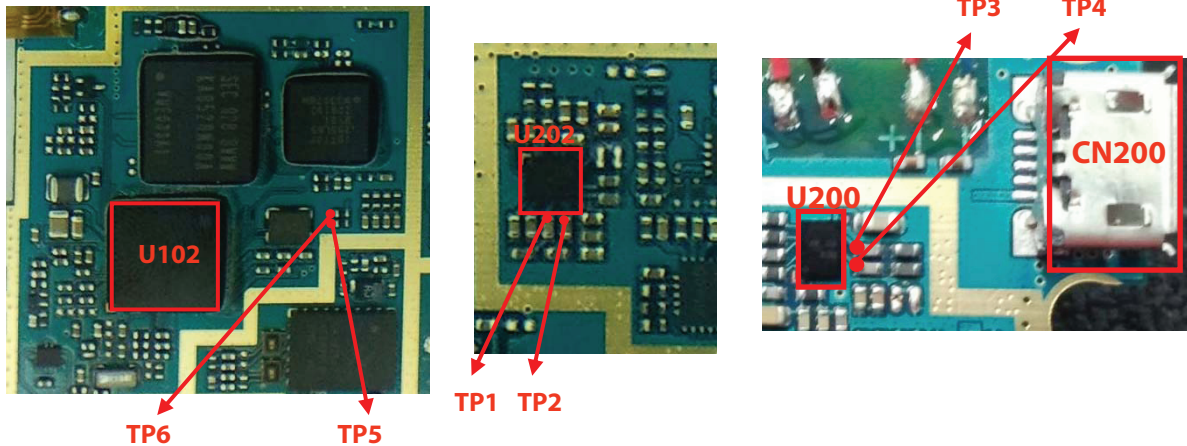


Figure 4.11.1

CIRCUIT

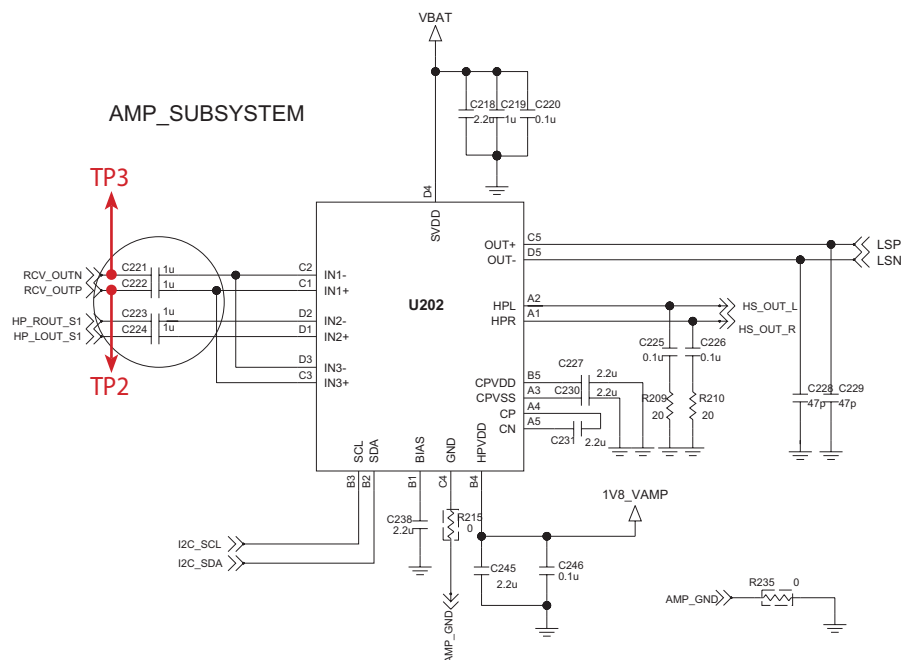
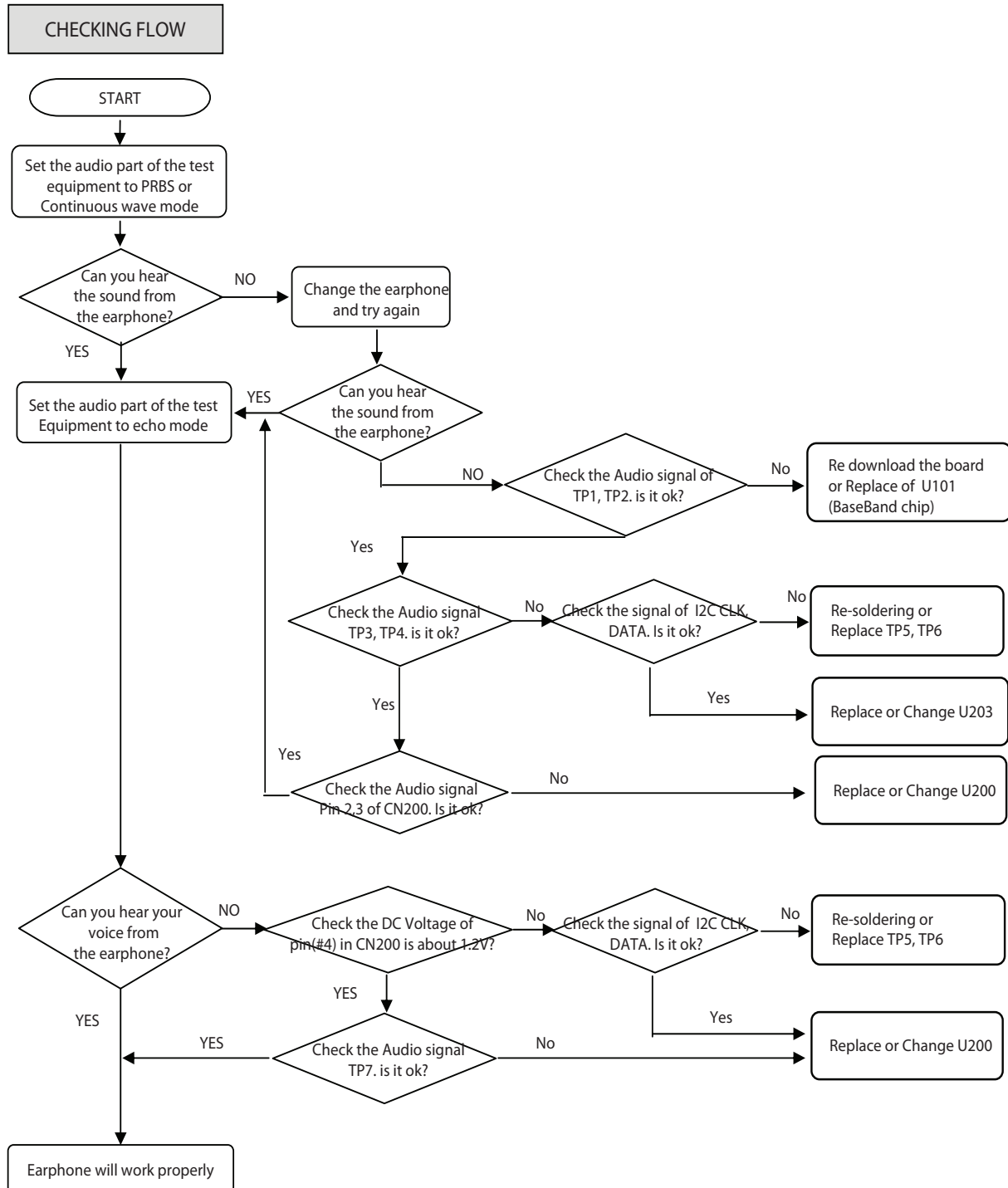


Figure 4.11.2

CIRCUIT



4. TROUBLE SHOOTING



4.12 Receiver Trouble

TEST POINT

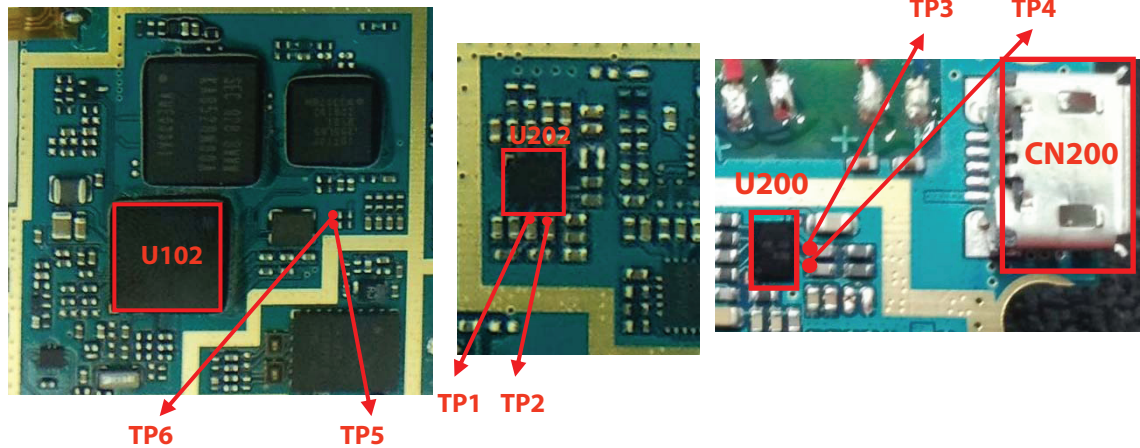


Figure 4.12.1

CIRCUIT

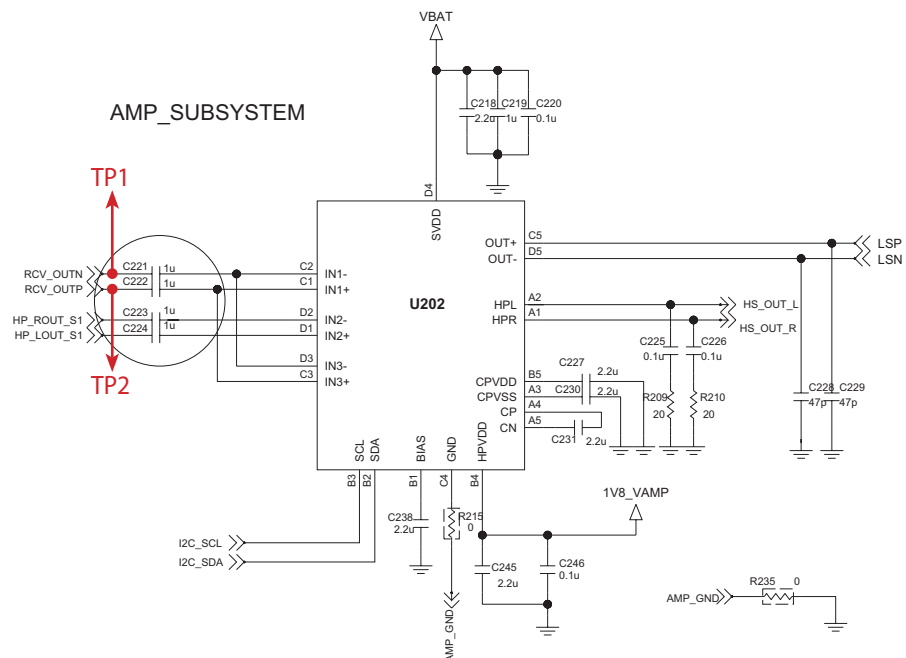
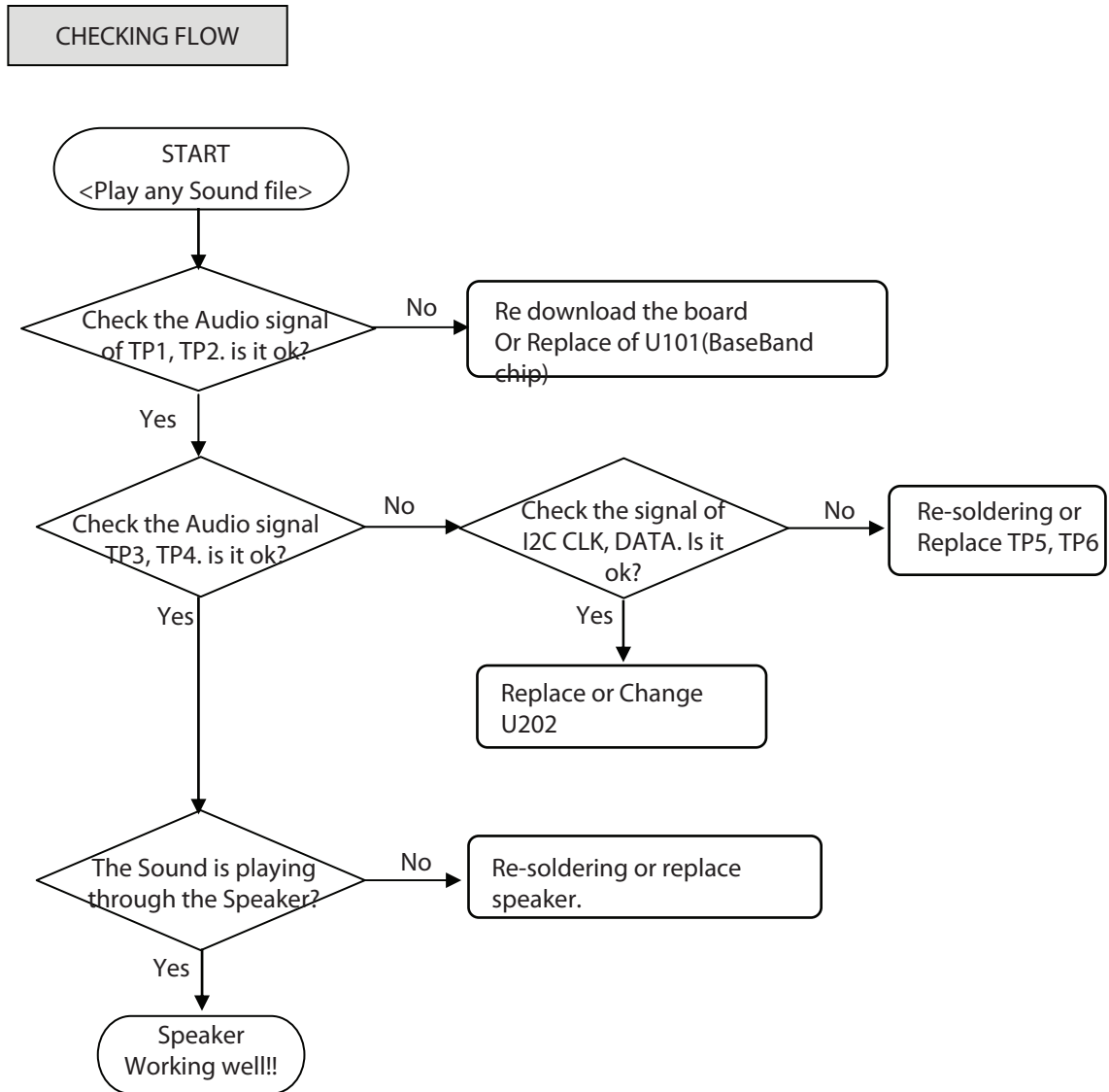


Figure 4.12.2



4. TROUBLE SHOOTING

4.13 Microphone Trouble

TEST POINT

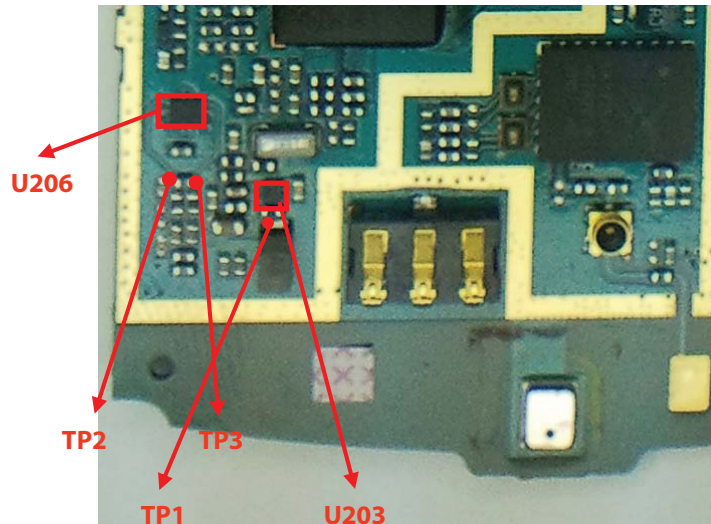
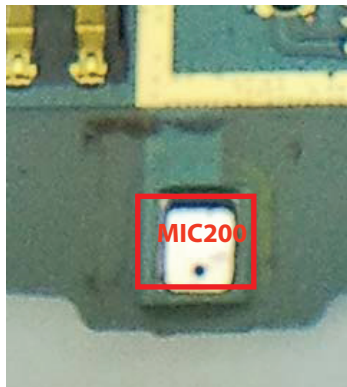


Figure 4.13.1

CIRCUIT

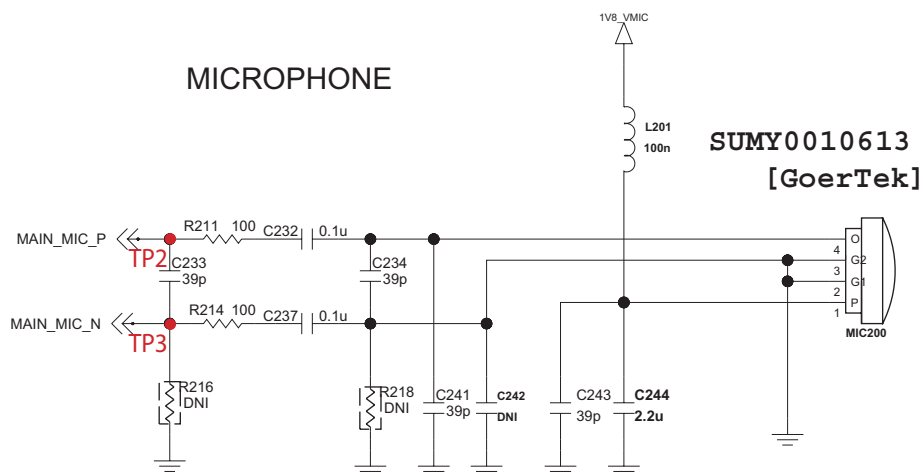
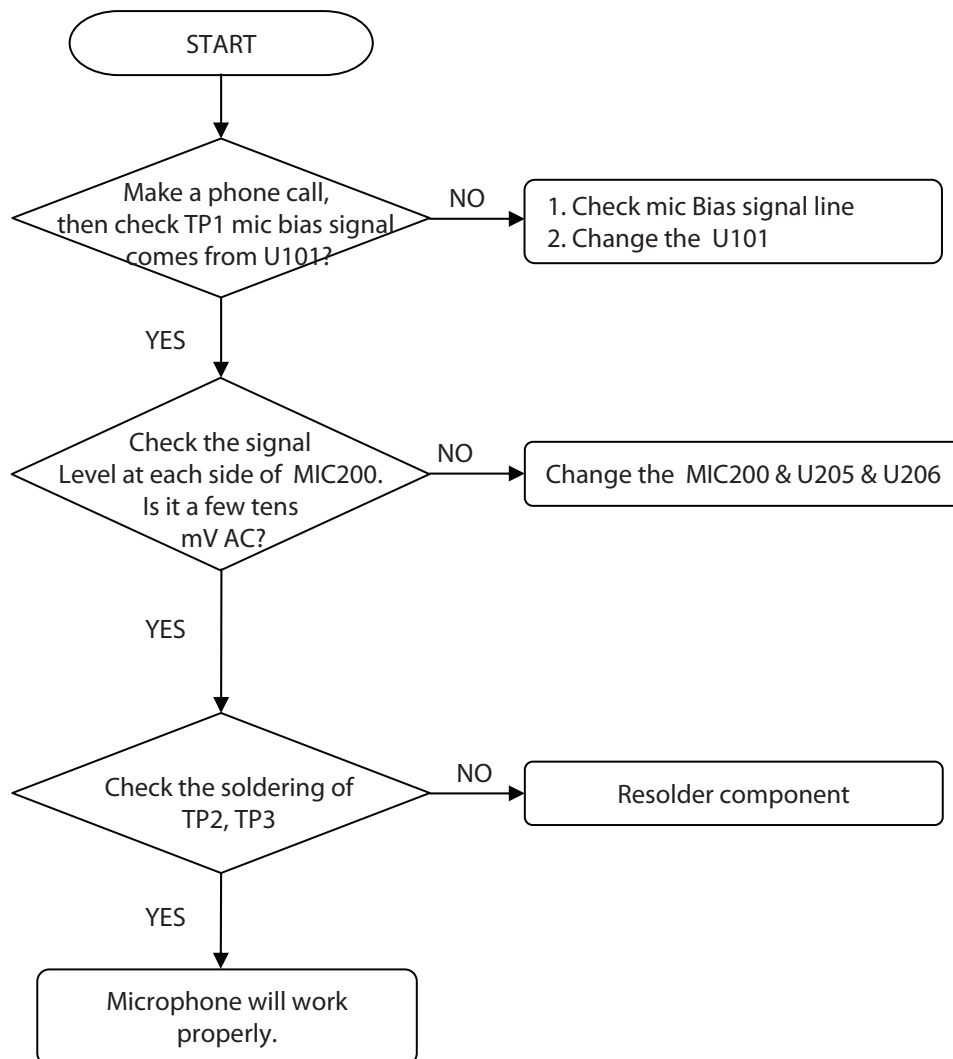


Figure 4.13.2

CHECKING FLOW

SETTING : After initialize Agilent 8960, Test EGSM900, DCS mode (or PCS mode)



4. TROUBLE SHOOTING

4.14 SIM Card Interface Trouble

TEST POINT

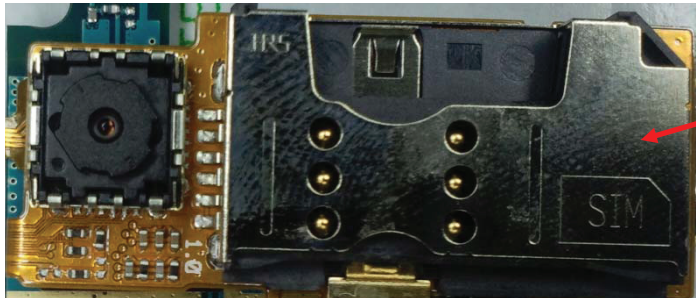


Figure 4.14.1

CIRCUIT

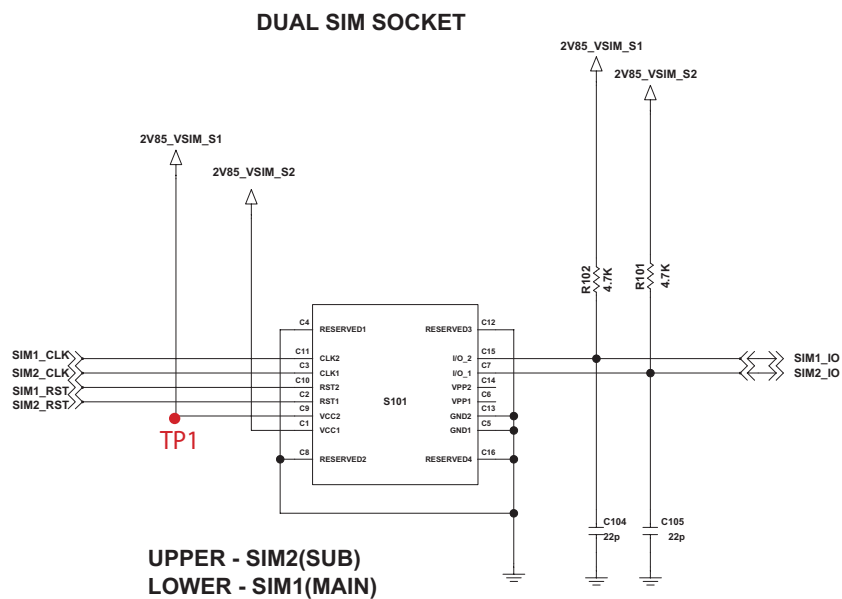
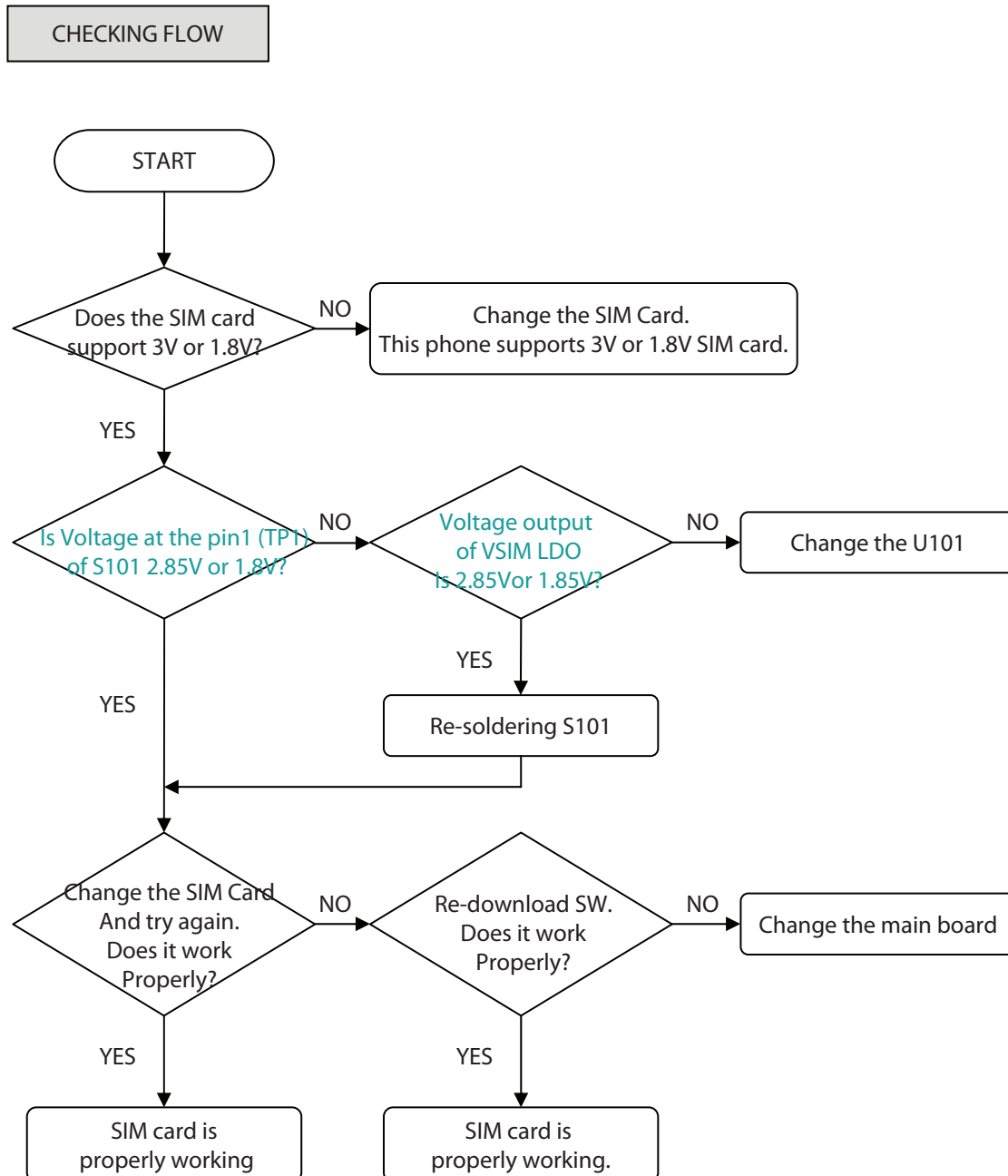


Figure 4.14.2



4. TROUBLE SHOOTING

4.15 Micro SD Trouble

TEST POINT

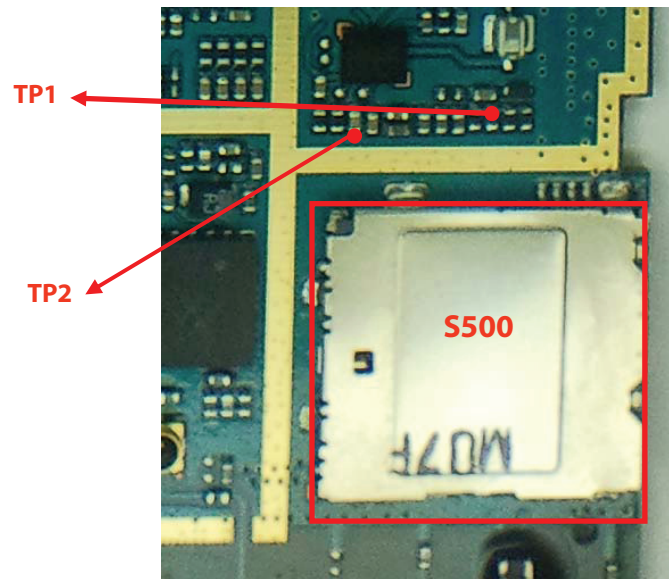


Figure 4.16.1

CIRCUIT

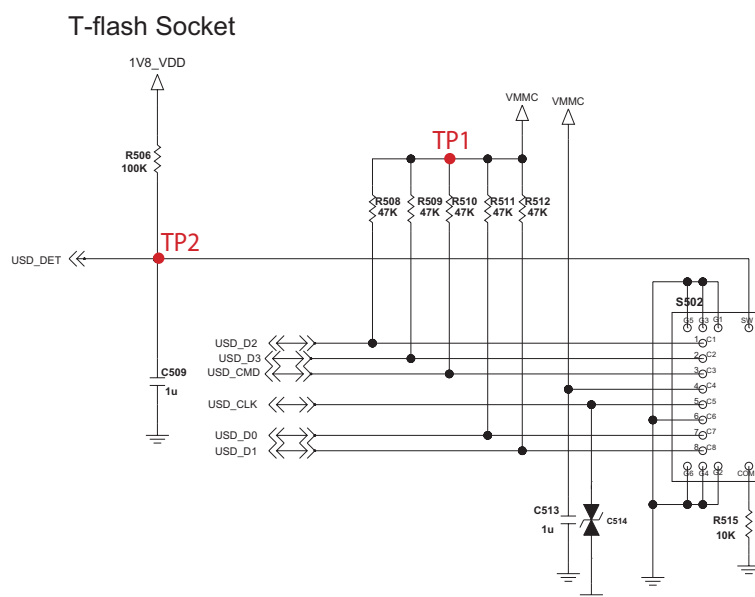
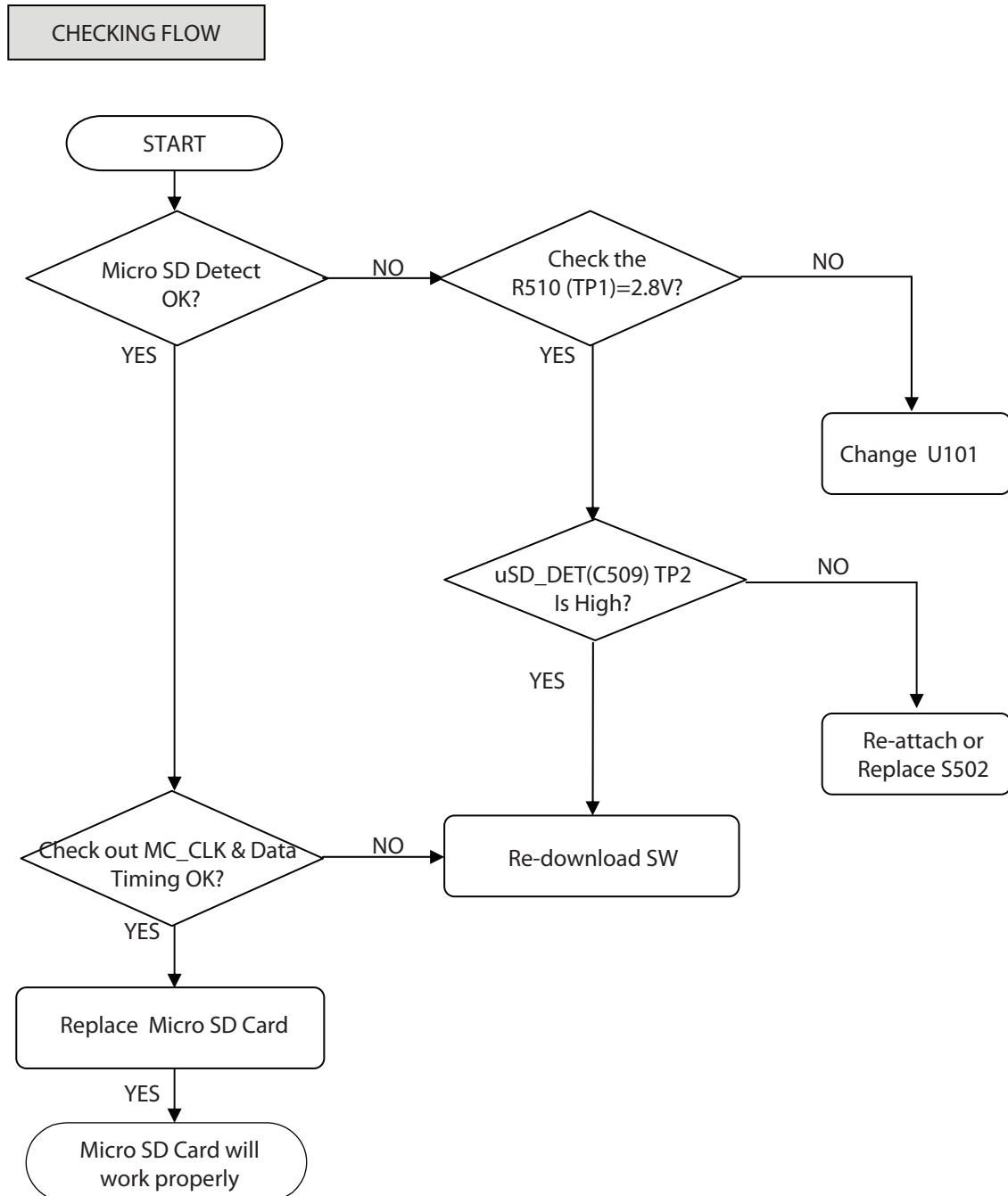
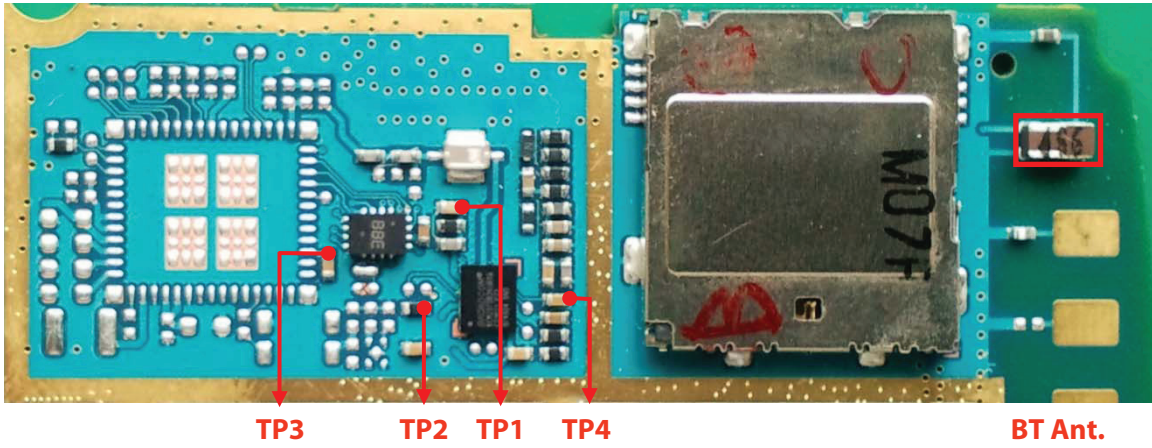


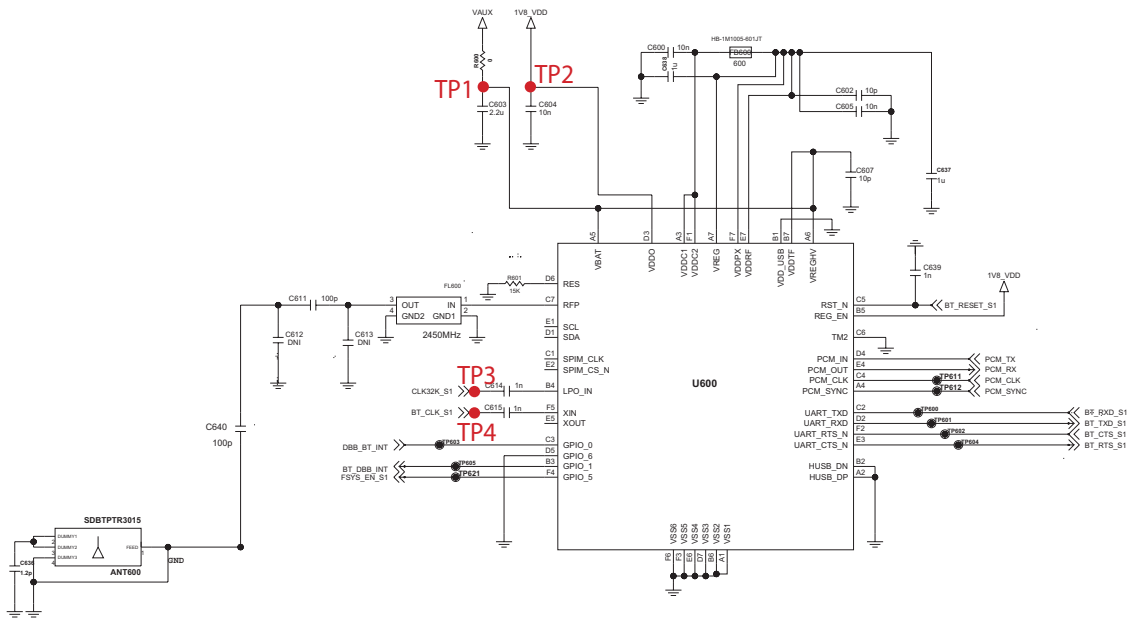
Figure 4.16.2



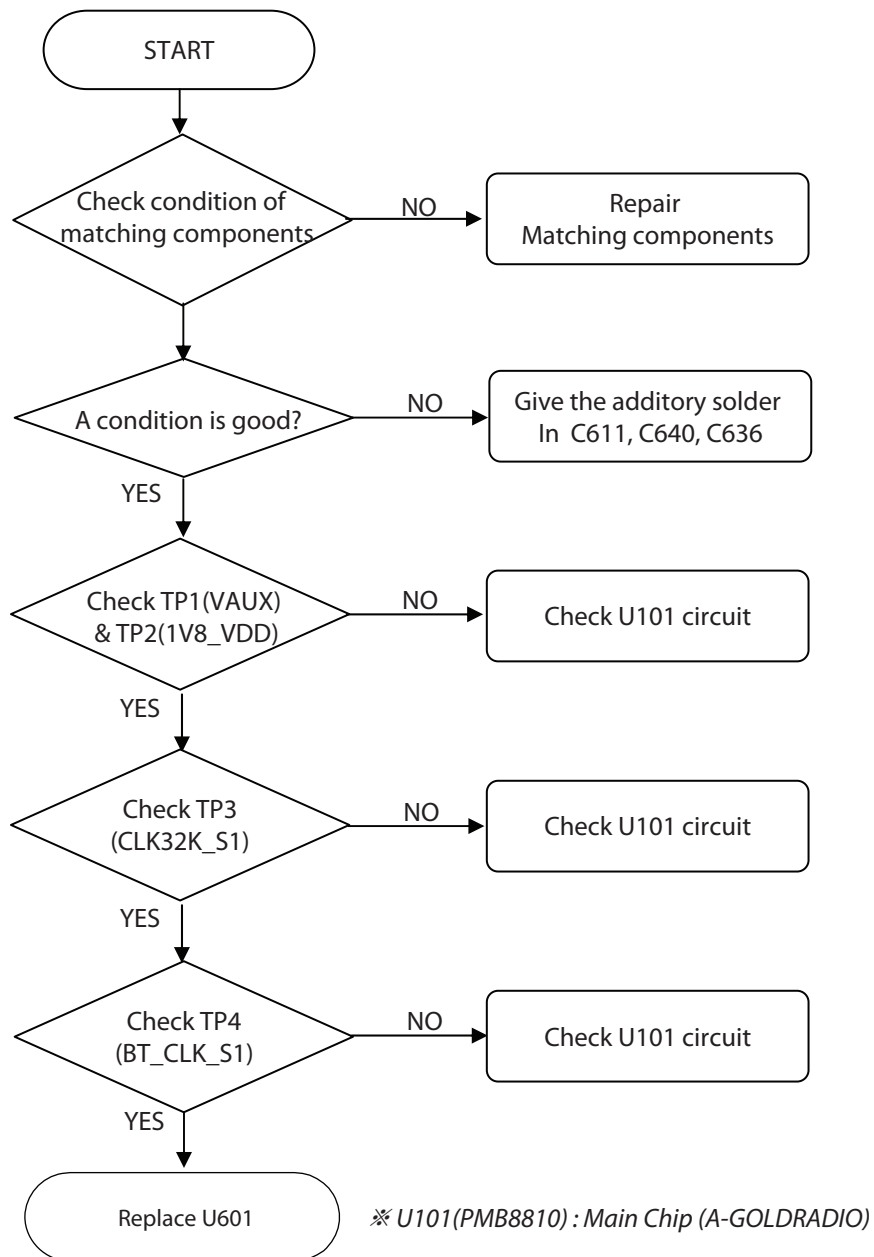
TEST POINT



CIRCUIT



CHECKING FLOW



4. TROUBLE SHOOTING

4.17 FM Radio Trouble

TEST POINT

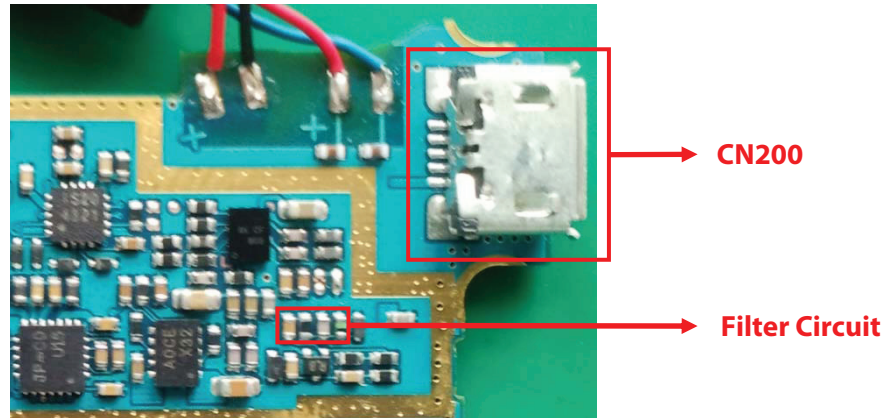


Figure 4.18.1 FM Radio test point

CIRCUIT

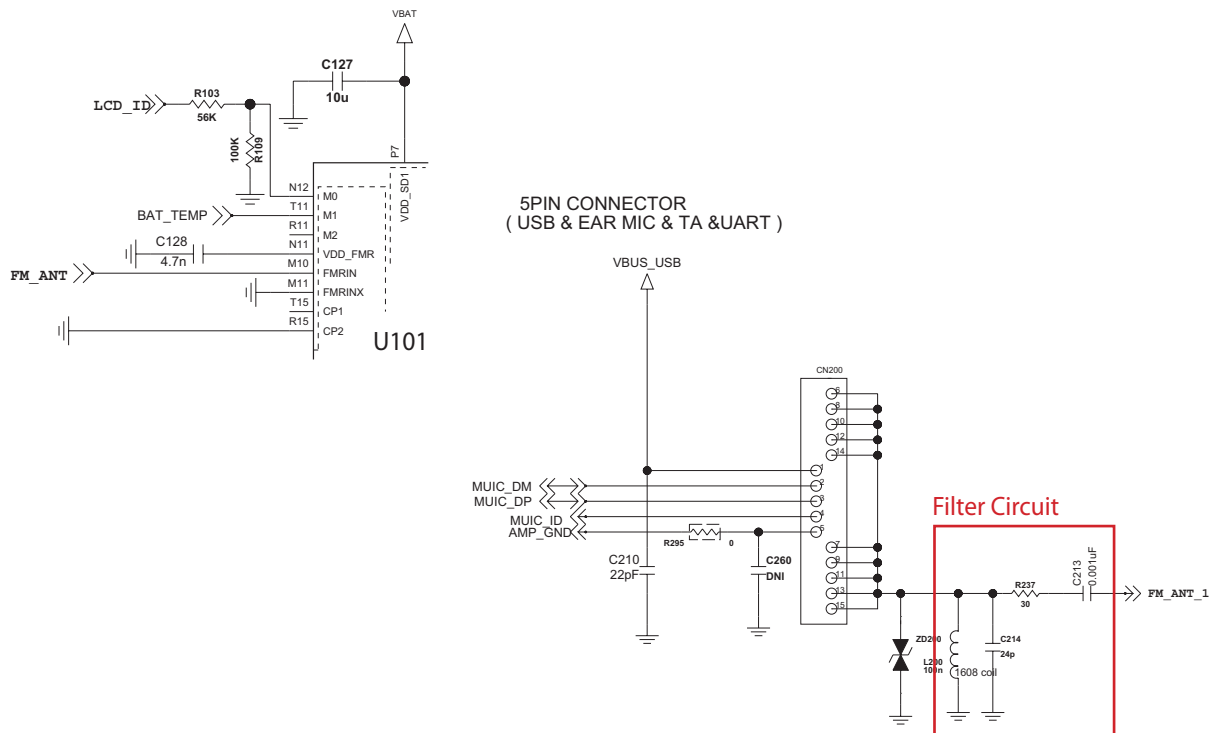
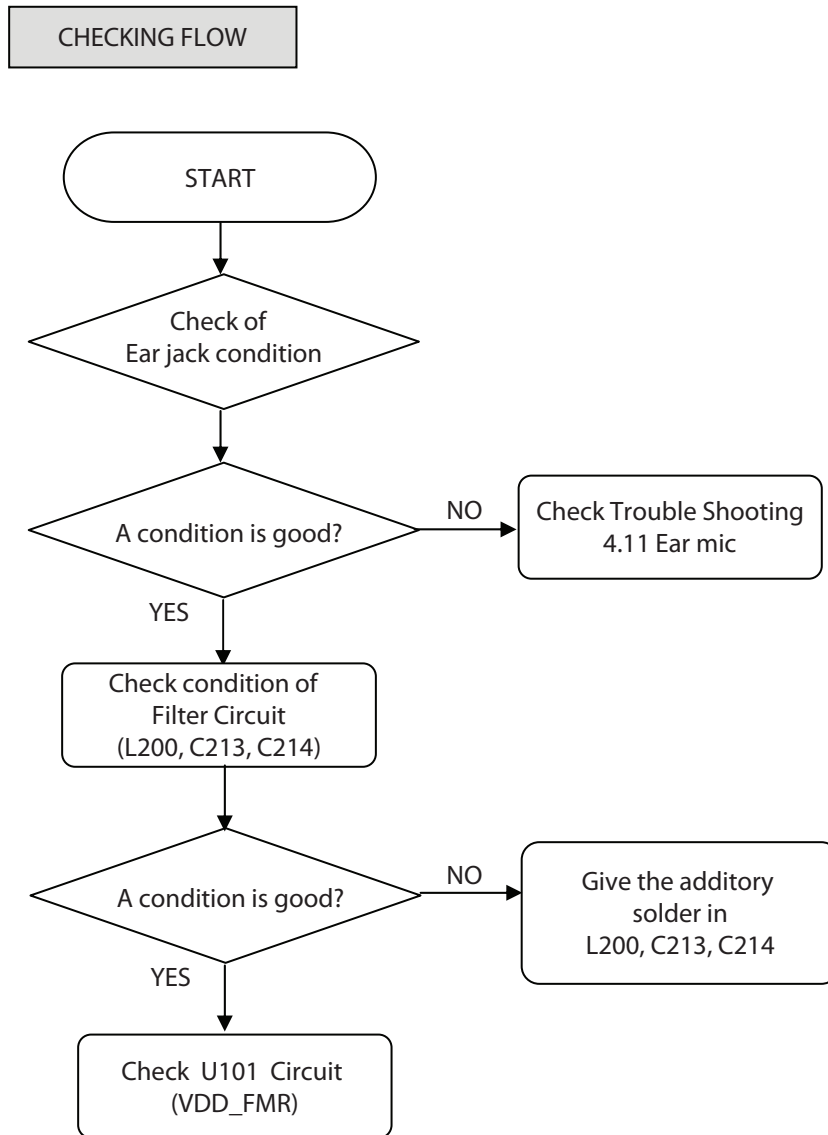
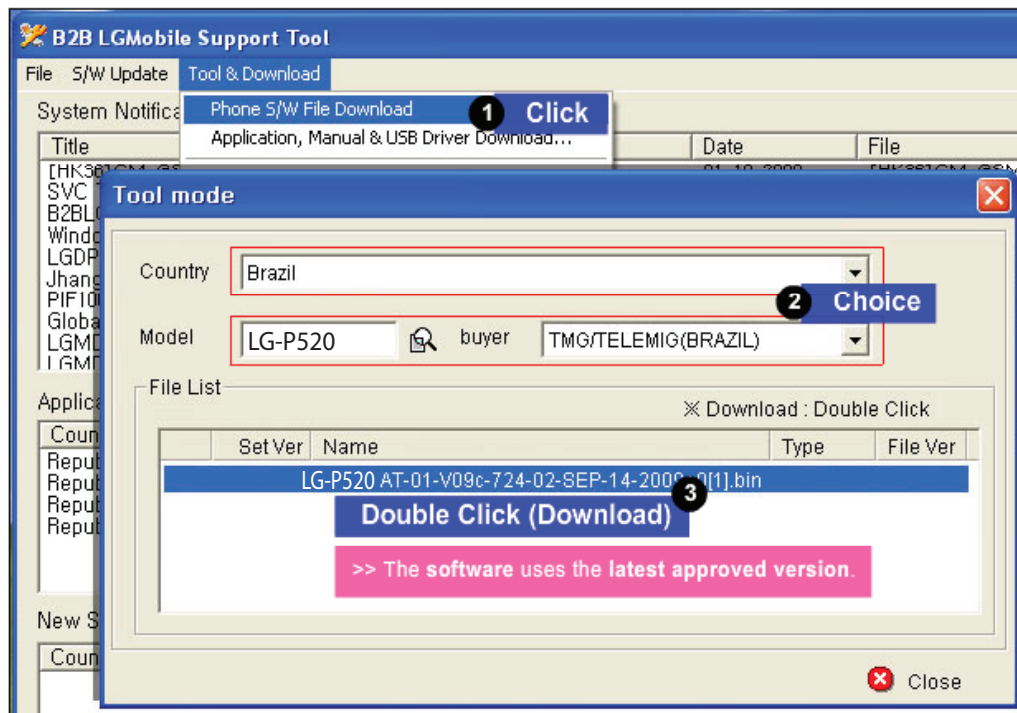
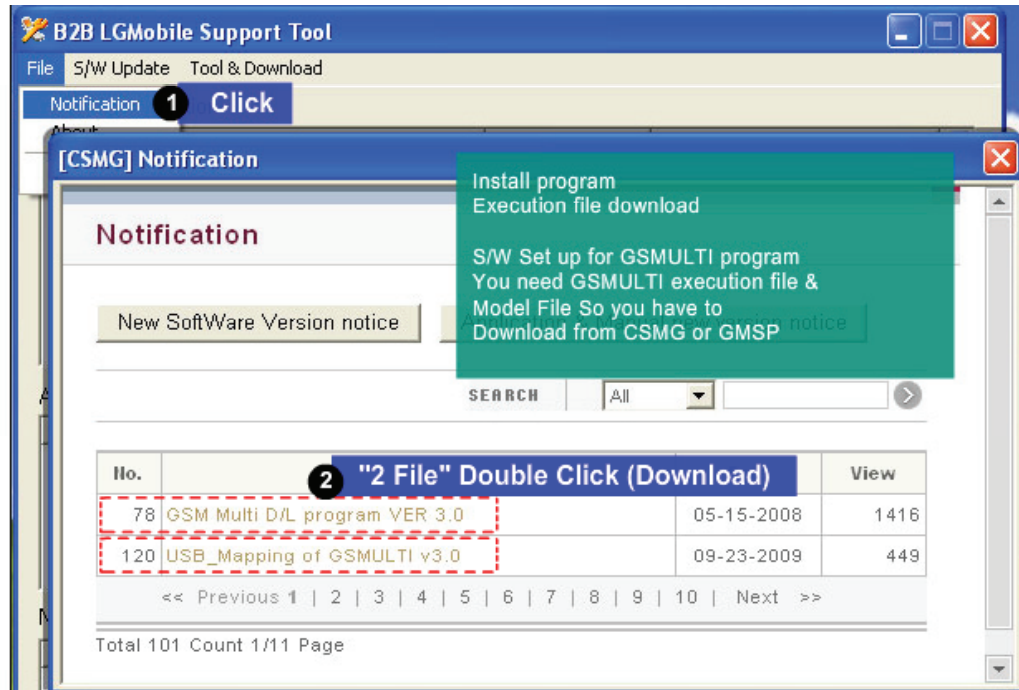


Figure 4.18.2 FM Radio circuit

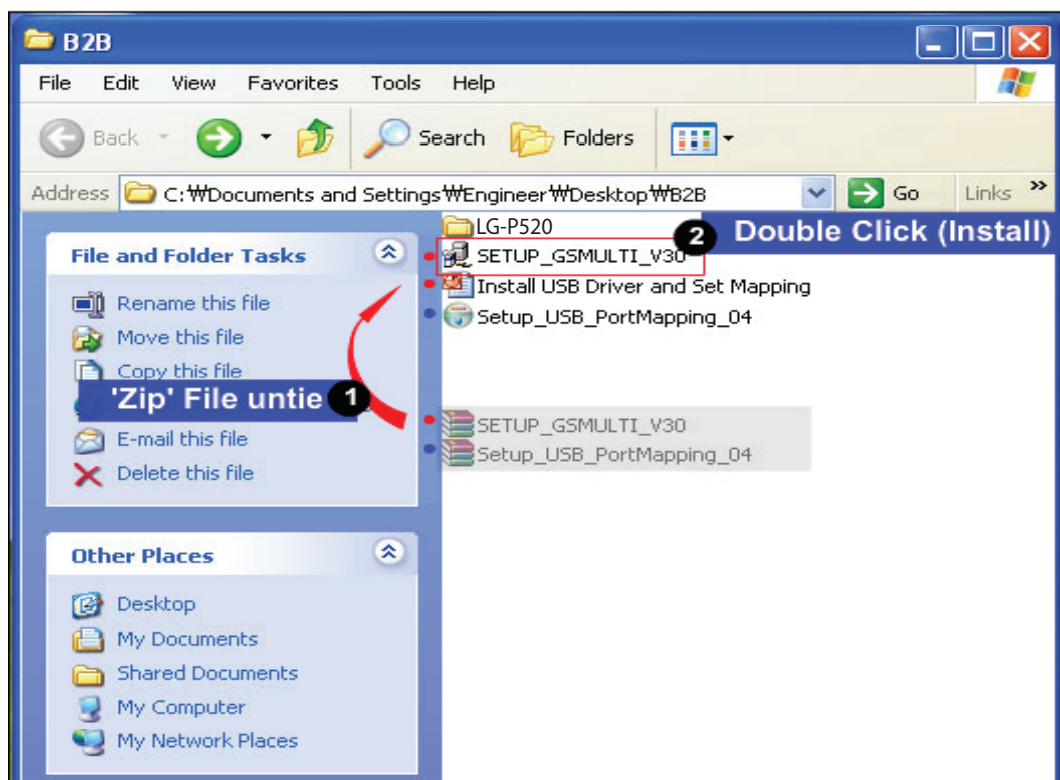
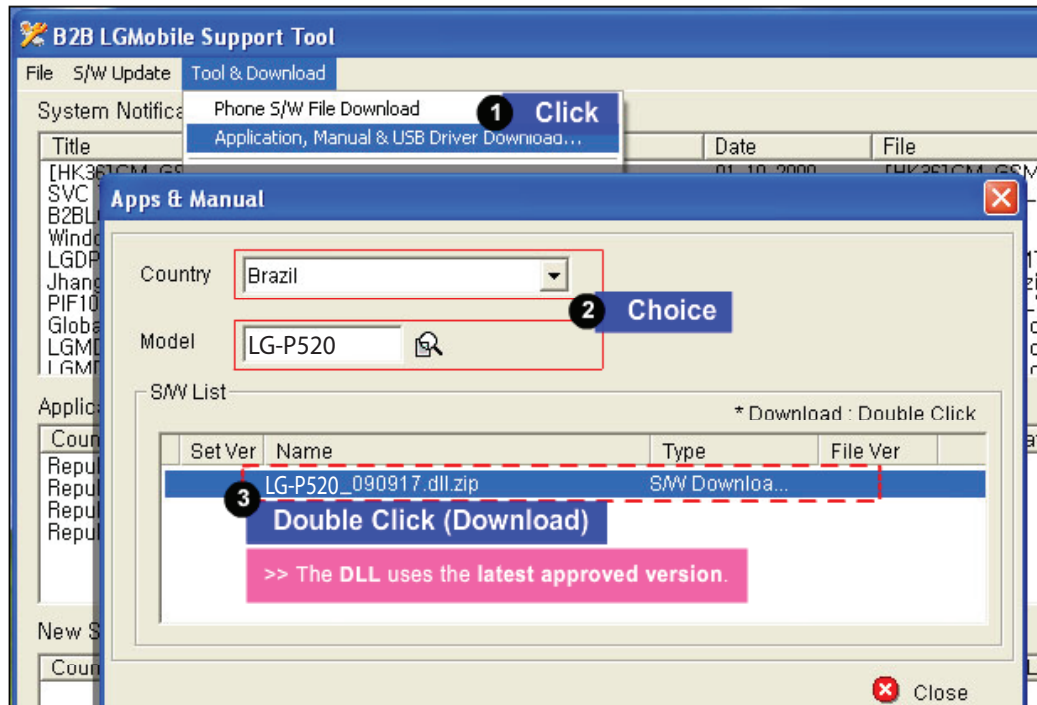


5. DOWNLOAD

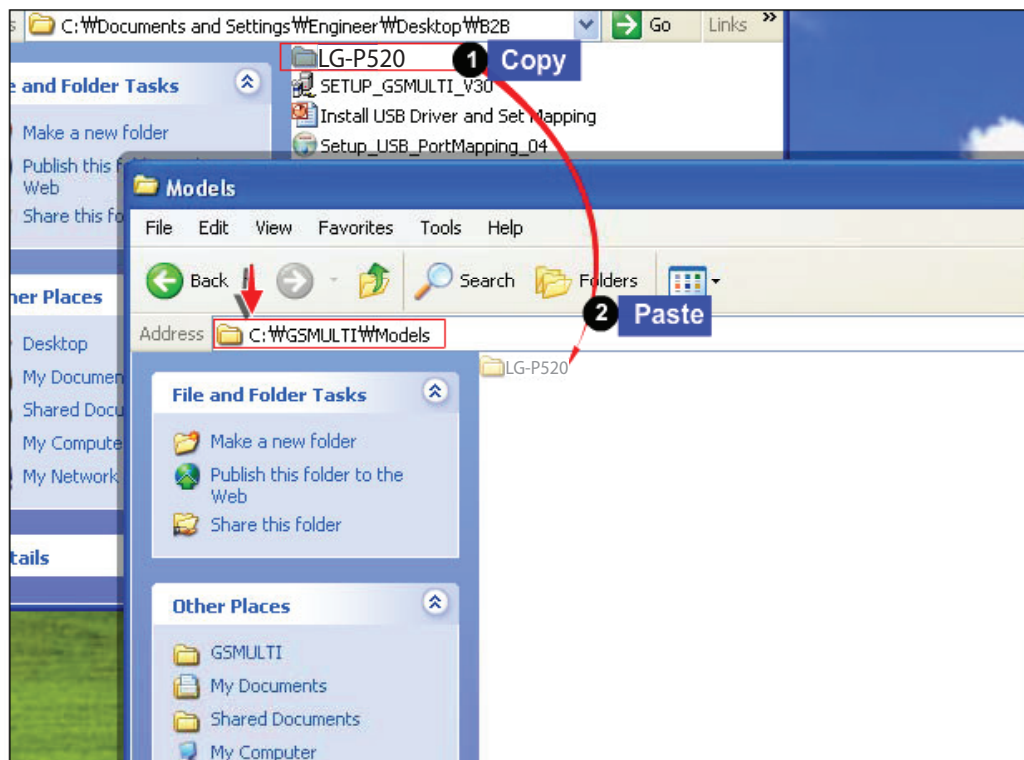
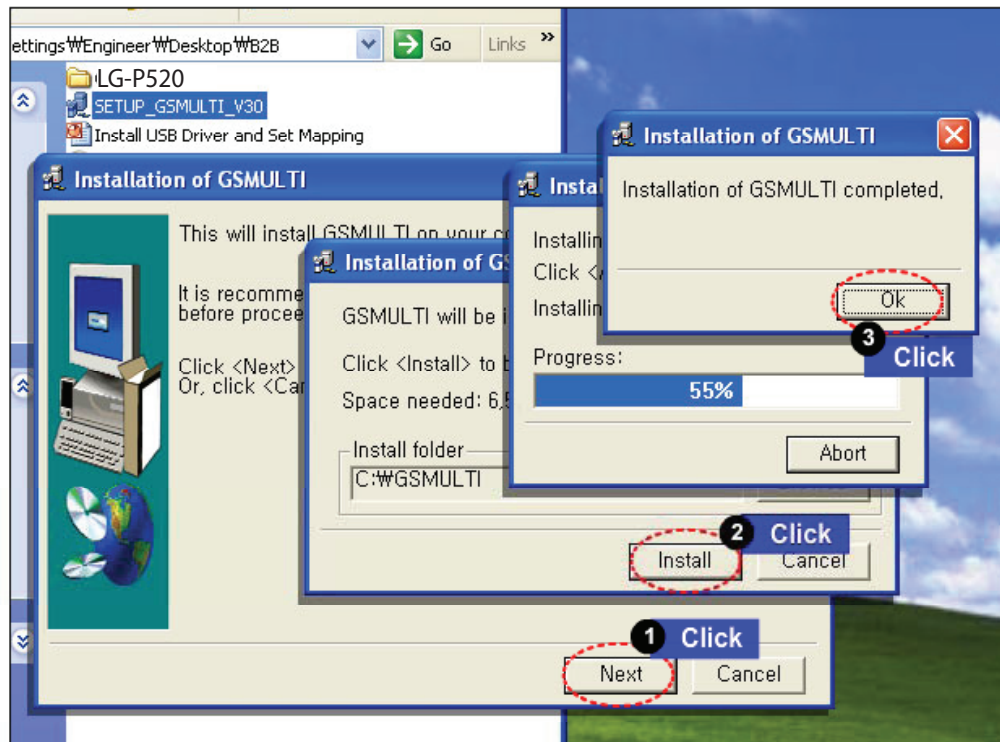
5. DOWNLOAD



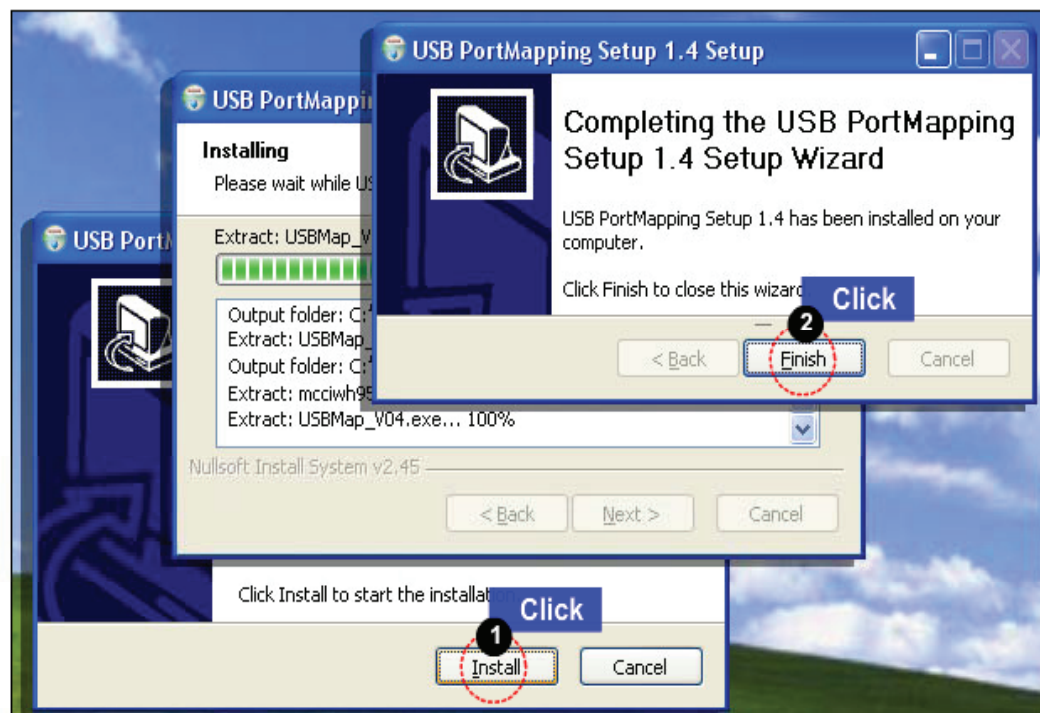
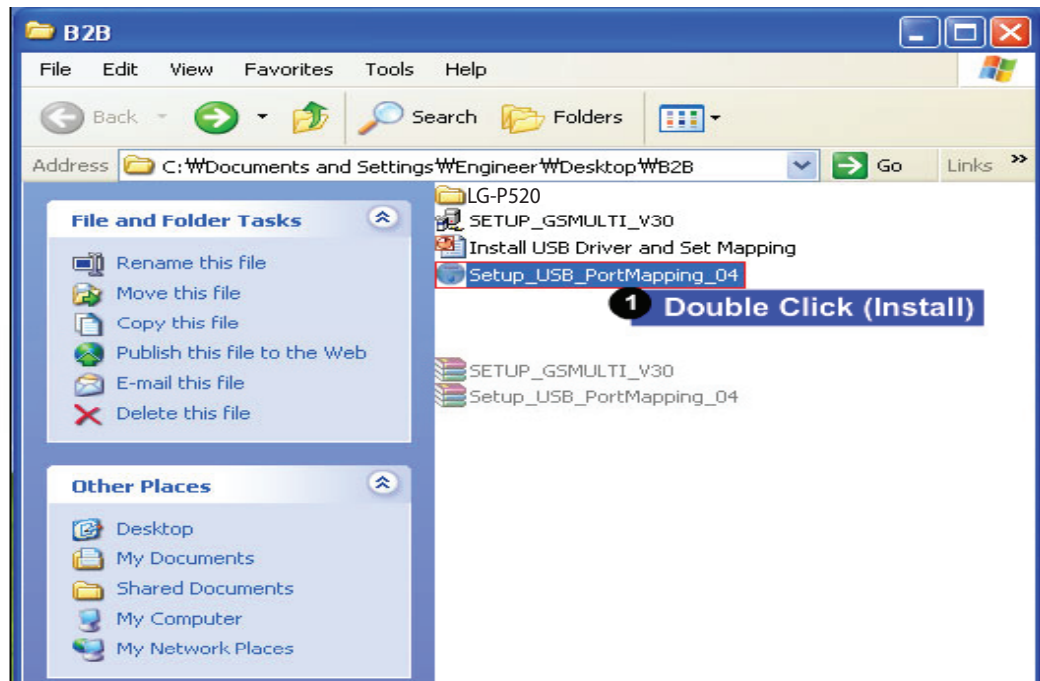
5. DOWNLOAD



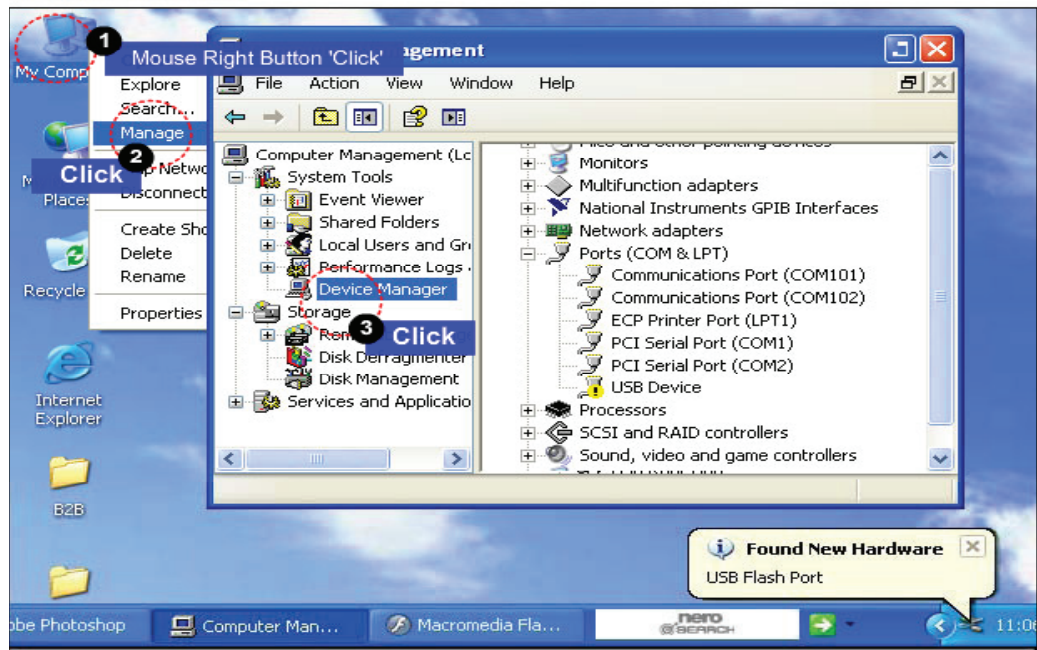
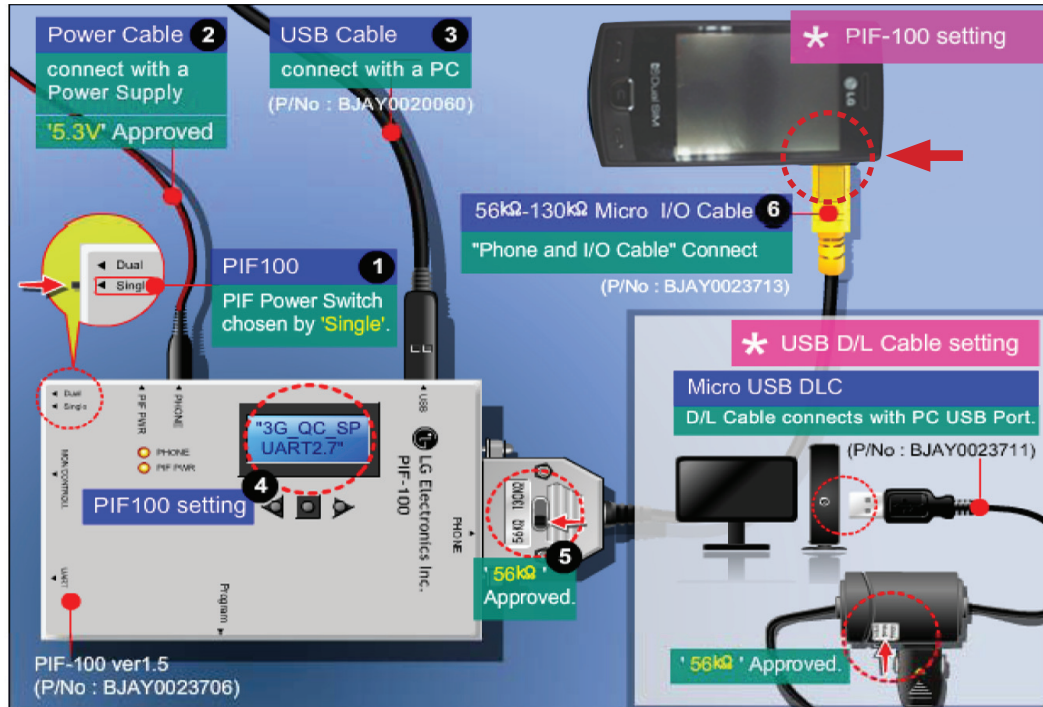
5. DOWNLOAD

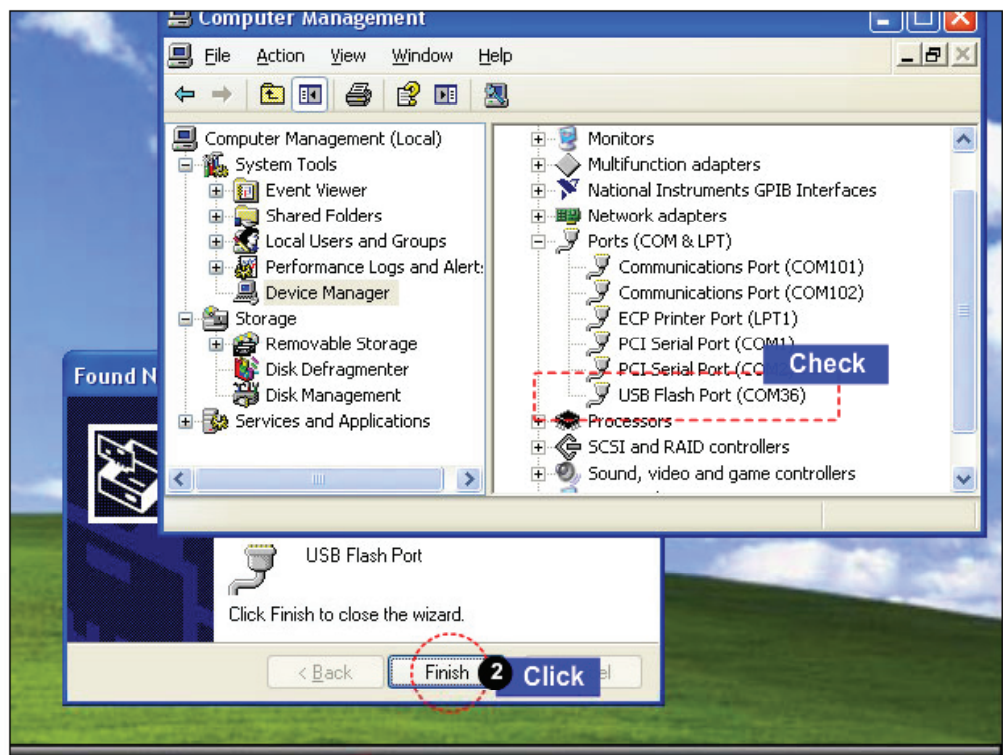
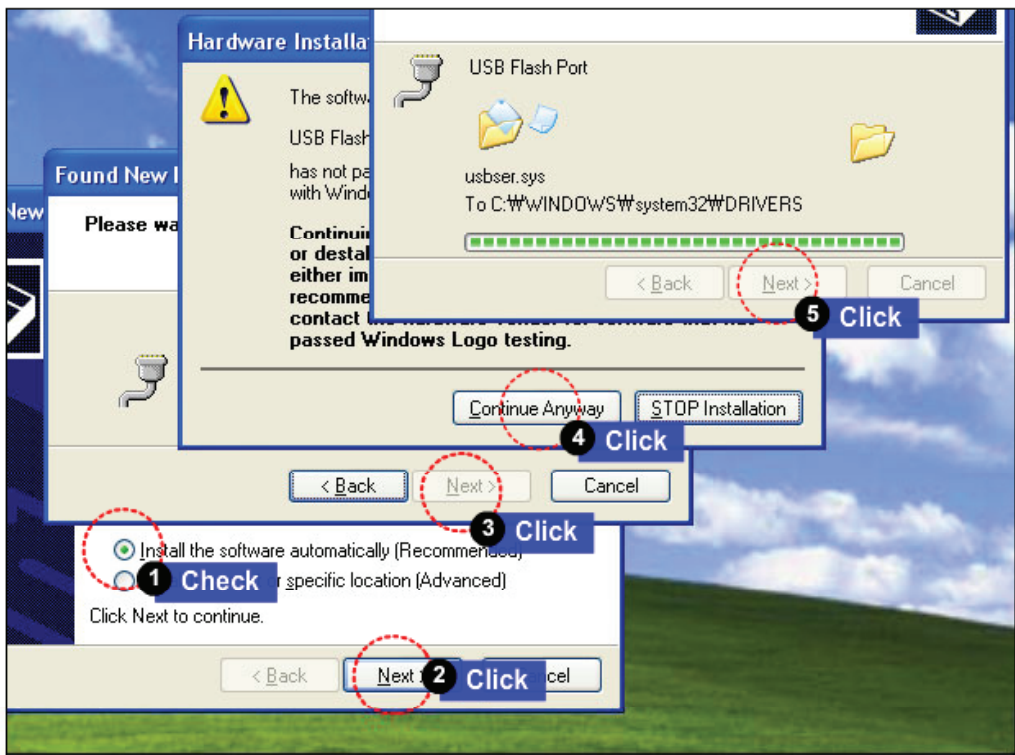


5. DOWNLOAD

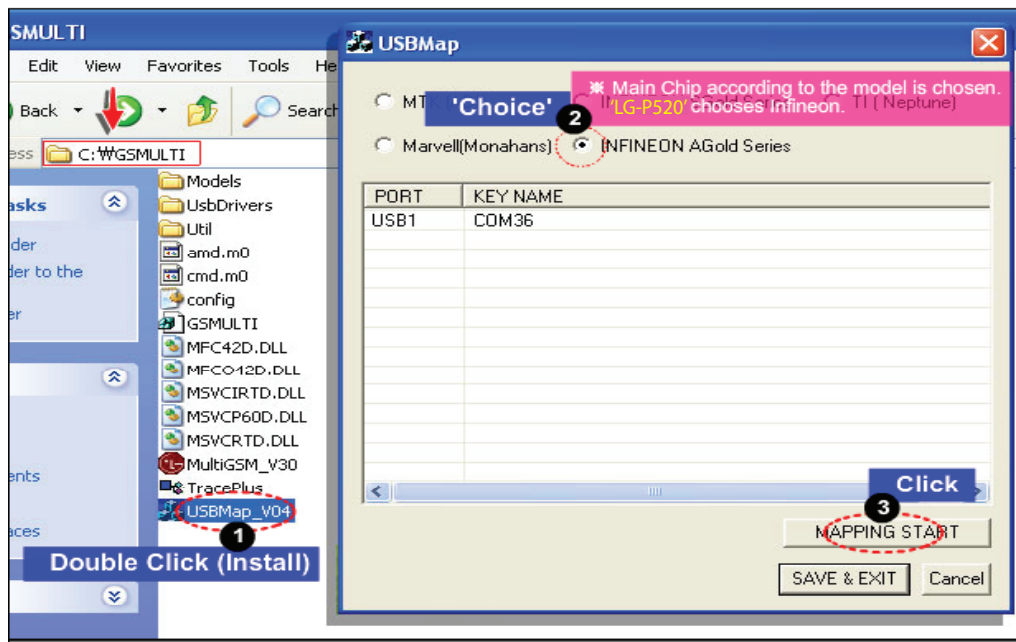


5. DOWNLOAD

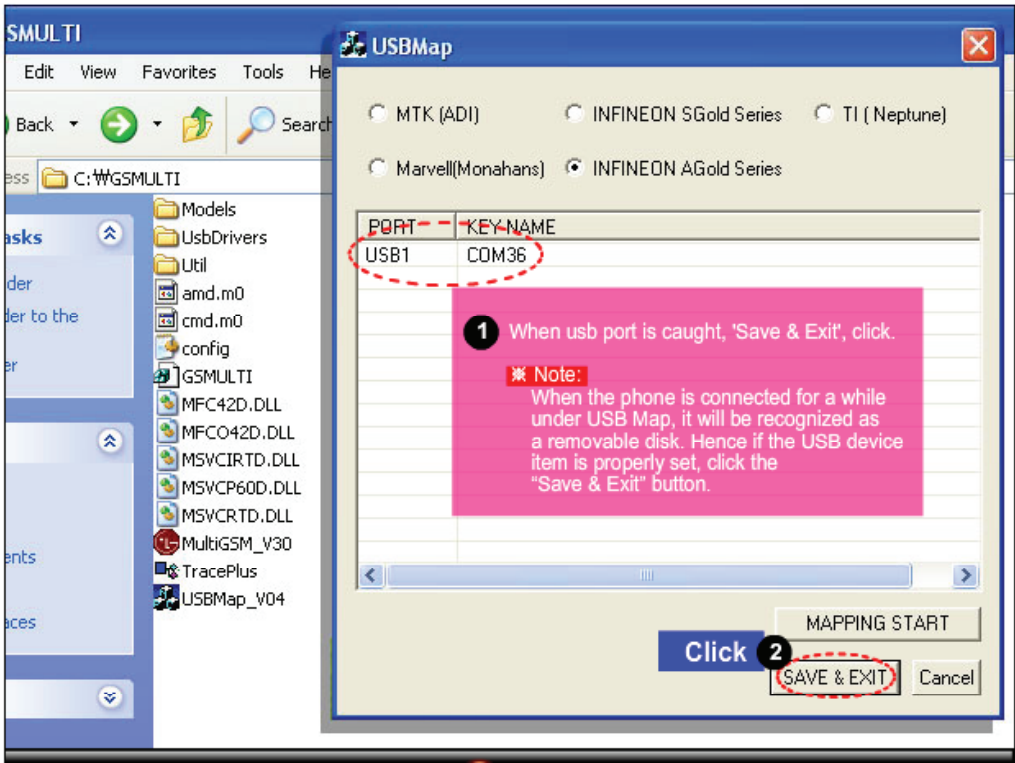




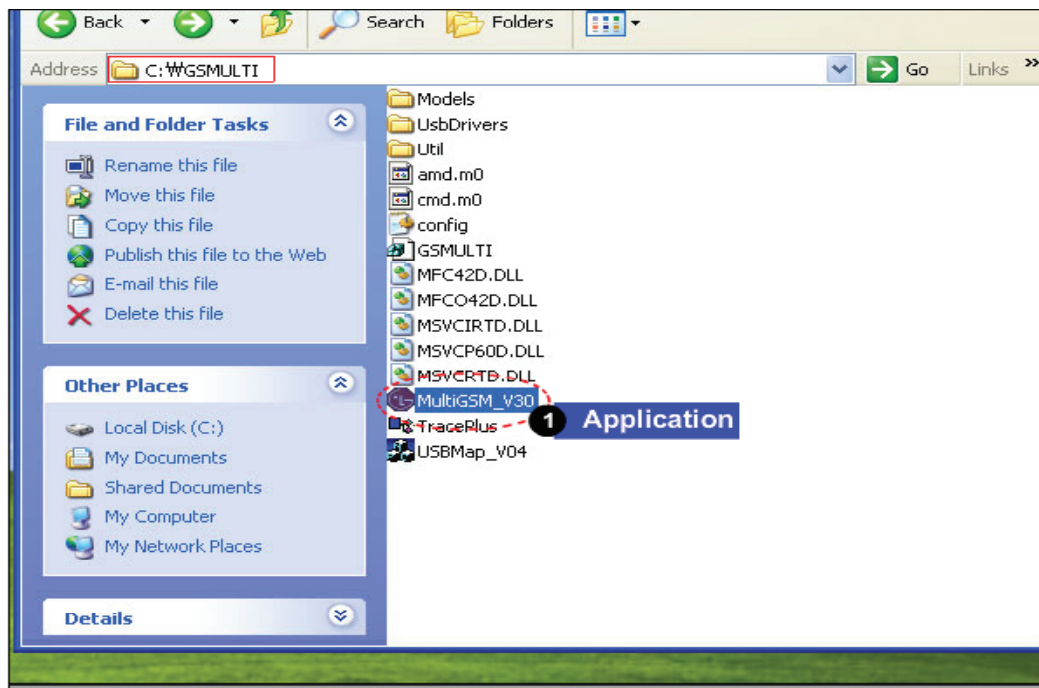
5. DOWNLOAD



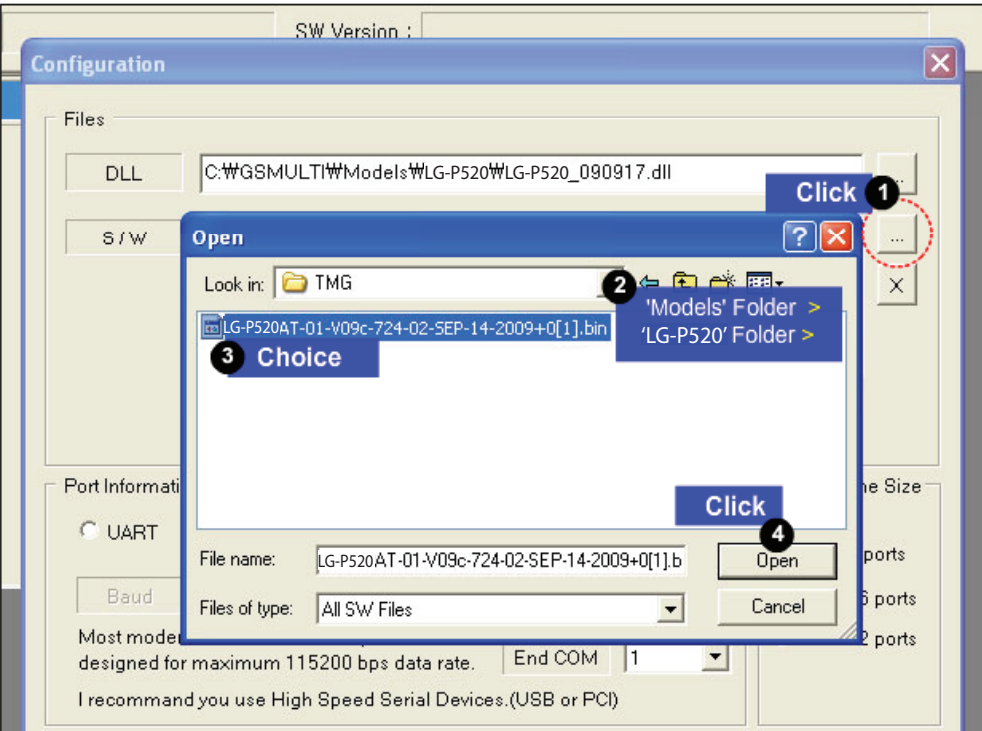
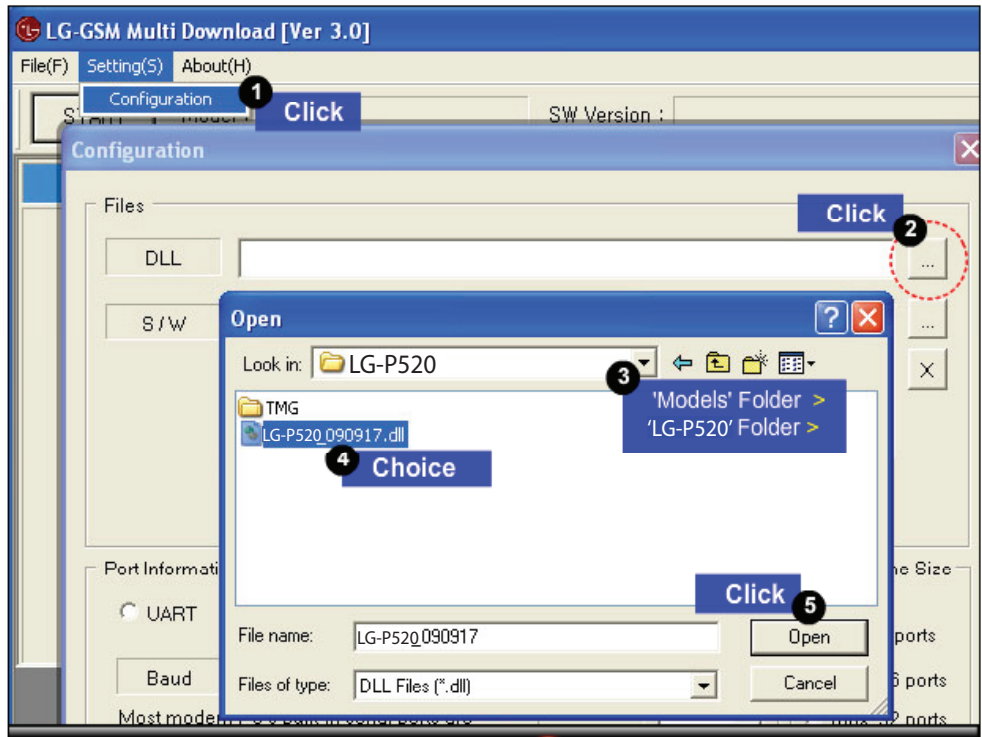
5. DOWNLOAD



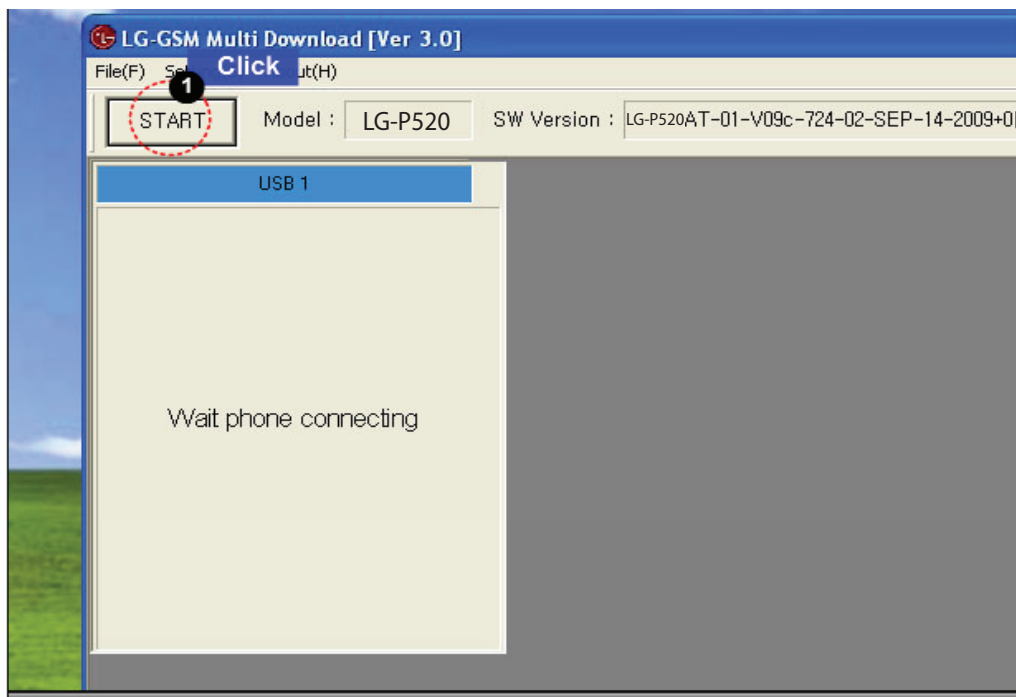
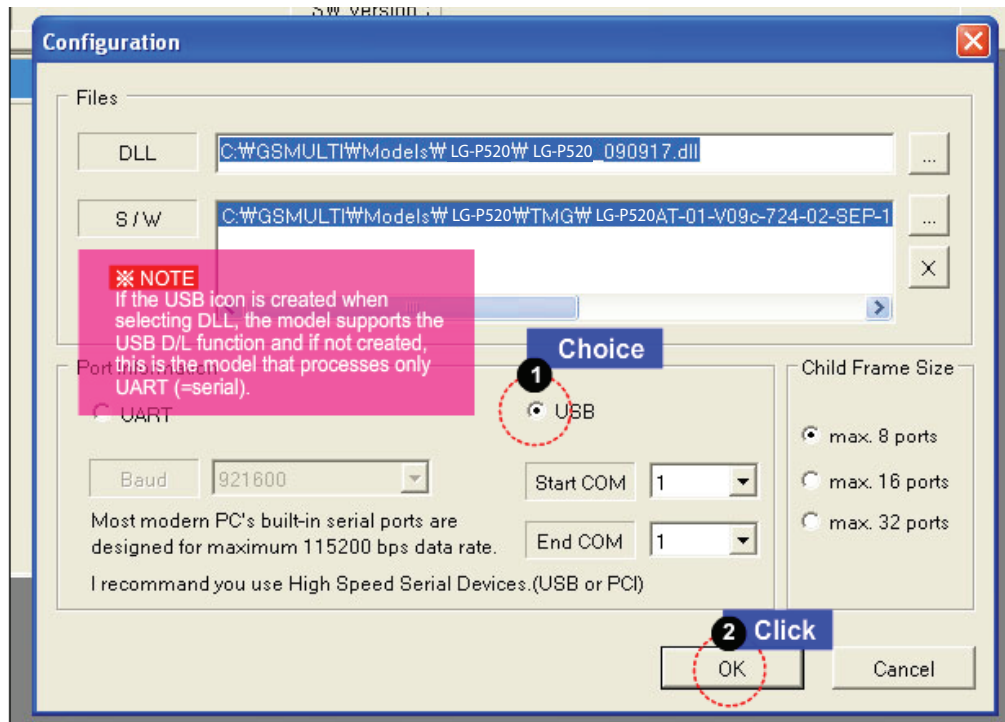
5. DOWNLOAD



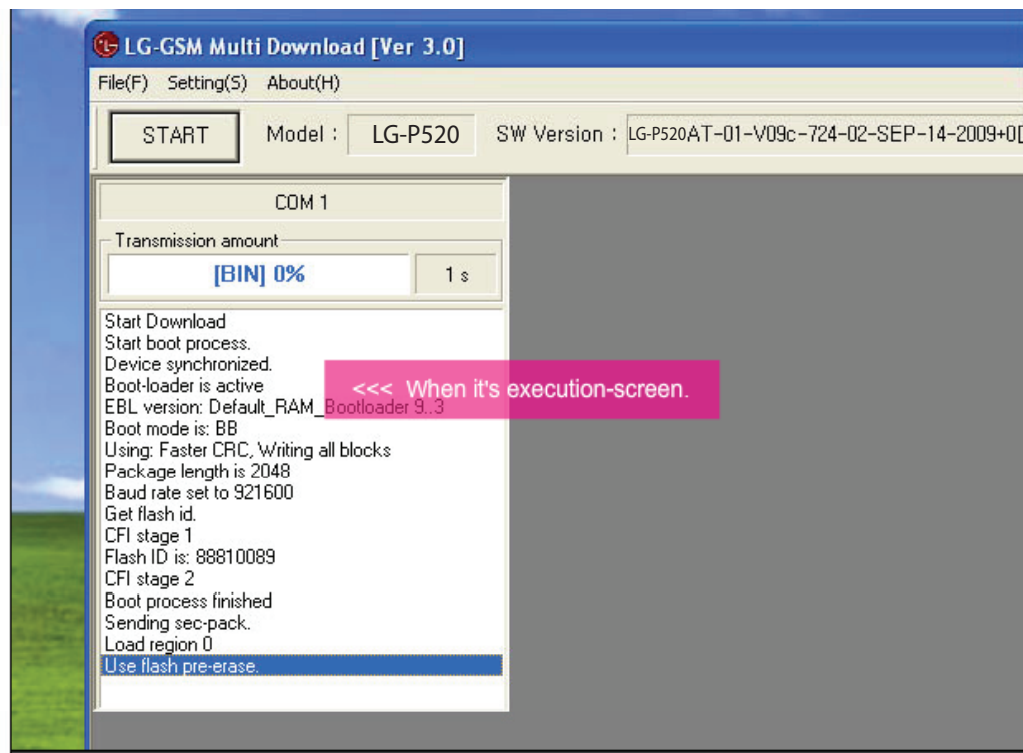
5. DOWNLOAD



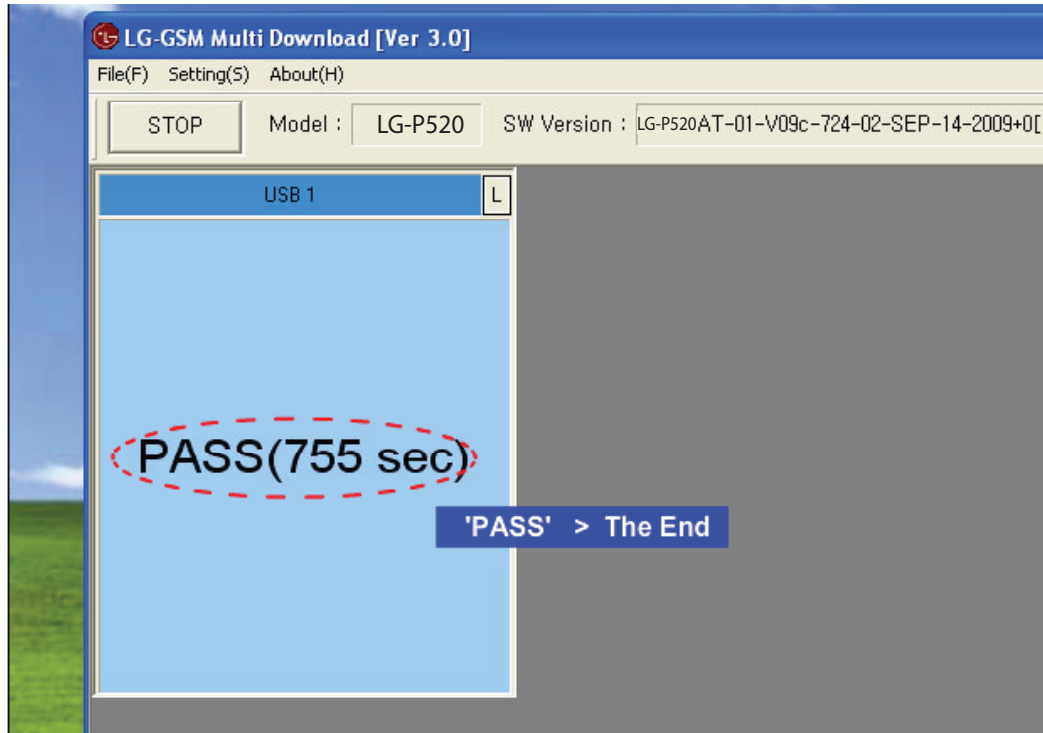
5. DOWNLOAD

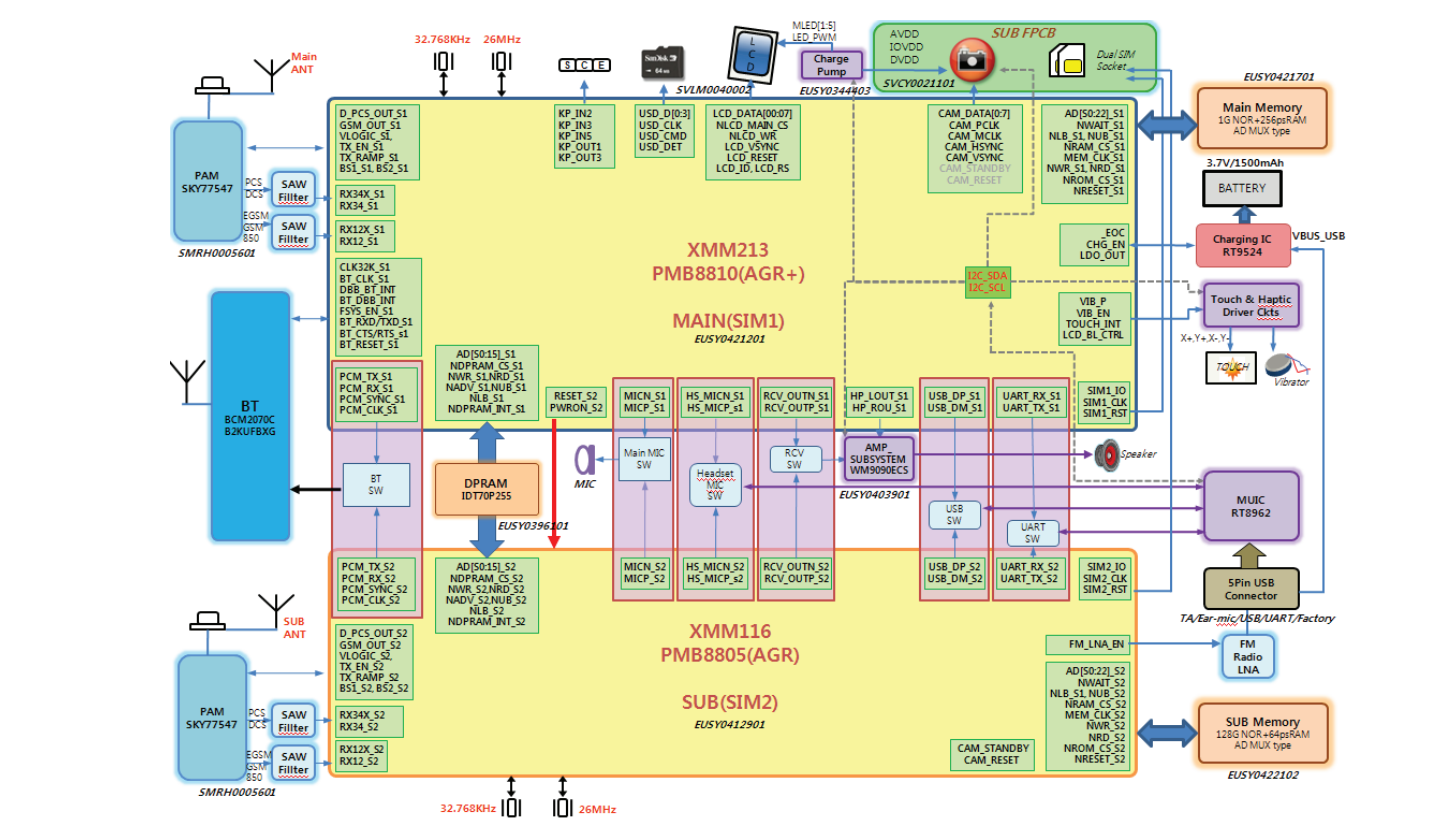


5. DOWNLOAD



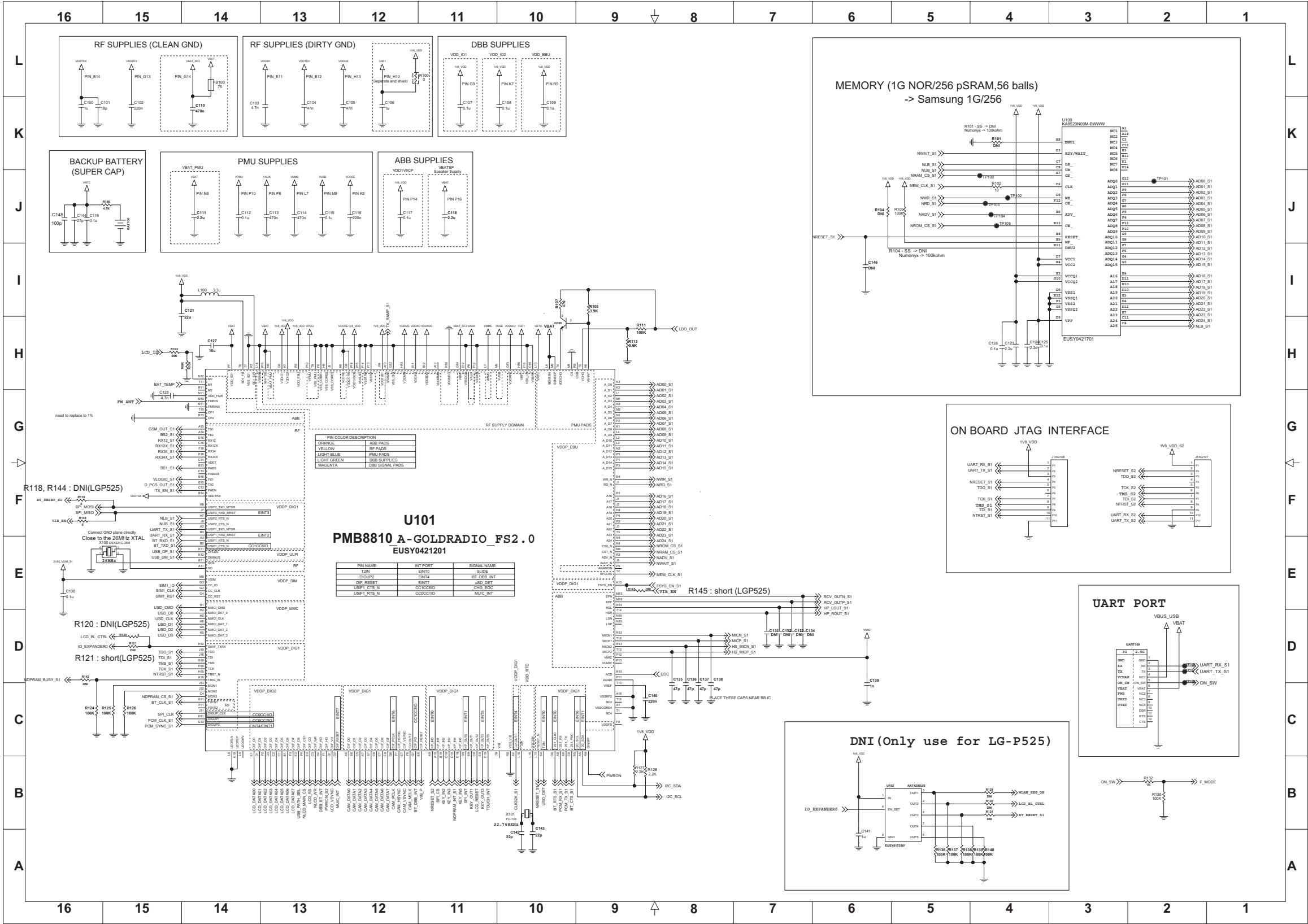
5. DOWNLOAD



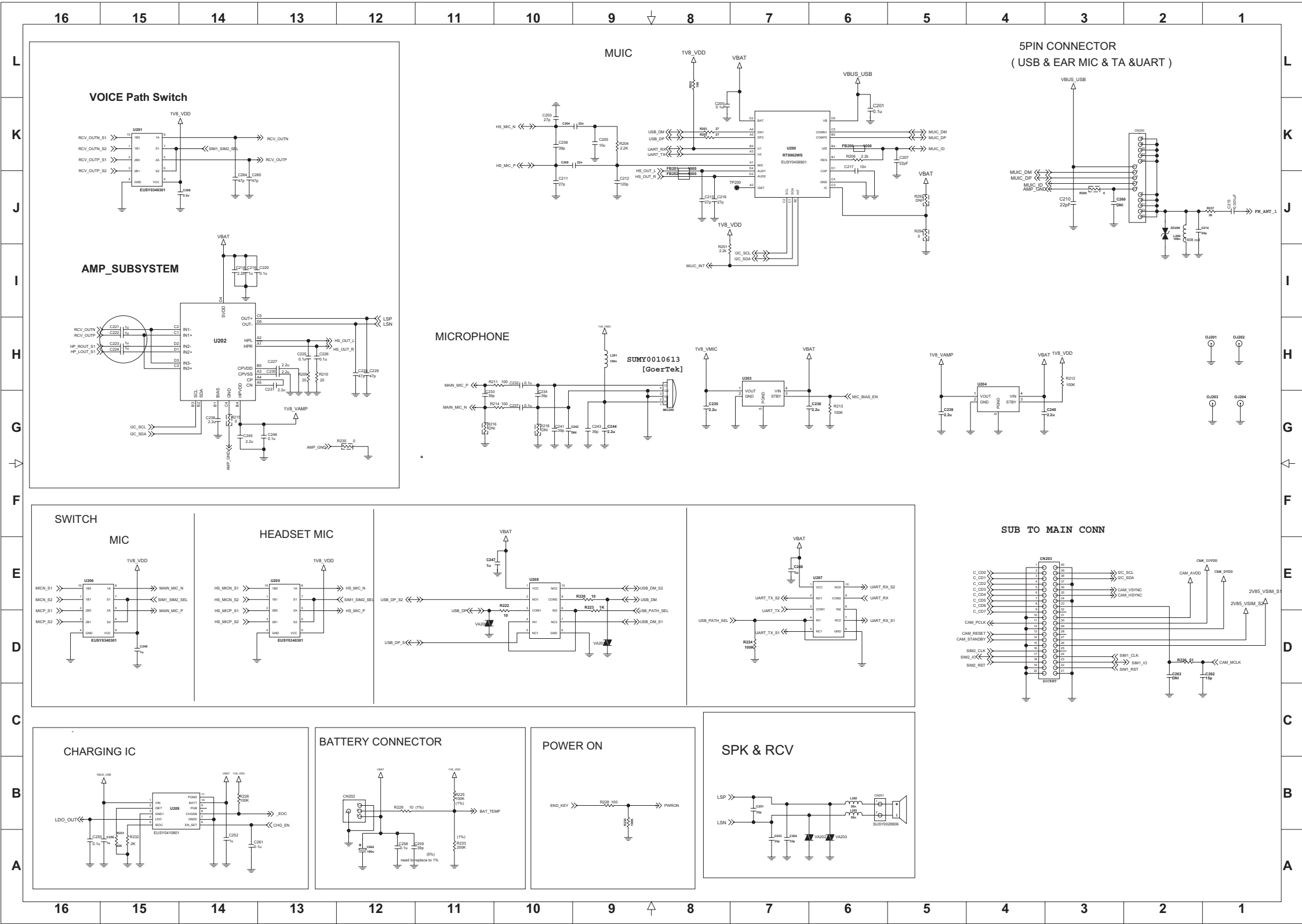




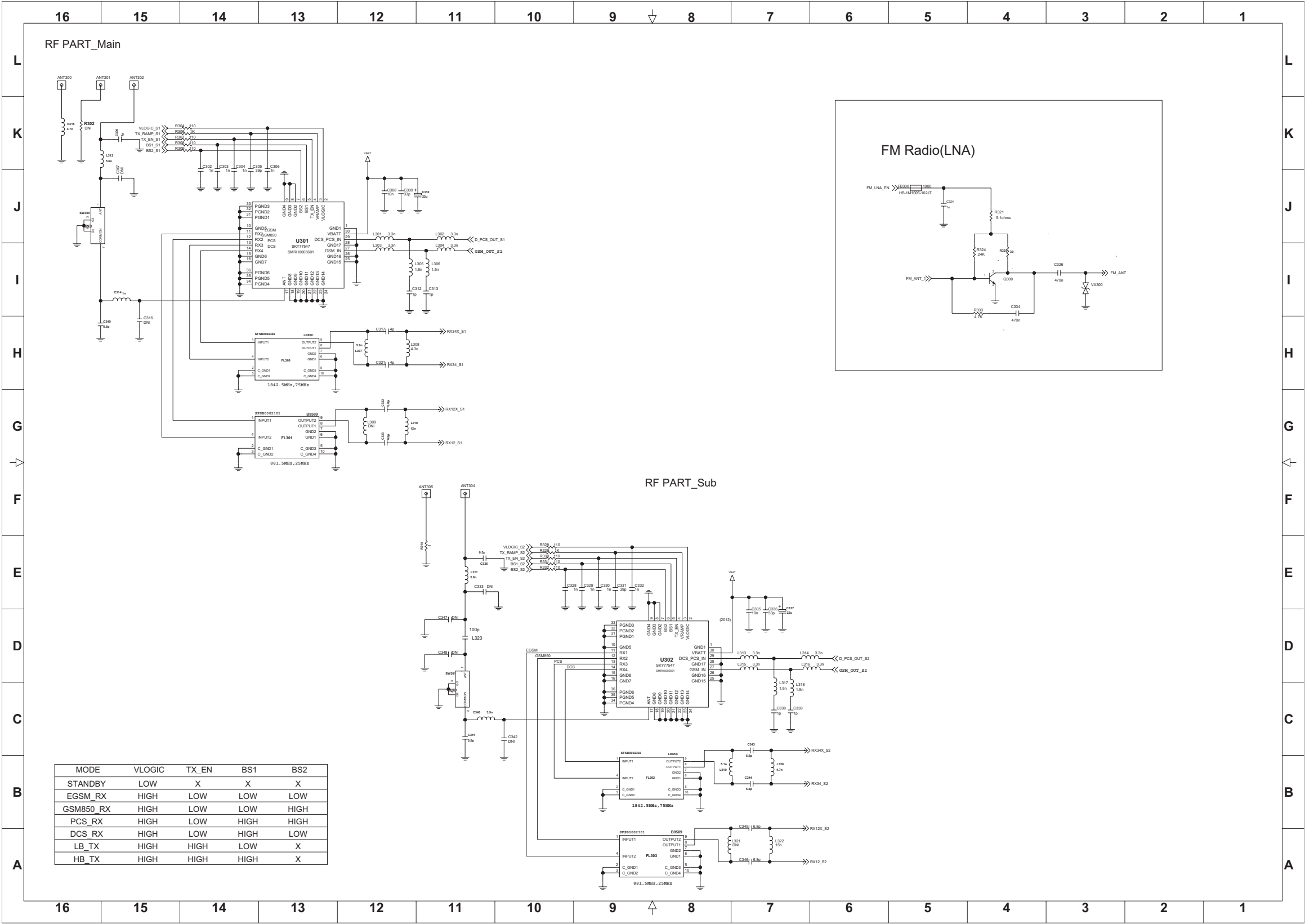
7. CIRCUIT DIAGRAM



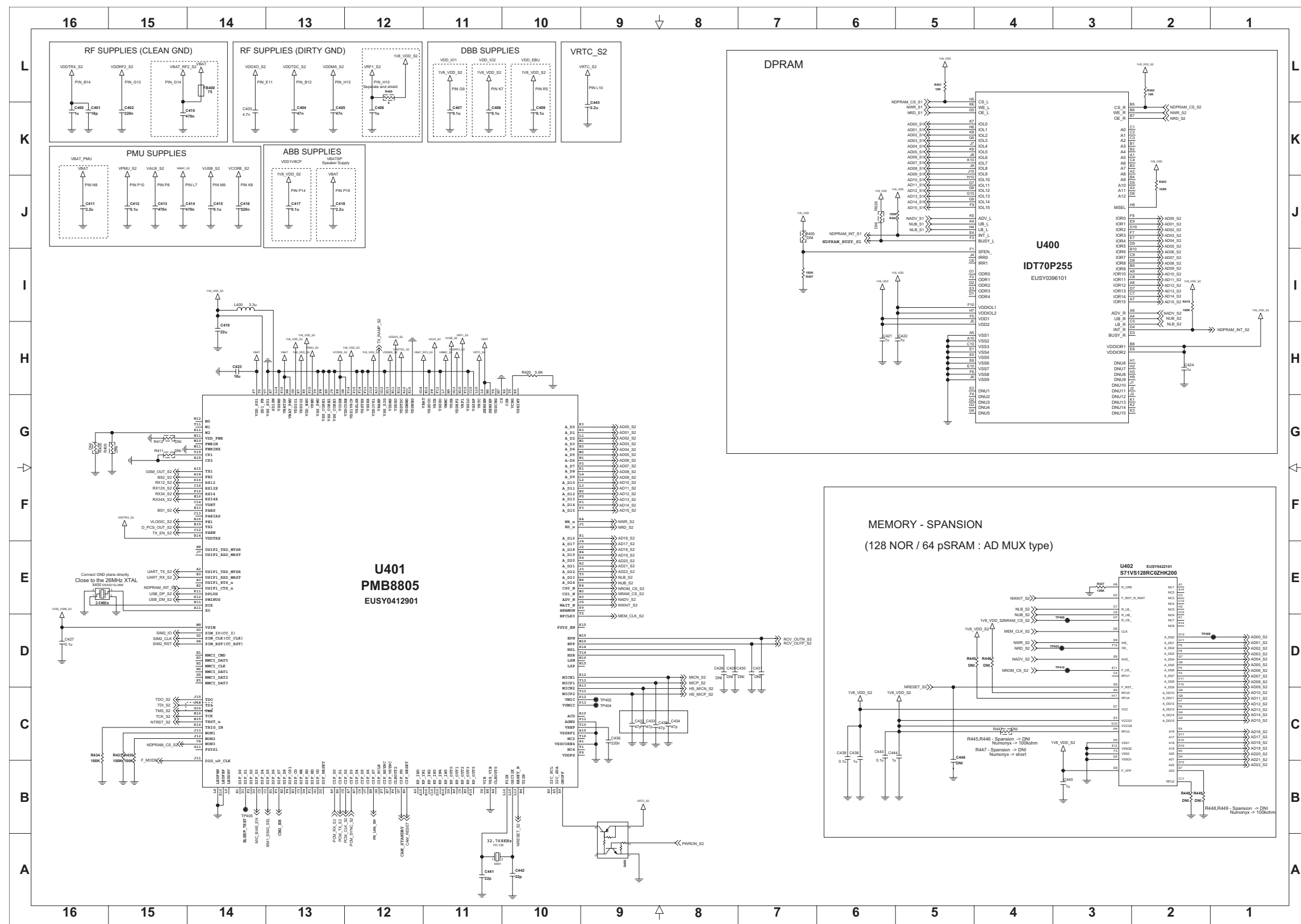
7. CIRCUIT DIAGRAM



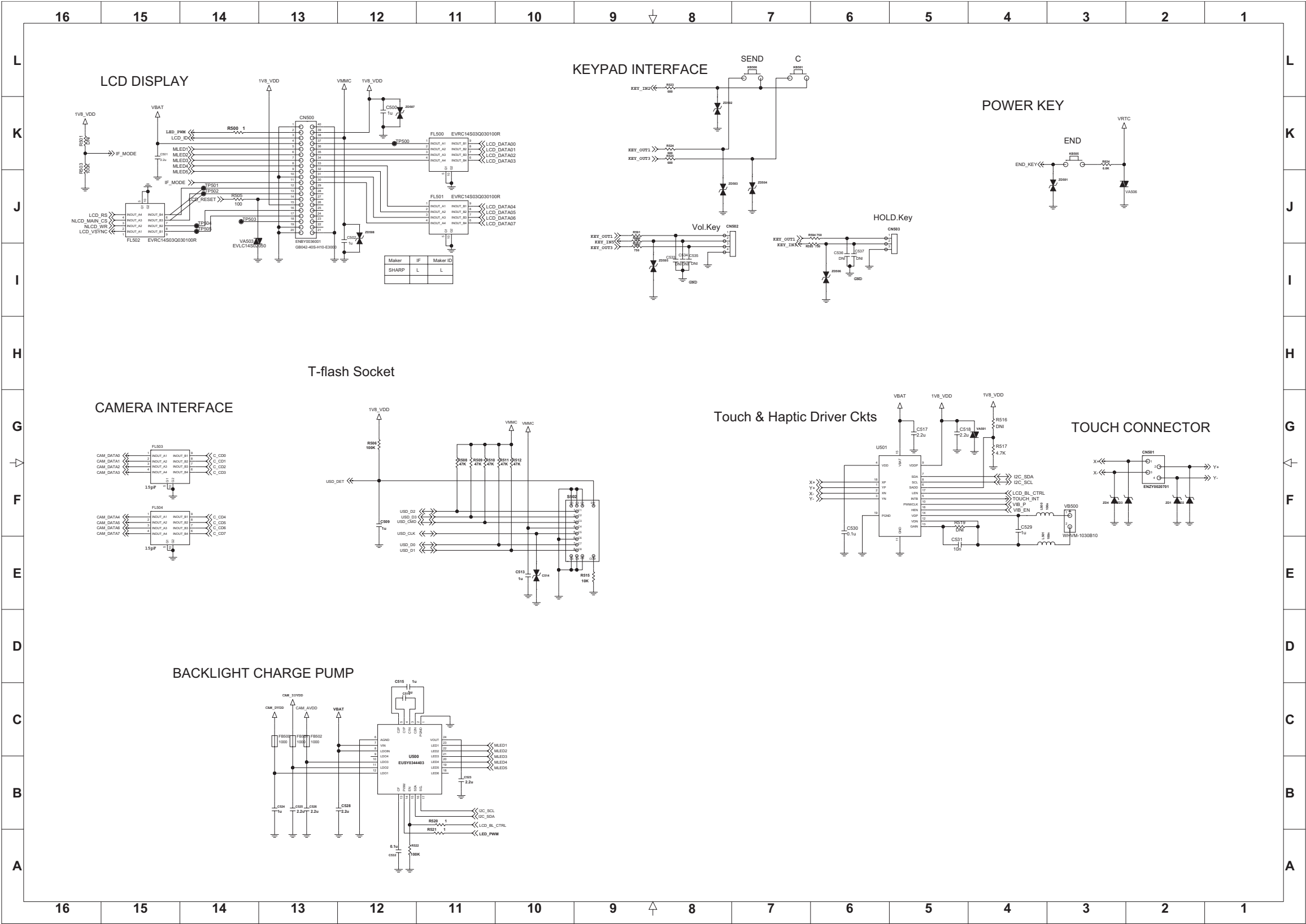
7. CIRCUIT DIAGRAM



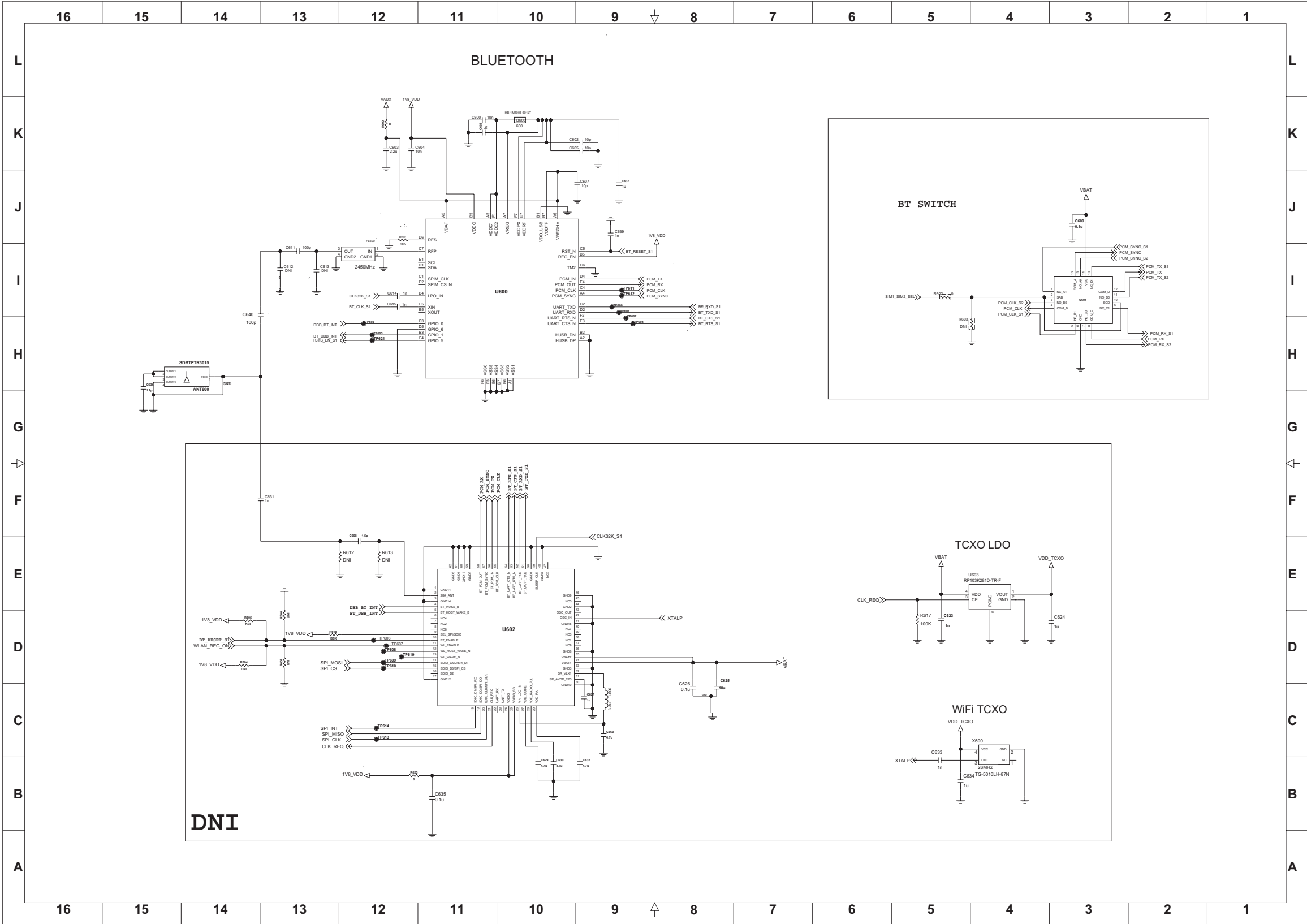
7. CIRCUIT DIAGRAM



7. CIRCUIT DIAGRAM



7. CIRCUIT DIAGRAM



8. BGA PIN MAP

8.1 BGA IC pin check (U101) - SIM 1

▪ Ball Diagram (Top View), PMB8810(A-GOLDRADIO+)

SIM 1

	A	B	C	D	E	F	G	H	J	K	L	M	N	P	R	T		
16	VSSRF2	FE1	RX12X	RX12	RX34X	RX34	TMS	TCK	TDI	TRIG_IN	F32K	EPP		VBATSP	VDDNEG		16	
15	TX1	TX2	VSSRF			VSSLO		TRST_n	TDO	FSYS_EN	OSC32K	EPN		VSSLSR	CP2	CP1	15	
14	FE2	VDDTRX				VSSTRX	VBAT				VSSMS			VDD1V8CP	HSL	HSR	14	
13	VRAMP	PABS				VSSRX	VDDRF2	VDDMS	MON1		RESET_N			VUMIC	MICN2	MICP2	13	
12		VDDTDC	PAEN		VSSDCO	VSSXO	VSSDIG	SWIF_TXRX	MON2	DMINUS				M0	VMIC	MICN1	MICP1	12
11	XO	XOX			VDDXO		FSYS1	DIGuP1	DIGuP_CLK	DPLUS		FMRINX	VDD_FMR	AGND	M2	M1	11	
10	KP_IN1	KP_IN2	KP_IN3	KP_IN4	KP_IN5	KP_OUT5	DIGuP2	VRF1	VDD1V81	LEDFBP	VRTC	FMRIN		VPMU	ACD	VREF	10	
9	KP_IN0	KP_OUT1	KP_OUT2	KP_OUT0	KP_OUT3		VDDIO1	VSSCORE2	VSSCORE3			VUSB			ONOFF	VSS_PMU	9	
8	I2S1_RX	I2S1_TX	I2S1_WA0	I2S1_CLK0	CIF_D7	VSSCORE1	VDDCORE	USIF2_TXD_MTSR	USIF2_CTS_n	VCORE	LEDfBN	VSIM	VBAT_PMU	VAUX	VSS_VIB	VIB	8	
7	CIF_D3	CIF_D4	CIF_D6		CIF_VSYNC	CIF_HSYNC	CIF_PD	USIF2_RTS_n	USIF2_RXD_MRST	VDDIO2	VMMC	CS		VDD_SD1	SD1SW	VSS_SD1	7	
6	CIF_D0	CIF_D1	CIF_D5		CIF_RESET	CLKOUT2	CIF_PCLK	MMCL_DAT1	WAIT_n	VSHNT	SENSEN	SENSEP				SD1_FB	6	
5	I2C_SDA	I2C_SCL	CIF_D2				MMCL_DAT2			MMCL_DAT3				A/D13	VDD_EBU	VCHG	5	
4	CLKOUT0	T2IN	MON3	DIF_RD		DIF_CS1	CC_RST	A19	A17	CS0_n	A/D9		A24	A20	WR_n	VDDCHG	4	
3	USIF1_RTS_n	USIF1_RXD_MRST	DIF_WR	DIF_D3	DIF_CD	DIF_D7	CC_IO	MMCL_DAT0	A22	A/D0	A/D11	CS1_n	A/D4	A/D15	ADV_n	A23	3	
2	USIF1_TXD_MTSR	USIF1_CTS_n	DIF_D4	DIF_RESET	DIF_D8	DIF_D2	CC_CLK	MMCL_CLK	A18	A/D1	A/D10	A/D5	A/D12	A/D7	A21	BFCLK0	2	
1	VSSCORE4	DIF_D6	DIF_D5	DIF_D1	DIF_D0	DIF_HD	DIF_VD	MMCL_CMD	RD_n	A/D8	A/D2	A/D3	A/D6	A/D14	A16		1	
	A	B	C	D	E	F	G	H	J	K	L	M	N	P	R	T		

 : not in use

8. BGA PIN MAP

8.2 BGA IC pin check (U401) - SIM 2

▪ Ball Diagram (Top View), PMB8810(A-GOLDRADIO+)

SIM 2

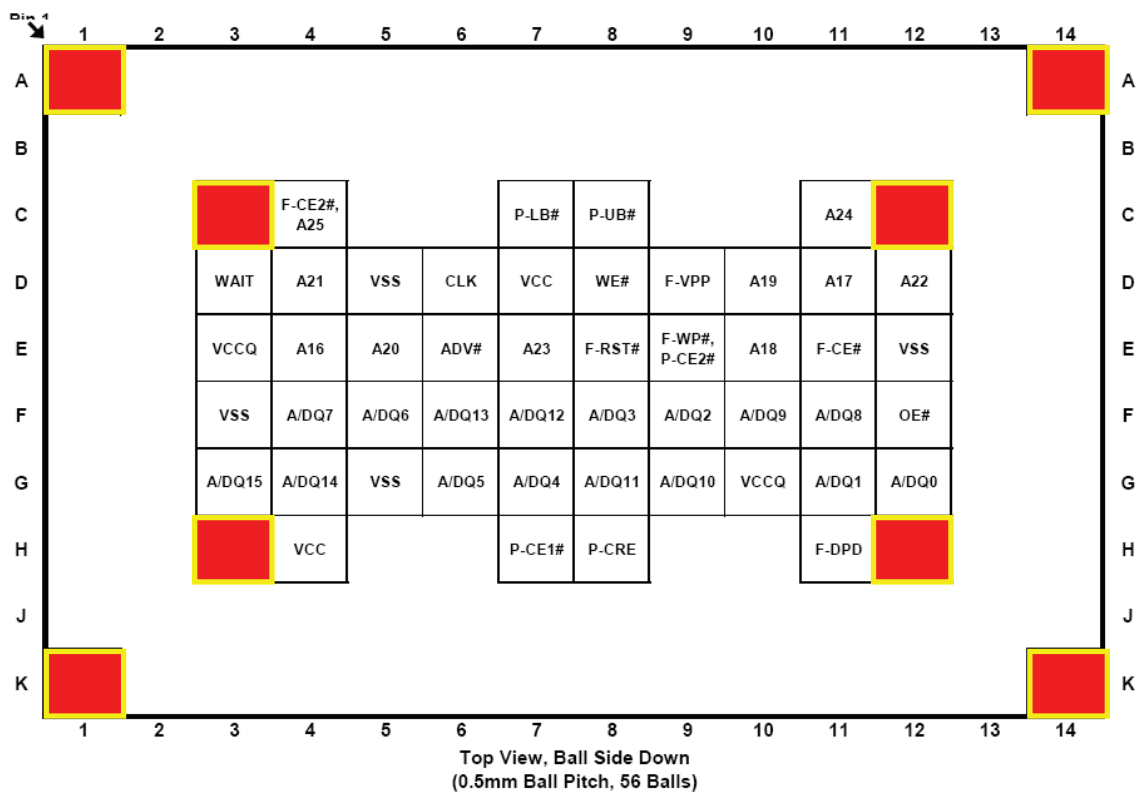
	A	B	C	D	E	F	G	H	J	K	L	M	N	P	R	T	
16	VSSRF2	FE1	RX12X	RX12	RX34X	RX34	TMS	TCK	TDI	TRIG_IN	F32K	EPP		VBATSP	VDDNEG		16
15	TX1	TX2	VSSRF			VSSLO		TRST_n	TDO		OSC32K	EPN		VSSLSR	CP2	CP1	15
14	FE2	VDDTRX				VSSTRX	VBAT				VSSMS			VDD1V8CP	HSL	HSR	14
13	VRAMP	PABS				VSSRX	VDDRF2	VDDMS	MON1		RESET_N			VUMIC	MICN2	MICP2	13
12		VDDTDC	PAEN		VSSDCO	VSSXO	VSSDIG		MON2	DMNLS				VMIC	MICN1	MICP1	12
11	XQ	XGX			VDDXO					DPLUS		FMRINX	VDD_FMR	AGND	M2	M1	11
10								VR1	VDD1V81	LED1BP	VRTC			VPMU		VREF	10
9							VDDQ1	VSSCORE2	VSSCORE3			VUSB			ONOFF	VSS_PMU	9
8	I2S1_RX	I2S1_TX	I2S1_WA0	I2S1_CLK0	CIF_D7	VSSCORE1	VDDCORE			VCORE	LED1BN	VSIM	VBAT_PMU	VAUX	VSS_VIB		8
7							CIF_PD			VDDQ2	VMMC	CS		VDD_SD1	SD1SW	VSS_SD1	7
6								MMCL_DAT1	WAIT_n		SENSEN	SENSEP				SD1_FB	6
5							MMCL_DAT2			MMCL_DAT3				A/D13	VDD_EBU	VCHG	5
4			MON3				CC_RST	A19	A17	CS0_n	A/D9		A24	A20	WR_n		4
3		USIF1_RXD_MSTR		DIF_D3		DIF_D7	CC_I0		A22	A/D0	A/D11	CS1_n	A/D4	A/D15	ADV_n	A23	3
2	USIF1_TXD_MTSR	USIF1_CTS_n					CC_CLK		A18	A/D1	A/D10	A/D5	A/D12	A/D7	A21	BFCLKO	2
1	VSSCORE4		DIF_D5	DIF_D1					RD_n	A/D8	A/D2	A/D3	A/D6	A/D14	A16		1
	A	B	C	D	E	F	G	H	J	K	L	M	N	P	R	T	


 : not in use

8.3 BGA IC pin check (U100) - SIM 1

▪ Ball Diagram (Top View), KA8520N00M-BWWW

SIM 1



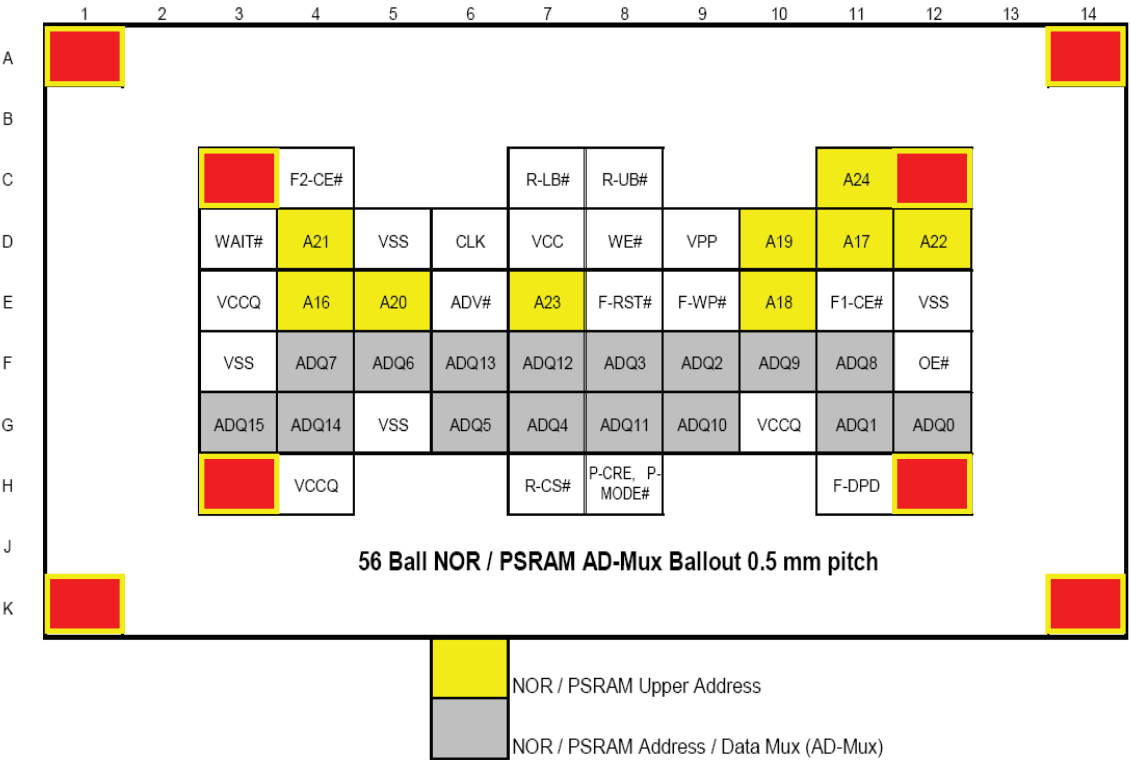
 : not in use

8. BGA PIN MAP

8.4 BGA IC pin check (U402) - SIM 2

▪ Ball Diagram (Top View), S71VS128RC0ZHK200

SIM 2



: not in use

8.5 BGA IC pin check (U400) – Dual Port SRAM

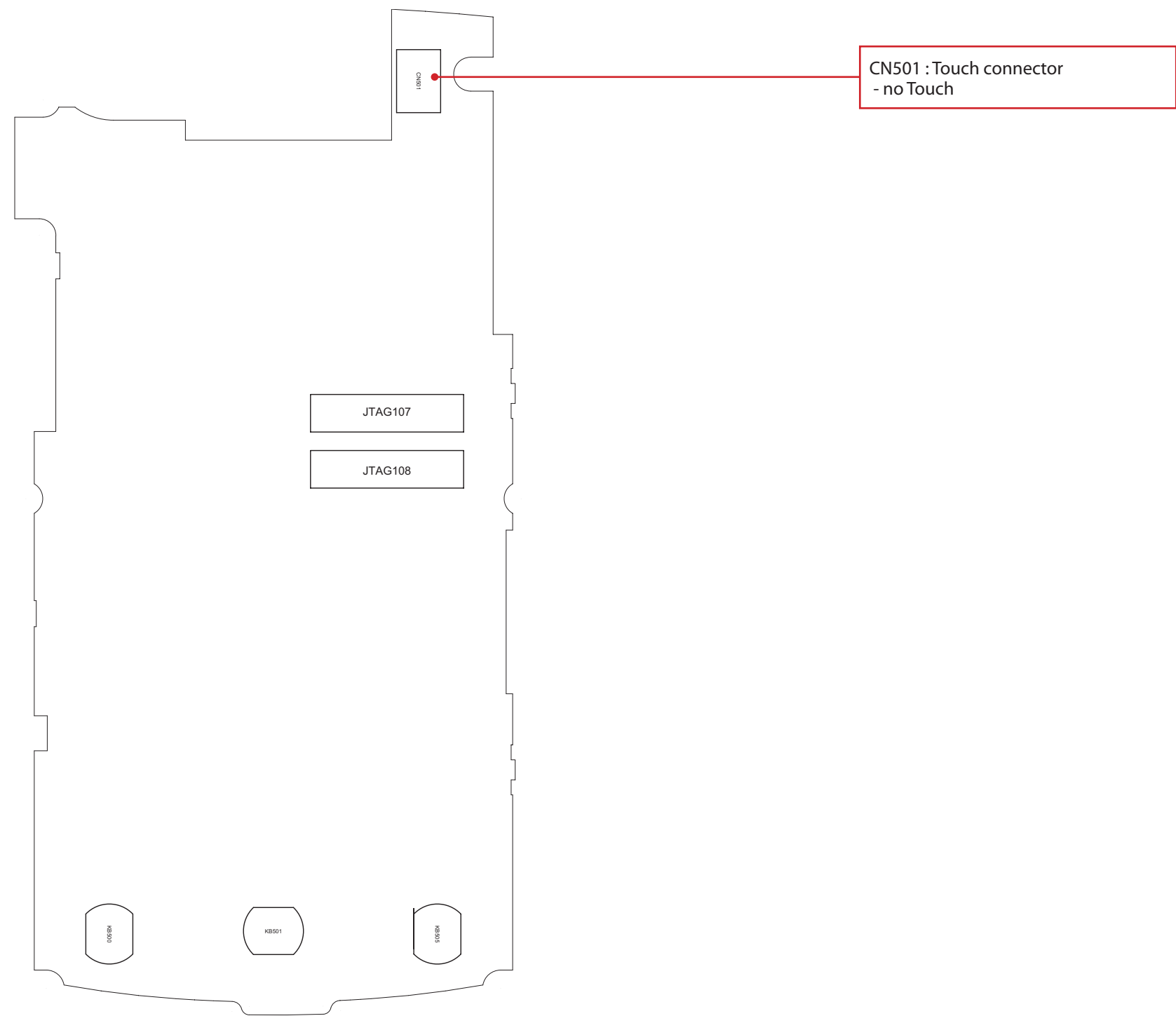
▪ Ball Diagram (Top View), IDT709255

DPRAM										
	1	2	3	4	5	6	7	8	9	10
A				UB#R	VSS	ADV#R	I/OR15	I/OR12	I/OR10	VSS
B					CE#R	WE#R	OE#R	VDDIOR	I/OR9	I/OR6
C					LB#R		I/OR14	I/OR11	I/OR7	VSS
D				INT#R			I/OR13	I/OR8	I/OR5	I/O2R
E	VSS			INT#L	VSS	VSS	I/OR4	VDDIOR	I/OR1	VSS
F	SFEN#				VCC	VSS	I/OR3	I/OR0	I/OL15	VDDIOL
G					OE#L	I/OL3	I/OL11	I/OL12	I/OL14	I/OL13
H				LB#L	CE#L	I/OL1	VDDIOL	MSEL		I/OL10
J					VCC	VSS	I/OL4	I/OL6	I/OL8	I/OL9
K				UB#L	ADV#L	WE#L	I/OL0	I/OL2	I/OL5	I/OL7
	1	2	3	4	5	6	7	8	9	10

 : not in use



9. PCB LAYOUT

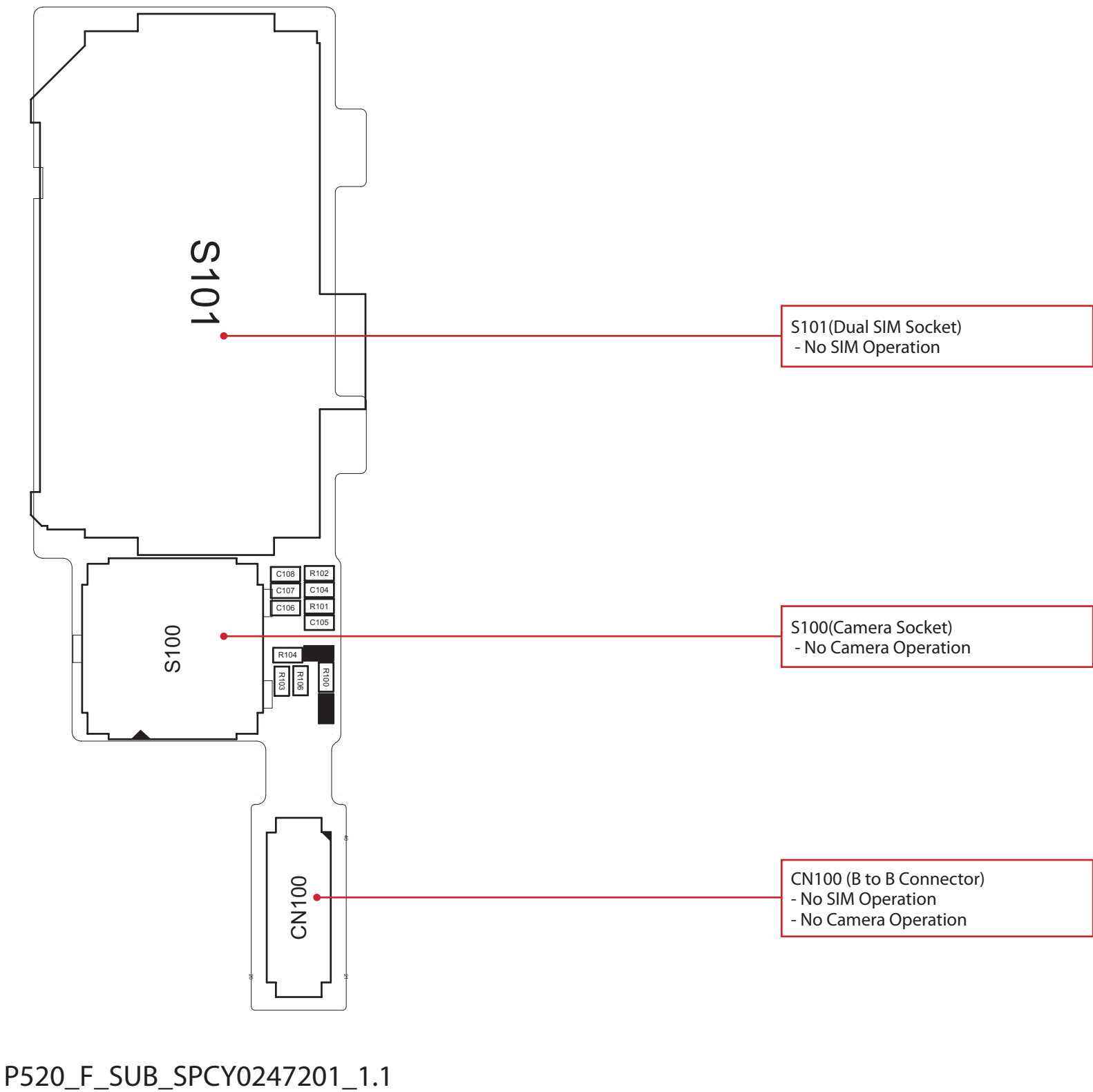


LG-P520_MAIN_SPFY0237101_1.1_TOP



LG-P520_MAIN_SPFY0237101_1.1_BOT

9. PCB LAYOUT



10. STAND ALONE TEST

10.1 Introduction

This manual explains how to examine the status of RX and TX of the model.

A. Tx Test

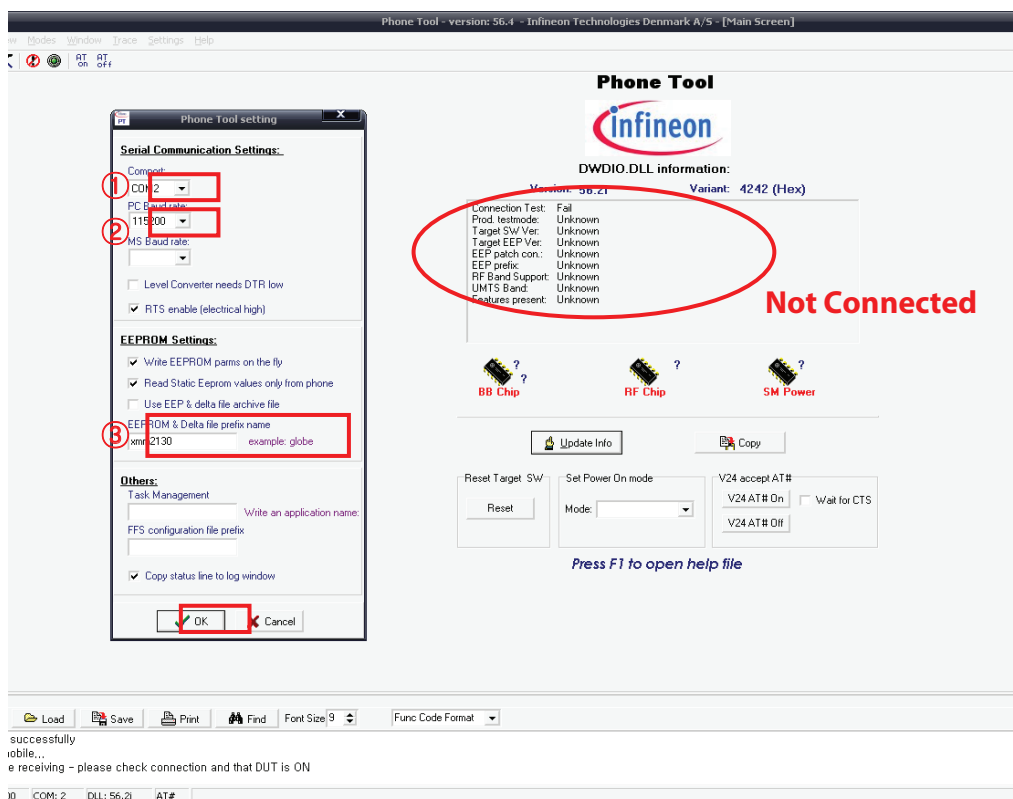
TX test - this is to see if the transmitter of the phones is activating normally.

B. Rx Test

RX test - this is to see if the receiver of the phones is activating normally.

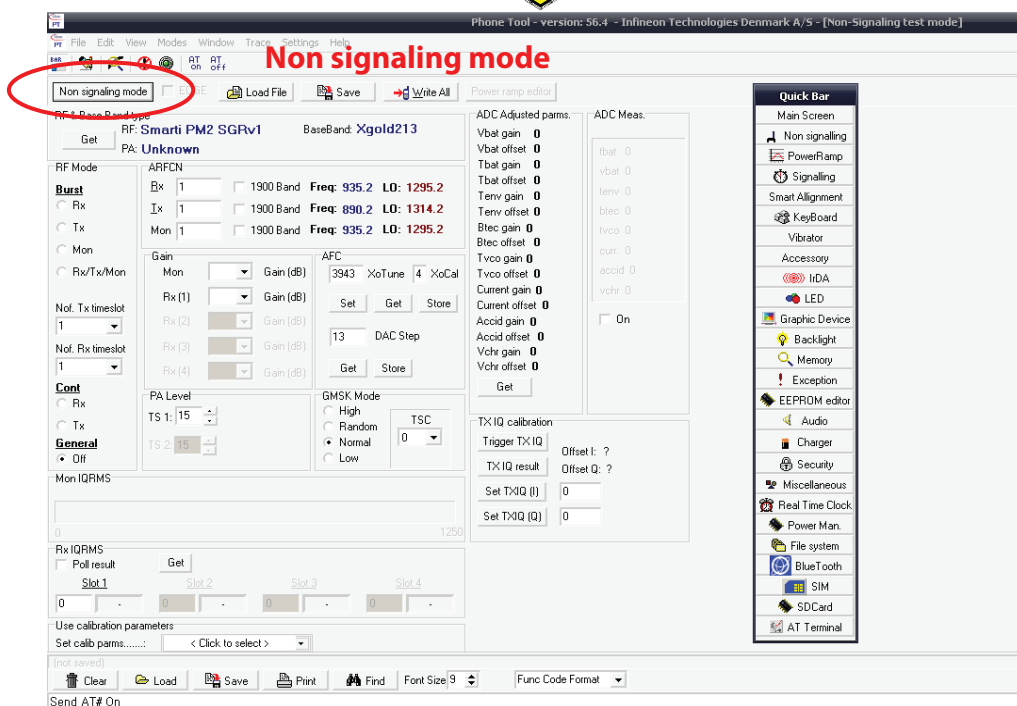
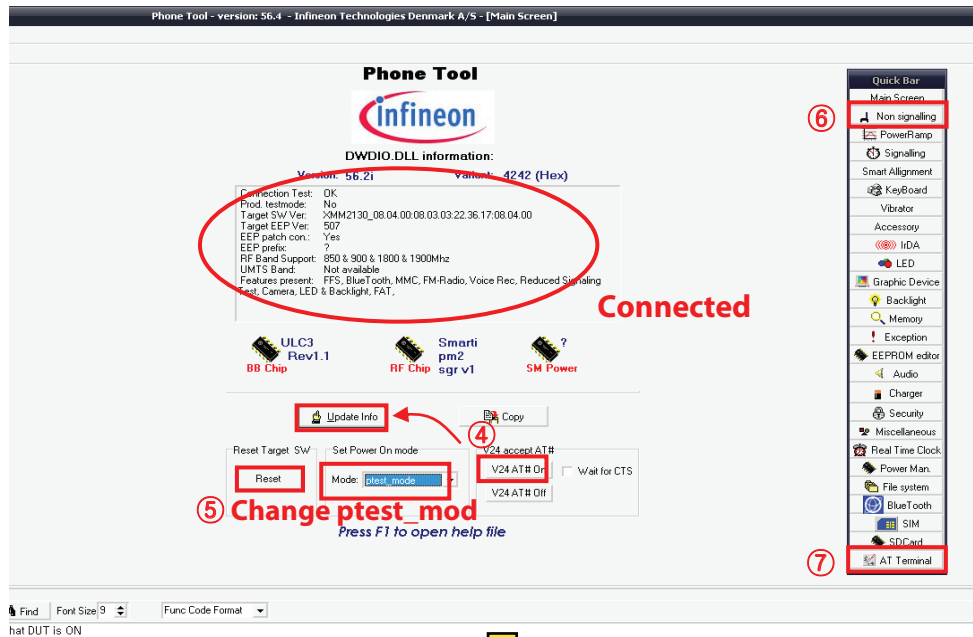
10.2 Setting Method

1. Set COM Port
2. Check PC Baud Rate
3. Confirm EEPROM & Delta file prefix name, and then click "OK".



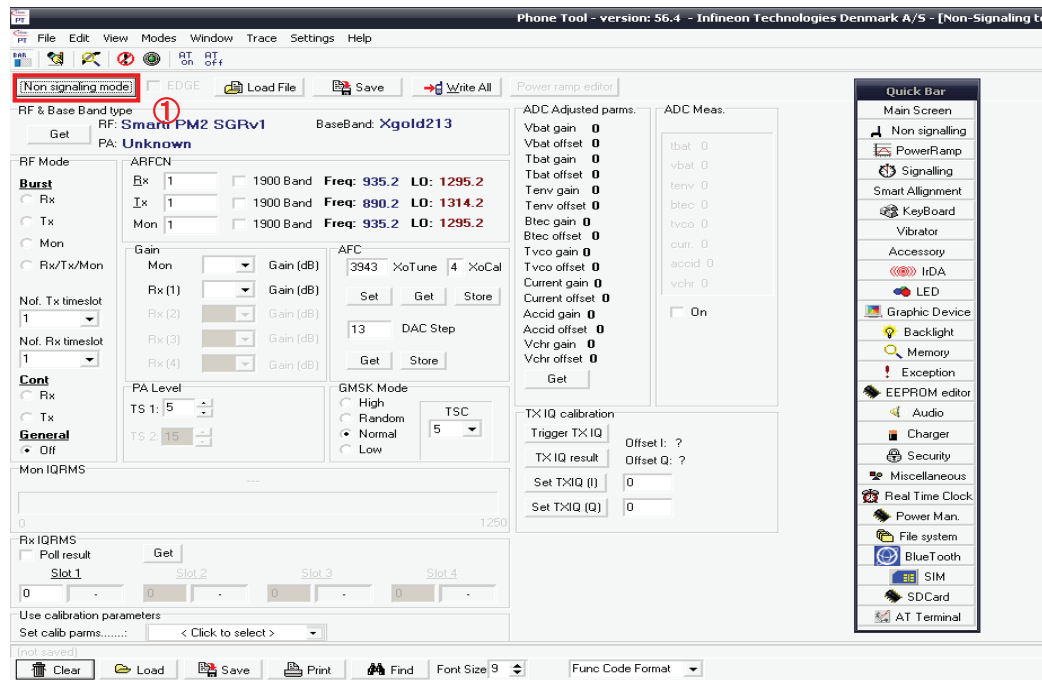
10. STAND ALONE TEST

- For communicating Phone and Test-Program, click "V24 AT# On" and "Update Info" one by one.
- For the purpose of the Standalone Test, Change the Phone to "ptest mode" and then Click the "Reset" bar.
- Select "Non signaling" in the Quick Bar menu. Then Standalone Test setup is finished.
- If you want to test the SIM2 equally, click the "AT Terminal" and then enter "AT%uartpath=1".
Then retry 4~6 step again. (uartpath=0 → SIM1, uartpath=1 → SIM2)

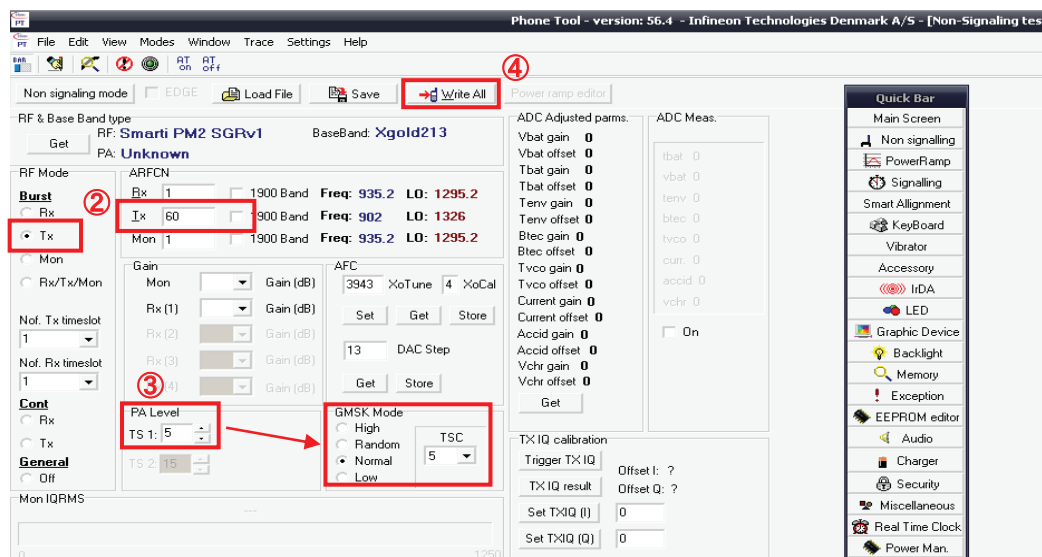


10.3 Tx Test

1. "Non signaling mode" bar and then confirm "OK" text in the command line.
2. Select "Tx" in the RF mode menu and put the number of TX Channel in the ARFCN.
3. Put the number of "PCL" in the PA Level menu.
4. Finally, Click "Write All" bar and try the efficiency test of Phone.



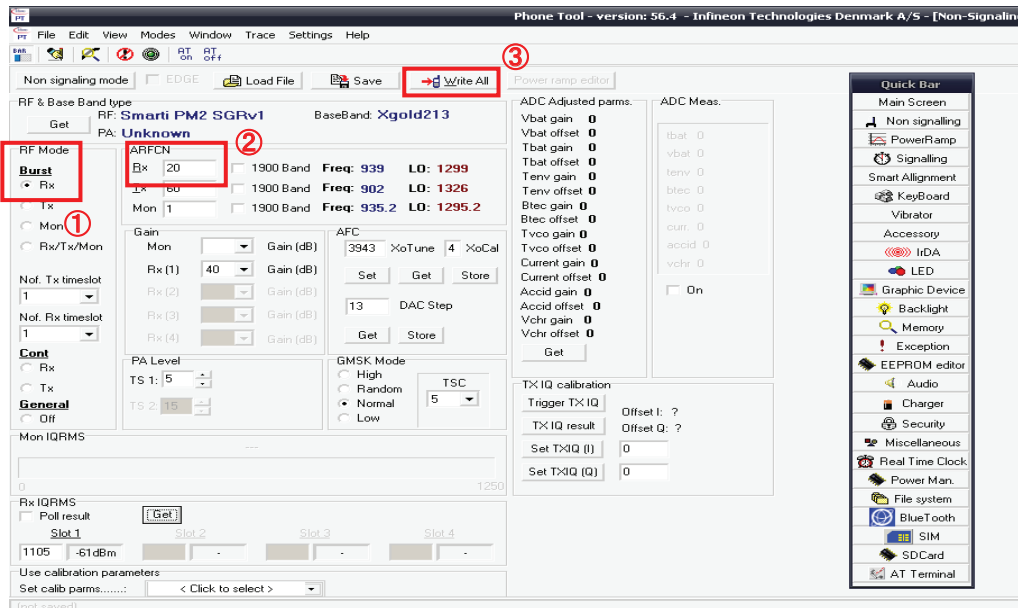
OK, Mobile in Non signaling test mode.



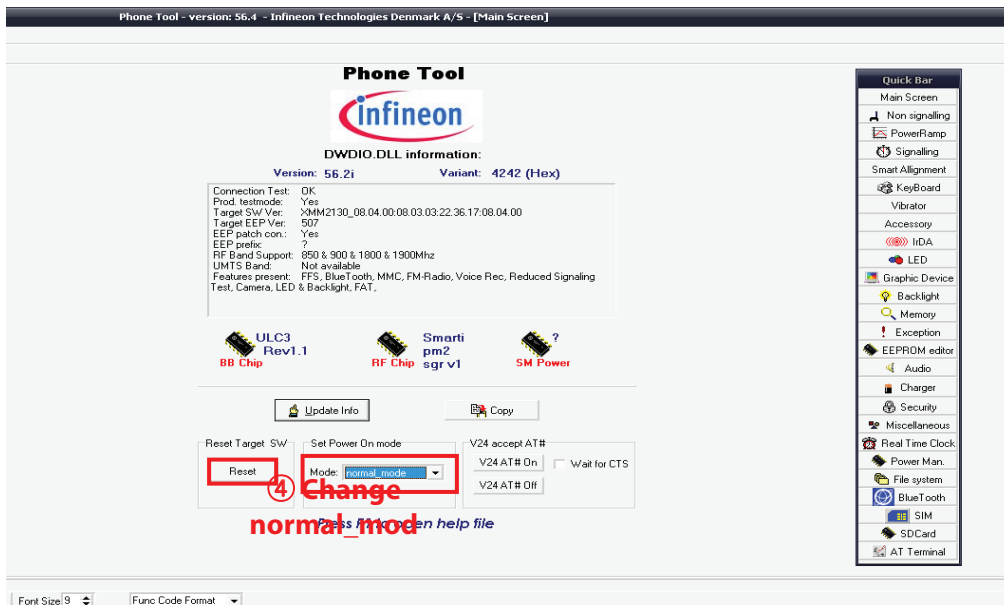
10. STAND ALONE TEST

10.4 Rx Test

1. Select "Rx" in the RF mode menu.
2. Put the number of RX Channel in the ARFCN.
3. Finally, Click "Write All" bar and try the efficiency test of Phone.



4. The Phone must be changed "normal mode" after finishing Test.
Change the Phone to "normal mode" and then Click the "Reset" bar.



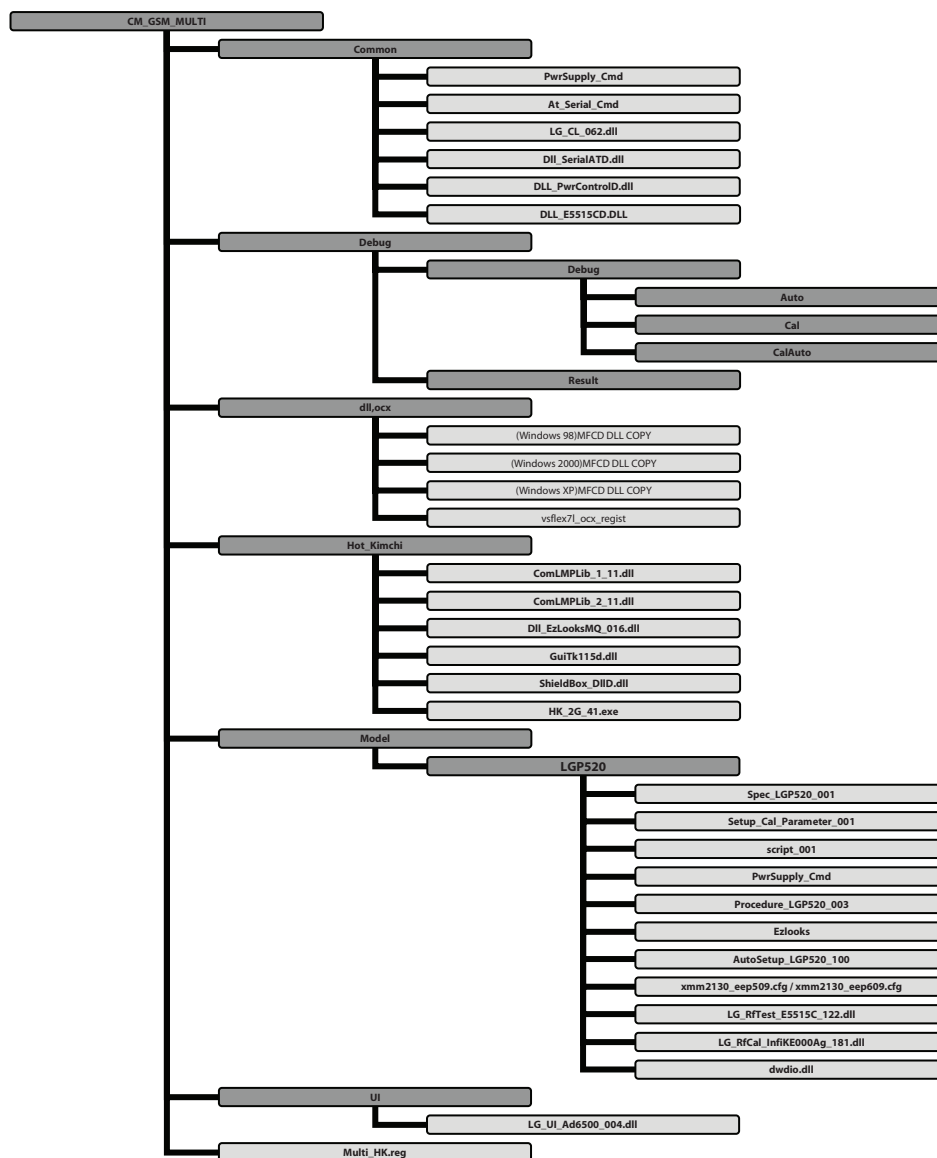
11. AUTO CALIBRATION

11.1 Overview

Auto-cal (Auto Calibration) is the PC side Calibration tool that perform Tx, Rx and Battery Calibration with Agilent 8960(GSM call setting instrument) and Tektronix PS2521G(Programmable Power supply).

Auto-cal generates calibration data by communicating with phone and measuring equipment then write it into calibration data block of flash memory in GSM phone.

11.2 Configuration of HotKimchi



11. AUTO CALIBRATION

11.3 Description of Basic File.

11.3.1 Common

- **LG_CL_062.dll** : Common logic dll, Module In Charge of Reading PID & S/W Version, Booting.
- **Dll_SerialATD.dll** : Serial Communication Module From Phone by AT Command.
- **DLL_PwrControlD.dll** : Communication Module From Power supply.
- **DLL_E5515CD.DLL** : Communication Module From Agilent 8960(Test Set).
- **At_Serial_Cmd.xml** : Definition File of AT Command.
- **PwrSupply_Cmd.xml** : Definition File of Power supply command.

11.3.2. Debug

- **Debug** - Cal : Result File of Calibration.
Auto : Result File of Auto Test.
CalAuto : Result File of Cal & Auto Test.

11.3.3. dll, ocx

- **vsflex7l_ocx_regist** : Registration File for System use
- **(Windows XXX)MFCD DLL** : Registration File for System use

11.3.4. HotKimchi

- **HK_2G_41.exe** : Execute File, HK_2G_XX → XX is File Version.
- **ComLMPLib_1_11.dll** : Communication Module With PLC or Shield Box In Automation Rack.
Support to J&S Shield Box and Tescom TC-5981A.
- **ComLMPLib_2_11.dll** : Communication Module With PLC or Shield Box In Automation Rack.
Support to J&S Shield Box and Tescom TC-5981A.
- **Dll_EzLooksMQ_016.dll** : Communication Module with ezTray Installed In Local PC.
- **GuiTk115d.dll** : control library
- **ShieldBox_DIID.dll** : Communication with Shield Box. Support to Tescom TC-5952B.

11.3.5. Model

- **LG_RfCal_InfiKE000Ag_181.dll** : Main Module of Calibration
- **LG_RfTest_E5515C_122.dll** : Main Module of Auto Test
- **Xmm2130_eep509.cfg** : Cal Data Save binary Module. → eepXXX.cfg : main, eep(XXX+100).cfg : sub
ex) eep509.cfg : main, eep609.cfb : sub
- **AutoSetup_LGP520_100.xml** : RF TEST Setup Module.
- **Ezlooks.xml** : Calibration ezLooks Item & Cal Spec Definition Module.
- **Procedure_LGP520_003.xml** : RF TEST Procedure Definition Module.
- **Script_001.xml** : RF TEST Setup & calibration Setup Module.
- **Spec_LGP520_001.xml** : Definition Module of Auto Test Spec
- **Setup_Cal_Parameter_001.xml** : Calibration Definition Module.

11.3.6. UI

- **LG_UI_Ad6500_002.dll** : ADI Model UI Dll.

11.3.7. Multi_HK

- Registration File For System Setting.

11.4 Auto Calibration setup

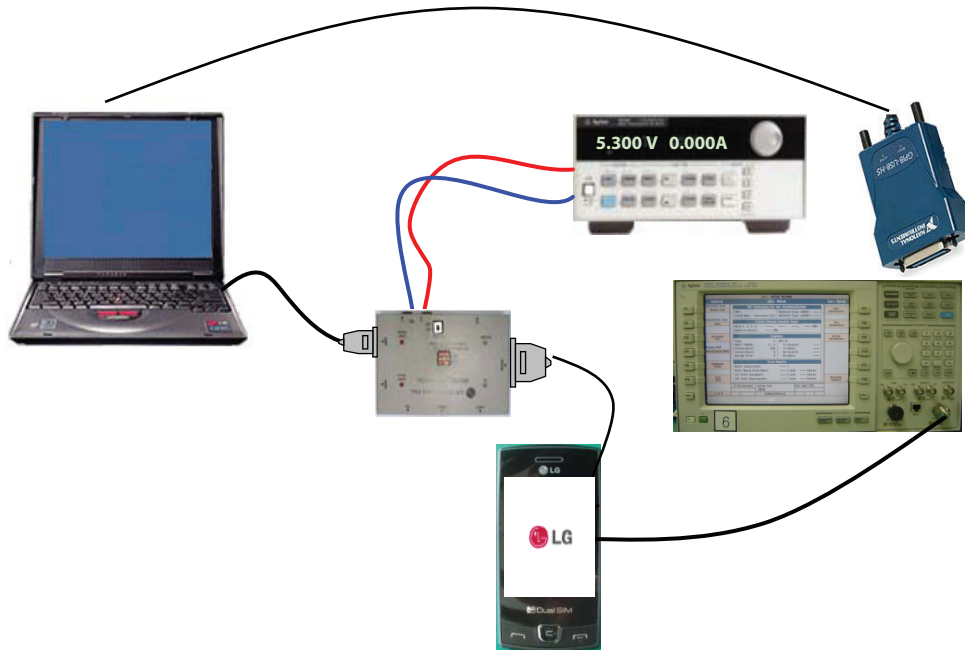


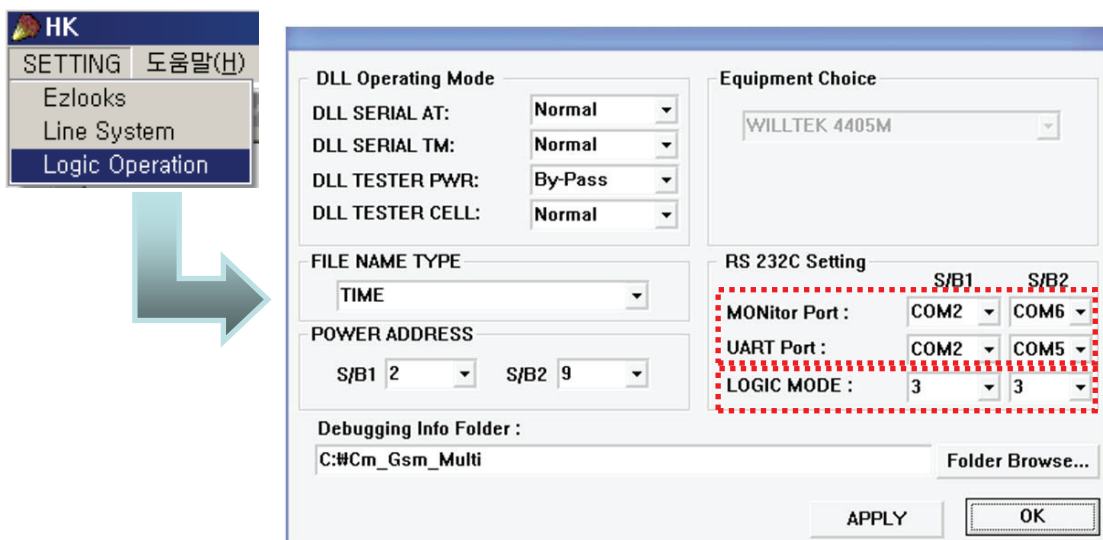
Figure 11.4.1 Equipment setup

1. Connect as Fig 13.4.1 (RS232 serial cable is connected between COM port of PC and MON port of TEST JIG, in general. GPIB-USB-HS cable is connected between HP8960 and PC.)
2. Set the Power Supply 5.3V
3. Set the 3rd, 4th of DIP SW ON state always
4. Press the Phone power key, if the Remote ON is used, 1st ON state

11. AUTO CALIBRATION

11.5 Procedure

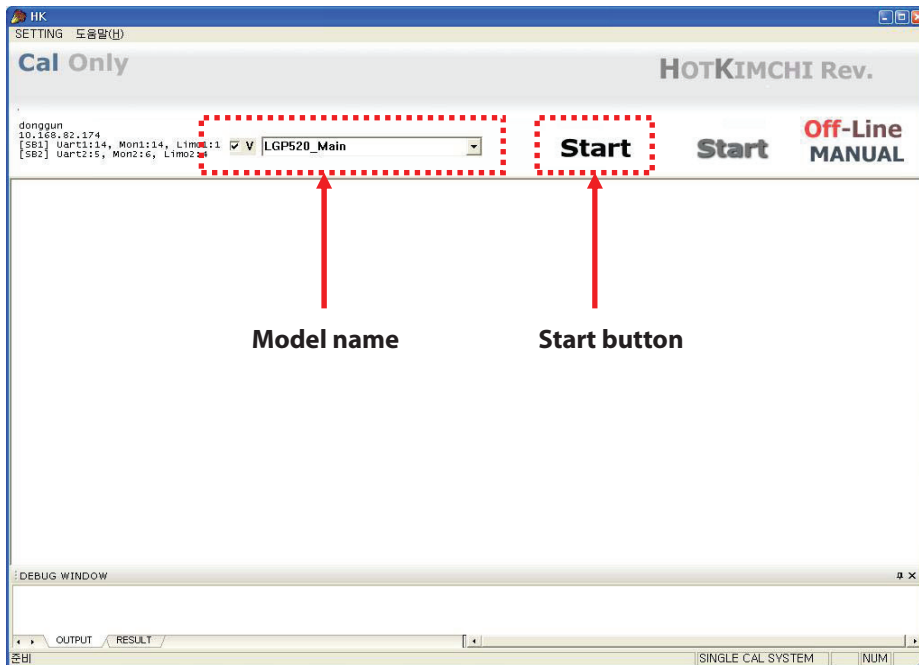
1. Copy the file to C:\Cm_Gsm_Multi
2. Copy the files of((Windows XXX)MFC DLL, vsflex7l_ocx_regist to C:\Cm_Gsm_Multi\dll,ocx
3. Select MFC DLL of your computer OS
4. Click on "vsflex7l_ocx_regist"
5. Click on "Multi_HK reg"
6. Connect as Fig 13.4.1.
7. Run HK_2G_41.exe to start calibration.
8. Click "Logic Operation" of "SETTING" menu bar



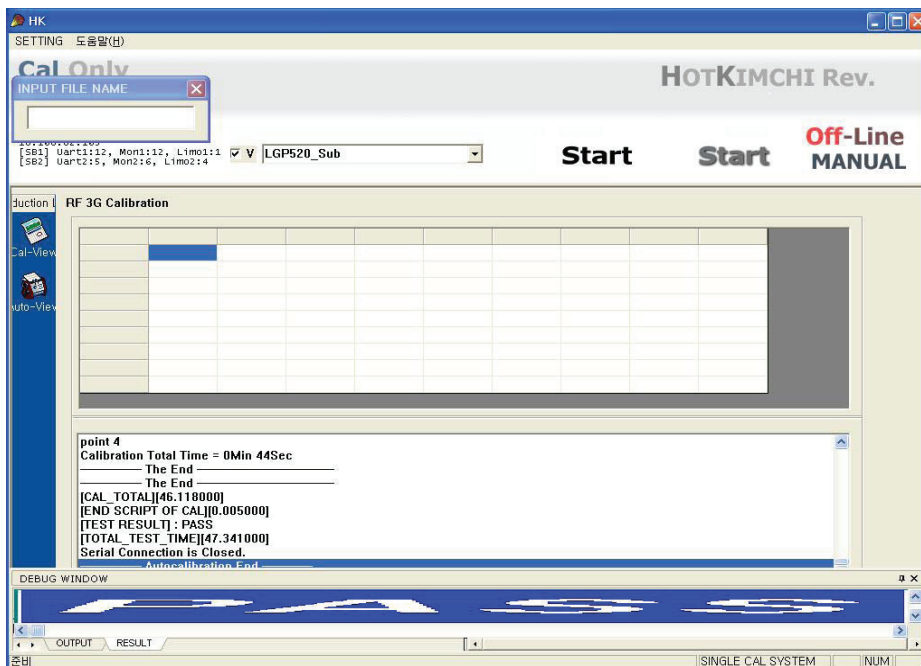
9. Set PORT (using RS232 cable) that PC can communicate with the phone
10. Select "LOGIC MODE" that you want
Logic mode: 1-> Calibration only
2-> Auto test only
3-> Cal & Auto

11. AUTO CALIBRATION

11. Select the model name "LGP520_Main" or "LGP520_Sub"



12. Click "start" button



11. AUTO CALIBRATION

11.6 AGC

This procedure is for Rx calibration.

In this procedure, We can get RSSI correction value. Set band EGSM and press Start button the result window will show correction values per every power level and gain code and the same measure is performed per every frequency.

11.7 APC

This procedure is for Tx calibration.

In this procedure you can get proper scale factor value and measured power level.

11.8 ADC

This procedure is for battery calibration.

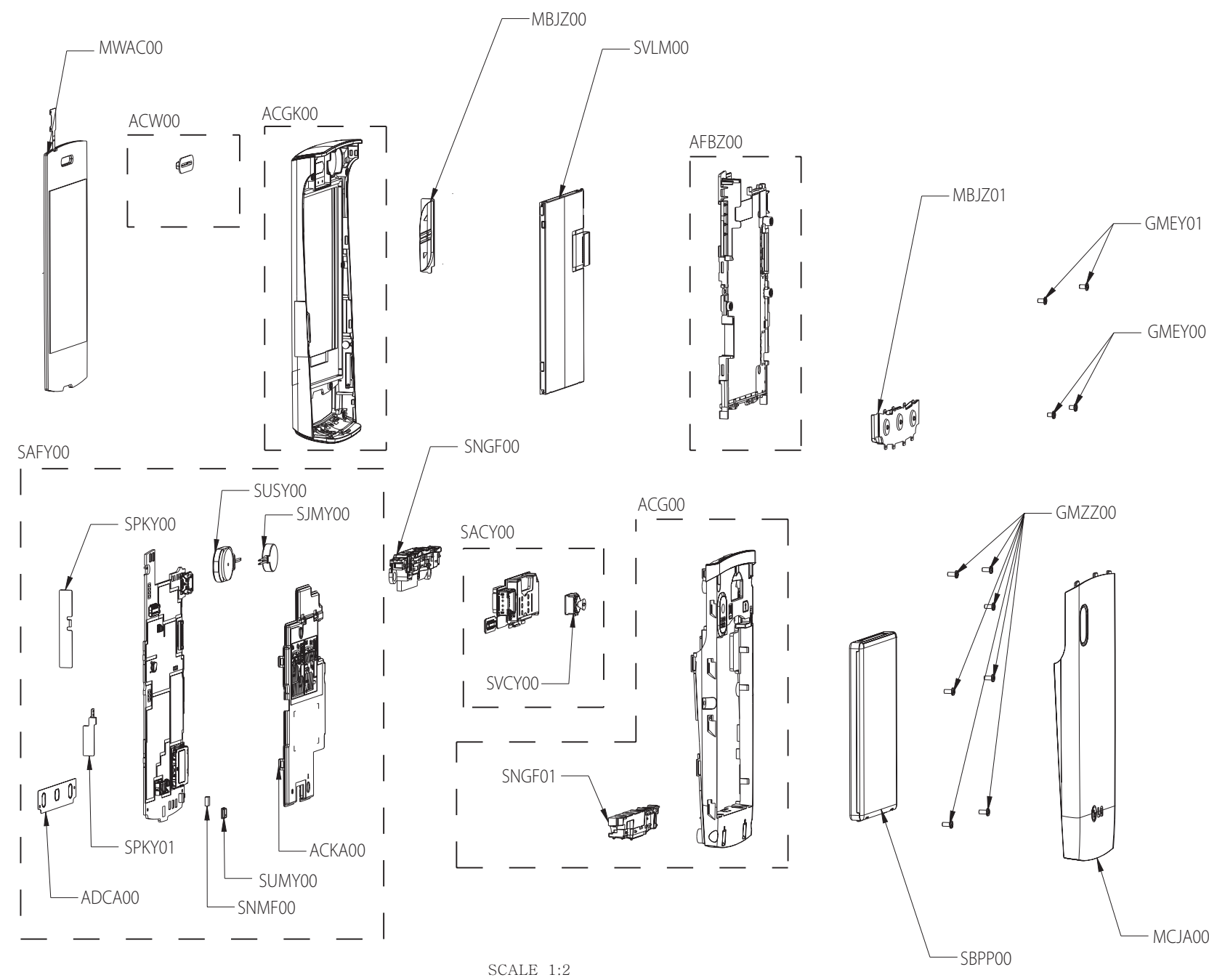
You can get main Battery Config Table and temperature Config Table will be reset.

11.9 Target Power

BAND	Description	Low	Middle	High
GSM 850	Channel	128	190	251
	Frequency	824.2 MHz	881.6 MHz	893.8 MHz
	Max power	33.0 dBm	33.0 dBm	33.0 dBm
EGSM 900	Channel	975	37	124
	Frequency	880.2 MHz	897.4 MHz	914.8 MHz
	Max power	33.0 dBm	33.0 dBm	33.0 dBm
DCS 1800	Channel	512	699	885
	Frequency	1710.2 MHz	1747.6 MHz	1784.8 MHz
	Max power	30.0 dBm	30.0 dBm	30.0 dBm
PCS 1900	Channel	512	661	810
	Frequency	1850.2 MHz	1880 MHz	1909.8 MHz
	Max power	30.0 dBm	30.0 dBm	30.0 dBm

12. EXPLODED VIEW & REPLACEMENT PART LIST

12.1 EXPLODED VIEW



26	Antenna,Helical	SNGF00
25	Microphone,Condenser	SUMY00
24	Antenna,Helical	SNMF00
23	Speaker,Dual Mode	SUSY00
22	Motor,DC	SJMY00
21	Dome Assembly,Metal	ADCA00
20	Can Assembly,Shield	ACKA00
19	PCB,Sidekey	SPKY01
18	PCB,Sidekey	SPKY00
17	PCB Assembly,Main	SAFY00
16	PCB Assembly,Flexible	SACY00
15	Screw,Machine	GMZZ00
14	Antenna,Helical	SNGF01
13	Cover Assembly,Rear	ACG00
12	FRAME ASSY	AFBZ00
11	Cover Assembly,Front	ACGK00
10	Button	MBJZ00
9	Screw,Machine	GMEY01
8	SCREW MACHINE,BIND	GMEY00
7	Decor Assembly	ACW00
6	WINDOW,LCD	MWAC00
5	LCD,Module-TFT	SVLM00
4	BUTTON	MBJZ01
3	Camera Module	SVCY00
2	Rechargeable Battery,Lithium Polymer	SBPP00
1	Cover,Battery	MCJA00
No	Description	Location

12. EXPLODED VIEW & REPLACEMENT PART LIST

12.2 Replacement Parts <Mechanic component>

Note: This Chapter is used for reference, Part order is ordered by SBOM standard on GCSC

Level	Location No.	Description	Part Number	Spec	Remark
1	AAD000000	Addition Assembly	AAD85592002 7	LGP520.ACISBK BK:Black -	
2	AFN053800	Manual Assembly,Operation	AFN75272802 3	LGP520.ACISBK ZZ:Without Color -	
3	MBM087200	Card,Warranty	MCDF0011303	COMPLEX GD350 CISBK ZZ:Without Color -	
3	MFL053800	Manual,Operation	MFL66982802	PRINTING LGP520.ACISBK ZZ:Without Color -	
2	MCK004100	Cover,Battery	MCJA0120802	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
1	APEY00	Phone Assembly	APEY0938301 3	LG-P520 CISBK BK:Black -	
2	ACGY00	Cover Assembly, EMS	ACGY0044501 6	LG-P520 CISBK BK:Black -	
3	ACQ063300	Cover Assembly, Rear	ACGM0169402 18	LG-P520 CISBK BK:Black -	
4	FAC010000	Common	GPZZ0003801	LG-P520 CISBK ZZ	
4	MBL025200	Cap,Earphone Jack	MCCC0073802	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MBL000000	Cap	MCCZ0045201	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MCK063300	Cover,Rear	MCJN0127901	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
4	MCQ000000	Damper	MCQ66490201	COMPLEX LGP520.ACISRD BK:Black -	
4	MCQ000001	Damper	MCQ66491401	COMPLEX LGP520.ACISRD ZZ:Without Color -	
4	MCQ000005	Damper	MCQ66498901	COMPLEX LGP520.ACISBK ZZ:Without Color -	
4	MJN000003	Tape	MJN67690601	COMPLEX LGP520.ACISRD ZZ:Without Color -	
4	MFG000000	Locker	MLEY0005201	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
4	MCQ000002	Damper	MPBZ0331201	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MCQ000003	Damper	MPBZ0331301	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MCQ000004	Damper	MPBZ0345101	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MHK000000	Sheet	MSAZ0074901	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty),	
4	MJN000000	Tape	MTAZ0352501	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
4	MJN000001	Tape	MTAZ0352601	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MJN000002	Tape	MTAZ0362401	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MKC009400	Window,Camera	MWAE0065501	COMPLEX LG-P520 CISBK ZZ:Without Color CUTTING, PMMA MR 200, , , ,	
3	ACQ003400	Cover Assembly,Bar	ACGV0021702 17	LG-P520 CISBK ZZ:Without Color -	
4	ACGK00	Cover Assembly, Front	ACGK0170501 17	LG-P520 CISBK ZZ:Without Color -	
5	GPZZ00	Common	GPZZ0003801	LG-P520 CISBK ZZ	
5	MBJZ00	Button	MBJZ0042501	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MTAZ02	Cap,Multimedia Card	MCCG0025901	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MCJK00	Cover,Front	MCJK0135601 4	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
6	MBFZ00	Bracket	MBFZ0055201	COMPLEX LG-P520 CISBK ZZ:Without Color PRESS, STS, , , ,	
6	MICE01	Insert,Nut	MICE0016901	COMPLEX MECH_COMMON ZZ:Without Color -	
6	MICE00	Insert,Nut	MICE0016903	COMPLEX MECH_COMMON ZZ:Without Color -	
6	MICE02	Insert,Nut	MICE0016911	COMPLEX MECH_COMMON ZZ:Without Color -	
5	MDAY01	Decor	MDAY0086401	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
5	MDAY00	Decor	MDAY0086501	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
5	MFBZ01	Filter	MFBZ0027301	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MPBG00	Damper,LCD	MPBG0114101	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MPBZ00	Damper	MPBZ0332301	COMPLEX LG-P500 TMO ZZ:Without Color COMPLEX, (empty), , , ,	
5	MTAB00	Tape,Protect	MTAB0429801	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MDAY02	Tape,Protect	MTAB0452801	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty),	
5	MFBZ00	Tape,Protect	MTAB0452901	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty),	
5	MTAZ01	Tape	MTAZ0351801	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MTAZ04	Tape	MTAZ0352101	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MTAZ00	Tape	MTAZ0352201	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
5	MTAZ05	Tape	MTAZ0361901	COMPLEX LG-P520 BALBK BK:Black COMPLEX, (empty), , , ,	
5	MTAZ06	Tape	MTAZ0362501	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	ACW000000	Decor Assembly	ACW73517001 2	LGP520.ACISRD BK:Black -	
5	MCR000000	Decor	MDAY0089001	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
5	MJN000000	Tape	MTAZ0352001	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	AFBZ00	Frame Assembly	AFBZ0021201 6	LG-P520 CISBK ZZ:Without Color -	
5	MDS000000	Gasket	MDS63533501	COMPLEX LGP520.ACISBK ZZ:Without Color -	
5	MFEZ00	Frame	MFEZ0037701 2	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
6	MBFZ00	Bracket	MBFZ0055301	COMPLEX LG-P520 CISBK ZZ:Without Color PRESS, STS, , , ,	
6	MICE00	Insert,Nut	MICE0016903	COMPLEX MECH_COMMON ZZ:Without Color -	
5	MJN000003	Tape	MJN67692001	COMPLEX LGP520.ACISBK ZZ:Without Color TAPE(FRAME_FRONT)	
5	MTAZ00	Tape	MTAZ0352301	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MTAZ01	Tape	MTAZ0362701	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
5	MTAZ02	Tape	MTAZ0362801	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	FAB010000	Screw,Machine	GMEY0010402	GMEY0010402 BH + 1.4mm 2mm MSWR FZB N - SERVEONE CO., LTD.	
4	FAB010001	Screw,Machine	GMEY0012901	GMEY0012901 FH + 1.4mm 2.5mm MSWR NI PLT N - LG ELECTRONICS INC.	
4	MBG000001	Button	MBJZ0042602	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MBG000000	Button	MBJZ0042801	COMPLEX LG-P520 CISBK ZZ:Without Color MAIN	
4	MCQ000002	Damper	MCQ66471301	COMPLEX LGP520.ACISBK ZZ:Without Color DAMPER(LCD_FRONT)	
4	MCQ000000	Damper	MCQ66487901	COMPLEX LGP520.ACISRD ZZ:Without Color -	
4	MDJ000000	Filter	MFBZ0027401	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MDS000000	Gasket	MGAZ0113301	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty),	
4	MCQ000001	Damper	MPBZ0345201	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	
4	MJN061100	Tape,Protect	MTAB0428601	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX, (empty), , , ,	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
4	MJN061101	Tape,Protect	MTAB0429701	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty), , , ,	
4	MJN061102	Tape,Protect	MTAB0453001	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty),	
4	MKC043300	Window,LCD	MWAC0152701	COMPLEX LG-P520 CISBK ZZ:Without Color MOLD, PC LUPOY SC-1004A, , , ,	
3	GMZZ00	Screw,Machine	GMZZ0017701	GMZZ0017701 BH + 1.4mM 3mM MSWR NI PLT N - ASIA BOLT	
4	MCQ000002	Damper	MCQ66467201	COMPLEX LGP520.ACISRD ZZ:Without Color -	
4	MPBZ00	Damper	MPBZ0344801	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty), , , ,	
4	MCQ000001	Damper	MPBZ0344901	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty), , , ,	
4	MJN000000	Tape	MTAZ0352401	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty), , , ,	
5	ACKA00	Can Assembly, Shield	ACKA0033601 8	LG-P520 CISBK ZZ:Without Color -	
6	MCBA00	Can,Shield	MCBA0087401	COMPLEX LG-P520 CISBK ZZ:Without Color PRESS,STS,	
6	MCQ000002	Damper	MCQ66499101	COMPLEX LGP520.ACISBK ZZ:Without Color -	
6	MKU101700	Absorber,Electromagnetic Wave	MKU30223401	COMPLEX LGP520.ACISBK ZZ:Without Color -	
6	MKU101701	Absorber,Electromagnetic Wave	MKU30243401	COMPLEX LGP520.ACISBK ZZ:Without Color P520_ABSORBER2_CAN_SHIELD	
6	MLAB	Label,After Service	MLAB0001102	COMPLEX C2000 CGRSV WA:White C2000 USASV DIA 4.0 PRINTING,	
6	MCQ000000	Damper	MPBZ0360701	COMPLEX LG-P520 BALBK ZZ:Without Color COMPLEX,(empty), , , ,	
6	MCQ000001	Damper	MPBZ0367101	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty),	
6	MTAZ01	Tape	MTAZ0352801	COMPLEX LG-P520 CISBK ZZ:Without Color COMPLEX,(empty), , , ,	
5	ADCA00	Dome Assembly, Metal	ADCA0119001	LG-P520 CISBK ZZ:Without Color -	
5	MCQ000000	Damper	MCQ66467901	COMPLEX LGP520.ACISRD ZZ:Without Color -	
5	MCQ000001	Damper	MCQ66468001	COMPLEX LGP520.ACISRD ZZ:Without Color -	
5	MEZ000900	Label,After Service	MLAB0004801	COMPLEX LG-LB3300 LGT ZZ:Without Color -	
5	MJN000000	Tape	MTAZ0362101	COMPLEX LG-P520 BALBK ZZ:Without Color COMPLEX,(empty), , , ,	
5	MEZ000000	Label	MLAZ0038301	COMPLEX LG-VX6000 ZZ:Without Color PID Label 4 Array PRINTING,	

12. EXPLODED VIEW & REPLACEMENT PART LIST

12.2 Replacement Parts <Main component>

Note: This Chapter is used for reference, Part order is ordered by SBOM standard on GCSC

Level	Location No.	Description	Part Number	Spec	Remark
4	EAA010400	Antenna, Helical	SNGF0065401	LS01-L-10LGP520-A0 3,-2 dBd, Quad(GSM850/900/DCS/PCS), QUAD,-2,50,3 LS Mtron Ltd.	
4	EAJ020200	LCD, Module-TFT	SVLM0040002	LM283DN1A Main, 2.8, QVGA, 47.4x70.21x1.9t, 262K, TFT, TM, RENESAS(R 61520), TOVIS	
3	SACY00	PCB Assembly, Flexible	SACY0119901 6	LG-P520 CISBK FLEXIBLE 1.0	
4	SACE00	PCB Assembly, Flexible, SMT	SACE0108201 3	LG-P520 CISBK FLEXIBLE 1.0	
5	SACC00	PCB Assembly, Flexible, SMT Bottom	SACC0081401 8	LG-P520 CISBK FLEXIBLE 1.0	
6	C104, C105	Capacitor, Ceramic, Chip	ECCH0000115	MCH155A220JK 22pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C106, C107, C108	Capacitor, Ceramic, Chip	ECZH0003103	GRM36X7R104K10PT 100nF 10% 10V X7R -55TO+125C 1005 R/TP - MURATA MANUFACTURING CO., LTD.	
6	CN100	Connector, BtoB	ENBY0035901	GB042-40P-H10-E3000 40P 0.4MM STRAIGHT PLUG SMD R/TP 1M - LS Mtron Ltd.	
6	S100	Card Socket	ENSY0022201	CAM-H88 24, ETC, mm, 7*7, 1.3M (1/5") Socket Type MITSUMI ELECTRIC CO., LTD.	
6	S101	Card Socket	ENSY0025301	KP09Y-12S-1.27SF SIM 12P ANGLE SMD R/TP - HIROSE KOREA CO., LTD	
6	R101, R102	Resistor, Chip	ERHY0000254	MCR01MZP5J472 4.7KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R106	Resistor, Chip	ERHZ0000406	MCR01MZP5J104 100KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R100, R103, R104	Resistor, Chip	ERHZ0000441	MCR01MZP5J220 22OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
5	SACD00	PCB Assembly, Flexible, SMT Top	SACD0094901	LG-P520 CISBK FLEXIBLE, A	
5	SPCY00	PCB, Flexible	SPCY0247201	SPCY0247201 LG-P520 CISBK, FLEXIBLE, E, POLYI, .26 mm, MULTI-3, F_SUB SI FLEX CO., LTD	
4	SVCY00	Camera Module	SVCY0021101	HSIS-LM23SS CMOS, MEGA, 2M FF SS-LSI(1/5"), 7x7x4.1, Socket HANSUNG ELCOMTEC CO., LTD.	
3	SAFY00	PCB Assembly, Main	SAFY0383001 2	LGP520.ACISBK MAIN 1.0	
4	SAFB00	PCB Assembly, Main, Insert	SAFB0123201 10	LGP520.ACISBK MAIN 1.0	
5	SJMY00	Motor, DC	SJMY0007117	WHVM-1030Q15 2 V, 65 mA, 10*3.0t, 3V, WOOSUNG G&T CO., LTD	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
5	EAX010500	PCB,Sidekey	SPKY0094401	SPKY0094401 LG-P520 CISBK,SIDEKEY,C,POLYI,0.62 mm,MULTI-2,F_SK_HOLD SI FLEX CO., LTD	
5	EAX010501	PCB,Sidekey	SPKY0094501	SPKY0094501 LG-P520 CISBK,SIDEKEY,B,POLYI,0.62 mm,MULTI-2,F_SK_VOL SI FLEX CO., LTD	
5	SUSY00	Speaker,Dual Mode	SUSY0028906	ISDT-181230-08W-01 Nd-Fe-B 700mW 8OHM 91DB 710HZ 1812*3.0T WIRE GoerTek Inc.	
4	SAFF00	PCB Assembly, Main,SMT	SAFF0285001 3	LGP520.ACISBK MAIN 1.0	
5	SAFC00	PCB Assembly, Main,SMT Bottom	SAFC0152801 140	LGP520.ACISBK MAIN 1.0	
6	C317,C321	Capacitor,Ceramic, Chip	ECCH0000105	MCH155A040C 4pF 0.25PF 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C602,C607	Capacitor,Ceramic, Chip	ECCH0000110	MCH155A100D 10pF 0.25PF 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C262	Capacitor,Ceramic, Chip	ECCH0000112	MCH155C150J 15pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C101,C401	Capacitor,Ceramic, Chip	ECCH0000113	MCH155A180J 18pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C142,C143, C207,C210, C441,C442	Capacitor,Ceramic, Chip	ECCH0000115	MCH155A220JK 22pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C144,C203, C211,C215, C216	Capacitor,Ceramic, Chip	ECCH0000117	CL05C270JB5NNNC 27pF 5% 50V NP0 -55TO+125C 1005 R/TP 0.5 SAMSUNG ELECTRO-MECHANICS CO., LTD.	
6	C206,C233, C234,C241, C243,C259, C305,C331	Capacitor,Ceramic, Chip	ECCH0000120	MCH155A390J 39pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C135,C136, C137,C138, C228,C229, C264,C265, C432,C433, C434,C435	Capacitor,Ceramic, Chip	ECCH0000122	MCH155A470JK 47pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C212	Capacitor,Ceramic, Chip	ECCH0000129	MCH155A121JK 120pF 5% 50V NP0 -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C139,C213, C302,C303, C304,C306, C328,C329, C330,C332, C614,C615, C639	Capacitor,Ceramic, Chip	ECCH0000143	MCH155CN102KK 1nF 10% 50V X7R -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C103,C128, C403	Capacitor,Ceramic, Chip	ECCH0000151	CL05B472KB5NNNC 4.7nF 10% 25V X7R -55TO+125C 1005 R/TP - SAMSUNG ELECTRO-MECHANICS CO., LTD.	
6	C217,C531, C600,C604, C605	Capacitor,Ceramic, Chip	ECCH0000155	MCH153CN103KK 10nF 10% 16V X7R -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	C335	Capacitor,Ceramic, Chip	ECCH0000161	MCH153CN333KK 33nF 10% 16V X7R -55TO+125C 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	C204,C209	Capacitor,Ceramic, Chip	ECCH0000179	GRM155R71C223K 22nF 10% 16V X7R -55TO+85C 1005 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C246,C255	Capacitor,Ceramic, Chip	ECCH0000182	GRM155R61A104K 0.1uF 10% 10V X5R -55TO+85C 1005 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C343,C344	Capacitor,Ceramic, Chip	ECCH0000185	GRM1555C1H5R6C 5.6pF 0.25PF 50V NP0 -55TO+125C 1005 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C208,C227, C230,C231, C238,C245, C445,C523, C525,C526, C603	Capacitor,Ceramic, Chip	ECCH0000198	CL05A225MQ5NSNC 2.2uF 20% 6.3V X5R -55TO+85C 1005 R/TP . SAMSUNG ELECTRO-MECHANICS CO., LTD.	
6	C636	Capacitor,Ceramic, Chip	ECCH0000701	C1005C0G1H1R2CT000F 1.2pF 0.25PF 50V NP0 - 55TO+125C 1005 R/TP - TDK CORPORATION	
6	C308	Capacitor,Ceramic, Chip	ECCH0000901	C1005C0G1H2R2CT000F 2.2pF 0.25PF 50V NP0 - 55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C322,C323, C345,C346	Capacitor,Ceramic, Chip	ECCH0001001	C1005C0G1H6R8CT000F 6.8pF 0.5PF 50V NP0 - 55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C225,C226	Capacitor,Ceramic, Chip	ECCH0002001	C1005JB0J104KT000F 0.1uF 10% 6.3V Y5P -30TO+85C 1005 R/TP - TDK CORPORATION	
6	C104,C105, C404,C405	Capacitor,Ceramic, Chip	ECCH0002002	C1005X7R1A473KT000F 47000pF 10% 10V Y5P - 30TO+85C 1005 R/TP - TDK CORPORATION	
6	C100,C106, C249,C324, C400,C406, C421,C422, C424,C438, C440,C444, C500,C502, C529,C637, C638	Capacitor,Ceramic, Chip	ECCH0004904	GRM155R60J105K 1uF 10% 6.3V X5R -55TO+85C 1005 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C244	Capacitor,Ceramic, Chip	ECCH0005603	GRM188R61A225K 2.2uF 10% 10V X5R -55TO+85C 1608 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C205	Capacitor,Ceramic, Chip	ECCH0005604	GRM188R60J106M 10000000 pF,6.3V,M,X5R,TC,1608,R/TP,0.8 mm MURATA MANUFACTURING CO.,LTD.	
6	C127,C423	Capacitor,Ceramic, Chip	ECCH0007803	CL10A106MP8NNNC 10uF 20% 10V X5R -55TO+85C 1608 R/TP 0.8MM SAMSUNG ELECTRO-MECHANICS CO., LTD.	
6	C111,C118, C123,C124, C218,C235, C236,C239, C240,C411, C418,C501, C517,C518, C528	Capacitor,Ceramic, Chip	ECCH0007804	CL05A225MP5NSNC 2.2uF 20% 10V X5R -55TO+85C 1005 R/TP 0.5MM SAMSUNG ELECTRO-MECHANICS CO., LTD.	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	C662	Capacitor,TA,Conformal	ECTH0002703	TCTAL1A107M8R 0.0001F 20% 10V 50UA -55TO+125C 00HM 3.2x1.6x1.1 NONE SMD R/TP ROHM CO.,LTD.	
6	C310,C337	Capacitor,TA,Conformal	ECTH0005703	251M1002226MR0S 22F 20% 10V 2.2A -55TO+85C 4OHM 2.2X1.25X0.9MM - SMD R/TP MATSUO ELECTRIC CO.,LTD	
6	C300,C312, C313,C338, C339	Capacitor,Ceramic, Chip	ECZH0000802	C1005C0G1H010CT 1pF 0.25PF 50V NP0 -55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C145,C611, C640,L323	Capacitor,Ceramic, Chip	ECZH0000813	C1005C0G1H101JT 100pF 5% 50V NP0 -55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C251,C253, C254,C309	Capacitor,Ceramic, Chip	ECZH0000830	C1005C0G1H330JT000F 33pF 5% 50V NP0 -55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C214	Capacitor,Ceramic, Chip	ECZH0000901	C1005C0G1H240JT000F 24pF 5% 50V NP0 -55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C325,C341, C349	Capacitor,Ceramic, Chip	ECZH0001002	C1005CH1H0R5BT000F 0.5pF 0.1PF 50V NP0 -55TO+125C 1005 R/TP - TDK KOREA COOPERATION	
6	C110,C410	Capacitor,Ceramic, Chip	ECZH0001210	C1005Y5V1A474ZT000F 470nF -20TO+80% 10V Y5V -30TO+85C 1005 R/TP - TDK KOREA COOPERATION	
6	C219,C221, C222,C223, C224,C247, C248,C252, C509,C513, C515,C516, C524	Capacitor,Ceramic, Chip	ECZH0001215	C1005X5R1A105KT000F 1uF 10% 10V X5R -55TO+85C 1005 R/TP - TDK KOREA COOPERATION	
6	C102,C116, C140,C402, C416,C436	Capacitor,Ceramic, Chip	ECZH0001216	C1005X5R1A224KT000E 220nF 10% 10V X5R -55TO+85C 1005 R/TP - TDK KOREA COOPERATION	
6	C113,C114, C326,C334, C413,C414	Capacitor,Ceramic, Chip	ECZH0001217	GRM155R60J474K 470nF 10% 6.3V X5R -25TO+70C 1005 BK-DUP - MURATA MANUFACTURING CO.,LTD.	
6	C107,C108, C109,C112, C115,C117, C119,C125, C126,C130, C200,C220, C232,C237, C258,C261, C336,C407, C408,C409, C412,C415, C417,C427, C439,C443, C530,C532, C609	Capacitor,Ceramic, Chip	ECZH0003103	GRM36X7R104K10PT 100nF 10% 10V X7R -55TO+125C 1005 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C256	Capacitor,Ceramic, Chip	ECZH0003503	GRM188R61E105K 1uF 10% 25V X5R -55TO+85C 1608 R/TP - MURATA MANUFACTURING CO.,LTD.	
6	C201	Capacitor,Ceramic, Chip	ECZH0003504	GRM188R71E104K 100nF 10% 25V X7R -55TO+125C 1608 R/TP - MURATA MANUFACTURING CO.,LTD.	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	C121,C419	Capacitor,Ceramic, Chip	ECZH0025502	GRM219R60J226M 0.000022F 20% 6.3V X5R -55TO+85C 2012 R/TP 0.85MM MURATA MANUFACTURING CO.,LTD.	
6	VA300	Diode,TVS	EDTY0008606	PRSB6.8C 4.7V 5.7 - - 10W - R/TP 2P 1 PROTEK DEVICES INC.	
6	ZD1,ZD2,ZD3,ZD4	Diode,TVS	EDTY0009101	ESD9X5.0ST5G 5V 6.2 12.3V 8.7A 107W SOD528 R/TP 2P 1 ON SEMICONDUCTOR	
6	ZD200, ZD501, ZD502, ZD503, ZD504, ZD505, ZD506, ZD507, ZD508	Diode,TVS	EDTY0009401	VMNZ6.8CST2R 5.5V 0 10V 0A 200mW SC70 R/TP 6P 5 ROHM.	
6	C514	Diode,TVS	EDTY0009601	Rclamp0521P.TCT 5V 6 5V 4A 100W - R/TP 2P 1 SEMTECH CORPORATION	
6	L305,L306, L317,L318	Inductor,Multilayer, Chip	ELCH0001033	HK1005 1N5S-T 1.5NH 0.3NH 0V 8A 13GOHM 50mHZ 300m NON SHIELD 1 1.0X0.5X0.5MM R/TP TAIYO YUDEN CO.,LTD	
6	R315	Inductor,Multilayer, Chip	ELCH0001035	HK1005 4N7S-T 4.7NH 0.3NH 0V 8A 6GOHM 120mHZ 300m NON SHIELD 1 1.0X0.5X0.5MM R/TP TAIYO YUDEN CO.,LTD	
6	L311	Inductor,Multilayer, Chip	ELCH0001036	HK1005 5N6S-T 5.6NH 0.3NH 0V 8A 5.7GOHM 150mHZ 300m NON SHIELD 1 1.0X0.5X0.5MM R/TP TAIYO YUDEN CO.,LTD	
6	C340	Inductor,Multilayer, Chip	ELCH0001040	HK1005 3N9S-T 3.9NH 0.3NH 0V 8A 7GOHM 120mHZ 300m NON SHIELD 1 1.0X0.5X0.5MM R/TP TAIYO YUDEN CO.,LTD	
6	C314	Inductor,Multilayer, Chip	ELCH0001403	LL1005-FHL1N0S 1NH 0.3NH 0V 500mA 0.1OHM 20GHZ 8 NON SHIELD 1 1.0X0.5X0.5MM R/TP TOKO, INC.	
6	L320	Inductor,Multilayer, Chip	ELCH0001406	LL1005-FHL4N7S 4.7NH 0.3NH 0V 400mA 0.2OHM 6GHZ 9 NON SHIELD 1 1.0X0.5X0.5MM R/TP TOKO, INC.	
6	L319	Inductor,Multilayer, Chip	ELCH0003814	LQG15HS5N1S02 5.1NH 0.3NH 0V 300mA 0.2OHM 5.3GHZ 8 NON SHIELD 1 1.0X0.5X0.5MM R/TP MURATA MANUFACTURING CO.,LTD.	
6	L310	Inductor,Multilayer, Chip	ELCH0003819	LQG15HS12NJ02D 12NH 5% 0V 300mA 0.28OHM 3GHZ 8 NON SHIELD 1 1.0X0.5X0.5MM R/TP MURATA MANUFACTURING CO.,LTD.	
6	L301,L302, L303,L304, L313,L314, L315,L316	Inductor,Multilayer, Chip	ELCH0003826	LQG15HS3N3S02D 3.3NH 0.3NH 0V 300mA 0.17OHM 6GHZ 8 NON SHIELD 1 1.0X0.5X0.5MM R/TP MURATA MANUFACTURING CO.,LTD.	
6	L307,L312	Inductor,Multilayer, Chip	ELCH0003836	LQG15HS5N6S02 5.6NH 0.3NH - 300mA 0.12OHM 6KHZ 8 SHIELD 1 1.0X0.5X0.55MM R/TP MURATA MANUFACTURING CO.,LTD.	
6	L200,L201	Inductor,Multilayer, Chip	ELCH0003842	LQG15HSR10J02 100NH 5% - 150mA 1.25OHM 600HZ 8 SHIELD 1 1.0X0.5X0.55MM R/TP MURATA MANUFACTURING CO.,LTD.	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	L322	Inductor,Multilayer, Chip	ELCH0004710	1005GC2T15NJ00 15NH 5% 0V 250mA 0.53OHM 2GHZ 8 NON SHIELD 1 1.0X0.5X0.5MM R/TP PILKOR ELECTRONICS LTD.	
6	L308	Inductor,Multilayer, Chip	ELCH0004733	1005GC2T4N3SLF 4.3NH 0.3NH 0V 300mA 0.23OHM 3.5GHZ 8 NON SHIELD 1 1.0X0.5X0.5MM R/TP PILKOR ELECTRONICS LTD.	
6	L500,L501	Inductor,Multilayer, Chip	ELCH0009114	0402CS-R10XJEW 100NH 5% 0V 30mA 2OHM 1.16GHZ 21 NON SHIELD 1 1.19X0.64X0.66MM R/TP COILCRAFT SINGAPORE PTE LTD.	
6	L202,L203	Inductor,Multilayer, Chip	ELCH0012503	LQW15AN56NJ00 56NH 5% 0V 200mA 1.17OHM 2.8GHZ 25 NON SHIELD 1 1.0X0.5X0.5MM R/TP MURATA MANUFACTURING CO.,LTD.	
6	L100,L400	Inductor,Wire Wound, Chip	ELCP0008003	MIP2520D3R3M 3.3UH 30% 0V 1.2A 0.1OHM 0HZ 0 SHIELD 2.5X2X1MM NONE R/TP FDK CORPORATION.	
6	CN203, CN500	Connector,BtoB	ENBY0036001	GB042-40S-H10-E3000 40P 0.4MM STRAIGHT SOCKET SMD R/TP 1M ENGINEERING PLASTIC UL94V-0 AU OVER NI LS Mtron Ltd.	
6	CN200	connector,I/O	ENRY0008801	GU073-5P-SD-E1500 GU073-5P-SD-E1500,5,mm,ANGLE LS Mtron Ltd.	
6	S502	Card Socket	ENSY0023302	SCHA5B0501 8,ETC,0.7 mm,15.0x15.0x1.62t,Reverse ALPS ELECTRIC CO.,LTD.	
6	SW300, SW301	Connector,RF	ENWY0008701	MS-156C NONE STRAIGHT SOCKET SMD T/REEL AU 50OHM 400mDB HIROSE KOREA CO.,LTD	
6	CN202	Connector, Terminal Block	ENZY0028601	04-9248-003-017-829+ 3P 2.50MM STRAIGHT SMD R/TP - KYOCERA ELCO KOREA SALES CO.,LTD.	
6	Q400	TR,Array	EQBA0000602	KRX102E NPN/PNP 40 30 6 0.1 0.2 TESV R/TP 5P 2 KEC CORPORAITION	
6	Q300	TR,Bipolar	EQBN0019201	KTC3770V VSM,0.1 W,R/TP,1.2*1.2*0.5 Vcbo=20,Vceo=12,Vebo=2V,Ic=100mA KEC CORPORAITION	
6	Q100	TR,Bipolar	EQBN0020501	KTC4075E NPN 5V 60V 50V 150mA 100NA 700 100mW ESM R/TP 3P KEC CORPORAITION	
6	R236	Resistor,Chip	ERHY0000105	MCR01MZIP5F51R0 51OHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R601	Resistor,Chip	ERHY0000128	MCR01MZIP5F1502 15KOHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R233	Resistor,Chip	ERHY0000161	MCR01MZIP5F2003 200KOHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R231	Resistor,Chip	ERHY0000185	MCR01MZIP5F8200 820OHM 1% 1/16W 1005 R/TP - ROHM.	
6	R203,R205	Resistor,Chip	ERHY0000193	MCR01MZSJ270 27 ohm,1/16W,F,1005,R/TP ROHM.	
6	R132,R223	Resistor,Chip	ERHY0000241	MCR01MZIP5J102 1KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R106,R517	Resistor,Chip	ERHY0000254	MCR01MZIP5J472 4.7KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R103	Resistor,Chip	ERHY0000275	MCR01MZIP5J563 56KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	R505	Resistor,Chip	ERHY0003301	MCR01MZP5J101 100OHM 5% 1/16W 1005 R/TP - ROHM.	
6	R211,R214, R228	Resistor,Chip	ERHZ0000201	MCR01MZP5F1000 100OHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R401,R402	Resistor,Chip	ERHZ0000203	MCR01MZP5F1002 10KOHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R111,R225, R506	Resistor,Chip	ERHZ0000204	MCR01MZP5F1003 100KOHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R229	Resistor,Chip	ERHZ0000206	MCR01MZP5F10R0 10OHM 0.1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R232	Resistor,Chip	ERHZ0000236	MCR01MZP5F2001 2KOHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R209,R210	Resistor,Chip	ERHZ0000240	MCR01MZP5F20R0 20OHM 1% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R118,R120, R144,R600	Resistor,Chip	ERHZ0000401	MCR01MZSJ000 0OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R102,R220, R222	Resistor,Chip	ERHZ0000402	MCR01MZP5J100 10OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R306,R329	Resistor,Chip	ERHZ0000404	MCR01MZP5J102 1KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R202,R515	Resistor,Chip	ERHZ0000405	MCR01MZP5J103 10KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R105,R109, R124,R125, R126,R135, R212,R213, R224,R226, R230,R403, R404,R407, R418,R427, R433,R434, R435,R503, R522	Resistor,Chip	ERHZ0000406	MCR01MZP5J104 100KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R304,R307, R308,R309, R328,R330, R331,R332	Resistor,Chip	ERHZ0000408	MCR01MZP5J111 110OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R314,R500, R520,R521	Resistor,Chip	ERHZ0000434	MCR01MZP5J1R0 1OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R127,R128, R201,R204, R206	Resistor,Chip	ERHZ0000443	MCR01MZP5J222 2.2KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R324	Resistor,Chip	ERHZ0000449	MCR01MZP5J243 24KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R237	Resistor,Chip	ERHZ0000457	MCR01MZP5J300 30OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R325	Resistor,Chip	ERHZ0000473	MCR01MZP5J390 39OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	R108	Resistor,Chip	ERHZ0000475	MCR01MZIP5J392 3.9KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R107	Resistor,Chip	ERHZ0000484	MCR01MZIP5J471 470OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R333	Resistor,Chip	ERHZ0000485	MCR01MZIP5J472 4.7KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R508,R509, R510,R511, R512	Resistor,Chip	ERHZ0000486	MCR01MZIP5J473 47KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R113,R420	Resistor,Chip	ERHZ0000499	MCR01MZIP5J562 5.6KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R523,R524, R525	Resistor,Chip	ERHZ0000505	MCR01MZIP5J681 680OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R624	Resistor,Chip	ERHZ0000506	MCR01MZIP5J682 6.8KOHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R591,R592, R593,R594, R595	Resistor,Chip	ERHZ0000510	MCR01MZIP5J751 750OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	R321	Resistor,Chip	ERHZ0003801	MCR01MZIP5J5R1 5.1OHM 5% 1/16W 1005 R/TP - ROHM Semiconductor KOREA CORPORATION	
6	U207,U208	IC,Analog Switch	EUSY0300101	NLAS5223BMNR2G 1.65~5.5 50SEC 30SEC 0W TQFN R/TP 10P 2 - ON SEMICONDUCTOR	
6	U201,U205, U206	IC,Analog Switch	EUSY0340301	FSA2268TUMX-F113 1.65~4.3 60SEC 35SEC 0W MLF R/TP 10P 2 - FAIRCHILD SEMICONDUCTOR	
6	U601	IC,Analog Switch	EUSY0342401	NLAST9431MT 2.0~5.5 16SEC 5SEC 0W TDFN R/TP 16P 4 - ON SEMICONDUCTOR	
6	U500	IC,Charge Pump	EUSY0344403	RT9396GQW QFN,24,R/TP,4CH+2LDO,IC,Sub PMICIC,Sub PMIC RICHTEK TECHNOLOGY CORP.	
6	U400	IC,Buffer	EUSY0396101	IDT70P255 128KB Asynchronous Dual Port SRAM,100,R/TP,BGA Package,IC,BufferIC,Buffer IDT INC.	
6	U202	IC,Audio Sub System	EUSY0403901	WM9093ECS/R 1.71~5.5V 0W WLCSP R/TP 20P - WOLFSON MICROELECTRONICS PLC	
6	U200	IC,Analog Multiplexer	EUSY0406901	RT8962WS WLCSP,20,R/TP,MUIC-Basic,2X2.5,IC,Analog SwitchIC,Analog Switch RICHTEK TECHNOLOGY CORP.	
6	U203,U204	IC,LDO Voltage Regulator	EUSY0407501	BU18TD4WNVX SSON004,4,R/TP,1.8V 150mA Single LDO,IC,LDO Voltage RegulatorIC,LDO Voltage Regulator ROHM.	
6	U209	IC,Voltage Reference	EUSY0410801	RT9524 DFN,10,R/TP,DFN Cal Test Mode Single Charger IC for Micro USB,IC,ChargerIC,Charger RICHTEK TECHNOLOGY CORP.	
6	U401	IC,Digital Signal Processors	EUSY0412901	PMB8805 0 0 0 NONE NONE BGA R/TP 207P - INFINEON TECHNOLOGIES (ASIA PACIFIC) PTE LTD.	
6	U501	IC,Resistive Touch Screen Controller	EUSY0416201	ISA2000 NONE NONE UQFN R/TP 18P - Imagis Co.,Ltd.	
6	U600	IC,Bluetooth	EUSY0418701	BCM2070B2KUBXG 2.3VTO5.5V 158.4mW WLBGA R/TP 42P - BROADCOM ASIA DISTRIBUTION PTE LTD	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	U101	IC,Digital Signal Processors	EUSY0421201	PMB8810 0 0 0 NONE NONE BGA R/TP 217P - INFINEON TECHNOLOGIES (ASIA PACIFIC) PTE LTD.	
6	U100	IC,MCP,NOR	EUSY0421701	KA8520N00A-BWWW NOR/1GBIT(512M*2) + PSRAM/256MBIT 1.7VTO1.9V 8 9.2 1.2 TR 56P - - - SAMSUNG ELECTRONIC CO.,LTD	
6	U402	IC,MCP,NOR	EUSY0422102	S71VS128RC0AHK4L0 7.7*6.2*1 ,56 ,ETC ,128Mb NOR+ 64Mb psRAM, Admux, 1.8V , ,IC,MCP SPANSION LLC	
6	X101,X401	Crystal	EXXY0018701	FC-135(12.5PF, +20PPM) 32.768KHZ 20PPM 12.5PF 32*15 SMD R/TP SEIKO EPSON CORP	
6	X100,X400	Crystal	EXXY0027001	DSX321G-26M(8PF) 26MHZ 10PPM 0F NONE SMD R/TP DAISHINKU CORPORATION.	
6	R216,R218, R293,R405, R408,R409, R411,R412, R447,R603, R626	Wire Pad,Open	SAFO0000501	AX3100 ATL SV_SHIPBACK,MAIN,A,0OHM_1005_DNI	
6	R400	Wire Pad,Short	SAFP0000401	AX3100 ATL SV_SHIPBACK,MAIN,A	
6	R100,R215, R235,R294, R295,R602	Wire Pad,Short	SAFP0000501	LG-VS760 VRZ	
6	VA501	Varistor	SEVY0000701	EVL14S02200 14V 0% 120F 1.0*0.5*0.6 NONE SMD R/TP AMOTECH CO., LTD.	
6	VA202, VA203, VA503	Varistor	SEVY0001001	EVLC14S02050 14V 0% 50F 1.0*0.5*0.6 NONE SMD R/TP AMOTECH CO., LTD.	
6	VA200, VA201, VA506	Varistor	SEVY0007301	ULCE0505C015FR 5V 0% 0.5F 1.0*0.5*0.55 NONE SMD R/TP INNOCHIPS TECHNOLOGY	
6	FB600	Filter,Bead	SFBH0000903	HB-1M1005-601JT 600 ohm 1.0*0.5*0.5 SMD R/TP 2P CERATECH CORPORATION	
6	FB200, FB201, FB202, FB300, FB500, FB501, FB502	Filter,Bead	SFBH0000912	HB-1M1005-102JT 1000 ohm 1.0*0.5*0.5 SMD R/TP 2P CERATECH CORPORATION	
6	FB100, FB400	Filter,Bead	SFBH0007103	BLM15BB750SN1J 75ohm 1.0x0.5x0.55 SMD R/TP 2P MURATA MANUFACTURING CO.,LTD.	
6	FL600	Filter,Dielectric	SFDY0003001	DEA202450BT-1275A1 DEA202450BT-1275A1,2450 MHz,2.0*1.25*1.05,SMD,2400M~2500M,IL 1.6,4pin,U-U,50-50,BT BPF TDK CORPORATION	
6	FL503, FL504	Filter,EMI/Power	SFEY0011601	ICVE10184E150R500FR ESD/EMI 0HZ 15pF 0H SMD R/TP INNOCHIPS TECHNOLOGY	
6	FL500, FL501, FL502	Filter,EMI/Power	SFEY0013201	EVRC14S03Q030100R ESD/EMI 0HZ 15pF 0H SMD R/TP AMOTECH CO., LTD.	

12. EXPLODED VIEW & REPLACEMENT PART LIST

Level	Location No.	Description	Part Number	Spec	Remark
6	FL301, FL303	Filter,Saw,Dual	SFSB0002301	B9509 B9509,881.5 MHz,25 MHz,2.6 dB,30 dB,942.5 MHz,35 MHz,30 dB,15 dB,1.8*1.4*0.68,SMD,869M~894M,925M~960M,10p,B,150,LH,GSM850+EGSM Rx,DIP_OUT EPCOS PTE LTD.	
6	FL300, FL302	Filter,Saw,Dual	SFSB0002302	B9508 B9508,1842.5 MHz,75 MHz,3.5 dB,10 dB,1960 MHz,60 MHz,3.5 dB,10 dB,1.8*1.4*0.68,SMD,1805M~1880M,1930M~1990M,10p,B,100,DCS+PCS Rx,LH,DIP_OUT EPCOS PTE LTD.	
6	U301,U302	RF Module	SMRH0005601	SKY77547 MHz,MHz,GSM Quad Tx Module 6x8, SKYWORKS SOLUTIONS INC.	
6	BAT100	Module,Assembly	SMZY0026701	EECEP0F333YD GM750 SFRTN Backup Capacitor,0.03F,3.8pi,Module Assembly PANASONIC INDUSTRIAL KOREA CO., LTD	
6	ANT600	Antenna,Helical	SNMF0051501	SDBTPTR3015 SINGLE -5DB 50OHM 5 PARTRON COMPANY LIMITED	
6	MIC200	Microphone, Condenser	SUMY0010613	S08OT423-06 -42DB 100OHM OMNI 1.5 TO 3.6V 3.76x2.95x1.1 SMD GoerTek Inc.	
5	SAFD00	PCB Assembly, Main,SMT Top	SAFD0150701 2	LGP520.ACISBK MAIN 1.0	
6	CN501	Connector, Terminal Block	ENZY0020701	KQ13L-4R 4P 2.7 ANGLE SMD R/TP - HIROSE KOREA CO.,LTD	
6	PCB	PCB,Main	SPFY0237101	SPFY0237101 FR-4 Staggered via STAGGERED-8 0.8 LG-P520 CISBK,MAIN,D,FR-4,0.8 mm,STAGGERED-8 ISUPETASYS	
3	SNGF00	Antenna,Helical	SNGF0065501	LS01-I-10LGP520(MRD)-A0 3,-2 dBd,Triples(GSM900/DCS/PCS),TRIPLE,-2,50,3 LS Mtron Ltd.	
2	MEZ002101	Label,Approval	MLAA0062305	COMPLEX KB770 DEUBK ZZ:Without Color -	
2	MEZ002100	Label,Approval	MLAA0062401	COMPLEX KE970 CISSS ZZ:Without Color -	

12. EXPLODED VIEW & REPLACEMENT PART LIST

12.3 Accessory

Note: This Chapter is used for reference, Part order is ordered by SBOM standard on GCSC

Level	Location No.	Description	Part Number	Spec	Remark
3	SAC000000	PCSYNC CD	SAC35035301	PC Sync CD Part Create CD n/a CD n/a	
2	EBX000000	Accessory, Data Cable	SGDY0016701	KCA-ET-8-0020 KCA-ET-8-0020 Micro USB, 1.2M KSD CO., LTD	
2	EAB010200	Earphone,Stereo	SGEY0003218	EMB-LGE011STKC 3mW 16OHM 115DB 85HZTO126HZ 1M BLACK 5PIN 5 CRESYN CO.,LTD	
2	EAY060000	Adapters	SSAD0032201	STA-U12RD STA-U12RD,100-240V,5060 Hz,5.1 V,0.7 A,CE,GOST,STA-U12RD,Russia,Cableless DONG DO ELECTRONICS CO., LTD	
2	EAY060000	Adapters	*S*SSAD0032202	STA-U12RS 150Vac~350Vac 5.1V 700mA 5060 GOST NONE NONE - SALCOMP OY	